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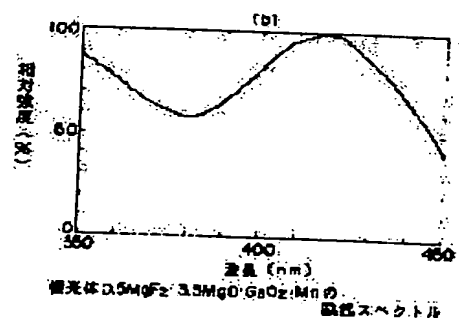
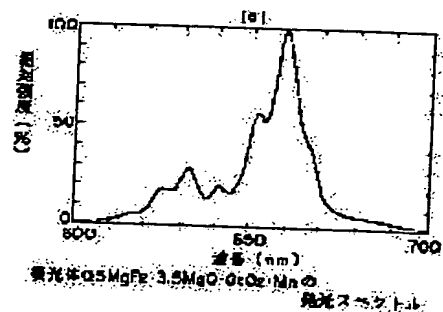
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(54) SEMICONDUCTOR LIGHT EMITTING DEVICE AND LIGHT EMITTING DISPLAY COMPRISING IT

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a monochromatic semiconductor light emitting device having a good color tone and insusceptible to light emitted from a semiconductor light emitting element.

SOLUTION: The semiconductor light emitting device comprises a semiconductor light emitting element having an emission wavelength of 390-420 nm and emission color from near ultraviolet to violet blue where the visual sensitivity of human being is low, and the wavelength of light from the semiconductor light emitting element is converted by a fluorescent material having a monochromatic emission peak. When the visual sensitivity of human being is taken into account, the light subjected to wavelength conversion by the fluorescent material is apparently insusceptible to direct light from the semiconductor light emitting element, and thereby the light from the fluorescent material has a good color tone. Since a semiconductor light emitting device having a desired emission color can be obtained by simply varying the fluorescent material without varying the structure of the semiconductor light emitting device or the semiconductor light emitting element, fabrication cost of the semiconductor light emitting device can be reduced.



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CLAIMS

[Claim(s)]

- [Claim 1] It is semi-conductor luminescence equipment characterized by for the above-mentioned semi-conductor light emitting device to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm in the semi-conductor luminescence equipment which comes to carry a semi-conductor light emitting device on a base, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 600nm thru/or 670nm with the fluorescent substance which carries out outgoing radiation of the red light which has the main luminescence peak.
- [Claim 2] the semi-conductor luminescence equipment according to claim 1 characterized by the above-mentioned fluorescent substance consisting of any one or 2 or more M_2O_2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), $0.5MgF_2$ and $3.5 MgO-GeO_2:Mn$, $Y_2O_3:Eu$, Y(P, V) $O_4:Eu$, $YVO_4:Eu$, and among the groups of a fluorescent substance come out of and expressed.
- [Claim 3] It is semi-conductor luminescence equipment characterized by for the above-mentioned semi-conductor light emitting device to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm in the semi-conductor luminescence equipment which comes to carry a semi-conductor light emitting device on a base, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 500nm thru/or 540nm with the fluorescent substance which carries out outgoing radiation of the green light which has the main luminescence peak.
- [Claim 4] the above-mentioned fluorescent substance — $RMg_2Al_{10}O_{17}$: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — $RMg_2Al_{10}O_{17}$: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — $It Eu(s)$ and $D(ies)$. $ZnS:Cu$, $SrAl_2O_4:Eu$, and $SrAl_2O_4$: — $ZnO:Zn$, $Zn_2germanium_2O_4:Mn$, $Zn_2SiO_4:Mn$, and $Q_3MgSi_2O_8:Eu$ — Mn the semi-conductor luminescence equipment according to claim 3 characterized by consisting of any one or 2 or more however, (any one or two or more elements) with which Q is chosen from Sr, Ba, and calcium, and among the groups of a fluorescent substance come out of and expressed.
- [Claim 5] It is semi-conductor luminescence equipment characterized by for the above-mentioned semi-conductor light emitting device to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm in the semi-conductor luminescence equipment which comes to carry a semi-conductor light emitting device on a base, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 410nm thru/or 480nm with the fluorescent substance which carries out outgoing radiation of the blue light which has the main luminescence peak.
- [Claim 6] The above-mentioned fluorescent substance $A_{10}(PO_4)_6Cl_2:Eu$ (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), $XMg_2Al_{10}O_{17}:Eu$ (however, any one as which X is chosen from Sr and Ba or both elements), $XMg_2Al_{10}O_{17}:Eu$ (however, any one as which X is chosen from Sr and Ba or both elements), $ZnS:Ag$, $Sr_{10}(PO_4)_6Cl_2:Eu$, calcium $10(PO_4)_6F_2:Sb$, $Z_3MgSi_2O_8:Eu$ (however, any one or two, or more elements with which Z is chosen from Sr, Ba, and calcium), $SrMgSi_2O_8:Eu$, $Sr_2P_2O_7:Eu$, and $CaAl_2O_4$: — the semi-conductor luminescence equipment according to claim 5 characterized by consisting of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed.
- [Claim 7] It is semi-conductor luminescence equipment characterized by for the above-mentioned semi-conductor light emitting device to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm in the semi-conductor luminescence equipment which comes to carry a semi-conductor light emitting device on a base, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 480nm thru/or 500nm with the fluorescent substance which carries out outgoing radiation of the light of a bluish-green color which has the main luminescence peak.
- [Claim 8] $It Eu(s)$ and $D(ies)$, the above-mentioned fluorescent substance — $Sr_4Al_{10}O_{17}:Eu$ and $Sr_4Al_{10}O_{17}:Eu$ — $L_{10}(PO_4)_6Cl_2:Eu$ (however, any one or two or more elements with which L is chosen from Ba, calcium, and Mg), the semi-conductor luminescence equipment according to claim 7 characterized by consisting of any one or 2 or more $Sr_2Si_3O_8$ and $2SrCl_2:Eu$, and among the groups of a fluorescent substance come out of and expressed.
- [Claim 9] It is semi-conductor luminescence equipment characterized by for the above-mentioned semi-conductor light emitting device to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm in the semi-conductor luminescence equipment which comes to carry a semi-conductor light emitting device on a

base, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 570nm thru/or 600nm with the fluorescent substance which carries out outgoing radiation of the orange light which has the main luminescence peak.

[Claim 10] the semi-conductor luminescence equipment according to claim 9 characterized by the above-mentioned fluorescent substance consisting of any one or 2 or more ZnS:Mn, ZnS:Cu, Mn and Co, and among the groups of a fluorescent substance come out of and expressed.

[Claim 11] Claim 1 characterized by having closure resin which closes at least the part and the above-mentioned semi-conductor light emitting device of the above-mentioned base, and the above-mentioned closure resin containing the above-mentioned fluorescent substance thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 12] It is semi-conductor luminescence equipment according to claim 11 characterized by for the above-mentioned base being a leadframe which has the mounting section of a cup configuration, and arranging the above-mentioned semi-conductor light emitting device at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe, and for wire bonding connecting with another leadframe electrically, and closing at least the part and the above-mentioned semi-conductor light emitting device of the two above-mentioned leadframes by the above-mentioned closure resin.

[Claim 13] It is semi-conductor luminescence equipment according to claim 11 characterized by for the above-mentioned base being an insulator connected at the head of the leadframe of a couple, and connecting the above-mentioned semi-conductor light emitting device to metal wiring formed in the above-mentioned insulator, and closing at least the part, the above-mentioned insulator, and the above-mentioned semi-conductor light emitting device of a leadframe of a up Norikazu pair by the above-mentioned closure resin.

[Claim 14] The above-mentioned base is a leadframe which has the mounting section of a cup configuration. The above-mentioned semi-conductor light emitting device It is arranged at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe. And while wire bonding connects with another leadframe electrically and the mounting section of the above-mentioned cup configuration is filled up with the above-mentioned fluorescent substance Claim 1 characterized by closing at least the part, the above-mentioned semi-conductor light emitting device, and the above-mentioned fluorescent substance of the two above-mentioned leadframes by closure resin thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 15] The above-mentioned base is a leadframe which has the mounting section of a cup configuration. The above-mentioned semi-conductor light emitting device It is arranged at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe. And while wire bonding connects with another leadframe electrically, filling up the mounting section of the above-mentioned cup configuration with a coating member and arranging the above-mentioned fluorescent substance on the above-mentioned coating member Claim 1 characterized by closing at least the part, the above-mentioned semi-conductor light emitting device, the above-mentioned coating member, and the above-mentioned fluorescent substance of the two above-mentioned leadframes by closure resin thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 16] They are claim 1 which the above-mentioned base is the substrate with which metal wiring was given, and the above-mentioned semi-conductor light emitting device is electrically connected to metal wiring of the above-mentioned substrate, is equipped with the closure resin which closes the above-mentioned semi-conductor light emitting device, and is characterized by the above-mentioned closure resin containing the above-mentioned fluorescent substance thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 17] They are claim 1 which the above-mentioned base is the substrate with which metal wiring was given, the above-mentioned semi-conductor light emitting device is arranged in the crevice while connecting with metal wiring of the above-mentioned substrate electrically, and is characterized by filling up with the above-mentioned fluorescent substance in the above-mentioned crevice thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 18] The above-mentioned crevice is semi-conductor luminescence equipment according to claim 17 characterized by being formed with the frame arranged at the above-mentioned substrate.

[Claim 19] The above-mentioned base is claim 1 characterized by being the substrate with which metal wiring was given, arranging the above-mentioned semi-conductor light emitting device in the crevice while connecting with metal wiring of the above-mentioned substrate electrically, and arranging the above-mentioned fluorescent substance on the above-mentioned closure resin while filling up the above-mentioned crevice with closure resin thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 20] The above-mentioned base is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with metal wiring and the electric target of the above-mentioned substrate, and it has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. Claim 1 characterized by having closure resin which the reflected light from the above-mentioned reflector penetrates while closing the above-mentioned semi-conductor light emitting device, and containing the above-mentioned fluorescent substance in the above-mentioned closure resin thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 21] The above-mentioned base is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and it has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. The exterior of semi-conductor luminescence equipment is equipped with the screen which interrupts the light which carries out direct outgoing radiation from the above-

mentioned semi-conductor light emitting device. Claim 1 to which it has closure resin which the reflected light from the above-mentioned reflector penetrates while closing the above-mentioned semi-conductor light emitting device, and the layer of the above-mentioned fluorescent substance is characterized by being prepared in the field which light reflects in the above-mentioned reflector thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 22] The above-mentioned base is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and a part for the light-emitting part of the above-mentioned semi-conductor light emitting device is arranged in the crevice of the above-mentioned substrate at least. It has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. Claim 1 to which it has closure resin which the reflected light from the above-mentioned reflector penetrates while closing the above-mentioned semi-conductor light emitting device, and the layer of the above-mentioned fluorescent substance is characterized by being prepared in the field which light reflects in the above-mentioned reflector thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 23] The above-mentioned base is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and it has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. Claim 1 characterized by being prepared in the field as for which is equipped with the closure resin which the reflected light from the above-mentioned reflector penetrates while closing the above-mentioned semi-conductor light emitting device, and the light of the above-mentioned closure resin carries out [the layer of the above-mentioned fluorescent substance] outgoing radiation thru/or semi-conductor luminescence equipment of any one publication of ten.

[Claim 24] In the semi-conductor luminescence equipment which comes to carry a semi-conductor light emitting device on a base the above-mentioned semi-conductor light emitting device It has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, and has the 1st fluorescent substance, the 2nd fluorescent substance, and the 3rd fluorescent substance. The 1st fluorescent substance of the above It has a red outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 600nm thru/or 670nm. The 2nd fluorescent substance of the above It has a green outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 500nm thru/or 540nm. The 3rd fluorescent substance of the above Semi-conductor luminescence equipment with which it has a blue outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 410nm thru/or 480nm, and the sum of the color of the outgoing radiation light from the 1st, 2nd, and 3rd fluorescent substance of the above is characterized by being a white system.

[Claim 25] The 1st fluorescent substance of the above M2O2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), 0.5MgF2 and 3.5 MgO-GeO2:Mn, Y2O3:Eu, It consists of any one or 2 or more Y(P, V) O4:Eu, YVO4:Eu, and among the groups of a fluorescent substance come out of and expressed. the 2nd fluorescent substance of the above RMg2aluminum16O27: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — RMgAl10O17: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — It Eu(s) and D(ies). ZnS:Cu, SrAl2O4:Eu, and SrAl2O4: — ZnO:Zn, Zn2germanium2O4:Mn, Zn2SiO4:Mn, and Q3MgSi2O8:Eu — Mn It consists of any one or 2 or more however, (any one or two or more elements) with which Q is chosen from Sr, Ba, and calcium, and among the groups of a fluorescent substance come out of and expressed. the 3rd fluorescent substance of the above A10(PO4) 6Cl2:Eu (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), XMg2aluminum16O27:Eu (however, any one as which X is chosen from Sr and Ba or both elements), XMgAl10O17:Eu (however, any one as which X is chosen from Sr and Ba or both elements), ZnS:Ag, Sr10(PO4) 6Cl2:Eu, calcium10 (PO4) 6F2:Sb, Z3MgSi2O8:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi2O8:Eu, Sr2P2O7:Eu, and CaAl2O4: — the semi-conductor luminescence equipment according to claim 24 characterized by consisting of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed.

[Claim 26] For 20 or less % of the weight and the 3rd fluorescent substance of the 7-% of the weight or more above, 70 or less % of the weight and the 2nd fluorescent substance of the 50-% of the weight or more above are [the 1st, 2nd, and 3rd fluorescent substance of the above] semi-conductor luminescence equipment according to claim 24 or 25 with which it is characterized by the 1st fluorescent substance of the above being 30 or less % of the weight 20 % of the weight or more noting that a total amount is 100 % of the weight.

[Claim 27] The above-mentioned closure resin is semi-conductor luminescence equipment according to claim 26 with which the 1st, 2nd, and 3rd fluorescent substance of the above is included, and the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is characterized by or more 0.5 being one or less.

[Claim 28] It is the luminescence display which is equipped with the light source using claim 24 thru/or the semi-conductor luminescence equipment of any one publication of 27, the light guide plate to which the light from the above-mentioned light source is led, and the light filter of green [which are made to penetrate the light from the above-mentioned light guide plate, and carry out a spectrum / the red and green], and blue, and is characterized by for the outgoing radiation light of the above-mentioned semi-conductor luminescence equipment to have the wavelength distribution which suited the spectral characteristic of the above-mentioned light filter.

[Claim 29] So that wavelength distribution of the outgoing radiation light of semi-conductor luminescence equipment

may suit the spectral characteristic of the above-mentioned light filter The luminescence wavelength of the above-mentioned semi-conductor light emitting device, and the luminescence wavelength of the 1st fluorescent substance of the above, The luminescence wavelength of the 2nd fluorescent substance of the above, the luminescence wavelength of the 3rd fluorescent substance of the above, and the mixed ratio of the 1st, 2nd, and 3rd fluorescent substance of the above, The luminescence display according to claim 28 characterized by adjusting at least one of the ratios of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin.

[Claim 30] The above-mentioned luminescence display is a luminescence display according to claim 28 or 29 characterized by being a liquid crystal display.

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DETAILED DESCRIPTION

[Detailed Description of the Invention]

[0001]

[Field of the Invention] This invention The light sources for back lights, such as a liquid crystal display, and a cellular phone, a Personal Digital Assistant, the indicator of the LED (light emitting diode) indicating equipment used for an announcement indoor outside etc., and an each kind pocket device -- It is a thing about the semi-conductor luminescence equipment used for the light source for an illumination switch and OA (office automation) devices etc. Especially, wavelength conversion of the outgoing radiation light from a semi-conductor light emitting device is carried out using a fluorescent substance, and it is related with semi-conductor luminescence equipment available as the light source of various luminescent color, and the luminescence display using it.

[0002]

[Description of the Prior Art] Semi-conductor luminescence equipment is small, and since power consumption can carry out high brightness luminescence to stability few, it is widely used as the light source in various displays. Moreover, semi-conductor luminescence equipment is used also as the light source for information record reading in various information processors. Green high brightness luminescence was possible for the semi-conductor light emitting device used for the long wavelength light semi-conductor luminescence equipment put in practical use widely until now from red by a semiconductor material, formation conditions, etc. of a luminous layer which are used. On the other hand, from blue, the semi-conductor light emitting device which emits light in the purple short wavelength light is developed, and, generally it is beginning to be put in practical use in recent years.

[0003] The LED display using the semi-conductor luminescence equipment which has the luminescent color of R (red), G (green), and B (blue) in three primary colors has begun to appear in the commercial scene, using the semi-conductor luminescence equipment of these various luminescent color.

[0004] Furthermore, the semi-conductor luminescence equipment which obtains white from blue combining the semi-conductor light emitting device and fluorescent substance which emit light in the purple short wavelength light with color mixture with the conversion light by which wavelength conversion was carried out with the outgoing radiation light and the fluorescent substance of a semi-conductor light emitting device is indicated by patent No. 2927279.

[0005] Moreover, in order to obtain the compact white luminescent color by high brightness, the semi-conductor luminescence equipment which combined the semi-conductor light emitting device which has the luminescent color of blue or a purple-blue color, and one sort or two kinds or more of fluorescent substances which absorb the light from this semi-conductor light emitting device, and emit light in the light of a visible region is indicated by JP,10-163535,A. The above-mentioned fluorescent substance is chosen so that the luminescent color of the above-mentioned semi-conductor light emitting device and the luminescent color of a fluorescent substance may become the relation of the complementary color mutually, the luminescent color of this semi-conductor light emitting device and the luminescent color of a fluorescent substance may be added and light may be emitted white.

[0006] Moreover, the semi-conductor luminescence equipment which equips JP,10-12925,A with the semi-conductor light emitting device which carries out outgoing radiation of ultraviolet radiation and the near-ultraviolet light, and the fluorescent substance which emits fluorescence by the light from this semi-conductor light emitting device is indicated. The above-mentioned semi-conductor light emitting device is a semi-conductor light emitting device which usually emits a blue light, and carries out outgoing radiation of ultraviolet radiation and the near-ultraviolet light by passing a pulse-like high current. Obtaining two or more luminescent color, using the semi-conductor light emitting device of a single class only by changing the class of the above-mentioned fluorescent substance is indicated.

[0007] Moreover, the display equipped with red, blue, and three kinds of fluorescent substance layers that emit light respectively in the green three primary colors dot-matrix type is indicated by JP,9-153644,A by receiving the ultraviolet rays from the luminous layer which is formed using 3 group nitrogen ghost semi-conductor, and emits light in the ultraviolet rays whose peak wavelength is 380nm, and this luminous layer.

[0008]

[Problem(s) to be Solved by the Invention] However, the above-mentioned Prior art has the following troubles.

[0009] The semi-conductor light emitting device which emits light the purple short wavelength light from the semi-conductor light emitting device which is used for long wavelength light semi-conductor luminescence equipment, and has the green luminescent color from red, and blue Since the ingredient and component configuration which are used according to the wavelength which emits light differ from each other, if the semiconductor device of mutually

different wavelength tends to be mounted and it is going to obtain semi-conductor luminescence equipment. Two or more mutually different mounting ingredients and mounting processes are needed, and while a production process becomes complicated, there is a problem of becoming the factor of a cost rise.

[0010] Furthermore, in order for color to acquire the good white light using two or more semi-conductor light emitting devices from which the above-mentioned luminescent color differs mutually, since it is necessary to adjust respectively the current to two or more above-mentioned semi-conductor light emitting devices, there is a problem that semi-conductor luminescence equipment becomes complicated. Moreover, when a luminescence display is formed using the above-mentioned semi-conductor luminescence equipment two or more, there is a trouble that adjustment of the color tone of the semi-conductor light emitting device of a large quantity is needed, and a production process becomes complicated.

[0011] Moreover, since the semi-conductor luminescence equipment currently indicated by the above-mentioned patent No. 2927279 and JP,10-163535,A carried out color mixture of the outgoing radiation light of a semi-conductor light emitting device, and this outgoing radiation light and the luminescence light of the fluorescent substance which has the relation of the complementary color and obtained the white luminescent color, it had the trouble that a color tone was not good, either, bad [the utilization effectiveness of light]. For example, when the semi-conductor luminescence equipment which acquires the white light with the color mixture of a blue outgoing radiation light of a semi-conductor light emitting device and the outgoing radiation light of the yellow of a fluorescent substance is used as a back light of a liquid crystal display, since there is little quantity of light of pure red and there are few amounts of the light which penetrates the red light filter with which the above-mentioned liquid crystal display is equipped, this white light has green pure and the trouble of giving an impression which carried out the color omission, when the above-mentioned liquid crystal display indicates by full color.

[0012] Moreover, since the semi-conductor luminescence equipment currently indicated by JP,10-12925,A impresses a pulse-like high current to a semi-conductor light emitting device, a semi-conductor light emitting device breaks, or it generates heat, and it deteriorates, and has the trouble that a life is short and it is unreliable. Moreover, since the above-mentioned semi-conductor light emitting device has the peak of luminescence wavelength also on blue wavelength while having the peak of luminescence wavelength on ultraviolet and near-ultraviolet wavelength, this blue glow carries out color mixture of it to the luminescence light of fluorescence, and it has the problem that a color tone is bad. Furthermore, since brightness does not deteriorate [the semi-conductor light emitting device which has the luminescent color from which plurality differs] uniformly and a blue wavelength component falls rapidly especially when semi-conductor luminescence equipment deteriorates, there is a trouble that the color tone of semi-conductor luminescence equipment will change. Furthermore, since the above-mentioned semi-conductor light emitting device carries out outgoing radiation of the light of the wavelength of the ultraviolet region by the side of short wavelength from near near-ultraviolet (390nm), the measure which prevents the effect on the body is required for it. Moreover, since the object for immobilization of the above-mentioned semi-conductor light emitting device and the resin for moulds also receive an adverse effect by the light of the wavelength of the above-mentioned ultraviolet region, they have the trouble that there is a possibility of causing lowering of the dependability by deterioration of the above-mentioned resin for immobilization and lowering of the luminescence brightness by the melanism of the above-mentioned resin for moulds.

[0013] While the semi-conductor luminescence equipment indicated by publication number No. 153644 [nine to] also needs to enforce the leakage control of the light of an ultraviolet region in order to prevent the effect on the body since it uses the luminescence wavelength of the ultraviolet region of 380nm, it has the trouble that the object for immobilization of a semi-conductor light emitting device and the resin for moulds cause lowering of dependability, and lowering of luminescence brightness in response to an adverse effect. Furthermore, this semi-conductor luminescence equipment has the trouble that the production process of semi-conductor luminescence equipment is complicated, and the yield and dependability fall on a substrate since red, blue, and the fluorescent substance layer that emits light in the green three primary colors are formed with a semi-conductor layer.

[0014] In spite of being made in order to solve the above-mentioned technical problem, and being able to carry out the outgoing radiation of the light of two or more luminescence wavelength, manufacture is easy and cheap, a color tone is good, there is little effect on the body, and this invention aims at offering the semi-conductor luminescence equipment which does not almost have degradation, and the luminescence display using it.

[0015]

[Means for Solving the Problem] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base in order to attain the above-mentioned object, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 600nm thru/or 670nm with the fluorescent substance which carries out the outgoing radiation of the red light which has the main luminescence peak.

[0016] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to a red wavelength field and carries out outgoing radiation of the light of monochromatic red. Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation

are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome red luminescence with a good color tone is obtained.

[0017] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0018] in the semi-conductor luminescence equipment of 1 operation gestalt, the above-mentioned fluorescent substance consists of any one or 2 or more M2O2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), 0.5MgF2 and 3.5 MgO-GeO2:Mn, Y2O3:Eu, Y(P, V) O4:Eu, YVO4:Eu, and among the groups of a fluorescent substance come out of and expressed.

[0019] Since according to the above-mentioned operation gestalt the above-mentioned fluorescent substance can be chosen according to the wavelength of the outgoing radiation light of the above-mentioned semi-conductor light emitting device even if it uses the semi-conductor light emitting device which has which outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, the semi-conductor luminescence equipment of monochrome red luminescence with which luminescence wavelength has a good luminescence peak to a red wavelength field is obtained. Moreover, since the wavelength of all abbreviation for the wavelength field of the outgoing radiation light of a semi-conductor light emitting device is convertible for red wavelength by combining two or more fluorescent substances, the semi-conductor luminescence equipment of efficient monochrome red luminescence is obtained.

[0020] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 500nm thru/or 540nm with the fluorescent substance which carries out outgoing radiation of the green light which has the main luminescence peak.

[0021] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to a green wavelength field and carries out outgoing radiation of the monochromatic green light Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome green luminescence with a good color tone is obtained.

[0022] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0023] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance RMg₂aluminum16O₂₇: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — RMgAl10O₁₇: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — It Eu(s) and D(ies). ZnS:Cu, SrAl₂O₄:Eu, and SrAl₂O₄: — ZnO:Zn, Zn₂germanium₂O₄:Mn, Zn₂SiO₄:Mn, and Q₃MgSi₂O₈: — it consists of any one or 2 or more Eu, Mn (however, any one or two or more elements with which Q is chosen from Sr, Ba, and calcium), and among the groups of a fluorescent substance come out of and expressed.

[0024] According to the above-mentioned operation gestalt, since the optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of monochrome green luminescence which has a good luminescence peak to the wavelength field where luminescence wavelength is green is obtained. Moreover, since the wavelength of all abbreviation for the wavelength field of the outgoing radiation light of a semi-conductor light emitting device is convertible for green wavelength by combining two or more fluorescent substances, the semi-conductor luminescence equipment of efficient monochrome green luminescence is obtained.

[0025] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 410nm thru/or 480nm with the fluorescent substance which carries out outgoing radiation of the blue light which has the main luminescence peak.

[0026] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to a blue wavelength field and carries out outgoing radiation of the monochromatic blue light Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome blue luminescence with a good color tone is obtained.

[0027] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0028] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance A10(PO₄) 6Cl₂:Eu (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), XMg₂aluminum16O₂₇:Eu (however, any one as which X is chosen from Sr and Ba or both elements), XMgAl10O₁₇:Eu (however, any one as which X is chosen from Sr and Ba or both elements), ZnS:Ag, Sr10(PO₄) 6Cl₂:Eu, calcium10(PO₄) 6F₂:Sb, Z₃MgSi₂O₈:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi₂O₈:Eu, Sr₂P₂O₇:Eu, and CaAl₂O₄: — it consists of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed.

[0029] According to the above-mentioned operation gestalt, since the optimal fluorescent substance can be chosen according to the luminescence wavelength of a semi-conductor light emitting device, the semi-conductor luminescence equipment of monochrome blue luminescence which has a good luminescence peak to the wavelength field where luminescence wavelength is blue is obtained. Moreover, since the wavelength of all abbreviation for the wavelength field of the outgoing radiation light of the above-mentioned semi-conductor light emitting device is convertible for blue wavelength by combining two or more fluorescent substances, the semi-conductor luminescence equipment of efficient monochrome blue luminescence is obtained.

[0030] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 480nm thru/or

500nm with the fluorescent substance which carries out outgoing radiation of the light of a bluish-green color which has the main luminescence peak.

[0031] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to the wavelength field of a bluish green color and carries out outgoing radiation of the light of a monochromatic bluish green color Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome bluish green color luminescence with a good color tone is obtained.

[0032] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0033] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance It Eu(s) and D(ies). Sr4aluminum14O25:Eu and Sr4aluminum14O25: — it consists of any one or 2 or more L10(PO4) 6Cl2:Eu (however, any one or two or more elements with which L is chosen from Ba, calcium, and Mg), Sr2Si3O8 and 2SrCl2:Eu, and among the groups of a fluorescent substance come out of and expressed.

[0034] According to the above-mentioned operation gestalt, since the optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of monochrome bluish green color luminescence with which luminescence wavelength has a good luminescence peak to the wavelength field of a bluish green color is obtained. Moreover, since the wavelength of all abbreviation for the wavelength field of light in which the above-mentioned semi-conductor light emitting device carries out outgoing radiation by combining two or more fluorescent substances is convertible for the wavelength of a bluish green color, the semi-conductor luminescence equipment of efficient monochrome bluish green color luminescence is obtained.

[0035] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 570nm thru/or 600nm with the fluorescent substance which carries out outgoing radiation of the orange light which has the main luminescence peak.

[0036] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to an orange wavelength field and carries out outgoing radiation of the monochromatic orange light Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome orange light emitting with a good color tone is obtained.

[0037] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand,

if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0038] in the semi-conductor luminescence equipment of 1 operation gestalt, the above-mentioned fluorescent substance consists of any one or 2 or more ZnS:Mn, ZnS:Cu, Mn and Co, and among the groups of a fluorescent substance come out of and expressed.

[0039] According to the above-mentioned operation gestalt, since the optimal fluorescent substance can be chosen according to the wavelength field of a semi-conductor light emitting device, luminescence wavelength can obtain the semi-conductor luminescence equipment of the monochrome orange light emitting which has the main luminescence peak to an orange luminescence wavelength field.

[0040] The semi-conductor luminescence equipment of 1 operation gestalt is equipped with the closure resin which closes at least the part and the above-mentioned semi-conductor light emitting device of the above-mentioned base, and the above-mentioned closure resin contains the above-mentioned fluorescent substance.

[0041] Since the closure resin which closes the above-mentioned semi-conductor light emitting device contains the fluorescent substance according to the above-mentioned operation gestalt, since wavelength conversion is surely carried out, the outgoing radiation light from a semi-conductor light emitting device has the good utilization effectiveness of the light of a semi-conductor light emitting device. Moreover, since a fluorescent substance can be arranged while forming closure resin and the process which arranges a fluorescent substance separately is unnecessary, manufacture of semi-conductor luminescence equipment becomes easy.

[0042] Moreover, the semiconductor device which has desired luminescence wavelength is obtained, without changing the structure of a semi-conductor light emitting device and semi-conductor luminescence equipment, when this semi-conductor luminescence equipment combines the semi-conductor light emitting device which has the wavelength field where luminescence wavelength is fixed, and a predetermined fluorescent substance. That is, by the same production process, since the semi-conductor luminescence equipment which has desired luminescence wavelength is obtained, the manufacturing cost of semi-conductor luminescence equipment is substantially reducible only only changing a fluorescent substance.

[0043] The semi-conductor luminescence equipment of 1 operation gestalt is a leadframe in which the above-mentioned base has the mounting section of a cup configuration, the above-mentioned semi-conductor light emitting device is arranged at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe, and wire bonding connects with another leadframe electrically, and at least the part and the above-mentioned semi-conductor light emitting device of the two above-mentioned leadframes are closed by the above-mentioned closure resin.

[0044] Since wavelength conversion of the outgoing radiation light from the above-mentioned semi-conductor light emitting device collected by the mounting section of the above-mentioned cup configuration is certainly carried out with the closure resin containing the above-mentioned fluorescent substance according to the above-mentioned operation gestalt, semi-conductor luminescence equipment with a color tone good luminous efficiency and sufficient is obtained with sufficient directivity.

[0045] The semi-conductor luminescence equipment of 1 operation gestalt is the insulator with which the above-mentioned base was connected at the head of the leadframe of a couple, the above-mentioned semi-conductor light emitting device is connected to metal wiring formed in the above-mentioned insulator, and at least the part, the above-mentioned insulator, and the above-mentioned semi-conductor light emitting device of a leadframe of a up Norikazu pair are closed by the above-mentioned closure resin.

[0046] According to the above-mentioned operation gestalt, since direct continuation of the above-mentioned semi-conductor light emitting device is carried out to metal wiring of the above-mentioned substrate for example, by a metal bump etc., the time and effort which connects a semi-conductor light emitting device and a leadframe with a metal wire etc. is saved. Moreover, wavelength conversion of the outgoing radiation light from a semi-conductor light emitting device is certainly carried out with the fluorescent substance contained in the above-mentioned closure resin. Therefore, manufacture effectiveness is good and, moreover, semi-conductor luminescence equipment with a color tone good luminous efficiency and sufficient is obtained.

[0047] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the leadframe which has the mounting section of a cup configuration. The above-mentioned semi-conductor light emitting device It is arranged at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe. And while wire bonding connects with another leadframe electrically and the mounting section of the above-mentioned cup configuration is filled up with the above-mentioned fluorescent substance At least the part, the above-mentioned semi-conductor light emitting device, and the above-mentioned fluorescent substance of the two above-mentioned leadframes are closed by closure resin.

[0048] Since the mounting section of the cup configuration for which the light from the above-mentioned semi-conductor light emitting device gathers is filled up with a fluorescent substance according to the above-mentioned operation gestalt, wavelength conversion is carried out certainly and the utilization effectiveness of light from a

semi-conductor light emitting device of light improves. Moreover, since the field which arranges a fluorescent substance is small, as compared with the semi-conductor luminescence equipment which does not collect the light from a semi-conductor light emitting device, the amount of the above-mentioned fluorescent substance used can be lessened.

[0049] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the leadframe which has the mounting section of a cup configuration. The above-mentioned semi-conductor light emitting device It is arranged at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe. And while wire bonding connects with another leadframe electrically, filling up the mounting section of the above-mentioned cup configuration with a coating member and arranging the above-mentioned fluorescent substance on the above-mentioned coating member At least the part, the above-mentioned semi-conductor light emitting device, the above-mentioned coating member, and the above-mentioned fluorescent substance of the two above-mentioned leadframes are closed by closure resin.

[0050] Since the above-mentioned fluorescent substance is arranged on the coating member filled up by the above-mentioned mounting section according to the above-mentioned operation gestalt, compared with the case where all the above-mentioned mounting circles are filled up with a fluorescent substance, the amount of the above-mentioned fluorescent substance used is reduced. Moreover, by the above-mentioned coating member, since the distance between the light-emitting part of the above-mentioned semi-conductor light emitting device and a fluorescent substance becomes abbreviation homogeneity, the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color is obtained. Furthermore, since the above-mentioned semi-conductor light emitting device and a fluorescent substance are estranged by the above-mentioned coating member, there is almost no electric and thermal degradation of the fluorescent substance by the semi-conductor light emitting device.

[0051] The above-mentioned base is the substrate with which metal wiring was given, the above-mentioned semi-conductor light emitting device is electrically connected to metal wiring of the above-mentioned substrate, the semi-conductor luminescence equipment of 1 operation gestalt is equipped with the closure resin which closes the above-mentioned semi-conductor light emitting device, and the above-mentioned closure resin contains the above-mentioned fluorescent substance.

[0052] According to the above-mentioned operation gestalt, direct continuation of the above-mentioned semi-conductor light emitting device is done by the metal bump etc., without using metal wires, such as Au, and aluminum, Cu, for the semi-conductor light emitting device of the same configuration or a single class, connecting on metal wiring or using a metal wire etc. for the above-mentioned substrate. Therefore, the manufacture process of semi-conductor luminescence equipment is easy rather than it manufactures the semi-conductor luminescence equipment of a different configuration using the semi-conductor light emitting device of a different configuration [as / in the former] corresponding to the luminescent color. In this semi-conductor luminescence equipment, since the semi-conductor luminescence equipment which has desired luminescence wavelength only by arranging the predetermined fluorescent substance corresponding to desired wavelength is obtained, compared with the former, manufacture of semi-conductor luminescence equipment becomes simplicity and low cost.

[0053] The semi-conductor luminescence equipment of 1 operation gestalt is arranged in the crevice while the above-mentioned base is the substrate with which metal wiring was given and is connected electrically [the above-mentioned semi-conductor light emitting device] to metal wiring of the above-mentioned substrate, and it fills up with the above-mentioned fluorescent substance in the above-mentioned crevice.

[0054] According to the above-mentioned operation gestalt, since the crevice of the above-mentioned substrate is filled up with the above-mentioned fluorescent substance, the amount of this fluorescent substance used becomes little, a manufacturing cost is cheap, luminous efficiency is good, and, moreover, semi-conductor luminescence equipment with a sufficient color tone is obtained by monochrome luminescence.

[0055] The semi-conductor luminescence equipment of 1 operation gestalt is formed with the frame with which the above-mentioned crevice has been arranged at the above-mentioned substrate.

[0056] Since according to the above-mentioned operation gestalt a frame is arranged to the above-mentioned substrate and the above-mentioned crevice is formed, the time and effort of processing which cuts a substrate, for example and forms a crevice is reduced. Moreover, in the configuration of the side face for example, by the side of the above-mentioned semi-conductor light emitting device, by processing the outgoing radiation light from the above-mentioned semi-conductor light emitting device into the condensing configuration, while the conversion efficiency of the wavelength of the above-mentioned outgoing radiation light improves further, the directivity of semi-conductor luminescence equipment improves the above-mentioned frame. Consequently, luminous efficiency is good and, moreover, semi-conductor luminescence equipment with a sufficient color tone is obtained by monochrome luminescence.

[0057] While in the semi-conductor luminescence equipment of 1 operation gestalt it is the given substrate, metal wiring is arranged in the crevice while the above-mentioned semi-conductor light emitting device is electrically connected to metal wiring of the above-mentioned substrate, and the above-mentioned base fills up the above-mentioned crevice with closure resin, the above-mentioned fluorescent substance is arranged on the above-mentioned closure resin.

[0058] According to the above-mentioned operation gestalt, since the above-mentioned fluorescent substance is arranged on the above-mentioned closure resin, the semi-conductor luminescence equipment which has desired luminescence wavelength is obtained by the amount of the still more nearly little fluorescent substance used rather

than it is filled up with a fluorescent substance inside the crevice of the above-mentioned substrate. Moreover, with the above-mentioned closure resin, since the distance between the light-emitting part of a semi-conductor light emitting device and a fluorescent substance becomes abbreviation homogeneity, the semi-conductor luminescence equipment of homogeneity luminescence which does not almost have an irregular color is obtained. Moreover, since the above-mentioned closure resin makes a high order semi-conductor light emitting device and a fluorescent substance estrange, it can reduce the electric and thermal effect of a semi-conductor light emitting device to the above-mentioned fluorescent substance, and its engine performance of semi-conductor luminescence equipment is stable.

[0059] It is connected with metal wiring and the electric target of the above-mentioned substrate, and the above-mentioned semi-conductor light emitting device is equipped with the reflector which reflects a part of outgoing-radiation light [at least] from the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of 1 operation gestalt is the substrate with which, as for the above-mentioned base, metal wiring was given, while closing the above-mentioned semi-conductor light emitting device, it has closure resin which the reflected light from the above-mentioned reflector penetrates, and the above-mentioned fluorescent substance is contained in the above-mentioned closure resin.

[0060] According to the above-mentioned operation gestalt, direct continuation of the above-mentioned semi-conductor light emitting device is done by the metal bump etc., without using metal wires, such as Au, and aluminum, Cu, for the semi-conductor light emitting device of the same configuration or a single class, connecting on metal wiring or using a metal wire etc. for the above-mentioned substrate. Therefore, the manufacture process of semi-conductor luminescence equipment is easy rather than it manufactures the semi-conductor luminescence equipment of a different configuration using the semi-conductor light emitting device of a different configuration [as / in the former] corresponding to the luminescent color. In this semi-conductor luminescence equipment, since the semi-conductor luminescence equipment which has desired luminescence wavelength only by arranging the predetermined fluorescent substance corresponding to desired wavelength is obtained, compared with the former, manufacture of semi-conductor luminescence equipment becomes simplicity and low cost.

[0061] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and it has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. The exterior of semi-conductor luminescence equipment is equipped with the screen which interrupts the light which carries out direct outgoing radiation from the above-mentioned semi-conductor light emitting device, while closing the above-mentioned semi-conductor light emitting device, it has closure resin which the reflected light from the above-mentioned reflector penetrates, and the layer of the above-mentioned fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector.

[0062] Since the layer of the above-mentioned fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector according to the above-mentioned operation gestalt, wavelength conversion of the light reflected by this reflector is carried out certainly. And since it is reflected in the above-mentioned reflector and outgoing radiation of the outgoing radiation light from the above-mentioned semi-conductor light emitting device is carried out to the semi-conductor luminescence equipment exterior, without leaking to the exterior of semi-conductor luminescence equipment by the above-mentioned screen, they is the light by which wavelength conversion of all was carried out. [most] Therefore, this semi-conductor luminescence equipment is formed only in a reflector, it is the amount of few fluorescent substances used, and the desired luminescent color is obtained efficiently. Furthermore, since the layer of the above-mentioned fluorescent substance is formed in the reflector of the reflector which makes a predetermined distance from a semi-conductor light emitting device, the distance between the light-emitting part of a semi-conductor light emitting device and a fluorescent substance becomes abbreviation homogeneity, and the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color is obtained. Furthermore, since a semi-conductor light emitting device and a fluorescent substance are estranged, the electric and thermal effect of a semi-conductor light emitting device to a fluorescent substance is eased, and the engine performance of semi-conductor luminescence equipment is stabilized.

[0063] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and a part for the light-emitting part of the above-mentioned semi-conductor light emitting device is arranged in the crevice of the above-mentioned substrate at least. It has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device, while closing the above-mentioned semi-conductor light emitting device, it has closure resin which the reflected light from the above-mentioned reflector penetrates, and the layer of the above-mentioned fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector.

[0064] According to the above-mentioned operation gestalt, since the semi-conductor light emitting device is arranged in the above-mentioned crevice, after wavelength conversion is surely reflected and carried out by the above-mentioned reflector in the exterior of semi-conductor luminescence equipment, without carrying out direct outgoing radiation, outgoing radiation of the light from a semi-conductor light emitting device is carried out to the exterior of semi-conductor luminescence equipment. Therefore, as for this semi-conductor luminescence equipment, the color tone of outgoing radiation light becomes good.

[0065] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and it has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. While closing the above-mentioned semi-conductor light emitting device, it has closure resin which the reflected light from the above-mentioned reflector penetrates, and the layer of the above-mentioned fluorescent substance is prepared in the field as for which the light of the above-mentioned closure resin carries out outgoing radiation.

[0066] According to the above-mentioned operation gestalt, just before outgoing radiation is carried out from semi-conductor luminescence equipment, wavelength conversion of the outgoing radiation light from a semi-conductor light emitting device is carried out by the layer of the fluorescent substance prepared in the field as for which the light of the above-mentioned closure resin carries out outgoing radiation. That is, since wavelength conversion of all the light from this semi-conductor luminescence equipment is carried out, it becomes semi-conductor luminescence equipment of the utilization effectiveness of a good light. Moreover, since the layer of the above-mentioned fluorescent substance is in the location which kept a predetermined distance from the semi-conductor light emitting device, the distance between the light-emitting part of a semi-conductor light emitting device and a fluorescent substance becomes abbreviation homogeneity, and the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color is obtained. Furthermore, since a semi-conductor light emitting device and a fluorescent substance are estranged, the electric and thermal effect of a semi-conductor light emitting device to a fluorescent substance is eased, and the engine performance of semi-conductor luminescence equipment is stabilized.

[0067] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base the above-mentioned semi-conductor light emitting device It has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, and has the 1st fluorescent substance, the 2nd fluorescent substance, and the 3rd fluorescent substance. The 1st fluorescent substance of the above It has a red outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 600nm thru/or 670nm. The 2nd fluorescent substance of the above It has a green outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 500nm thru/or 540nm. The 3rd fluorescent substance of the above It has a blue outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 410nm thru/or 480nm, and the sum of the color of the outgoing radiation style from the 1st, 2nd, and 3rd fluorescent substance of the above is characterized by being a white system.

[0068] According to the above-mentioned configuration, the light in which the above-mentioned semi-conductor light emitting device has upwards the short wavelength field where human being's visibility is very low, and the above 1st thru/or the 3rd fluorescent substance carry out outgoing radiation Since it is the light of red, green, and the monochrome that has the main peak of luminescence wavelength respectively to a blue wavelength field Even if the above 1st thru/or the outgoing radiation light from the 3rd fluorescent substance and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of semi-conductor luminescence equipment will hardly change seemingly. That is, the above 1st thru/or the light from which [3rd] fluorescent substance are not influenced of the direct light from the above-mentioned semi-conductor light emitting device, either. Therefore, the semi-conductor luminescence equipment with which a color tone has the luminescent color of a good white system is obtained. Moreover, since color mixture is not carried out to the light from a fluorescent substance in human being's visible region, even if, as for the light by which direct outgoing radiation is carried out to the semi-conductor luminescence equipment exterior from a semi-conductor light emitting device about the outgoing radiation light of semi-conductor luminescence equipment, the luminescence engine performance of a semi-conductor light emitting device falls according to secular change after the activity of the long duration of semi-conductor luminescence equipment, it is only that the brightness of semi-conductor luminescence equipment falls, and a color tone does not change. Therefore, the light of a white system with a good color tone is stabilized by the above-mentioned semi-conductor luminescence equipment, and it is obtained.

[0069] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0070] The semi-conductor luminescence equipment of 1 operation gestalt the 1st fluorescent substance of the above M2O2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), 0.5MgF2 and 3.5 MgO-GeO2:Mn, Y2O3:Eu, It consists of any one or 2 or more Y(P, V) O4:Eu, YVO4:Eu, and among the groups of a fluorescent substance come out of and expressed. the 2nd fluorescent substance of the above

RMg2aluminum16O27: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — RMgAl10O17: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — It Eu(s) and D(ies). ZnS:Cu, SrAl2O4:Eu, and SrAl2O4: — ZnO:Zn, Zn2germanium2O4:Mn, Zn2SiO4:Mn, and Q3MgSi2O8:Eu — Mn It consists of any one or 2 or more however, (any one or two or more elements) with which Q is chosen from Sr, Ba, and calcium, and among the groups of a fluorescent substance come out of and expressed. the 3rd fluorescent substance of the above A10(PO4) 6Cl2:Eu (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), XMg2aluminum16O27:Eu (however, any one as which X is chosen from Sr and Ba or both elements), XMgAl10O17:Eu (however, any one as which X is chosen from Sr and Ba or both elements), ZnS:Ag, Sr10(PO4) 6Cl2:Eu, calcium10(PO4) 6F2:Sb, Z3MgSi2O8:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi2O8:Eu, Sr2P2O7:Eu, and CaAl2O4: — it consists of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed. [0071] According to the above-mentioned operation gestalt, even if it uses the semi-conductor light emitting device which has which luminescence wavelength of the inside whose luminescence wavelength is 390nm thru/or 420nm, red, monochromatic green, and a monochromatic blue luminescence light are respectively obtained by choosing a suitable fluorescent substance from two or more above-mentioned fluorescent substances corresponding to the luminescence wavelength of this semi-conductor light emitting device. Color mixture of the light of red and green and blue wavelength is respectively carried out appropriately by this, and the luminescent color of the white system of a good color tone is obtained. Moreover, since the light of the wavelength of all abbreviation for the wavelength field which a semi-conductor light emitting device has by combining two or more fluorescent substances is respectively convertible for red and green and blue wavelength, the utilization effectiveness of the outgoing radiation light of a semi-conductor light emitting device improves, and the semi-conductor luminescence equipment of efficient white system luminescence is obtained.

[0072] As for the 1st, 2nd, and 3rd fluorescent substance of the above, for the 1st fluorescent substance of the above, the 2nd fluorescent substance of the above is [the 3rd fluorescent substance of the above of the semi-conductor luminescence equipment of 1 operation gestalt] 30 or less % of the weight 20 % of the weight or more 70 or less % of the weight 50 % of the weight or more 20 or less % of the weight 7 % of the weight or more noting that a total amount is 100 % of the weight.

[0073] According to the above-mentioned operation gestalt, since 50-% of the weight or more 70 or less % of the weight and the 2nd fluorescent substance of the above are [7 % of the weight or more 20 or less % of the weight and the 3rd fluorescent substance of the above] 30 or less % of the weight 20 % of the weight or more for the 1st fluorescent substance of the above, the red in which the 1st fluorescent substance with low visibility carries out outgoing radiation compared with a green light in which the 2nd fluorescent substance of the above carries out outgoing radiation, and the blue luminous intensity the 3rd fluorescent substance carries out [luminous intensity] outgoing radiation are strengthened. Therefore, human being's visibility is taken into consideration and the semi-conductor luminescence equipment of white system luminescence of a good color tone is obtained.

[0074] In here, if there are more mixed ratios of the 1st fluorescent substance of the above than 70 % of the weight while it will turn into white of the color tone which green cut, if the luminescent color of semi-conductor luminescence equipment has few mixed ratios of the 1st fluorescent substance than 50 % of the weight, it will turn into white of the color tone which red cut. Moreover, the luminescent color of the above-mentioned semi-conductor luminescence equipment turns into white of the color tone which red cut when there were few mixed ratios of the 2nd fluorescent substance than 7 % of the weight, and if there are more mixed ratios of the 2nd fluorescent substance of the above than 20 % of the weight, it will turn into white of the color tone which green cut. Moreover, the luminescent color of the above-mentioned semi-conductor luminescence equipment turns into white of the color tone which red cut when there were few mixed ratios of the 3rd fluorescent substance than 20 % of the weight, and if there are more mixed ratios of the 3rd fluorescent substance of the above than 30 % of the weight, it will turn into white of the color tone which green cut.

[0075] As for the above-mentioned closure resin, the semi-conductor luminescence equipment of 1 operation gestalt contains the 1st, 2nd, and 3rd fluorescent substance of the above, and the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is one or less [0.5 or more].

[0076] According to the above-mentioned operation gestalt, the semi-conductor luminescence equipment which carries out outgoing radiation of the light of the white system near the natural light is obtained by making the ratio of the AUW of the above-mentioned fluorescent substance to the weight of the above-mentioned closure resin or less [0.5 or more] into one. In addition, if the above-mentioned ratio becomes smaller than 0.5 while the brightness of the outgoing radiation light of semi-conductor luminescence equipment becomes bright and a color tone will become pale, if the above-mentioned ratio becomes larger than 1, while the brightness of the outgoing radiation light of semi-conductor luminescence equipment becomes dark, a color tone will wear redness.

[0077] The luminescence display of 1 operation gestalt is equipped with the light source which used the above-mentioned semi-conductor luminescence equipment, the light guide plate to which the light from the above-mentioned light source is led, and the light filter of green [which are made to penetrate the light from the above-mentioned light guide plate, and carry out a spectrum / the red and green], and blue, and the outgoing radiation light of the above-mentioned semi-conductor luminescence equipment has the wavelength distribution which suited the spectral characteristic of the above-mentioned light filter.

[0078] According to the above-mentioned operation gestalt, the outgoing radiation light from the above-mentioned

semi-conductor luminescence equipment Since it has the above-mentioned red, green, and the wavelength distribution that suited the spectral characteristic of a blue light filter The light to which luminescence wavelength has a peak to a red wavelength field with this light filter, the light which has a peak to the wavelength field where luminescence wavelength is green, and the light which has a peak to the wavelength field where luminescence wavelength is blue — each — since it has suitable reinforcement and a spectrum is carried out — the utilization effectiveness of the light of semi-conductor luminescence equipment — good — moreover — high — it becomes a brightness luminescence display.

[0079] The luminescence display of 1 operation gestalt so that wavelength distribution of the outgoing radiation light of semi-conductor luminescence equipment may suit the spectral characteristic of the above-mentioned light filter The luminescence wavelength of the above-mentioned semi-conductor light emitting device, and the luminescence wavelength of the 1st fluorescent substance of the above, At least one of the luminescence wavelength of the 2nd fluorescent substance of the above, the luminescence wavelength of the 3rd fluorescent substance of the above, the mixed ratio of the 1st, 2nd, and 3rd fluorescent substance of the above, and the ratios of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above, and the ratios of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is adjusted.

[0080] Since according to the above-mentioned operation gestalt it is adjusted certainly and effectively so that the outgoing radiation light from the above-mentioned semi-conductor luminescence equipment may suit the spectral characteristic of the above-mentioned light filter, and the outgoing radiation light from the above-mentioned luminescence display has comparatively large reinforcement by the above-mentioned light filter and a spectrum is carried out to the red of abbreviation monochrome, green, and blue, the above-mentioned luminescence display does not have a color omission etc., and becomes the full color display of high brightness and high contrast.

[0081] The above-mentioned luminescence display of the luminescence display of 1 operation gestalt is a liquid crystal display.

[0082] According to the above-mentioned operation gestalt, there is almost no color omission and the liquid crystal display of high brightness and high contrast is obtained.

[0083]

[Embodiment of the Invention] Hereafter, the operation gestalt of a graphic display explains this invention to a detail.

[0084] Drawing 1 (a), (b), and (c) are the sectional views showing the semi-conductor light emitting device used in the operation gestalt of this invention.

[0085] Drawing 1 (a) is the sectional view showing the semi-conductor light emitting device which has the substrate which consists of an insulating semiconductor material. This semi-conductor light emitting device 7a is carrying out the laminating of the N type gallium nitride system compound semiconductor layer 2, the P type gallium nitride system compound semiconductor layer 3, and the electrode 4 for P type layers that consists of a metal thin film or transparence electric conduction film to order on insulating silicon-on-sapphire 1a. While the pad electrode 5 for N type is formed on the exposed surface formed in right-hand side in drawing 1 (a) of the above-mentioned N type gallium nitride system compound semiconductor layer 2, the pad electrode 6 for P type is formed on the above-mentioned electrode 4 front face for P type layers. If a current is passed between the above-mentioned pad electrode 5 for N type, and the pad electrode 6 for P type, light will be emitted from luminescence field 8a.

[0086] Drawing 1 (b) is the sectional view showing the semi-conductor light emitting device which has the substrate which consists of a conductive semiconductor material. On conductive gallium nitride semi-conductor substrate 1b, this semi-conductor light emitting device 7b carries out the laminating of the electrode 4 for P type layers which consists of the N type gallium nitride system compound semiconductor layer 2, the P type gallium nitride system compound semiconductor layer 3, a metal thin film, or transparence electric conduction film one by one, and is formed. While the pad electrode 5 for N type is formed in the underside of the above-mentioned semi-conductor substrate 1b, the pad electrode 6 for P type is formed in the top face of the above-mentioned electrode 4 for P type layers. If a current is passed between the above-mentioned pad electrode 5 for N type, and the pad electrode 6 for P type, light will be emitted from luminescence field 8b.

[0087] Drawing 1 (c) is the sectional view showing the semi-conductor light emitting device of the type which is made to penetrate a substrate and takes out light. This semi-conductor light emitting device 7c on insulating silicon-on-sapphire 1a (it sets to drawing 1 (c) and is the lower part of silicon-on-sapphire 1a) The laminating of the electrode 4 for P type layers which consists of the N type gallium nitride system compound semiconductor layer 2, the P type gallium nitride system compound semiconductor layer 3, a metal thin film, or transparence electric conduction film is carried out one by one. While forming the pad electrode 5 for N type in the exposed surface of the above-mentioned N type gallium nitride system compound semiconductor layer 2, the pad electrode 6 for P type is formed in the front face of the electrode 4 for P type layers. And as shown in drawing 1 (c), direct ball bonding of the above-mentioned pad electrode 5 for N type and the pad electrode 6 for P type is carried out to metal wiring of submounting which has been arranged under the semi-conductor light emitting device 7c and which is not illustrated etc. by the metal bumps 16a and 16b who consist of Au etc. If a current is passed between the above-mentioned pad electrode 5 for N type, and the pad electrode 6 for P type, light is emitted from the luminescence field 8, and this luminescence light will penetrate the above-mentioned silicon-on-sapphire 1a, and will be emitted up in drawing 1 (c).

[0088] In addition, other ingredients, such as ZnO, GaN, SiC, and ZnSe, may be used for insulating silicon-on-sapphire 1a of the above-mentioned semi-conductor light emitting devices 7a and 7c. Moreover, other ingredients, such as SiC, ZnSe, and Si, may be used for conductive gallium nitride semi-conductor substrate 1b in the above-

mentioned semi-conductor light emitting device 7b. Semi-conductor light emitting device 7b equipped with this conductive semi-conductor substrate 1b. Since an electrode is formed also in the underside of the above-mentioned device 7b. Compared with the semi-conductor light emitting devices 7a and 7b which have insulator substrate 1a and arrange two electrodes on one side, while being able to form the luminescence field of a semi-conductor layer widely in the same size, there is an advantage that mounting to a leadframe or a mounting substrate is easy.

[0089] As an ingredient of the semi-conductor layer in the above-mentioned semi-conductor light emitting devices 7a, 7b, and 7c, although a nitride system compound semiconductor ($\text{In}_x\text{Ga}_y\text{Al}_z\text{N}$ ($x+y+z=1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$)) can use suitably, semiconductor materials, such as SiC and ZnSe, may be used in addition to it.

[0090] As for the above-mentioned semi-conductor light emitting devices 7a, 7b, and 7c, a wavelength field emits light in the light from 390nm to 420nm. Since human being's visibility to the light of this wavelength field is very low, if the fluorescent substance which changes the light of this wavelength field into the light of other wavelength is used, only the color of the light changed by this fluorescent substance will be recognized as the luminescent color, and the semi-conductor luminescence equipment which has a good color tone will be obtained. If the wavelength of a semi-conductor light emitting device is longer than 420nm, it becomes human being's eyes that it is easy to be recognized as the light, and the light by which wavelength conversion was carried out with the fluorescent substance will be mixed with a direct outgoing radiation light from a semi-conductor light emitting device, and the color tone of the luminescent color will worsen. Moreover, if the wavelength of a semi-conductor light emitting device is shorter than 390nm, this light will carry out melanism of the mould resin as opposed to the resin part currently used for semi-conductor luminescence equipment, and will do the adverse effect of reducing brightness, or deteriorating resin and reducing dependability while it becomes ultraviolet rays harmful to the body.

[0091] Next, the fluorescent substance used for the semi-conductor luminescence equipment of this invention is stated to a detail.

[0092] A following table 1 and a following table 2 are a table having shown the result of having excited various fluorescent substances and having evaluated luminescence brightness using the semi-conductor light emitting device which created the gallium nitride system compound semiconductor whose peak of luminescence wavelength is 410nm as a light emitting device. Moreover, the peak wavelength (nm) of luminescence which excited the above-mentioned fluorescent substance and was obtained is shown simultaneously. In red, green, blue, a bluish green color, and each orange luminescent color, assessment of the brightness of luminescence measured the luminescence brightness for every fluorescent substance, evaluated superiority or inferiority, and gave x to what is inferior to what luminescence brightness is inferior to an excellent thing in O, and is a little inferior to an ordinary thing in O in **. The luminescent color shows red, the peak wavelength about a green fluorescent substance, and the assessment result of brightness, and, as for a table 1, the luminescent color shows blue and a bluish green color, the peak wavelength about an orange fluorescent substance, and the assessment result of brightness, as for a table 2.

[0093]

[A table 1]

発光色	蛍光体	発光ピーク 波長 (nm)	評価
赤色	$\text{La}_2\text{O}_2\text{S}:\text{Eu}$	623	◎
	$\text{Gd}_2\text{O}_2\text{S}:\text{Eu}$	625	○
	$\text{Y}_2\text{O}_2\text{S}:\text{Eu}$	626	△
	$0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2:\text{Mn}$	658	◎
	$\text{Y}_2\text{O}_3:\text{Eu}$	611	△
	$\text{Y}(\text{P}, \text{V})\text{O}_4:\text{Eu}$	618	△
	$\text{YVO}_4:\text{Eu}$	618	△
	$\text{CaS}:\text{Eu}$	655	○
	$\text{CaS}:\text{Eu}, \text{Tm}$	650	◎
	$\text{BaMg}_2\text{Al}_{10}\text{O}_{27}:\text{Eu}, \text{Mn}$	515	○
緑色	$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}, \text{Mn}$	512	○
	$\text{ZnS}:\text{Cu}$	527	△
	$\text{SrAl}_2\text{O}_4:\text{Eu}$	522	◎
	$\text{SrAl}_2\text{O}_4:\text{Eu}, \text{Dy}$	522	○
	$\text{ZnO}:\text{Zn}$	508	△
	$\text{Zn}_2\text{Ge}_2\text{O}_4:\text{Mn}$	537	○
	$\text{Zn}_2\text{SiO}_4:\text{Mn}$	525	○
	$\text{Ba}_3\text{MgSi}_2\text{O}_8:\text{Eu}, \text{Mn}$	512	○
	$\text{Sr}_3\text{MgSi}_2\text{O}_8:\text{Eu}, \text{Mn}$	532	○

[0094]

[A table 2]

発光色	蛍光体	発光ピーク波長 (nm)	評価
青色	$(\text{Sr}, \text{Ca}, \text{Ba}, \text{Ce})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	457	◎
	$\text{BaMg}_2\text{Al}_{16}\text{O}_{27}:\text{Eu}$	455	◎
	$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}$	452	○
	$\text{ZnS}:\text{Ag}$	450	△
	$\text{Sr}_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	447	○
	$\text{Ca}_{10}(\text{PO}_4)_6\text{F}_2:\text{Sb}$	480	△
	$\text{Sr}_3\text{MgSi}_2\text{O}_8:\text{Eu}$	462	○
	$\text{SrMgSi}_2\text{O}_8:\text{Eu}$	460	△
	$\text{SrAl}_{12}\text{O}_{19}:\text{Eu}$	400	×
	$\text{Sr}_2\text{P}_2\text{O}_7:\text{Eu}$	420	△
	$\text{CaAl}_2\text{O}_4:\text{Eu}, \text{Nd}$	440	△
	$\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}$	492	◎
青緑色	$\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}, \text{Dy}$	492	◎
	$(\text{Ba}, \text{Ca}, \text{Mg})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	482	○
	$\text{Sr}_2\text{Si}_3\text{O}_8 \cdot 2\text{SrCl}_2:\text{Eu}$	490	△
橙色	$\text{ZnS}:\text{Mn}$	586	○
	$\text{ZnS}:\text{Cu}, \text{Mn}, \text{Co}$	580	○

As shown in a table 1, in order to obtain the luminescent color of the red of high brightness, the fluorescent substance of $\text{La}_2\text{O}_2\text{S}:\text{Eu}$, 0.5MgF_2 and $3.5\text{MgO}-\text{GeO}_2:\text{Mn}$, $\text{CaS}:\text{Eu}$, and Tm is suitable, and in order to obtain the green luminescent color of high brightness, the fluorescent substance of $\text{SrAl}_2\text{O}_4:\text{Eu}$ is suitable. moreover — as shown in a table 2, in order the fluorescent substance of $10(\text{Sr}, \text{calcium}, \text{Ba}, \text{Ce})(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$ is suitable in order to obtain the blue luminescent color of high brightness and to obtain the luminescent color of the bluish green color of high brightness — $\text{Sr}_4\text{aluminum}_{14}\text{O}_{25}:\text{Eu}$ and $\text{Sr}_4\text{aluminum}_{14}\text{O}_{25}:$ — the fluorescent substance of Eu and Dy is suitable.

[0095] Drawing 2 thru/or 7 are drawings having shown the emission spectrum and excitation spectrum of the main fluorescent substances which are used for the operation gestalt of this invention. An axis of abscissa is wavelength (nm) and any drawing of an axis of ordinate is relative intensity (%).

[0096] The luminescence wavelength of the semi-conductor light emitting device used for this invention is 390nm thru/or 420nm. The more nearly optimal luminescence wavelength range changes with the class of fluorescent substance excited by the luminescence wavelength of a semi-conductor light emitting device, and the luminescent color of a fluorescent substance.

[0097] For example, when it is going to obtain the luminescent color of the red which has a luminescence wavelength peak in 658nm by fluorescent substance 0.5MgF_2 and $3.5\text{MgO}-\text{GeO}_2:\text{Mn}$ shown in drawing 2 (a), it is effective for the wavelength range of 410nm thru/or 420nm to excite the above-mentioned fluorescent substance by the semi-conductor light emitting device which has the peak of luminescence wavelength so that clearly from drawing 2 (b).

[0098] It is effective to, excite the above-mentioned fluorescent substance on the other hand, by the semi-conductor light emitting device which has the luminescence wavelength of 390nm so that clearly from drawing 3 (b) when it is going to obtain the luminescent color of the red which is fluorescent substance $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ shown in drawing 3 (a), and has a luminescence wavelength peak in 623nm.

[0099] Originally, although the peak of the excitation wavelength of fluorescent substance 0.5MgF_2 , $3.5\text{MgO}-\text{GeO}_2:\text{Mn}$, and $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ is in a short wavelength side from 390nm If the luminescence wavelength of the semi-conductor light emitting device which excites a fluorescent substance is shorter than 390nm Since ultraviolet rays harmful to the body will be emitted, it is not practical, and ***** is also given to the resin part currently used for semi-conductor luminescence equipment, and it becomes the cause of lowering of the brightness by the melanism of closure resin, or lowering of the dependability by deterioration of resin.

[0100] Besides the above-mentioned fluorescent substance, $\text{Gd}_2\text{O}_2\text{S}:\text{Eu}$, $\text{Y}_2\text{O}_2\text{S}:\text{Eu}$, $\text{Y}_2\text{O}_3:\text{Eu}$, $\text{Y}(\text{P}, \text{V})\text{O}_4:\text{Eu}$, $\text{YVO}_4:\text{Eu}$, etc. are available with the operation gestalt of this invention. Moreover, these fluorescent substances can be more effectively changed into the light of the red whose peaks of luminescence wavelength are 600nm thru/or 670nm by using more than one using the outgoing radiation light of a semi-conductor light emitting device.

[0101] moreover, fluorescent substance BaMg₂aluminum₁₆O₂₇: shown in drawing 4 (a) — it is Eu and Mn, and when it is going to obtain the green luminescent color which has a luminescence wavelength peak in 515nm, it is effective to excite the above-mentioned fluorescent substance by the semi-conductor light emitting device which has the luminescence wavelength of 390nm so that clearly from drawing 4 (b).

[0102] It is effective for the wavelength range of 390nm thru/or 420nm to excite the above-mentioned fluorescent substance by the semi-conductor light emitting device which has the peak of luminescence wavelength so that clearly [, on the other hand, it is fluorescent substance SrAl₂O₄:Eu shown in drawing 5 (a), and] from drawing 5 (b), when it is going to obtain the green luminescent color which has a luminescence wavelength peak in 522nm.

[0103] original — fluorescent substance BaMg₂aluminum₁₆O₂₇:. although the peak of the excitation wavelength of Eu, Mn, and SrAl₂O₄:Eu is in a short wavelength side from 390nm If the luminescence wavelength of the semi-conductor light emitting device which excites a fluorescent substance is shorter than 390nm Since ultraviolet rays harmful to the body will be emitted, it is not practical, and it has an adverse effect also on the resin part currently used for semi-conductor luminescence equipment, and becomes the cause of lowering of the brightness by the melanism of closure resin, or lowering of the dependability by deterioration of resin.

[0104] except for the above-mentioned fluorescent substance — the operation gestalt of this invention — ZnS:Cu and SrAl₂O₄: — Eu, Dy, ZnO:Zn, Zn₂germanium₂O₄:Mn, Zn₂SiO₄:Mn, and Ba<SUB>3MgSi₂O₈: — Eu, Mn, and Sr₃MgSi₂O₈: — Eu, Mn, etc. are available. Moreover, these fluorescent substances can be more effectively changed into a green light whose peaks of luminescence wavelength are 500nm thru/or 540nm by using more than one using the outgoing radiation light of a semi-conductor light emitting device.

[0105] Moreover, when it is going to obtain the blue luminescent color which has a luminescence wavelength peak in 457nm, it is effective [it is fluorescent substance (Sr, calcium, Ba, Ce) 10(PO₄).6Cl₂:Eu shown in drawing 6 (a), and] for the wavelength range of 390nm thru/or 400nm to excite the above-mentioned fluorescent substance by the semi-conductor light emitting device which has the peak of luminescence wavelength so that clearly from drawing 6 (b). Originally, although the peak of the excitation wavelength of fluorescent substance (Sr, calcium, Ba, Ce) 10(PO₄).6Cl₂:Eu is in a short wavelength side from 390nm If the luminescence wavelength of the semi-conductor light emitting device which excites a fluorescent substance is shorter than 390nm Since ultraviolet rays harmful to the body will be emitted, it is not practical, and it has an adverse effect also on the resin part currently used for semi-conductor luminescence equipment, and becomes the cause of lowering of the brightness by the melanism of closure resin, or lowering of the dependability by deterioration of resin.

[0106] It is effective to, excite the above-mentioned fluorescent substance on the other hand, by the semi-conductor light emitting device which has the luminescence wavelength of 390nm so that clearly [it is fluorescent substance BaMgAl₁₀O₁₇:Eu shown in drawing 7 (a), and] from drawing 7 (b), when it is going to obtain the blue luminescent color which has a luminescence wavelength peak in 452nm. Since ultraviolet rays harmful to the body will be emitted when the luminescence wavelength of the semi-conductor light emitting device which excites a fluorescent substance is originally shorter than 390nm, although the peak of the excitation wavelength of fluorescent substance BaMgAl₁₀O₁₇:Eu is in 390nm, it is not practical, and it has an adverse effect also on the resin part currently used for semi-conductor luminescence equipment, and becomes the cause of lowering of the brightness by the melanism of closure resin, or lowering of the dependability by deterioration of resin.

[0107] except for the above-mentioned fluorescent substance — the operation gestalt of this invention — BaMg₂aluminum₁₆O₂₇:Eu, ZnS:Ag, and Sr₁₀(PO₄).6Cl₂: — Eu, calcium₁₀(PO₄).6F₂:Sb, Sr₃MgSi₂O₈:Eu, SrMgSi₂O₈:Eu, Sr₂P₂O₇:Eu, and CaAl₂O₄: — Eu, Nd, etc. are available. Moreover, the outgoing radiation light of a semi-conductor light emitting device can be more effectively changed into a blue light whose peaks of luminescence wavelength are 410nm thru/or 480nm by using two or more these fluorescent substances.

[0108] It Eu(s) and D(ies). furthermore, an activity application — responding — Sr₄aluminum₁₄O₂₅:Eu and Sr₄aluminum₁₄O₂₅: — Any one of fluorescent substances, such as 10(PO₄).6Cl₂:Eu, and Sr₂Si₃O₈, 2SrCl₂:Eu, (Ba, calcium, Mg) Or the outgoing radiation light of a semi-conductor light emitting device is effectively convertible for the light of the bluish green color whose peaks of luminescence wavelength are 480nm thru/or 500nm by using plurality.

[0109] Moreover, the outgoing radiation light of a semi-conductor light emitting device is convertible for a fluorescent substance by using ZnS:Mn, ZnS:Cu, and Mn and Co at an orange light whose peaks of luminescence wavelength are 570nm thru/or 600nm.

[0110] Hereafter, the semi-conductor luminescence equipment of the operation gestalt of this invention is explained in detail with reference to a drawing.

[0111] (1st operation gestalt) Drawing 8 (a) thru/or (c) are the sectional views showing the semi-conductor luminescence equipment of the 1st operation gestalt of this invention.

[0112] Drawing 8 (a) is the sectional view of the ramp-type semi-conductor luminescence equipment which closed the above-mentioned semi-conductor light emitting device 7a with the mould resin as closure resin of the shape of ramp type which it had [shape] semi-conductor light emitting device 7a which has an insulating substrate, and distributed the fluorescent substance.

[0113] This semi-conductor luminescence equipment has mounting section 10a which is the depression of a cup configuration at the head of the leadframe 101 as a base. The above-mentioned semi-conductor light emitting device 7a is being fixed to mounting section 10a of this cup configuration with the adhesives 11 which consist of an epoxy resin etc. P lateral electrode 6a prepared in the top face of the above-mentioned semi-conductor light emitting device 7a is connected to polar-zone 10b of a leadframe 101 by metal wire 6p which consists of Au,

aluminum, Cu, etc. Moreover, N lateral electrode 5a prepared in the top face of the above-mentioned semi-conductor light emitting device 7a is connected to polar-zone 10c of the right-hand side leadframe 102 by metal wire 5n. And the upper part of above-mentioned semi-conductor light emitting device 7a and a leadframe 101,102 is closed with the mould resin 130 which distributed the fluorescent substance, such as an epoxy resin of translucency, and ramp type-like semi-conductor luminescence equipment is formed. In addition, the adhesives 11 which join the above-mentioned semi-conductor light emitting device 7a and mounting section 10a of a leadframe 101 will not be limited especially if it is the ingredient which does not absorb the light from semi-conductor light emitting device 7a. For example, the resin ingredient containing the ingredient which reflects and scatters the other light efficiently etc. may be used for mounting section 10a of a leadframe 101 from the resin ingredient which mixed the thermally conductive good metallic material for the heat-characteristic improvement of the above-mentioned semi-conductor light emitting device 7a, and above-mentioned semi-conductor light emitting device 7a.

[0114] Drawing 8 (b) is the sectional view of the ramp-type semi-conductor luminescence equipment which closed the above-mentioned semi-conductor light emitting device 7b with the mould resin 130 as closure resin of the shape of ramp type which it had [shape] semi-conductor light emitting device 7b which has a conductive substrate, and distributed the fluorescent substance. Among drawing, the part which has the same function as the semi-conductor luminescence equipment shown in drawing 8 (a) attaches the same reference number, and omits detailed explanation.

[0115] As for this semi-conductor luminescence equipment, direct continuation of the N lateral electrode section 5of above-mentioned semi-conductor light emitting device 7b b is carried out to mounting section 10a of a leadframe 101 by the adhesives 15 which consist of the conductive wax material or Au-epoxy resin which consists of metal systems, such as an indium, an Ag-epoxy resin, etc. On the other hand, P lateral electrode 6b prepared in the top face of the above-mentioned semi-conductor light emitting device 7b is connected to polar-zone 10c of the right-hand side leadframe 102 by metal wire 6p in drawing 8 (b). And the upper part of above-mentioned semi-conductor light emitting device 7b and a leadframe 101,102 is closed with the mould resin 130 which distributed the fluorescent substance, and forms ramp type-like semi-conductor luminescence equipment. Since the electrodes 6b and 5b with which semi-conductor light emitting device 7b was prepared up and down are the same as that of the semi-conductor light emitting device of the conventional GaAs system or a GaP system, the leadframe used for conventional semi-conductor luminescence equipment can be used as it is.

[0116] Drawing 8 (c) is the sectional view of the ramp-type semi-conductor luminescence equipment which closed the above-mentioned semi-conductor light emitting device 7c with the mould resin 130 as closure resin of the shape of ramp type which it had [shape] semi-conductor light emitting device 7c which has an insulating substrate, and this semi-conductor light emitting device 7c and leadframe 103,103 were connected [shape], without using a metal wire, and distributed the fluorescent substance.

[0117] This semi-conductor luminescence equipment has connected the submounting 17 as a base at the head of the leadframe 103,103 which countered mutually and has been arranged. This submounting 17 consists of Si, it is insulation and the electrode wiring 17a and 17b is formed in the top face of the submounting 17. The above-mentioned semi-conductor light emitting device 7c makes a semi-conductor layer side face (bottom side of semi-conductor light emitting device 7c in drawing 1 (c)) counter the top face of this submounting 17, and is carried in it. P lateral electrode 6c and N lateral electrode 5c which were prepared in the bottom side of the above-mentioned semi-conductor light emitting device 7c are connected to the electrode wiring 17a and 17b formed in the top face of the above-mentioned submounting 17 using Au bump etc. It connected with the points 10d and 10e of a leadframe, and the electrode wiring 17a and 17b formed in the top face of the above-mentioned submounting 17 is connected to the exterior and an electric target. And it closes with the mould resin 130 which consists a fluorescent substance of a distributed epoxy resin in above-mentioned semi-conductor light emitting device 7c and the submounting 17, and the upper part of a leadframe 103,103, and ramp type-like semi-conductor luminescence equipment is formed. Since this semi-conductor luminescence equipment is carrying out direct continuation of the above-mentioned semi-conductor light emitting device 7c to the submounting 17, it has the advantage that the heat from the luminescence field of the above-mentioned semi-conductor light emitting device 7c can be quickly missed to the exterior of semi-conductor luminescence equipment through the submounting 17 and a leadframe 103,103.

[0118] The semi-conductor luminescence equipment of the shape of ramp type shown in drawing 8 (a), (b), and (c) The light emitted has the other directivity above drawing 8 (a), (b), and (c). Especially the semi-conductor luminescence equipment of drawing 8 (a) and (b) Since the light by which outgoing radiation was carried out from the semi-conductor light emitting devices 7a and 7b is condensed efficiently, mounting section 10a of a leadframe 101 is formed in the cup configuration. The thermosetting which has the translucency of silicon resin, urethane resin, polycarbonate resin, etc. in addition to an epoxy resin, and thermoplastic resin may be used for the above-mentioned mould resin 130. Moreover, although the mould resin 130 whole may be made to distribute the above-mentioned fluorescent substance to homogeneity, if the content ratio of a fluorescent substance is gradually made high toward the semi-conductor light emitting devices 7a, 7b, and 7c from the front face of mould resin 130, degradation of the fluorescent substance under the effect of the moisture from the outside of mould resin 130 etc. can be reduced. moreover, the fluorescent substance by the semi-conductor light emitting devices 7a, 7b, and 7c if the content ratio of a fluorescent substance is gradually made high toward the front face of mould resin 130 from the semi-conductor light emitting devices 7a, 7b, and 7c — electric and thermal effect can also be eased. Thus, distribution of the fluorescent substance in mould resin 130 can make various gestalten according to the class of mould resin, the class of fluorescent substance, an operating environment, conditions, or an application.

[0119] (2nd operation gestalt) Drawing 9 (a) and (b) are the sectional views having shown the semi-conductor luminescence equipment in the 2nd operation gestalt of this invention. The semi-conductor luminescence equipment of drawing 9 (a) is the same as the semi-conductor luminescence equipment shown in drawing 8 (a) except mould resin 131 not containing a fluorescent substance while being filled up with a fluorescent substance in mounting section 10a of a leadframe 101. Also about the semi-conductor luminescence equipment of drawing 9 (b), while being filled up with a fluorescent substance in mounting section 10a of a leadframe 101, it is the same as that of the semi-conductor luminescence equipment shown in drawing 8 (b) except mould resin 131 not containing a fluorescent substance. Therefore, the same reference number is given to the part which has the same function as the semi-conductor luminescence equipment shown in drawing 8 (a) and (b), and detailed explanation is omitted. Also in other following operation gestalten, it is the same.

[0120] While the semi-conductor luminescence equipment shown in drawing 9 (a) and (b) arranges the semi-conductor light emitting devices 7a and 7b at the bottom of mounting section 10a of a cup configuration, it fills up this mounting section 10a with a fluorescent substance 12, and he is trying to change the wavelength of the light from the semi-conductor light emitting devices 7a and 7b with this fluorescent substance 12. That is, by arranging the above-mentioned fluorescent substance 12 to mounting section 10a which collects the light from the semi-conductor light emitting devices 7a and 7b, it does not leak, the light from the semi-conductor light emitting devices 7a and 7b is transformed, and the conversion efficiency of light is raised. Therefore, compared with the case where the whole mould resin [as / in the operation gestalt of the above 1st] is made to distribute a fluorescent substance, the color tone of semi-conductor luminescence equipment is good, and since what is necessary is to arrange a fluorescent substance only in mounting section 10a moreover, the amount of the fluorescent substance used is reduced.

[0121] In the above-mentioned operation gestalt, although filled up with the fluorescent substance 12 in [of a leadframe 101 / whole] mounting section 10a, as long as the bleedoff light from the semi-conductor light emitting devices 7a and 7b is convertible for wavelength predetermined enough, you do not need to make it filled up with a fluorescent substance 12 in [whole] mounting section 10a not necessarily, and a concave may be filled up with a fluorescent substance 12 in mounting section 10a. Or what is necessary is to have been filled up with the fluorescent substance 12 so that it might rise to convex rather than the above-mentioned mounting section 10a upper bed, and just to, have filled up mounting section 10a with the fluorescent substance 12 of an amount which can change the wavelength of the light from the semi-conductor light emitting devices 7a and 7b into desired wavelength in short.

[0122] (3rd operation gestalt) Drawing 10 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment of the 3rd operation gestalt of this invention. The semi-conductor luminescence equipment of drawing 10 (a) is the same as the semi-conductor luminescence equipment shown in drawing 9 (a) in mounting section 10a of a leadframe 101 except having arranged pre coating 13a so that the whole semi-conductor light emitting device 7a may be covered, and having arranged the fluorescent substance 12 on it. It is the same as that of the semi-conductor luminescence equipment shown in drawing 9 (b) except having arranged pre coating 13a so that having arranged the fluorescent substance 12 on it also about the semi-conductor luminescence equipment of drawing 10 (b). Therefore, the same reference number is given to the part which has the same function as the semi-conductor luminescence equipment shown in drawing 9 (a) and (b), and detailed explanation is omitted.

[0123] In drawing 10 (a) and (b), pre coating 13a which consists of an epoxy resin, silicon resin, urethane resin, etc. so that the semi-conductor light emitting devices 7a and 7b may be arranged and this semi-conductor light emitting device 7a and the whole 7b may be covered is formed in the bottom of mounting section 10a of the cup configuration formed at left-hand side leadframe 101 head. The fluorescent substance 12 is arranged in the shape of a layer so that the above-mentioned mounting section 10a inside may be filled on this pre coating 13. The above-mentioned fluorescent substance 12 carries out dipping of the mounting section 10a in which pre coating 13a was formed, or forms it on the pre coating 13 potting or the fuel spray, and by vapor-depositing on pre coating 13a in mounting section 10a. In drawing 10 (a) and (b), although the fluorescent substance 12 was formed only inside [mounting section 10a] the leadframe 101, you may form so that all the top faces of a leadframe 101 may be covered.

[0124] The above-mentioned fluorescent substance 12 sets the abbreviation equal distance by pre coating 13a from the luminescence field of the semi-conductor light emitting devices 7a and 7b, and the semi-conductor luminescence equipment shown in drawing 10 (a) and (b) is formed in homogeneity thickness. Therefore, a uniform luminescence light in which this semi-conductor luminescence equipment does not have nonuniformity is obtained by that abbreviation etc. requires the quantity of light passed in all the fields of a fluorescent substance 12 by carrying out. Moreover, since a fluorescent substance 12 is arranged in the location estranged from the semi-conductor light emitting devices 7a and 7b, the electric and thermal effect of a semi-conductor light emitting device to a fluorescent substance 12 can be eased. Consequently, a luminescence property is good and, moreover, semi-conductor luminescence equipment with sufficient endurance is obtained.

[0125] (4th operation gestalt) Drawing 11 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment by the 4th operation gestalt of this invention.

[0126] Drawing 11 (a) carries semi-conductor light emitting device 7a which has an insulating substrate on the printed-circuit board 18 as a base, and is closing the above-mentioned semi-conductor light emitting device 7a with the mould resin 132 as closure resin which distributed the fluorescent substance.

[0127] This semi-conductor luminescence equipment has pasted up semi-conductor light emitting device 7a with the adhesives 11 which consist of an epoxy resin on the printed-circuit board 18 of the rectangular parallelepiped configuration which consists of glass epoxy which has thermal resistance. P lateral electrode 6a and N lateral electrode 5a which were prepared in the top face of this semi-conductor light emitting device 7a are respectively connected to the polar zone 18a and 18b of printed-circuit board 18 top face by the metal wires 6p and 5n. Through the through hole of the shape of cross-section radii which connects the top face and underside of a printed-circuit board 18 which is not illustrated, these polar zone 18a and 18b was taken about on the underside of the printed-circuit board 18 as a component side, and is prolonged even to the both ends of this component side. In addition, an insulating film may be used for the above-mentioned printed-circuit board 18.

[0128] And on the above-mentioned printed-circuit board 18, it forms so that a parabolic edge section as shows the mould resin 132 which distributed the fluorescent substance, such as an epoxy resin as closure resin (for example, translucency), to drawing 11 (a) may be made, and the semi-conductor luminescence equipment of a chip part shape is formed so that the above-mentioned whole semi-conductor light emitting device 7a may be covered.

[0129] The adhesives 11 on which the above-mentioned semi-conductor light emitting device 7a and a printed-circuit board 18 are pasted up will not be limited especially if it is the ingredient with which the light from semi-conductor light emitting device 7a is not absorbed. For example, the resin ingredient which mixed the thermally conductive good metallic material for the heat-characteristic improvement of semi-conductor light emitting device 7a, the resin ingredient containing the ingredient which reflects and scatters efficiently the light emitted toward the printed-circuit board 18 from semi-conductor light emitting device 7a, etc. may be used. However, to use the resin ingredient containing a metallic material, it is necessary to take care that P lateral electrode 6a and N lateral electrode 5a do not connect too hastily.

[0130] Drawing 11 (b) is the same as that of the semi-conductor luminescence equipment of drawing 11 (a) except having semi-conductor light emitting device 7c which changes to semi-conductor light emitting device 7a in drawing 11 (a), and has an insulating substrate. Therefore, the same reference number is given to the part which has the same function as drawing 11 (a), and detailed explanation is omitted.

[0131] In the semi-conductor luminescence equipment of drawing 11 (b), semi-conductor light emitting device 7c carries out outgoing radiation of the light through the insulating substrate located in an upside in drawing 11 (b) of semi-conductor light emitting device 7c. The above-mentioned semi-conductor light emitting device 7c is carrying out direct continuation of P lateral electrode 6c and N lateral electrode 5c which were formed in the semi-conductor laminating side which is the bottom in drawing 11 (b) to the polar zone 18a and 18b on a printed-circuit board 18 respectively through Au bump. In addition, semi-conductor light emitting device 7c may be carried in submounting which consists of Si beforehand given to metal wiring, and this submounting may be electrically connected to a printed-circuit board 18 with die bond, wire bond, etc. Since this semi-conductor luminescence equipment turns the field by the side of a semi-conductor laminating to a printed-circuit board 18 and mounts semi-conductor light emitting device 7c, it can miss quickly the heat from the luminescence field of the above-mentioned semi-conductor light emitting device 7c to the exterior.

[0132] The thermosetting which has the translucency of silicon resin, urethane resin, Pori force-BONETO resin, etc. in addition to an epoxy resin, and thermoplastic resin may be used for the mould resin 132 in the semi-conductor luminescence equipment of drawing 11 (a) and (b). Moreover, although the mould resin 132 whole may be made to distribute a fluorescent substance to homogeneity, if the content ratio of a fluorescent substance is gradually made high toward a semi-conductor light emitting device from the front face of mould resin 132, degradation of the fluorescent substance under the effect of moisture etc. can be reduced. Moreover, if the content ratio of a fluorescent substance is gradually made high toward the front face of mould resin 132 from the semi-conductor light emitting devices 7a and 7c, the electric and thermal effect of the semi-conductor light emitting devices 7a and 7c to a fluorescent substance can be eased. Thus, distribution of the fluorescent substance in mould resin 132 can make various gestalten according to the class of mould resin, the class of fluorescent substance, an operating environment, conditions, an application, etc.

[0133] In addition, it may change to the above-mentioned semi-conductor light emitting devices 7a and 7c, and semi-conductor light emitting device 7b which has a conductive substrate may be used. In this case, direct continuation of the N type electrode formed in the underside of semi-conductor light emitting device 7b is carried out to one electrode on a printed-circuit board with the adhesives which have conductivity. P lateral electrode prepared in the top face of the above-mentioned semi-conductor light emitting device 7b is connected to the polar zone of another side on a printed-circuit board with a metal wire. Like the semi-conductor luminescence equipment of the conventional GaAs system or a GaP system, since the above-mentioned semi-conductor light emitting device 7b has an electrode to vertical both sides of semi-conductor light emitting device 7b, it has the advantage that the conventional leadframe can be used as it is.

[0134] (5th operation gestalt) Drawing 12 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment of the 5th operation gestalt of this invention. The semi-conductor luminescence equipment of drawing 12 (a) is equipped with the frame 19 which consists of resin on the printed-circuit board 18 as a base. Semi-conductor light emitting device 7b which is on this printed-circuit board 18, and has a conductive substrate inside the above-mentioned resin frame 19 is arranged. And it is filled up with the mould resin 134 as closure resin which contains a fluorescent substance inside the above-mentioned resin frame 19, and semi-conductor light emitting device 7b is closed.

[0135] This semi-conductor luminescence equipment has formed the frame 19 which consists of resin on the

printed circuit board 18 of the rectangular parallelepiped configuration which consists of glass epoxy which has thermal resistance. When this resin frame 19 is filled up with mould resin 134 inside, it has the height whose resin 134 is fully wrap extent about semi-conductor light emitting device 7b. In the inside of this frame 19, one polar-zone 18a on a printed-circuit board 18 and N lateral electrode 5b under semi-conductor light emitting device 7b are pasted up and connected with the adhesives which have conductivity. On the other hand, P lateral electrode 6b prepared in the top face of semi-conductor light emitting device 7b is connected to polar-zone 18b of another side on a printed-circuit board 18 by metal wire 6p. Through the through hole of the shape of cross-section radii which penetrates a printed-circuit board 18 which is not illustrated, these polar zone 18a and 18b was taken about in three dimensions from the top face of a printed-circuit board 18 to the underside which is a component side, and is prolonged even to the ends of printed-circuit board 18 underside, respectively. The above-mentioned printed-circuit board 18 top and inside the resin frame 19, it fills up with the mould resin 134 which consists of an epoxy resin of the translucency which distributed the fluorescent substance so that the whole semi-conductor light emitting device 7b may be covered. Since the above-mentioned semi-conductor light emitting device 7b has Electrodes 6b and 5b to vertical both sides like the semi-conductor light emitting device of the conventional GaAs system or a GaP system, it has the advantage that it is common and the conventional leadframe can be used. In addition, as a base, the insulating film other than the above-mentioned printed-circuit board may be used.

[0136] The semi-conductor luminescence equipment of drawing 12 (b) is filled up with the mould resin 134 as closure resin which distributed the fluorescent substance while it is equipped with resin frame 19a on the printed circuit board 18 as a base and is equipped with semi-conductor light emitting device 7c which has an insulating substrate inside this resin frame 19a. The above-mentioned resin frame 19a inclines so that the side face facing semi-conductor light emitting device 7c may reflect the light by which outgoing radiation was carried out to the longitudinal direction from the side face of semi-conductor light emitting device 7c in the direction of a right angle of a printed circuit board 18.

[0137] This semi-conductor luminescence equipment is equipped with resin frame 19a toward which the side face which faces at semi-conductor light emitting device 7c on the printed circuit board 18 of the rectangular parallelepiped configuration which consists of glass epoxy inclined. The above-mentioned semi-conductor light emitting device 7c turns a semi-conductor laminating side face downward, and is carried in the printed-circuit board 18. P lateral electrode 6c and N lateral electrode 5c with which semi-conductor light emitting device 7c is equipped are respectively connected to the polar zone 18a and 18b on a printed-circuit board 18 through Au bump. The above-mentioned polar zone 18a and 18b is taken about in three dimensions to an underside like the semi-conductor luminescence equipment shown in drawing 12 (a) through the through hole which is not illustrated from the top face of a printed-circuit board 18, and is extended even to the underside ends of a printed-circuit board 18. In addition, as a base, the insulating film other than the above-mentioned printed-circuit board 18 may be used. Moreover, although direct continuation of the above-mentioned semi-conductor light emitting device 7c was carried out to the printed-circuit board 18, it may carry semi-conductor light emitting device 7c in submounting which gives metal wiring beforehand and consists of Si, and may connect this submounting to a printed-circuit board 18 electrically with die bond, wire bond, etc.

[0138] Since this semi-conductor luminescence equipment mounts the semi-conductor laminating side face of semi-conductor light emitting device 7c in the immediate printing wiring substrate 18, it has the advantage that the heat from the luminescence field of semi-conductor light emitting device 7c can be quickly missed to the exterior through submounting and a leadframe.

[0139] The mould resin 134 in the semi-conductor luminescence equipment of drawing 12 (a) and (b) is the same ingredient as the mould resin 13 of drawing 8 (a), (b), and (c), and distribution of the fluorescent substance in the above-mentioned mould resin can take various gestalten according to the class of mould resin, the class of fluorescent substance, an operating environment, conditions, an application, etc.

[0140] In drawing 12 (a) and (b), although the above-mentioned resin frames 19 and 19a were stuck on the printed-circuit board 18 after forming them apart from a printed-circuit board 18, they may remove some thicker printed-circuit boards, may form a crevice, and may use the surroundings of this crevice as a frame. Furthermore, while forming a through hole in a printed-circuit board, arranging an electrode-cum-wiring by the metallic foil on the base of this printed-circuit board and arranging a semi-conductor light emitting device after an electrode-cum-this wiring, the above-mentioned through hole part may be closed by closure resin.

[0141] Moreover, in the semi-conductor luminescence equipment of drawing 12 (a) and (b), semi-conductor light emitting device 7a shown in drawing 1 (a) is sufficient as the semi-conductor light emitting devices 7b and 7c, and when this semi-conductor light emitting device 7a is used, they connect the electrode of semi-conductor light emitting device 7a, and the polar zone of a printed-circuit board with a metal wire.

[0142] (6th operation gestalt) Drawing 13 is the sectional view showing the semi-conductor luminescence equipment in the 6th operation gestalt of this invention.

[0143] This semi-conductor luminescence equipment has the same frame 19a as the frame with which the semi-conductor luminescence equipment shown in drawing 12 (b) is equipped. This frame 19a is installed on the printed circuit board 18 as a base of the shape of a rectangular parallelepiped which consists of glass epoxy, and the side face facing semi-conductor light emitting device 7c of this frame 19a inclines so that the light from the side face of semi-conductor light emitting device 7c may be reflected in the direction of a right angle of a printed circuit board 18. The above-mentioned semi-conductor light emitting device 7c is carried on the printed-circuit board 18 so that outgoing radiation of the light may be carried out [in / for a semi-conductor laminating side / drawing 13] from an

upper substrate side towards the bottom in drawing 13. The electrodes 6c and 5c of this semi-conductor light emitting device 7c are being connected to the polar zone 18a and 18b of a printed-circuit board 18 by the bump like the semi-conductor luminescence equipment shown in drawing 12 (b). It is filled up with the mould resin 135 as closure resin of the translucency which consists of an epoxy resin inside frame 19a arranged on the above-mentioned printed-circuit board 18, and the above-mentioned semi-conductor light emitting device 7c is closed. And on above-mentioned frame 19a and mould resin 13, a fluorescent substance 12 has predetermined thickness and is formed in the shape of a layer.

[0144] Since the fluorescent substance 12 is formed in the location of the abbreviation equal distance by the thickness of homogeneity from the luminescence field of semi-conductor light emitting device 7c, in the location of all the fluorescent substances 12, uniform luminescence which does not have nonuniformity by the quantity of light which passes a fluorescent substance 12 becoming abbreviation regularity is possible for the semi-conductor luminescence equipment in this operation gestalt. Moreover, since the above-mentioned fluorescent substance 12 keeps a predetermined distance and is formed from semi-conductor light emitting device 7c, it can ease the electric and thermal effect of a semi-conductor light emitting device to a fluorescent substance 12.

[0145] With the above-mentioned operation gestalt, although the fluorescent substance 12 was formed also in the top face of resin frame 19a, as long as resin frame 19a is formed with the ingredient of protection-from-light nature, it may form a fluorescent substance 12 in the upper chisel of mould resin 135. Moreover, the height of resin frame 19a is made high, after filling up extent slightly exceeding the upper bed of semi-conductor light emitting device 7c with mould resin 13, it is in the above-mentioned resin frame 19a, and a fluorescent substance may be arranged by potting etc. on the above-mentioned mould resin 135.

[0146] The above-mentioned resin frame 19a may use as a frame the heights which removed some thicker printed-circuit boards 18 like the time of describing the semi-conductor luminescence equipment of drawing 12 (b), and remained. Furthermore, an electrode-cum-wiring by the metallic foil may be prepared in the pars basilaris ossis occipitalis of a printed-circuit board which has a through hole, and a crevice may be formed in it.

[0147] Moreover, although the optical drawing effectiveness to the exterior falls, the resin frame in which the side face facing semi-conductor light emitting device 7c was formed vertically may be used.

[0148] In addition, the semi-conductor light emitting devices 7a and 7b shown in drawing 1 may be used for the above-mentioned semi-conductor light emitting device 7c. Especially semi-conductor light emitting device 7b that has a conductive substrate equips an upside and the bottom with an electrode, and since it is the same electrode structure as the semi-conductor light emitting device of the conventional GaAs system or a GaP system, it has the advantage that the conventional leadframe can be used as it is.

[0149] (7th operation gestalt) Drawing 14 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment in the 7th operation gestalt of this invention.

[0150] Drawing 14 (a) is the sectional view which looked at this semi-conductor luminescence equipment from luminescence, and drawing 14 (b) is the sectional view seen from the right angle to the luminescence direction.

[0151] P lateral electrode 6a and N lateral electrode 5a which semi-conductor light emitting device 7a pasted up this semi-conductor luminescence equipment with the adhesives 11, such as an epoxy resin, on the printed-circuit board 18 as a base of the shape of a rectangular parallelepiped which consists of glass epoxy, and were prepared on the top face of this semi-conductor light emitting device 7a are respectively connected to the polar zone 18a and 18b of a printed-circuit board 18 by the metal wires 6p and 5n. These polar zone 18a and 18b was taken about in three dimensions on the underside of a printed-circuit board 18 through the through holes 19 and 19 of the shape of cross-section radii formed by penetrating a printed-circuit board 18, and is prolonged to the ends of the component side which is an underside of this printed-circuit board 18. In addition, it may change to the above-mentioned printed-circuit board 18, and an insulating film may be used.

[0152] Furthermore, the above-mentioned whole semi-conductor light emitting device 7a is closed with the mould resin 136 as closure resin which consists of an epoxy resin of the translucency which distributed the fluorescent substance. While this mould resin 136 has the abbreviation quadrant elliptical cross section where a left side edge and a bottom edge make a straight line in drawing 14 (b), it has the rectangle cross section where the cross direction is longer than the height direction in drawing 14 (a). And the reflector 20 for reflecting the light from above-mentioned semi-conductor light emitting device 7a on the above-mentioned mould resin 136 is formed.

[0153] As for the above-mentioned mould resin 136, it is desirable to use the thermosetting resin which has translucency and can also bear the elevated temperature in the case of a solder reflow in a mounting process, and it forms it by the resin potting method, the transfermold method, the injection molding method, etc. on a printed-circuit board 18. The top face of the above-mentioned mould resin 136 arranges semi-conductor light emitting device 7a more nearly up than center line I-I of this parabola while a parabola is made and it curves, as shown in drawing 14 (b). Moreover, the outgoing radiation side face A of the light of the above-mentioned mould resin 136 is formed evenly, and is made into the side face and abbreviation same side of a printed-circuit board 18. In addition, the curved surface of the above-mentioned mould resin 136 may be formed so that the above-mentioned semi-conductor light emitting device 7a may be caudad located rather than center line I-I of the parabola of a curved surface.

[0154] Including at least the ingredient which reflects the light by which wavelength conversion was carried out with the light and the fluorescent substance 12 of semi-conductor light emitting device 7a, like the above-mentioned mould resin 136, using the thermosetting resin or thermoplastics which can also bear the elevated temperature in the case of a solder reflow, the above-mentioned reflector 20 is formed by the resin potting method, the

transfermold method, the injection molding method, etc. so that the upside side of the above-mentioned mould resin 136 may be covered. The right side edge of a reflector 20 makes a straight line, and as shown in the cross section of drawing 14 (b), while the bottom edge curves in contact with the upside edge of mould resin 136, this reflector 20 is formed so that the right side edge side of the above-mentioned printed-circuit board 18 may be followed, so that the flat surface as the optical outgoing radiation side A of mould resin 136 where a left side edge edge is the same may be made. And the upper bed edge of the above-mentioned reflector is formed in parallel at the above-mentioned printed-circuit board 18. As for this semi-conductor luminescence equipment, the interface of the top face of mould resin 136 and the underside of a reflector 20 is a reflector. While diffusing the light which reflects and carries out outgoing radiation in this reflector on the left-hand side of horizontal in drawing 14 (a), it is interrupted with a reflector 20 and a printed-circuit board 18 in the vertical direction. Therefore, the direct light and the reflected light from semi-conductor light emitting device 7a serve as directional characteristics extracted horizontally. Specifically, the horizontal half power angle in exposure light has ≈ 65 degrees and the directional characteristics whose vertical half power angle is ≈ 30 degrees. therefore — since wavelength conversion is carried out with the fluorescent substance 12 in mould resin 136, it is reflected by the reflector 20 and outgoing radiation of it is carried out from the lateral portion of mould resin 136 to the exterior, while the light from semi-conductor light emitting device 7a carries out direct outgoing radiation — horizontal — an effective exposure field — large — and high — brightness side luminescence mold semi-conductor luminescence equipment can be offered.

[0155] In addition, since the reflector 20 should have reflex action only into the part which touches mould resin 136, it is good to prepare the reflecting layer which becomes either the upside side where mould resin 136 curved, or the bottom side as for which the reflector 20 carried out the bend from a metal, a white coating, etc.

[0156] The resin which pastes up the above-mentioned semi-conductor light emitting device 7a on a printed-circuit board 18 is [that there is especially no definition] available if the light from semi-conductor light emitting device 7a is not absorbed. For example, the resin which mixed the thermally conductive good metal for the heat-characteristic improvement of semi-conductor light emitting device 7a, the resin containing the ingredient which reflects and scatters efficiently the light emitted in the direction of the leadframe mounting section, etc. may be used. However, to use the resin containing a metal, it is necessary to take care that P lateral electrode and N lateral electrode do not short-circuit.

[0157] In addition, in the semi-conductor luminescence equipment in this operation gestalt, it may change to the above-mentioned semi-conductor light emitting device 7a, and semi-conductor light emitting device 7b which equips with an electrode the top face and underside which were shown in drawing 1 (b), respectively, and semi-conductor light emitting device 7c of the type which carries out outgoing radiation of the light from the substrate side shown in drawing 1 (c) may be used. Since the above-mentioned semi-conductor light emitting device 7b has the same electrode structure as the semi-conductor luminescence equipment of the conventional GaAs system or a GaP system, it has the advantage that the conventional leadframe can be used as it is. Since the above-mentioned semi-conductor light emitting device 7c mounts a semi-conductor laminating side face in direct electric wiring, it has the advantage that the heat from a luminescence field can be promptly missed to the exterior through a submounting leadframe.

[0158] (8th operation gestalt) Drawing 15 (a) and (b) are the sectional views showing the side luminescence mold semi-conductor luminescence equipment as 8th operation gestalt of this invention.

[0159] Drawing 15 (a) shows the sectional view which looked at this semi-conductor luminescence equipment from luminescence, and drawing 15 (b) is the sectional view seen from the right angle to the luminescence direction. The semi-conductor luminescence equipment of drawing 15 (a) and (b) used semi-conductor light emitting device 7b which has an electrode for the top face and the underside, Except having formed the fluorescent substance 12 in the outgoing radiation side A side of the light of the mould resin 137 as closure resin in the shape of a layer, without distributing a fluorescent substance in closure resin It is the same as that of the semi-conductor luminescence equipment of drawing 14 (a) and (b), and the same reference number is given to the part which has the same function, and detailed explanation is omitted.

[0160] The amount of the light which passes in the abbreviation whole region of a fluorescent substance 12 becomes always fixed [equipment], since this side luminescence mold semi-conductor luminescence equipment formed the fluorescent substance 12 in the location of the abbreviation equal distance from the luminescence field of semi-conductor light emitting device 7b at the thickness of homogeneity, and uniform luminescence without nonuniformity is attained. Moreover, since the fluorescent substance 12 has been arranged in the location estranged from semi-conductor light emitting device 7b, the effect by the current and heat of semi-conductor light emitting device 7b to a fluorescent substance 12 can be eased. Moreover, since the type which has arranged Electrodes 6b and 5b on the top face and the underside in the above-mentioned semi-conductor light emitting device 7b has same semi-conductor light emitting device and electrode structure of the conventional GaAs system or a GaP system, it has the advantage that the conventional leadframe can be used as it is.

[0161] In the operation gestalt of this invention, the above-mentioned semi-conductor light emitting device 7b may use semi-conductor light emitting device 7a of drawing 1 (a), and semi-conductor light emitting device 7c of drawing 1 (c).

[0162] (9th operation gestalt) Drawing 16 (a) and (b) are drawings showing the side luminescence mold semi-conductor luminescence equipment which is the 9th operation gestalt of this invention.

[0163] Drawing 16 (a) is the sectional view which looked at this semi-conductor luminescence equipment from luminescence, and (b) is the sectional view seen from the right angle to the luminescence direction. This semi-

conductor luminescence equipment is equipped with the mould resin 139 as closure resin which closes semi-conductor light emitting device 7c on the printed-circuit board 18 as a base. This mould resin 139 has the left-hand side of an ellipse, and an abbreviation quadrant elliptical cross section where the lower part was removed and which is a configuration in drawing 16 (b) while having an abbreviation half elliptical cross section where the lower half of an ellipse was removed in drawing 16 (a) and which is a configuration. That is, the above-mentioned mould resin 139 makes the shape of dome shape in which the field except the optical outgoing radiation side A has predetermined radius of curvature in a printed-circuit board 18 top. And the curved-surface part of the lateral surface of this mould resin 139 is covered, fluorescent substance layer 12a as a fluorescent substance is formed, and the reflector 20 for reflecting the light from semi-conductor light emitting device 7c in that lateral surface further is formed.

[0164] Furthermore, the obstruction object 21 as a screen intercepted so that light from semi-conductor light emitting device 7c may not be directly taken out to the exterior is formed in the optical outgoing radiation side A side of semi-conductor light emitting device 7c on a printed-circuit board 18. This obstruction object 21 is seen from the luminescence side A side of semi-conductor luminescence equipment 94 (refer to drawing 16 (a)), it has the height and width of face which interrupt the luminescence field of semi-conductor light emitting device 7c, and an opaque resin metallurgy group etc. is used to the light of semi-conductor light emitting device 7c. Moreover, although the ingredient which absorbs light as an ingredient of the obstruction object 21 may be used, the utilization effectiveness of light worsens in that case. Moreover, as a broken line shows, obstruction object 21a which consists of a resin frame surrounding the surroundings of semi-conductor light emitting device 7c may be used for drawing 16 (b). Moreover, in order to interrupt the light by which direct outgoing radiation is carried out from above-mentioned semi-conductor light emitting device 7c, a crevice may be formed in some thicker printed-circuit boards, and a semi-conductor light emitting device may be arranged so that a luminescence field may hide in this crevice. Since the luminescence field of a semi-conductor light emitting device is located caudad, it can make the height of an obstruction object low, and its utilization effectiveness of light is large while it can miss the heat from a luminescence field quickly to the exterior through a submounting leadframe, since semi-conductor light emitting device 7c connects and carries a semi-conductor laminating side in the immediate printing wiring substrate 18. In addition, it is also possible to use for the semi-conductor luminescence equipment of the 7th operation gestalt which showed above-mentioned Screens 21 and 21a and an above-mentioned crevice to drawing 14 (a) and (b).

[0165] It is reflected by the reflector 20 which touches this fluorescent substance layer 12a after wavelength conversion is carried out by the above-mentioned fluorescent substance layer 12a, and after wavelength conversion is again carried out by fluorescent substance layer 12a, outgoing radiation of the outgoing radiation light from above-mentioned semi-conductor light emitting device 7c is carried out to the semi-conductor luminescence equipment exterior. Therefore, compared with semi-conductor luminescence equipment equipped with the fluorescent substance arranged in the direction of outgoing radiation of light so that the light from a semi-conductor light emitting device may only penetrate, as for this semi-conductor luminescence equipment, it has the wavelength conversion efficiency of abbreviation two times. Therefore, since sufficient wavelength conversion effectiveness is expectable even if it makes fluorescent substance layer 12a thin, the amount of the fluorescent substance used can be reduced and the cost of semi-conductor luminescence equipment can be reduced.

[0166] Although fluorescent substance layer 12a in the above-mentioned operation gestalt made light penetrate and wavelength conversion was performed, it is nontransparent and the fluorescent substance reflected while carrying out wavelength conversion of the light may be formed as a reflector. For example, the fluorescent substance which applied the fluorescence ingredient to the front face with the property to reflect and scatter light of a very fine particle can be considered.

[0167] In addition, in this operation gestalt, the semi-conductor light emitting devices 7a and 7b which change to semi-conductor light emitting device 7c, and are shown in drawing 1 (a) and (b) may be used. Since especially the semi-conductor light emitting device 7 (b) that has a conductive substrate has the same electrode structure as the semi-conductor light emitting device of the conventional GaAs system which has an electrode in a vertical both-sides side, or a GaP system, it can use the conventional leadframe as it is.

[0168] (10th operation gestalt) Drawing 17 (a) and (b) are the sectional views showing the side luminescence mold semi-conductor luminescence equipment as 10th operation gestalt of this invention.

[0169] Drawing 17 (a) shows the sectional view which looked at the above-mentioned semi-conductor luminescence equipment from luminescence, and drawing 17 (b) is the sectional view seen from the right angle to the luminescence direction. The point that this operation gestalt differs from the 9th operation gestalt shown in drawing 16 (a) and (b) The point using semi-conductor light emitting device 7b which changes to semi-conductor light emitting device 7c, and has a conductive substrate, It is a point using printed-circuit board 18a as a base which comes to equip the ultra-thin mold printed-circuit board 23 which changed to the printed-circuit board 18, became the base of the glass epoxy group plate which has a through hole B from the metallic foil, and was equipped with an electrode-cum-wiring.

[0170] As shown in drawing 17 (a) and (b), this side luminescence mold semi-conductor luminescence equipment is installed on the above-mentioned ultra-thin printed-circuit board 23 so that semi-conductor light emitting device 7b may be hidden in the breakthrough B of printed-circuit board 18a. Therefore, since the luminescence field of semi-conductor light emitting device 7b hides thoroughly from the outside while thin shape-ization of semi-conductor luminescence equipment is attained, since the height of semi-conductor light emitting device 7b is absorbable by the thickness of printed-circuit board 18a, the light by which outgoing radiation is carried out does not come out of semi-conductor light emitting device 7b outside directly. That is, since outgoing radiation only of the light from

which wavelength was changed by fluorescent substance layer 12a as a fluorescent substance is carried out to the exterior of semi-conductor luminescence equipment, the color tone of semi-conductor luminescence equipment becomes still better. In addition, the depth of the above-mentioned breakthrough B should just be extent in which the luminescence field of semi-conductor light emitting device 7b sees and hides from the outgoing radiation side A (refer to drawing 17 (b)) side of light at least.

[0171] In addition, in the above-mentioned operation gestalt, the semi-conductor light emitting devices 7a and 7c shown in drawing 1 (a) and (c) may be used for semi-conductor light emitting device 7b. Since a luminescence field is located near the pars basilaris ossis occipitalis of a through hole B when it has arranged in Breakthrough B, semi-conductor luminescence equipment is further made especially as for the above-mentioned semi-conductor light emitting device 7c to a thin shape.

[0172] (11th operation gestalt) Drawing 18 (a), (b), (c) and drawing 19 (a), (b), and (c) are drawings having shown the wavelength distribution of light in which the semi-conductor luminescence equipment of the 11th operation gestalt of this invention carries out outgoing radiation. This semi-conductor luminescence equipment is equipped with a semi-conductor light emitting device on a base, and the outgoing radiation light of this semi-conductor light emitting device has the peak of luminescence wavelength in 410nm of a wavelength field (390nm thru/or 420nm). Furthermore, this semi-conductor luminescence equipment is equipped with the 1st, 2nd, and 3rd fluorescent substance which changes the outgoing radiation light of the above-mentioned semi-conductor light emitting device. The above-mentioned semi-conductor light emitting device is closed by the closure resin which consists of resin substance of the above has been mixed by abbreviation homogeneity, it is contained in this closure resin. The 1st fluorescent substance of the above consists of a fluorescent substance of 0.5MgF₂ and 3.5 MgO-GeO₂:Mn, it is excited by the outgoing radiation light of the above-mentioned semi-conductor light emitting device, and luminescence wavelength carries out outgoing radiation of the red light which has the main peak in 658nm. The 2nd fluorescent substance of the above consists of a fluorescent substance of SrAl₂O₄:Eu, and luminescence wavelength carries out outgoing radiation of the green light which has the main peak in 522nm. The 3rd fluorescent substance of the above consists of a fluorescent substance of BaMgAl₁₀O₁₇:Eu, and luminescence wavelength carries out outgoing radiation of the blue light which has the main peak in 452nm. By carrying out color mixture of the outgoing radiation light from the 1st, 2nd, and 3rd fluorescent substance of the above, this semi-conductor luminescence equipment carries out outgoing radiation of the white light, and is used as the light source for back lights of indicating equipments, such as a cellular phone, and a Personal Digital Assistant, a personal computer. In addition, although it is in a wavelength field (390nm thru/or 420nm), if the peak of the luminescence wavelength of the above-mentioned semi-conductor light emitting device is in a wavelength field (400nm thru/or 420nm), it is more desirable.

[0173] In the above-mentioned semi-conductor luminescence equipment, drawing 18 (a), (b), and (c) are drawings having shown change produced in wavelength distribution of outgoing radiation light, when the mixed ratio of the 1st, 2nd, and 3rd fluorescent substance of the above is changed. An axis of abscissa is wavelength (nm) and all of an axis of ordinate are relative intensity (%). Moreover, also in any, the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is 0.5.

[0174] Drawing 18 (a) is drawing in which the 1st fluorescent substance showed wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case 47 % of the weight and the 2nd fluorescent substance are [13 % of the weight and the 3rd fluorescent substance] 40 % of the weight noting that the total amount of the 1st, 2nd, and 3rd fluorescent substance is 100 % of the weight. The outgoing radiation light of the semi-conductor luminescence equipment in this case becomes the white of the color tone which green cut a little.

[0175] Drawing 18 (b) is drawing in which the 1st fluorescent substance showed wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case 56 % of the weight and the 2nd fluorescent substance are [11 % of the weight and the 3rd fluorescent substance] 33 % of the weight noting that the total amount of the 1st, 2nd, and 3rd fluorescent substance is 100 % of the weight. The outgoing radiation light of the semi-conductor luminescence equipment in this case becomes the white of a good color tone.

[0176] Drawing 18 (c) is drawing in which the 1st fluorescent substance showed wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case 65 % of the weight and the 2nd fluorescent substance are [26 % of the weight and the 3rd fluorescent substance] 9 % of the weight noting that the total amount of the 1st, 2nd, and 3rd fluorescent substance is 100 % of the weight. The outgoing radiation light of the semi-conductor luminescence equipment in this case becomes the white of the color tone which red cut a little, and the so-called daytime white.

[0177] moreover, La₂O₂S:Eu as the 1st fluorescent substance and BaMg₂aluminum₁₆O₂₇: as the 2nd fluorescent substance — the semi-conductor luminescence equipment equipped with Eu, Mn, and 10(Sr, calcium, Mg, Ce) (PO₄)₆Cl₂:Eu as the 3rd fluorescent substance in order at 72 % of the weight, 7 % of the weight, and 21% of the weight of a rate was formed. The outgoing radiation light of this semi-conductor luminescence equipment was the good white light. Furthermore, a white outgoing radiation light also with the good semi-conductor luminescence equipment equipped with the 1st, 2nd, and 3rd fluorescent substance of the above in order at 58 % of the weight, 22 % of the weight, and 20% of the weight of a rate was obtained. While becoming the white of the color tone which green cut when the above experimental result was taken into consideration, and the luminescent color of the above-mentioned semi-conductor luminescence equipment had few mixed ratios of the 1st fluorescent substance, i.e., the

fluorescent substance of red luminescence, than 50 % of the weight, when there were more mixed ratios of the 1st fluorescent substance of the above than 70 % of the weight, it turned out that it becomes the white of the color tone which red cut. Moreover, it turned out that the luminescent color of the above-mentioned semi-conductor luminescence equipment turns into white of the color tone which red cut when there were few mixed ratios of the 2nd fluorescent substance, i.e., the fluorescent substance of green luminescence, than 7 % of the weight, and it will become the white of the color tone which green cut if there are more mixed ratios of the 2nd fluorescent substance of the above than 20 % of the weight. Moreover, it turned out that the luminescent color of the above-mentioned semi-conductor luminescence equipment turns into white of the color tone which red cut when there were few mixed ratios of the 3rd fluorescent substance, i.e., the fluorescent substance of blue luminescence, than 20 % of the weight, and it will become the white of the color tone which green cut if there are more mixed ratios of the 3rd fluorescent substance of the above than 30 % of the weight. therefore, the case where the ratio of the AUW of the 1st [as opposed to the weight of closure resin in the semi-conductor luminescence equipment of the 11th operation gestalt] thru/or the 3rd fluorescent substance is 0.5 — the 1st, 2nd, and 3rd fluorescent substance — 56 % of the weight of each, 11 % of the weight, and 33% of the weight of a mixing ratio — a good white outgoing radiation light is obtained with it being a rate.

[0178] In the above-mentioned semi-conductor luminescence equipment, drawing 19 (a), (b), and (c) are drawings having shown change produced in wavelength distribution of outgoing radiation light, when the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is changed. An axis of abscissa is wavelength (nm) and all of an axis of ordinate are relative intensity (%). Moreover, also in any, for the 1st fluorescent substance, the 2nd fluorescent substance is [the 3rd fluorescent substance] 9% of the weight of a mixed ratio 26% of the weight 65% of the weight noting that the total amount of the 1st, 2nd, and 3rd fluorescent substance is 100 % of the weight.

[0179] Drawing 19 (a) is drawing having shown wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 0.5. The outgoing radiation light of this semi-conductor luminescence equipment becomes the white of the color tone which red cut a little, and the so-called daytime white.

[0180] Drawing 19 (b) is drawing having shown wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 0.66. The outgoing radiation light of this semi-conductor luminescence equipment becomes the white of a good color tone.

[0181] Drawing 19 (c) is drawing having shown wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 1.0. The outgoing radiation light of this semi-conductor luminescence equipment becomes the white of the color tone which green cut a little.

[0182] Drawing 19 (a), (b), and (c) show that a white outgoing radiation light of a color tone with the above-mentioned semi-conductor luminescence equipment good when the 1st, 2nd, and 3rd fluorescent substance of the above is 65 % of the weight, 26 % of the weight, and 9 % of the weight respectively and the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 1.0 or less [0.5 or more] is obtained.

[0183] Drawing 20 is drawing showing the emission spectrum 150 of the semi-conductor luminescence equipment shown in drawing 19 (a), and the effective emission spectrum 152 of the semi-conductor luminescence equipment in consideration of human being's relative luminous efficiency 151. An axis of abscissa is wavelength (nm) and an axis of ordinate is relative intensity (%).

[0184] Since it has a larger luminescence wavelength field than the wavelength field which human being's relative luminous efficiency 151 has and the effective emission spectrum 152 of the wavelength field which covers the wavelength field of the above-mentioned relative luminous efficiency 151 is obtained, in human being's vision, a color tone is made as for the emission spectrum 150 of the above-mentioned semi-conductor luminescence equipment to the good white luminescent color, so that drawing 20 may show.

[0185] Furthermore, since the above-mentioned semi-conductor luminescence equipment is resin which the above-mentioned closure resin does not damage by the outgoing radiation light from a semi-conductor light emitting device, inconvenience, such as melanism, does not produce this closure resin. Therefore, inconvenience, such as lowering of the brightness of semi-conductor luminescence equipment, can be prevented, it continues at a long period of time, and the engine performance of semi-conductor luminescence equipment is made to stability.

[0186] In the above-mentioned semi-conductor luminescence equipment, the wavelength field range of human being's relative luminous efficiency 151, abbreviation, etc. may spread and carry out the wavelength field of the above-mentioned effective emission spectrum 152 by using two or more fluorescent substances of a class for the 1st, 2nd, and 3rd fluorescent substance of the above respectively. Since the luminescence wavelength field of semi-conductor luminescence equipment is made by this only in human being's visible region while being able to make good the color tone of the luminescent color of semi-conductor luminescence equipment, the luminous efficiency of semi-conductor luminescence equipment can be improved.

[0187] Although the semi-conductor luminescence equipment of this operation gestalt mixed the 1st, 2nd, and 3rd fluorescent substance of the above at abbreviation homogeneity to the closure resin which closes a semi-conductor light emitting device Only the 1st, 2nd, and 3rd fluorescent substance of the above may be mixed, and this mixed fluorescent substance may be arranged in the shape of a layer on the front face of closure resin, and the 1st, 2nd, and 3rd fluorescent substance of the above may be respectively prepared in the front face of the above-mentioned

closure resin in the shape of a layer separately. In this case, it is desirable to arrange in consideration of luminescence / absorption wavelength of light etc. toward a side far from the side near a semi-conductor light emitting device in order with the short luminescence wavelength of the fluorescent substance with which that layer contains each layer. Moreover, the semiconductor device of this operation gestalt may be formed in the same structure as the semi-conductor luminescence equipment of the above 1st thru/or the operation gestalt of 10. By this, white luminescence of a good color tone can be obtained in the semi-conductor luminescence equipment of a ramp type, a chip mold, and a side luminescence mold.

[0188] (12th operation gestalt) Drawing 21 is the mimetic diagram showing the luminescence display of the 12th operation gestalt of this invention. This luminescence display 200 is a liquid crystal display which has the light source 201 which consists of semi-conductor luminescence equipment of the operation gestalt of the above 11th, the light guide plate 202 to which the light 205 from the light source 201 is led, and the liquid crystal panel 203 equipped with the light filter which carries out the spectrum of the light from this light guide plate 202.

[0189] The above-mentioned light source 201 may be formed using any of the semi-conductor luminescence equipment of the above 1st thru/or the operation gestalt of 11. Especially when the above-mentioned luminescence display 200 is used as displays, such as a cellular phone, and a Personal Digital Assistant, a personal computer, the semi-conductor luminescence equipment of white luminescence of the operation gestalt of the above 11th is suitable as the light source 201. Moreover, if the 1st, 2nd, and 3rd fluorescent substance with which the semi-conductor luminescence equipment of the operation gestalt of the above 11th is equipped is used as a fluorescent substance of the semi-conductor luminescence equipment of the above 4th thru/or the operation gestalt of 6, it will have a chip part shape and the semi-conductor luminescence equipment for which light can be emitted white will be obtained. Since this semi-conductor luminescence equipment has a chip part shape, the handling at the time of mounting in the luminescence display 200 becomes easy. Moreover, since the semi-conductor luminescence equipment which has the above-mentioned chip part shape can be attached to side-face 202a of the above-mentioned light guide plate 202 direct picking, it can lead luminescence light to a light guide plate 202 efficiently. Moreover, if the light source 201 is constituted using the semi-conductor luminescence equipment carrying the fluorescent substance of the 11th operation gestalt to the semi-conductor luminescence equipment of the above 7th thru/or the operation gestalt of 10 Since this semi-conductor luminescence equipment is a side luminescence mold, so that the printed-circuit board 18 as a base may turn into a light guide plate 202 to abbreviation parallel By attaching semi-conductor luminescence equipment in side-face 202a of a light guide plate, thickness of the luminescence display 200 of the direction of optical outgoing radiation of this light guide plate 202 can be effectively made small. In addition, although two or more semi-conductor luminescence equipments were used for it, as long as the above-mentioned light source 201 has enough luminous intensity, one semi-conductor luminescence equipment may constitute it.

[0190] The above-mentioned light guide plate 202 is formed from a polycarbonate, acrylic resin, etc. Moreover, if the light reflex section is prepared in fields other than side-face 202a into which the light from the light source 201 is introduced, and light emission side 202b which emits the introduced light, the light from the light source 201 can be efficiently emitted from light emission side 202b. Moreover, you may introduce from two side faces which the light to a light guide plate 202 is not only from one side-face 202a, for example, counter, or may introduce from three and four side faces. Furthermore, in order to make bleedoff luminous intensity in light emission side 202b into homogeneity, a light-scattering agent may be mixed into a light guide plate 202, or the field by the side of the bottom in the above-mentioned light emission side 202b and drawing 21 which counters may be made to incline, the light introduced from side-face 202a of a light guide plate may be reflected on the above-mentioned bottom side face in which dip was carried out, and you may emit from light emission side 202b. If a light-scattering pattern is prepared in the above-mentioned bottom side face, reinforcement of the light 206 from light emission side 202b will be further made to homogeneity.

[0191] The above-mentioned liquid crystal panel 203 is equipped with the light filter stuck on the liquid crystal enclosed between two transparent substrates which prepared the transparent electrode, and these two substrates, the polarizing plate, and the above-mentioned substrate. Corresponding to two or more pixels by which the quantity of light which penetrates the above-mentioned liquid crystal is adjusted, red and a green and blue light filter are formed in the above-mentioned light filter by the signal impressed to the above-mentioned transparent electrode. It is a color or a pigment of light transmission nature etc., and it is colored red, green, and blue and red and a green and blue light filter are formed so that this light filter may make the pixel of a minute honeycomb configuration or a delta array configuration to a polycarbonate, polyethylene terephthalate, etc. which were formed in the shape of a sheet.

[0192] Drawing 22 is drawing having shown the spectral characteristic of the above-mentioned light filter, 210 is the spectral characteristic of a red light filter, and 212 is [211 is the spectral characteristic of a green light filter, and] the spectral characteristic of a blue light filter. Wavelength distribution of the light from the above-mentioned light source 201 is adjusted so that the spectral characteristic 210,211,212 of this light filter may be suited. In more detail, in the semi-conductor luminescence equipment which constitutes the light source 201, the luminescence wavelength of a semi-conductor light emitting device, the luminescence wavelength of the 1st, 2nd, and 2nd fluorescent substance and a mixed ratio, the rate of a compounding ratio of the AUW of the fluorescent substance of the 1st thru/or 3 and the weight of the resin for closure, etc. are adjusted, and wavelength distribution of the light 205 from the light source 201 is fitted to the spectral characteristic 210,211,212 of the above-mentioned light filter. For example, the semi-conductor luminescence equipment which has a good color tone and makes wavelength

distribution of drawing 19 (b) conforms to the spectral characteristic of drawing 22. This semi-conductor luminescence equipment is because the above 1st thru/or the rate of a compounding ratio of the AUV of the fluorescent substance of 3 and the weight of the resin for closure are adjusted so that the above-mentioned spectral characteristic may be suited. Thus, since the above-mentioned light source 201 has the wavelength distribution which suits the spectral characteristic of the above-mentioned light filter, if the light 205 from this light source 201 is led to a liquid crystal panel 203 through the above-mentioned light guide plate 202, with the light filter of this liquid crystal panel 203, its brightness will be high and a spectrum will be carried out to the red of an abbreviation single, and the green and blue light 207. Consequently, a deer with a color tone good [this luminescence display 200] can also display the image and image of high brightness and high contrast.

[0193] [Effect of the Invention] So that clearly as mentioned above, the semi-conductor luminescence equipment of this invention While having the outgoing radiation light of 390nm thru/or a short wavelength field with human being's visibility very low at 420nm, luminescence wavelength the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into red (600nm thru/or 670nm) of luminescence wavelength, the light from this fluorescent substance Seemingly, if human being's visibility is taken into consideration, since a color tone hardly changes by the direct light from the above-mentioned semi-conductor light emitting device, this semi-conductor luminescence equipment has a good color tone, and light can be emitted in the light of monochrome red. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0194] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance $M2O2S:Eu$ (however, any one or two or more elements with which M is chosen from La, Gd, and Y), since it consists of any one or 2 or more $0.5MgF2$ and $3.5MgO-GeO2:Mn, Y2O3:Eu, Y(P, V)O4:Eu, YVO4:Eu$, and among the groups of a fluorescent substance come out of and expressed The optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of monochrome red luminescence of a good color tone can be obtained, and utilization effectiveness of the light of a semi-conductor light emitting device is made to high semi-conductor luminescence equipment combining two or more fluorescent substances.

[0195] While having the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, the semi-conductor luminescence equipment of this invention the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into the green luminescence wavelength of 500nm thru/or 540nm, the light from this fluorescent substance Seemingly, if human being's visibility is taken into consideration, since a color tone hardly changes by the direct light from the above-mentioned semi-conductor light emitting device, this semi-conductor luminescence equipment has a good color tone, and light can be emitted in the light of monochrome green. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0196] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance $RMg2aluminum16O27:Eu$ and Mn (however, any one as which R is chosen from Sr and Ba or both elements) -- $RMgAl10O17:Eu$ and Mn (however, any one as which R is chosen from Sr and Ba or both elements) -- $ItEu(s)$ and D(ies). $ZnS:Cu, SrAl2O4:Eu, and SrAl2O4:ZnO:Zn, Zn2germanium2O4:Mn, Zn2SiO4:Mn, and Q3MgSi2O8:Eu - Mn$ since it consists of any one or 2 or more however, (any one or two or more elements) with which Q is chosen from Sr, Ba, and calcium, and among the groups of a fluorescent substance come out of and expressed The optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of green monochrome luminescence can be obtained, and utilization effectiveness of the light of a semi-conductor light emitting device is made to high semi-conductor luminescence equipment combining two or more fluorescent substances.

[0197] The semi-conductor luminescence equipment of this invention the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into the blue luminescence wavelength of 410nm thru/or 480nm while having the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm Seemingly, if the light from this fluorescent substance takes human being's visibility into consideration, since a color tone hardly changes by the direct light from the above-mentioned semi-conductor light emitting device, this semi-conductor luminescence equipment has a good color tone, and light can be emitted in the light of monochrome blue. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0198] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance $A10(PO4)6Cl2:Eu$ (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), $XMg2aluminum16O27:Eu$ (however, any one as which X is chosen from Sr and Ba or both elements), $XMgAl10O17:Eu$ (however, any one as which X is chosen from Sr and Ba or both elements), $ZnS:Ag, Sr10$

(PO4) 6Cl2:Eu, calcium10(PO4) 6F2:Sb, Z3MgSi2O8:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi2O8:Eu, Sr2P2O7:Eu, and CaAl2O4, since it consists of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed The optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of blue monochrome luminescence can be obtained, and utilization effectiveness of the light of a semi-conductor light emitting device is made to high semi-conductor luminescence equipment combining two or more fluorescent substances.

[0199] The semi-conductor luminescence equipment of this invention the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into with a bluish green color (480nm thru/or 500nm) luminescence wavelength while having the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm Seemingly, if the light from this fluorescent substance takes human being's visibility into consideration, since a color tone hardly changes by the direct light from the above-mentioned semi-conductor light emitting device, this semi-conductor luminescence equipment has a good color tone, and light can be emitted in the light of a monochrome bluish green color. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0200] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance It Eu(s) and D(ies). Sr4aluminum14O25:Eu and Sr4aluminum14O25: — L10(PO4) 6Cl2:Eu (however, any one or two or more elements with which L is chosen from Ba, calcium, and Mg), since it consists of any one or 2 or more Sr2Si3O8 and 2SrCl2:Eu, and among the groups of a fluorescent substance come out of and expressed The optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of bluish green color monochrome luminescence of a good color tone can be obtained, and semi-conductor luminescence equipment with the high utilization effectiveness of the light of a semi-conductor light emitting device can be obtained combining two or more fluorescent substances.

[0201] The semi-conductor luminescence equipment of this invention the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into the orange luminescence wavelength of 570nm thru/or 600nm while having the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm If human being's visibility is taken into consideration, since the light from this fluorescent substance hardly changes a color tone by the direct light from the above-mentioned semi-conductor light emitting device, it can emit light seemingly in a monochrome orange light with a color tone good [this semi-conductor luminescence equipment]. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0202] since the above-mentioned fluorescent substance consists of any one or 2 or more ZnS:Mn, ZnS:Cu, Mn and Co, and among the groups of a fluorescent substance come out of and expressed, it can choose the optimal fluorescent substance according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, and the semi-conductor luminescence equipment of 1 operation gestalt can obtain the semi-conductor luminescence equipment of orange monochrome luminescence.

[0203] Since the closure resin which closes at least the part and the above-mentioned semi-conductor light emitting device of the base which carries a semi-conductor light emitting device contains the fluorescent substance, the semi-conductor luminescence equipment of 1 operation gestalt can carry out wavelength conversion of the outgoing radiation light from a semi-conductor light emitting device certainly, and is made into efficient semi-conductor luminescence equipment. Moreover, if closure resin is formed, since a fluorescent substance can be arranged, it is not necessary to arrange a fluorescent substance separately, and manufacture of semi-conductor luminescence equipment can be made easy.

[0204] Moreover, since the above-mentioned semi-conductor luminescence equipment obtains desired luminescence wavelength when luminescence wavelength combines the semi-conductor light emitting device which has a fixed wavelength field, and the fluorescent substance which has predetermined luminescence wavelength and it can obtain the semi-conductor luminescence luminescence equipment of desired luminescence wavelength only by changing a fluorescent substance by the same production process, it can reduce the manufacturing cost of semi-conductor luminescence equipment substantially.

[0205] While the semi-conductor luminescence equipment of 1 operation gestalt arranges a semi-conductor light emitting device at the bottom of the mounting section of the cup configuration formed at the head of a leadframe Since it connects with another leadframe electrically and at least the part and the above-mentioned semi-conductor light emitting device of the two above-mentioned leadframes are closed by the above-mentioned closure resin Since wavelength conversion of the outgoing radiation light from the semi-conductor light emitting device collected in the mounting section of the above-mentioned cup configuration is certainly carried out with the fluorescent substance which the above-mentioned closure resin contains, luminous efficiency can obtain semi-conductor luminescence equipment with a good and sufficient color tone with sufficient directivity.

[0206] Since the semi-conductor luminescence equipment of 1 operation gestalt carries out direct continuation of the above-mentioned semi-conductor light emitting device to metal wiring of the insulator connected at the head of

the leadframe of a couple and is closing at least the part, the above-mentioned insulator, and the above-mentioned semi-conductor light emitting device of a leadframe of a up Norikazu pair by the above-mentioned closure resin, it can manufacture semi-conductor luminescence equipment easily rather than it connects a semi-conductor light emitting device to metal wiring by wire bonding etc.

[0207] While the semi-conductor luminescence equipment of 1 operation gestalt arranges a semi-conductor light emitting device at the bottom of the mounting section of the cup configuration formed at the head of a leadframe. Since it connects with another leadframe electrically, the mounting section of the above-mentioned cup configuration is filled up with a fluorescent substance and at least the part, the above-mentioned semi-conductor light emitting device, and the above-mentioned fluorescent substance of the above-mentioned leadframe are closed by closure resin. While being able to carry out the wavelength conversion of the light from a semi-conductor light emitting device certainly and being able to make it efficient semi-conductor luminescence equipment, it can do few rather than it makes closure resin contain a fluorescent substance so that in the above-mentioned operation gestalt for the amount of the above-mentioned fluorescent substance used.

[0208] While the semi-conductor luminescence equipment of 1 operation gestalt arranges a semi-conductor light emitting device at the bottom of the mounting section of the cup configuration formed at the head of a leadframe. Connect with another leadframe electrically, fill up the mounting section of the above-mentioned cup configuration with a coating member, and a fluorescent substance is further arranged on the above-mentioned coating member. Since at least the part, the above-mentioned semi-conductor light emitting device, the above-mentioned coating member, and the above-mentioned fluorescent substance of the two above-mentioned leadframes are closed by closure resin, the amount of the fluorescent substance used can be made fewer than the case where all the above-mentioned mounting circles are filled up with a fluorescent substance. Moreover, since distance between the light-emitting part of the above-mentioned semi-conductor light emitting device and a fluorescent substance is made to abbreviation homogeneity by the above-mentioned coating member, there is no irregular color and light of semi-conductor luminescence equipment is made to homogeneity. Furthermore, since the above-mentioned coating member estranges the above-mentioned semi-conductor light emitting device and a fluorescent substance, electric and thermal degradation of the fluorescent substance by the semi-conductor light emitting device can be prevented.

[0209] The semi-conductor luminescence equipment of 1 operation gestalt connects with metal wiring of a substrate, and carries a semi-conductor light emitting device, and since the above-mentioned semi-conductor light emitting device is closed with the closure resin containing a fluorescent substance, it. Since the semi-conductor luminescence equipment of the luminescence wavelength of the request only by only changing the class of fluorescent substance contained in the above-mentioned closure resin without changing the class of the above-mentioned semi-conductor light emitting device is obtained, the semi-conductor luminescence equipment of two or more requests can manufacture more easily than before, consequently semi-conductor luminescence equipment can manufacture to low cost.

[0210] Since the amount of the above-mentioned fluorescent substance used can be made little since it is arranged in the crevice of a substrate while connecting to metal wiring of a substrate electrically [the semi-conductor luminescence equipment of 1 operation gestalt / a semi-conductor light emitting device], and the above-mentioned crevice is filled up with the fluorescent substance, a manufacturing cost can be made cheap and wavelength conversion of the light from a semi-conductor light emitting device is moreover certainly carried out with the above-mentioned fluorescent substance, semi-conductor luminescence equipment with sufficient luminous efficiency is obtained.

[0211] Since the above-mentioned crevice is formed with the frame arranged at the above-mentioned substrate, the semi-conductor luminescence equipment of 1 operation gestalt can reduce the time and effort of processing which cuts a substrate, for example and forms a crevice. Moreover, if the field by the side of the semi-conductor light emitting device of the above-mentioned frame is processed into the configuration which condenses the outgoing radiation light from the above-mentioned semi-conductor light emitting device, the conversion efficiency of the wavelength of the above-mentioned outgoing radiation light can be improved further.

[0212] Since the semi-conductor luminescence equipment of 1 operation gestalt is arranged in the crevice of a substrate while the semi-conductor light emitting device is electrically connected to metal wiring of a substrate, and it arranges the fluorescent substance on the above-mentioned closure resin while it has filled up this crevice with closure resin, it can reduce the amount of the above-mentioned fluorescent substance used rather than it is filled up with a fluorescent substance inside the crevice of a substrate like the above-mentioned operation gestalt. Moreover, since the above-mentioned closure resin makes abbreviation homogeneity distance between the light-emitting part of a semi-conductor light emitting device, and a fluorescent substance, it can obtain luminescence of the homogeneity which does not almost have an irregular color. Moreover, since the above-mentioned closure resin makes a high order semi-conductor light emitting device and a fluorescent substance estrange, it reduces the electric and thermal effect of a semi-conductor light emitting device to the above-mentioned fluorescent substance, and the engine performance of semi-conductor luminescence equipment is made as for it to stability.

[0213] As for the semi-conductor luminescence equipment of 1 operation gestalt, a semi-conductor light emitting device is connected to metal wiring of a substrate. Since it has closure resin which the reflected light from the above-mentioned reflector penetrates and the fluorescent substance is contained in the above-mentioned closure resin while having the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device and closing the above-mentioned semi-conductor light emitting

device Since the semi-conductor luminescence equipment of desired luminescence wavelength is obtained only by changing the class of the above-mentioned fluorescent substance without changing the class of the above-mentioned semi-conductor light emitting device, semi-conductor luminescence equipment can be manufactured easily and cheaply conventionally. Moreover, since wavelength conversion of the outgoing radiation light from the above-mentioned semi-conductor light emitting device and the reflected light reflected by the above-mentioned reflector is carried out certainly, semi-conductor luminescence equipment with the sufficient utilization effectiveness of light can be obtained.

[0214] While connecting with metal wiring and the electric target of a substrate and equipping a semi-conductor light emitting device with the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of 1 operation gestalt The exterior of semi-conductor luminescence equipment is equipped with the screen which interrupts the light which carries out direct outgoing radiation from the above-mentioned semi-conductor light emitting device. Since it has closure resin which the reflected light from the above-mentioned reflector penetrates and the layer of a fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector while closing the above-mentioned semi-conductor light emitting device Since wavelength conversion is carried out while the light from a semi-conductor light emitting device is surely reflected by the above-mentioned reflector, and outgoing radiation is carried out to the exterior of semi-conductor luminescence equipment, since what is necessary is to prepare a fluorescent substance only in a reflector, the amount of the fluorescent substance used can be reduced, and cheaply efficient semi-conductor luminescence equipment is obtained. Furthermore, the layer of the above-mentioned fluorescent substance is formed in the reflector of the reflector which makes a predetermined distance from a semi-conductor light emitting device, and since the distance of abbreviation homogeneity is kept and it is arranged from a semi-conductor light emitting device, it is made to the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color. Furthermore, since a semi-conductor light emitting device and a fluorescent substance are estranged, it is made to electric and the semi-conductor luminescence equipment which has the engine performance which thermal effect was eased and was stabilized of the semi-conductor light emitting device to this fluorescent substance.

[0215] While connecting with metal wiring and the electric target of a substrate and equipping a semi-conductor light emitting device with the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of 1 operation gestalt A part for the light-emitting part of the above-mentioned semi-conductor light emitting device is arranged in the crevice of the above-mentioned substrate. Since it has closure resin which the reflected light from the above-mentioned reflector penetrates and the layer of a fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector while closing the above-mentioned semi-conductor light emitting device Since outgoing radiation of the light from the above-mentioned semi-conductor light emitting device is carried out to the exterior of semi-conductor luminescence equipment after wavelength conversion is carried out, while surely being reflected in the exterior of semi-conductor luminescence equipment by the above-mentioned reflector, without carrying out direct outgoing radiation, a color tone is made as for it to the semi-conductor luminescence equipment which has a good outgoing radiation light.

[0216] The semi-conductor light emitting device is connected to metal wiring and the electric target of a substrate for the semi-conductor luminescence equipment of 1 operation gestalt. It has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. Since it has closure resin which the reflected light from the above-mentioned reflector penetrates and the layer of a fluorescent substance is prepared in the field as for which the light of the above-mentioned closure resin carries out outgoing radiation while closing the above-mentioned semi-conductor light emitting device, wavelength conversion is surely carried out and light by which outgoing radiation is carried out from semi-conductor luminescence equipment is made to the semi-conductor luminescence equipment with sufficient utilization effectiveness of light. Moreover, it is made to electric and the semi-conductor luminescence equipment which has the engine performance which could ease thermal effect and was stabilized of the semi-conductor light emitting device to the above-mentioned fluorescent substance while it is made to the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color, since the layer of the above-mentioned fluorescent substance keeps the distance of abbreviation homogeneity and is arranged from a semi-conductor light emitting device.

[0217] The semi-conductor luminescence equipment of this invention carries on a base the semi-conductor light emitting device which has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm. The 1st fluorescent substance which has a red outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 600nm thru/or 670nm, The 2nd fluorescent substance which has a green outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 500nm thru/or 540nm, Equip the wavelength field whose luminescence wavelength is 410nm thru/or 480nm with the 3rd fluorescent substance which has a blue outgoing radiation light which has the main luminescence peak, and since the sum of the color of the outgoing radiation light from the 1st, 2nd, and 3rd fluorescent substance of the above is a white system the light in which the above-mentioned semi-conductor light emitting device has upwards the luminescence wavelength of the short wavelength field where human being's visibility is very low, and the fluorescent substance of each above carries out outgoing radiation the luminescent color of the white system of a good color tone can be obtained without a color tone changing with outgoing radiation light with an outgoing radiation light direct from the above-mentioned semi-conductor light emitting device from the

fluorescent substance of each above, since it is the light of red and green and blue monochrome respectively. Moreover, since color mixture of the light by which direct outgoing radiation is carried out to the semi-conductor luminescence equipment exterior is not carried out to the light from a fluorescent substance in human being's visible region from the above-mentioned semi-conductor light emitting device, even if the luminescence engine performance of a semi-conductor light emitting device falls according to secular change, it is only that the brightness of semi-conductor luminescence equipment falls, and can prevent that a color tone changes. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0218] The semi-conductor luminescence equipment of 1 operation gestalt the 1st fluorescent substance of the above M2O2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), 0.5MgF2 and 3.5 MgO-GeO2:Mn, Y2O3:Eu, It consists of any one or 2 or more Y(P, V) O4:Eu, YVO4:Eu, and among the groups of a fluorescent substance come out of and expressed. the 2nd fluorescent substance of the above RMg2aluminum16O27: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — RMgAl10O17: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — It Eu(s) and D(ies). ZnS:Cu, SrAl2O4:Eu, and SrAl2O4: — ZnO:Zn, Zn2germanium2O4:Mn, Zn2SiO4:Mn, and Q3MgSi2O8:Eu — Mn It consists of any one or 2 or more however, (any one or two or more elements) with which Q is chosen from Sr, Ba, and calcium, and among the groups of a fluorescent substance come out of and expressed. the 3rd fluorescent substance of the above A10(PO4) 6Cl2:Eu (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), XMg2aluminum16O27:Eu (however, any one as which X is chosen from Sr and Ba or both elements), XMgAl10O17:Eu (however, any one as which X is chosen from Sr and Ba or both elements), ZnS:Ag, Sr10(PO4) 6Cl2:Eu, calcium10(PO4) 6F2:Sb, Z3MgSi2O8:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi2O8:Eu, Sr2P2O7:Eu, and CaAl2O4:, since it consists of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed Even if it uses the semi-conductor light emitting device which has which luminescence wavelength of the inside whose luminescence wavelength is 390nm thru/or 420nm By choosing a suitable fluorescent substance from two or more above-mentioned fluorescent substances corresponding to the luminescence wavelength of this semi-conductor light emitting device Since red, monochromatic green, and a monochromatic blue luminescence light can obtain respectively, the light of the white system of a good color tone can be obtained with the red of these monochrome, and the color mixture of a green and blue light. Moreover, since the light of the wavelength of all abbreviation for the luminescence wavelength of a semi-conductor light emitting device is respectively convertible for red and green and blue wavelength by forming the above-mentioned fluorescent substance combining two or more fluorescent substances, the utilization effectiveness of the outgoing radiation light of a semi-conductor light emitting device can be improved, and it is made to the semi-conductor luminescence equipment which has the luminescent color of an efficient white system.

[0219] The semi-conductor luminescence equipment of 1 operation gestalt the 1st, 2nd, and 3rd fluorescent substance of the above Since the 2nd fluorescent substance of the above is 30 or less % of the weight, the 3rd fluorescent substance of the above 20% of the weight or more 20 or less % of the weight 7% of the weight or more 70 or less % of the weight 50% of the weight or more, noting that a total amount is 100 % of the weight [the 1st fluorescent substance of the above] Since human being's visibility strengthens the luminous intensity of a low outgoing radiation light of the 1st and 3rd fluorescent substances, i.e., blue, and red compared with a green light in which the 2nd fluorescent substance of the above carries out outgoing radiation, in consideration of human being's visibility, it is made to the semi-conductor luminescence equipment which has the luminescent color of the white system of a good color tone.

[0220] The above-mentioned closure resin contains the 1st, 2nd, and 3rd fluorescent substance of the above, and the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is made as for the semi-conductor luminescence equipment of 1 operation gestalt to the or more 0.5 luminescence [semi-conductor] equipment which has the luminescent color of the white system near the natural light since it is one or less.

[0221] The light source for which the luminescence display of 1 operation gestalt used the above-mentioned semi-conductor luminescence equipment, It has the light guide plate to which the light from the above-mentioned light source is led, and the light filter of green [which are made to penetrate the light from the above-mentioned light guide plate, and carry out a spectrum / the red and green], and blue. The outgoing radiation light of the above-mentioned semi-conductor luminescence equipment Since it has the wavelength distribution which suited the spectral characteristic of the above-mentioned light filter, the outgoing radiation light of the above-mentioned semi-conductor luminescence equipment is the monochrome of red, green, and blue, and since it can carry out a spectrum to the light of comparatively large reinforcement, its utilization effectiveness of light is good and is made as for it to the luminescence display of high brightness.

[0222] The luminescence display of 1 operation gestalt so that wavelength distribution of the outgoing radiation light of semi-conductor luminescence equipment may suit the spectral characteristic of the above-mentioned light filter. The luminescence wavelength of the above-mentioned semi-conductor light emitting device, and the luminescence wavelength of the 1st fluorescent substance of the above, The luminescence wavelength of the 2nd fluorescent substance of the above, the luminescence wavelength of the 3rd fluorescent substance of the above, and the mixed ratio of the 1st, 2nd, and 3rd fluorescent substance of the above, Since at least one of the ratios of the AUW of the

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1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin was adjusted. With the above-mentioned light filter, since the spectrum of the light from the above-mentioned semiconductor luminescence equipment can be certainly carried out to the monochrome of red, green, and blue, and the light of comparatively high reinforcement, the above-mentioned luminescence display does not have a color omission etc., and the full color display of high brightness and high contrast can do it.

[0223] Since the above-mentioned luminescence display is a liquid crystal display, the luminescence display of 1 operation gestalt does not almost have a color omission, and the liquid crystal display of high brightness and high contrast is obtained.

[Translation done.]

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TECHNICAL FIELD

[Field of the Invention] This invention The light sources for back lights, such as a liquid crystal display, and a cellular phone, a Personal Digital Assistant, the indicator of the LED (light emitting diode) indicating equipment used for an announcement indoor outside etc., and an each kind pocket device — It is a thing about the semi-conductor luminescence equipment used for the light source for an illumination switch and OA (office automation) devices etc. Especially, wavelength conversion of the outgoing radiation light from a semi-conductor light emitting device is carried out using a fluorescent substance, and it is related with semi-conductor luminescence equipment available as the light source of various luminescent color, and the luminescence display using it.

[Translation done.]

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PRIOR ART

[Description of the Prior Art] Semi-conductor luminescence equipment is small, and since power consumption can carry out high brightness luminescence to stability few, it is widely used as the light source in various displays. Moreover, semi-conductor luminescence equipment is used also as the light source for information record reading in various information processors. Green high brightness luminescence was possible for the semi-conductor light emitting device used for the long wavelength light semi-conductor luminescence equipment put in practical use widely until now from red by a semiconductor material, formation conditions, etc. of a luminous layer which are used. On the other hand, from blue, the semi-conductor light emitting device which emits light in the purple short wavelength light is developed, and, generally it is beginning to be put in practical use in recent years.

[0003] The LED display using the semi-conductor luminescence equipment which has the luminescent color of R (red), G (green), and B (blue) in three primary colors has begun to appear in the commercial scene, using the semi-conductor luminescence equipment of these various luminescent color.

[0004] Furthermore, the semi-conductor luminescence equipment which obtains white from blue combining the semi-conductor light emitting device and fluorescent substance which emit light in the purple short wavelength light with color mixture with the conversion light by which wavelength conversion was carried out with the outgoing radiation light and the fluorescent substance of a semi-conductor light emitting device is indicated by patent No. 2927279.

[0005] Moreover, in order to obtain the compact white luminescent color by high brightness, the semi-conductor luminescence equipment which combined the semi-conductor light emitting device which has the luminescent color of blue or a purple-blue color, and one sort or two kinds or more of fluorescent substances which absorb the light from this semi-conductor light emitting device, and emit light in the light of a visible region is indicated by JP,10-163535,A. The above-mentioned fluorescent substance is chosen so that the luminescent color of the above-mentioned semi-conductor light emitting device and the luminescent color of a fluorescent substance may become the relation of the complementary color mutually, the luminescent color of this semi-conductor light emitting device and the luminescent color of a fluorescent substance may be added and light may be emitted white.

[0006] Moreover, the semi-conductor luminescence equipment which equips JP,10-12925,A with the semi-conductor light emitting device which carries out outgoing radiation of ultraviolet radiation and the near-ultraviolet light, and the fluorescent substance which emits fluorescence by the light from this semi-conductor light emitting device is indicated. The above-mentioned semi-conductor light emitting device is a semi-conductor light emitting device which usually emits a blue light, and carries out outgoing radiation of ultraviolet radiation and the near-ultraviolet light by passing a pulse-like high current. Obtaining two or more luminescent color, using the semi-conductor light emitting device of a single class only by changing the class of the above-mentioned fluorescent substance is indicated.

[0007] Moreover, the display equipped with red, blue, and three kinds of fluorescent substance layers that emit light respectively in the green three primary colors dot-matrix type is indicated by JP,9-153644,A by receiving the ultraviolet rays from the luminous layer which is formed using 3 group nitrogen group semi-conductor, and emits light in the ultraviolet rays whose peak wavelength is 380nm, and this luminous layer.

[Translation done.]

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EFFECT OF THE INVENTION

[Effect of the Invention] So that clearly as mentioned above, the semi-conductor luminescence equipment of this invention While having the outgoing radiation light of 390nm thru/or a short wavelength field with human being's visibility very low at 420nm, luminescence wavelength the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into red (600nm thru/or 670nm) of luminescence wavelength, the light from this fluorescent substance Seemingly, if human being's visibility is taken into consideration, since a color tone hardly changes by the direct light from the above-mentioned semi-conductor light emitting device, this semi-conductor luminescence equipment has a good color tone, and light can be emitted in the light of monochrome red. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0194] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance M_2O_2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), since it consists of any one or 2 or more $0.5MgF_2$ and $3.5 MgO-GeO_2:Mn$, $Y_2O_3:Eu$, Y(P, V) $O_4:Eu$, $YVO_4:Eu$, and among the groups of a fluorescent substance come out of and expressed The optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of monochrome red luminescence of a good color tone can be obtained, and utilization effectiveness of the light of a semi-conductor light emitting device is made to high semi-conductor luminescence equipment combining two or more fluorescent substances.

[0195] While having the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, the semi-conductor luminescence equipment of this invention the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into the green luminescence wavelength of 500nm thru/or 540nm, the light from this fluorescent substance Seemingly, if human being's visibility is taken into consideration, since a color tone hardly changes by the direct light from the above-mentioned semi-conductor light emitting device, this semi-conductor luminescence equipment has a good color tone, and light can be emitted in the light of monochrome green. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0196] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance $RMg_2Al_{10}O_{27}$: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — $RMgAl_{10}O_{17}$: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — $It Eu(s)$ and D(ies). $ZnS:Cu$, $SrAl_2O_4:Eu$, and $SrAl_2O_4$: — $ZnO:Zn$, $Zn_2germanium_2O_4:Mn$, $Zn_2SiO_4:Mn$, and $Q_3MgSi_2O_8:Eu$ — Mn since it consists of any one or 2 or more however, (any one or two or more elements) with which Q is chosen from Sr, Ba, and calcium, and among the groups of a fluorescent substance come out of and expressed The optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of green monochrome luminescence can be obtained, and utilization effectiveness of the light of a semi-conductor light emitting device is made to high semi-conductor luminescence equipment combining two or more fluorescent substances.

[0197] The semi-conductor luminescence equipment of this invention the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into the blue luminescence wavelength of 410nm thru/or 480nm while having the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm Seemingly, if the light from this fluorescent substance takes human being's visibility into consideration, since a color tone hardly changes by the direct light from the above-mentioned semi-conductor light emitting device, this semi-conductor luminescence equipment has a good color tone, and light can be emitted in the light of monochrome blue. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0198] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance $A_{10}(PO_4)_6Cl_2:Eu$ (however, any one or two or more elements with which A is chosen from Sr, calcium,

Ba, Mg, and Ce), $\text{XMg}_2\text{aluminum16O27:Eu}$ (however, any one as which X is chosen from Sr and Ba or both elements), XMgAl10O17:Eu (however, any one as which X is chosen from Sr and Ba or both elements), $\text{ZnS:Ag, Sr10(PO4) 6Cl2:Eu}$, calcium10(PO4) 6F2:Sb, Z3MgSi2O8:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi2O8:Eu , Sr2P2O7:Eu , and CaAl2O4 , since it consists of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed The optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of blue monochrome luminescence can be obtained, and utilization effectiveness of the light of a semi-conductor light emitting device is made to high semi-conductor luminescence equipment combining two or more fluorescent substances.

[0199] The semi-conductor luminescence equipment of this invention the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into with a bluish green color (480nm thru/or 500nm) luminescence wavelength while having the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm. Seemingly, if the light from this fluorescent substance takes human being's visibility into consideration, since a color tone hardly changes by the direct light from the above-mentioned semi-conductor light emitting device, this semi-conductor luminescence equipment has a good color tone, and light can be emitted in the light of a monochrome bluish green color. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0200] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance $\text{It Eu(s) and D(ies)}$. $\text{Sr4aluminum14O25:Eu}$ and $\text{Sr4aluminum14O25: — L10(PO4) 6Cl2:Eu}$ (however, any one or two or more elements with which L is chosen from Ba, calcium, and Mg), since it consists of any one or 2 or more Sr2Si3O8 and 2SrCl2:Eu , and among the groups of a fluorescent substance come out of and expressed The optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of bluish green color monochrome luminescence of a good color tone can be obtained, and semi-conductor luminescence equipment with the high utilization effectiveness of the light of a semi-conductor light emitting device can be obtained combining two or more fluorescent substances.

[0201] The semi-conductor luminescence equipment of this invention the above-mentioned semi-conductor light emitting device Since it has the fluorescent substance which changes the outgoing radiation light from this semi-conductor light emitting device into the orange luminescence wavelength of 570nm thru/or 600nm while having the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm. If human being's visibility is taken into consideration, since the light from this fluorescent substance hardly changes a color tone by the direct light from the above-mentioned semi-conductor light emitting device, it can emit light seemingly in a monochrome orange light with a color tone good [this semi-conductor luminescence equipment]. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0202] since the above-mentioned fluorescent substance consists of any one or 2 or more ZnS:Mn , ZnS:Cu , Mn and Co, and among the groups of a fluorescent substance come out of and expressed, it can choose the optimal fluorescent substance according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, and the semi-conductor luminescence equipment of 1 operation gestalt can obtain the semi-conductor luminescence equipment of orange monochrome luminescence.

[0203] Since the closure resin which closes at least the part and the above-mentioned semi-conductor light emitting device of the base which carries a semi-conductor light emitting device contains the fluorescent substance, the semi-conductor luminescence equipment of 1 operation gestalt can carry out wavelength conversion of the outgoing radiation light from a semi-conductor light emitting device certainly, and is made into efficient semi-conductor luminescence equipment. Moreover, if closure resin is formed, since a fluorescent substance can be arranged, it is not necessary to arrange a fluorescent substance separately, and manufacture of semi-conductor luminescence equipment can be made easy.

[0204] Moreover, since the above-mentioned semi-conductor luminescence equipment obtains desired luminescence wavelength when luminescence wavelength combines the semi-conductor light emitting device which has a fixed wavelength field, and the fluorescent substance which has predetermined luminescence wavelength and it can obtain the semi-conductor luminescence luminescence equipment of desired luminescence wavelength only by changing a fluorescent substance by the same production process, it can reduce the manufacturing cost of semi-conductor luminescence equipment substantially.

[0205] While the semi-conductor luminescence equipment of 1 operation gestalt arranges a semi-conductor light emitting device at the bottom of the mounting section of the cup configuration formed at the head of a leadframe Since it connects with another leadframe electrically and at least the part and the above-mentioned semi-conductor light emitting device of the two above-mentioned leadframes are closed by the above-mentioned closure resin Since wavelength conversion of the outgoing radiation light from the semi-conductor light emitting device collected in the mounting section of the above-mentioned cup configuration is certainly carried out with the fluorescent substance which the above-mentioned closure resin contains, luminous efficiency can obtain semi-conductor luminescence equipment with a good and sufficient color tone with sufficient directivity.

[0206] Since the semi-conductor luminescence equipment of 1 operation gestalt carries out direct continuation of the above-mentioned semi-conductor light emitting device to metal wiring of the insulator connected at the head of the leadframe of a couple and is closing at least the part, the above-mentioned insulator, and the above-mentioned semi-conductor light emitting device of a leadframe of a up Norikazu pair by the above-mentioned closure resin, it can manufacture semi-conductor luminescence equipment easily rather than it connects a semi-conductor light emitting device to metal wiring by wire bonding etc.

[0207] While the semi-conductor luminescence equipment of 1 operation gestalt arranges a semi-conductor light emitting device at the bottom of the mounting section of the cup configuration formed at the head of a leadframe. Since it connects with another leadframe electrically, the mounting section of the above-mentioned cup configuration is filled up with a fluorescent substance and at least the part, the above-mentioned semi-conductor light emitting device, and the above-mentioned fluorescent substance of the above-mentioned leadframe are closed by closure resin. While being able to carry out the wavelength conversion of the light from a semi-conductor light emitting device certainly and being able to make it efficient semi-conductor luminescence equipment, it can do few for the amount of the above-mentioned fluorescent substance used.

[0208] While the semi-conductor luminescence equipment of 1 operation gestalt arranges a semi-conductor light emitting device at the bottom of the mounting section of the cup configuration formed at the head of a leadframe. Connect with another leadframe electrically, fill up the mounting section of the above-mentioned cup configuration with a coating member, and a fluorescent substance is further arranged on the above-mentioned coating member. Since at least the part, the above-mentioned semi-conductor light emitting device, the above-mentioned coating member, and the above-mentioned fluorescent substance of the two above-mentioned leadframes are closed by closure resin, the amount of the fluorescent substance used can be made fewer than the case where all the above-mentioned mounting circles are filled up with a fluorescent substance. Moreover, since distance between the light-emitting part of the above-mentioned semi-conductor light emitting device and a fluorescent substance is made to abbreviation homogeneity by the above-mentioned coating member, there is no irregular color and light of semi-conductor luminescence equipment is made to homogeneity. Furthermore, since the above-mentioned coating member estranges the above-mentioned semi-conductor light emitting device and a fluorescent substance, electric and thermal degradation of the fluorescent substance by the semi-conductor light emitting device can be prevented.

[0209] The semi-conductor luminescence equipment of 1 operation gestalt connects with metal wiring of a substrate, and carries a semi-conductor light emitting device, and since the above-mentioned semi-conductor light emitting device is closed with the closure resin containing a fluorescent substance, it Since the semi-conductor luminescence equipment of the luminescence wavelength of the request only by only changing the class of fluorescent substance contained in the above-mentioned closure resin without changing the class of the above-mentioned semi-conductor light emitting device is obtained, the semi-conductor luminescence equipment of two or more requests can manufacture more easily than before, consequently semi-conductor luminescence equipment can manufacture to low cost.

[0210] Since the amount of the above-mentioned fluorescent substance used can be made little since it is arranged in the crevice of a substrate while connecting to metal wiring of a substrate electrically [the semi-conductor luminescence equipment of 1 operation gestalt / a semi-conductor light emitting device], and the above-mentioned crevice is filled up with the fluorescent substance, a manufacturing cost can be made cheap and wavelength conversion of the light from a semi-conductor light emitting device is moreover certainly carried out with the above-mentioned fluorescent substance, semi-conductor luminescence equipment with sufficient luminous efficiency is obtained.

[0211] Since the above-mentioned crevice is formed with the frame arranged at the above-mentioned substrate, the semi-conductor luminescence equipment of 1 operation gestalt can reduce the time and effort of processing which cuts a substrate, for example and forms a crevice. Moreover, if the field by the side of the semi-conductor light emitting device of the above-mentioned frame is processed into the configuration which condenses the outgoing radiation light from the above-mentioned semi-conductor light emitting device, the conversion efficiency of the wavelength of the above-mentioned outgoing radiation light can be improved further.

[0212] Since the semi-conductor luminescence equipment of 1 operation gestalt is arranged in the crevice of a substrate while the semi-conductor light emitting device is electrically connected to metal wiring of a substrate, and it arranges the fluorescent substance on the above-mentioned closure resin while it has filled up this crevice with closure resin, it can reduce the amount of the above-mentioned fluorescent substance used rather than it is filled up with a fluorescent substance inside the crevice of a substrate like the above-mentioned operation gestalt. Moreover, since the above-mentioned closure resin makes abbreviation homogeneity distance between the light-emitting part of a semi-conductor light emitting device, and a fluorescent substance, it can obtain luminescence of the homogeneity which does not almost have an irregular color. Moreover, since the above-mentioned closure resin makes a high order semi-conductor light emitting device and a fluorescent substance estrange, it reduces the electric and thermal effect of a semi-conductor light emitting device to the above-mentioned fluorescent substance, and the engine performance of semi-conductor luminescence equipment is made as for it to stability.

[0213] As for the semi-conductor luminescence equipment of 1 operation gestalt, a semi-conductor light emitting device is connected to metal wiring of a substrate. Since it has closure resin which the reflected light from the above-mentioned reflector penetrates and the fluorescent substance is contained in the above-mentioned closure

resin while having the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device and closing the above-mentioned semi-conductor light emitting device Since the semi-conductor luminescence equipment of desired luminescence wavelength is obtained only by changing the class of the above-mentioned fluorescent substance without changing the class of the above-mentioned semi-conductor light emitting device, semi-conductor luminescence equipment can be manufactured easily and cheaply conventionally. Moreover, since wavelength conversion of the outgoing radiation light from the above-mentioned semi-conductor light emitting device and the reflected light reflected by the above-mentioned reflector is carried out certainly, semi-conductor luminescence equipment with the sufficient utilization effectiveness of light can be obtained.

[0214] While connecting with metal wiring and the electric target of a substrate and equipping a semi-conductor light emitting device with the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of 1 operation gestalt The exterior of semi-conductor luminescence equipment is equipped with the screen which interrupts the light which carries out direct outgoing radiation from the above-mentioned semi-conductor light emitting device. Since it has closure resin which the reflected light from the above-mentioned reflector penetrates and the layer of a fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector while closing the above-mentioned semi-conductor light emitting device Since wavelength conversion is carried out while the light from a semi-conductor light emitting device is surely reflected by the above-mentioned reflector, and outgoing radiation is carried out to the exterior of semi-conductor luminescence equipment, since what is necessary is to prepare a fluorescent substance only in a reflector, the amount of the fluorescent substance used can be reduced, and cheaply efficient semi-conductor luminescence equipment is obtained. Furthermore, the layer of the above-mentioned fluorescent substance is formed in the reflector of the reflector which makes a predetermined distance from a semi-conductor light emitting device, and since the distance of abbreviation homogeneity is kept and it is arranged from a semi-conductor light emitting device, it is made to the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color. Furthermore, since a semi-conductor light emitting device and a fluorescent substance are estranged, it is made to electric and the semi-conductor luminescence equipment which has the engine performance which thermal effect was eased and was stabilized of the semi-conductor light emitting device to this fluorescent substance.

[0215] While connecting with metal wiring and the electric target of a substrate and equipping a semi-conductor light emitting device with the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of 1 operation gestalt A part for the light-emitting part of the above-mentioned semi-conductor light emitting device is arranged in the crevice of the above-mentioned substrate. Since it has closure resin which the reflected light from the above-mentioned reflector penetrates and the layer of a fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector while closing the above-mentioned semi-conductor light emitting device Since outgoing radiation of the light from the above-mentioned semi-conductor light emitting device is carried out to the exterior of semi-conductor luminescence equipment after wavelength conversion is carried out, while surely being reflected in the exterior of semi-conductor luminescence equipment by the above-mentioned reflector, without carrying out direct outgoing radiation, a color tone is made as for it to the semi-conductor luminescence equipment which has a good outgoing radiation light.

[0216] The semi-conductor light emitting device is connected to metal wiring and the electric target of a substrate for the semi-conductor luminescence equipment of 1 operation gestalt. It has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. Since it has closure resin which the reflected light from the above-mentioned reflector penetrates and the layer of a fluorescent substance is prepared in the field as for which the light of the above-mentioned closure resin carries out outgoing radiation while closing the above-mentioned semi-conductor light emitting device, wavelength conversion is surely carried out and light by which outgoing radiation is carried out from semi-conductor luminescence equipment is made to the semi-conductor luminescence equipment with sufficient utilization effectiveness of light. Moreover, it is made to electric and the semi-conductor luminescence equipment which has the engine performance which could ease thermal effect and was stabilized of the semi-conductor light emitting device to the above-mentioned fluorescent substance while it is made to the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color, since the layer of the above-mentioned fluorescent substance keeps the distance of abbreviation homogeneity and is arranged from a semi-conductor light emitting device.

[0217] The semi-conductor luminescence equipment of this invention carries on a base the semi-conductor light emitting device which has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm. The 1st fluorescent substance which has a red outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 600nm thru/or 670nm, The 2nd fluorescent substance which has a green outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 500nm thru/or 540nm, Equip the wavelength field whose luminescence wavelength is 410nm thru/or 480nm with the 3rd fluorescent substance which has a blue outgoing radiation light which has the main luminescence peak, and since the sum of the color of the outgoing radiation light from the 1st, 2nd, and 3rd fluorescent substance of the above is a white system the light in which the above-mentioned semi-conductor light emitting device has upwards the luminescence wavelength of the short wavelength field where human being's visibility is very low, and the fluorescent substance of each above carries out outgoing radiation the luminescent

color of the white system of a good color tone can be obtained without a color tone changing with outgoing radiation light with an-outgoing radiation light direct from the above-mentioned semi-conductor light emitting device from the fluorescent substance of each above, since it is the light of red and green and blue monochrome respectively. Moreover, since color mixture of the light by which direct outgoing radiation is carried out to the semi-conductor luminescence equipment exterior is not carried out to the light from a fluorescent substance in human being's visible region from the above-mentioned semi-conductor light emitting device, even if the luminescence engine performance of a semi-conductor light emitting device falls according to secular change, it is only that the brightness of semi-conductor luminescence equipment falls, and can prevent that a color tone changes. Moreover, since the luminescence wavelength of the above-mentioned semi-conductor light emitting device is 390nm thru/or 420nm, breakage on the components which constitute the above-mentioned semi-conductor luminescence equipment, and the adverse effect to the body can be prevented effectively.

[0218] The semi-conductor luminescence equipment of 1 operation gestalt the 1st fluorescent substance of the above M2O2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), 0.5MgF2 and 3.5 MgO-GeO2:Mn, Y2O3:Eu. It consists of any one or 2 or more Y(P, V) O4:Eu, YVO4:Eu, and among the groups of a fluorescent substance come out of and expressed. the 2nd fluorescent substance of the above RMg2aluminum16O27: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — RMgAl10O17: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — It Eu(s) and D(ies). ZnS:Cu, SrAl2O4:Eu, and SrAl2O4: — ZnO:Zn, Zn2germanium2O4:Mn, Zn2SiO4:Mn, and Q3MgSi2O8:Eu — Mn It consists of any one or 2 or more however, (any one or two or more elements) with which Q is chosen from Sr, Ba, and calcium, and among the groups of a fluorescent substance come out of and expressed. the 3rd fluorescent substance of the above A10(PO4) 6Cl2:Eu (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), XMg2aluminum16O27:Eu (however, any one as which X is chosen from Sr and Ba or both elements), XMgAl10O17:Eu (however, any one as which X is chosen from Sr and Ba or both elements), ZnS:Ag, Sr10(PO4) 6Cl2:Eu, calcium10(PO4) 6F2:Sb, Z3MgSi2O8:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi2O8:Eu, Sr2P2O7:Eu, and CaAl2O4:, since it consists of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed Even if it uses the semi-conductor light emitting device which has which luminescence wavelength of the inside whose luminescence wavelength is 390nm thru/or 420nm By choosing a suitable fluorescent substance from two or more above-mentioned fluorescent substances corresponding to the luminescence wavelength of this semi-conductor light emitting device Since red, monochromatic green, and a monochromatic blue luminescence light can obtain respectively, the light of the white system of a good color tone can be obtained with the red of these monochrome, and the color mixture of a green and blue light. Moreover, since the light of the wavelength of all abbreviation for the luminescence wavelength of a semi-conductor light emitting device is respectively convertible for red and green and blue wavelength by forming the above-mentioned fluorescent substance combining two or more fluorescent substances, the utilization effectiveness of the outgoing radiation light of a semi-conductor light emitting device can be improved, and it is made to the semi-conductor luminescence equipment which has the luminescent color of an efficient white system.

[0219] The semi-conductor luminescence equipment of 1 operation gestalt the 1st, 2nd, and 3rd fluorescent substance of the above Since the 2nd fluorescent substance of the above is 30 or less % of the weight, the 3rd fluorescent substance of the above 20% of the weight or more 20 or less % of the weight 7% of the weight or more 70 or less % of the weight 50% of the weight or more, noting that a total amount is 100 % of the weight [the 1st fluorescent substance of the above] Since human being's visibility strengthens the luminous intensity of a low outgoing radiation light of the 1st and 3rd fluorescent substances, i.e., blue, and red compared with a green light in which the 2nd fluorescent substance of the above carries out outgoing radiation, in consideration of human being's visibility, it is made to the semi-conductor luminescence equipment which has the luminescent color of the white system of a good color tone.

[0220] The above-mentioned closure resin contains the 1st, 2nd, and 3rd fluorescent substance of the above, and the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is made as for the semi-conductor luminescence equipment of 1 operation gestalt to the or more 0.5 luminescence. [semi-conductor] equipment which has the luminescent color of the white system near the natural light since it is one or less.

[0221] The light source for which the luminescence display of 1 operation gestalt used the above-mentioned semi-conductor luminescence equipment, It has the light guide plate to which the light from the above-mentioned light source is led, and the light filter of green [which are made to penetrate the light from the above-mentioned light guide plate, and carry out a spectrum / the red and green], and blue. The outgoing radiation light of the above-mentioned semi-conductor luminescence equipment Since it has the wavelength distribution which suited the spectral characteristic of the above-mentioned light filter, the outgoing radiation light of the above-mentioned semi-conductor luminescence equipment is the monochrome of red, green, and blue, and since it can carry out a spectrum to the light of comparatively large reinforcement, its utilization effectiveness of light is good and is made as for it to the luminescence display of high brightness.

[0222] The luminescence display of 1 operation gestalt so that wavelength distribution of the outgoing radiation light of semi-conductor luminescence equipment may suit the spectral characteristic of the above-mentioned light filter The luminescence wavelength of the above-mentioned semi-conductor light emitting device, and the luminescence wavelength of the 1st fluorescent substance of the above, The luminescence wavelength of the 2nd fluorescent

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substance of the above, the luminescence wavelength of the 3rd fluorescent substance of the above, and the mixed ratio of the 1st, 2nd, and 3rd fluorescent substance of the above, Since at least one of the ratios of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin was adjusted With the above-mentioned light filter, since the spectrum of the light from the above-mentioned semi-conductor luminescence equipment can be certainly carried out to the monochrome of red, green, and blue, and the light of comparatively high reinforcement, the above-mentioned luminescence display does not have a color omission etc., and the full color display of high brightness and high contrast can do it.

[0223] Since the above-mentioned luminescence display is a liquid crystal display, the luminescence display of 1 operation gestalt does not almost have a color omission, and the liquid crystal display of high brightness and high contrast is obtained.

[Translation done.]

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TECHNICAL PROBLEM

[Problem(s) to be Solved by the Invention] However, the above-mentioned Prior art has the following troubles.

[0009] The semi-conductor light emitting device which emits light the purple short wavelength light from the semi-conductor light emitting device which is used for long wavelength light semi-conductor luminescence equipment, and has the green luminescent color from red, and blue Since the ingredient and component configuration which are used according to the wavelength which emits light differ from each other, if the semiconductor device of mutually different wavelength tends to be mounted and it is going to obtain semi-conductor luminescence equipment Two or more mutually different mounting ingredients and mounting processes are needed, and while a production process becomes complicated, there is a problem of becoming the factor of a cost rise.

[0010] Furthermore, in order for color to acquire the good white light using two or more semi-conductor light emitting devices from which the above-mentioned luminescent color differs mutually, since it is necessary to adjust respectively the current to two or more above-mentioned semi-conductor light emitting devices, there is a problem that semi-conductor luminescence equipment becomes complicated. Moreover, when a luminescence display is formed using the above-mentioned semi-conductor luminescence equipment two or more, there is a trouble that adjustment of the color tone of the semi-conductor light emitting device of a large quantity is needed, and a production process becomes complicated.

[0011] Moreover, since the semi-conductor luminescence equipment currently indicated by the above-mentioned patent No. 2927279 and JP,10-163535,A carried out color mixture of the outgoing radiation light of a semi-conductor light emitting device, and this outgoing radiation light and the luminescence light of the fluorescent substance which has the relation of the complementary color and obtained the white luminescent color, it had the trouble that a color tone was not good, either, bad [the utilization effectiveness of light]. For example, when the semi-conductor luminescence equipment which acquires the white light with the color mixture of a blue outgoing radiation light of a semi-conductor light emitting device and the outgoing radiation light of the yellow of a fluorescent substance is used as a back light of a liquid crystal display, since there is little quantity of light of pure red and there are few amounts of the light which penetrates the red light filter with which the above-mentioned liquid crystal display is equipped, this white light has green pure and the trouble of giving an impression which carried out the color omission, when the above-mentioned liquid crystal display indicates by full color.

[0012] Moreover, since the semi-conductor luminescence equipment currently indicated by JP,10-12925,A impresses a pulse-like high current to a semi-conductor light emitting device, a semi-conductor light emitting device breaks, or it generates heat, and it deteriorates, and has the trouble that a life is short and it is unreliable. Moreover, since the above-mentioned semi-conductor light emitting device has the peak of luminescence wavelength also on blue wavelength while having the peak of luminescence wavelength on ultraviolet and near-ultraviolet wavelength, this blue glow carries out color mixture of it to the luminescence light of fluorescence, and it has the problem that a color tone is bad. Furthermore, since brightness does not deteriorate [the semi-conductor light emitting device which has the luminescent color from which plurality differs] uniformly and a blue wavelength component falls rapidly especially when semi-conductor luminescence equipment deteriorates, there is a trouble that the color tone of semi-conductor luminescence equipment will change. Furthermore, since the above-mentioned semi-conductor light emitting device carries out outgoing radiation of the light of the wavelength of the ultraviolet region by the side of short wavelength from near near-ultraviolet (390nm), the measure which prevents the effect on the body is required for it. Moreover, since the object for immobilization of the above-mentioned semi-conductor light emitting device and the resin for moulds also receive an adverse effect by the light of the wavelength of the above-mentioned ultraviolet region, they have the trouble that there is a possibility of causing lowering of the dependability by deterioration of the above-mentioned resin for immobilization and lowering of the luminescence brightness by the melanism of the above-mentioned resin for moulds.

[0013] While the semi-conductor luminescence equipment indicated by publication number No. 153644 [nine to] also needs to enforce the leakage control of the light of an ultraviolet region in order to prevent the effect on the body since it uses the luminescence wavelength of the ultraviolet region of 380nm, it has the trouble that the object for immobilization of a semi-conductor light emitting device and the resin for moulds cause lowering of dependability, and lowering of luminescence brightness in response to an adverse effect. Furthermore, this semi-conductor luminescence equipment has the trouble that the production process of semi-conductor luminescence equipment is complicated, and the yield and dependability fall on a substrate since red, blue, and the fluorescent substance layer that emits light in the green three primary colors are formed with a semi-conductor layer.

[0014] In spite of being made in order to solve the above-mentioned technical problem, and being able to carry out

the outgoing radiation of the light of two or more luminescence wavelength, manufacture is easy and cheap, a color tone is good, there is little effect on the body, and this invention aims at offering the semi-conductor luminescence equipment which does not almost have degradation, and the luminescence display using it.

[Translation done.]

* NOTICES *

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1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
3. In the drawings, any words are not translated.

MEANS

[Means for Solving the Problem] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base in order to attain the above-mentioned object, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 600nm thru/or 670nm with the fluorescent substance which carries out the outgoing radiation of the red light which has the main luminescence peak.

[0016] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to a red wavelength field and carries out outgoing radiation of the light of monochromatic red Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome red luminescence with a good color tone is obtained.

[0017] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0018] in the semi-conductor luminescence equipment of 1 operation gestalt, the above-mentioned fluorescent substance consists of any one or 2 or more M2O2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), 0.5MgF2 and 3.5 MgO-GeO2:Mn, Y2O3:Eu, Y(P, V) O4:Eu, YVO4:Eu, and among the groups of a fluorescent substance come out of and expressed.

[0019] Since according to the above-mentioned operation gestalt the above-mentioned fluorescent substance can be chosen according to the wavelength of the outgoing radiation light of the above-mentioned semi-conductor light emitting device even if it uses the semi-conductor light emitting device which has which outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, the semi-conductor luminescence equipment of monochrome red luminescence with which luminescence wavelength has a good luminescence peak to a red wavelength field is obtained. Moreover, since the wavelength of all abbreviation for the wavelength field of the outgoing radiation light of a semi-conductor light emitting device is convertible for red wavelength by combining two or more fluorescent substances, the semi-conductor luminescence equipment of efficient monochrome red luminescence is obtained.

[0020] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 500nm thru/or 540nm with the fluorescent substance which carries out outgoing radiation of the green light which has the main luminescence peak.

[0021] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to a green wavelength field and carries out outgoing radiation of the monochromatic green light Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome green luminescence with a good color tone is obtained.

[0022] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0023] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance $\text{RMg}_2\text{aluminum16O27}$: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — RMgAl10O17 : — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — It Eu(s) and D(ies). ZnS:Cu , $\text{SrAl}_2\text{O}_4\text{:Eu}$, and SrAl_2O_4 : — ZnO:Zn , $\text{Zn}_2\text{germanium2O4:Mn}$, $\text{Zn}_2\text{SiO}_4\text{:Mn}$, and Q3MgSi2O8 : — it consists of any one or 2 or more Eu, Mn (however, any one or two or more elements with which Q is chosen from Sr, Ba, and calcium), and among the groups of a fluorescent substance come out of and expressed.

[0024] According to the above-mentioned operation gestalt, since the optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of monochrome green luminescence which has a good luminescence peak to the wavelength field where luminescence wavelength is green is obtained. Moreover, since the wavelength of all abbreviation for the wavelength field of the outgoing radiation light of a semi-conductor light emitting device is convertible for green wavelength by combining two or more fluorescent substances, the semi-conductor luminescence equipment of efficient monochrome green luminescence is obtained.

[0025] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 410nm thru/or 480nm with the fluorescent substance which carries out outgoing radiation of the blue light which has the main luminescence peak.

[0026] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to a blue wavelength field and carries out outgoing radiation of the monochromatic blue light Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome blue luminescence with a good color tone is obtained.

[0027] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence

wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0028] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance A10(PO₄) 6Cl₂:Eu (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), XMg₂aluminum16O₂₇:Eu (however, any one as which X is chosen from Sr and Ba or both elements), XMgAl₁₀O₁₇:Eu (however, any one as which X is chosen from Sr and Ba or both elements), ZnS:Ag, Sr₁₀(PO₄) 6Cl₂:Eu, calcium₁₀(PO₄) 6F₂:Sb, Z₃MgSi₂O₈:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi₂O₈:Eu, Sr₂P₂O₇:Eu, and CaAl₂O₄: — it consists of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed.

[0029] According to the above-mentioned operation gestalt, since the optimal fluorescent substance can be chosen according to the luminescence wavelength of a semi-conductor light emitting device, the semi-conductor luminescence equipment of monochrome blue luminescence which has a good luminescence peak to the wavelength field where luminescence wavelength is blue is obtained. Moreover, since the wavelength of all abbreviation for the wavelength field of the outgoing radiation light of the above-mentioned semi-conductor light emitting device is convertible for blue wavelength by combining two or more fluorescent substances, the semi-conductor luminescence equipment of efficient monochrome blue luminescence is obtained.

[0030] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 480nm thru/or 500nm with the fluorescent substance which carries out outgoing radiation of the light of a bluish-green color which has the main luminescence peak.

[0031] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to the wavelength field of a bluish green color and carries out outgoing radiation of the light of a monochromatic bluish green color Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome bluish green color luminescence with a good color tone is obtained.

[0032] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0033] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned fluorescent substance It Eu(s) and D(ies). Sr₄aluminum₁₄O₂₅:Eu and Sr₄aluminum₁₄O₂₅: — it consists of any one or 2 or more L₁₀(PO₄) 6Cl₂:Eu (however, any one or two or more elements with which L is chosen from Ba, calcium, and Mg), Sr₂Si₃O₈ and 2SrCl₂:Eu, and among the groups of a fluorescent substance come out of and expressed.

[0034] According to the above-mentioned operation gestalt, since the optimal fluorescent substance can be chosen according to the luminescence wavelength of the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of monochrome bluish green color luminescence with which luminescence wavelength has a good luminescence peak to the wavelength field of a bluish green color is obtained. Moreover, since the wavelength of all abbreviation for the wavelength field of light in which the above-mentioned semi-conductor light emitting device carries out outgoing radiation by combining two or more fluorescent substances is convertible for the wavelength of a bluish green color, the semi-conductor luminescence equipment of efficient

monochrome bluish green color luminescence is obtained.

[0035] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base, the above-mentioned semi-conductor light emitting device is characterized by to have the outgoing-radiation light whose luminescence wavelength is 390nm thru/or 420nm, to be excited by the outgoing-radiation light from the above-mentioned semi-conductor light emitting device, and to equip the wavelength field whose luminescence wavelength is 570nm thru/or 600nm with the fluorescent substance which carries out outgoing radiation of the orange light which has the main luminescence peak.

[0036] According to this invention, in the above-mentioned semi-conductor luminescence equipment, the above-mentioned semi-conductor light emitting device has upwards the outgoing radiation light of the short wavelength field where human being's visibility is very low, and the above-mentioned fluorescent substance Since luminescence wavelength has the main luminescence peak to an orange wavelength field and carries out outgoing radiation of the monochromatic orange light Even if the light and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device the above-mentioned fluorescent substance carries out [light] outgoing radiation are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of the above-mentioned fluorescent substance will hardly change seemingly. That is, outgoing radiation of the light from the above-mentioned fluorescent substance is carried out from semi-conductor luminescence equipment, without being influenced of the direct light from the above-mentioned semi-conductor light emitting device. Therefore, the semi-conductor luminescence equipment of monochrome orange light emitting with a good color tone is obtained.

[0037] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. On the other hand, if the luminescence wavelength of the above-mentioned semi-conductor light emitting device is longer than 420nm, since the outgoing radiation light from this semi-conductor light emitting device comes to have the luminescence wavelength of a visible region, it will carry out color mixture to the outgoing radiation light from the above-mentioned fluorescent substance, and the color tone of the luminescent color of semi-conductor luminescence equipment will change. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0038] in the semi-conductor luminescence equipment of 1 operation gestalt, the above-mentioned fluorescent substance consists of any one or 2 or more ZnS:Mn, ZnS:Cu, Mn and Co, and among the groups of a fluorescent substance come out of and expressed.

[0039] According to the above-mentioned operation gestalt, since the optimal fluorescent substance can be chosen according to the wavelength field of a semi-conductor light emitting device, luminescence wavelength can obtain the semi-conductor luminescence equipment of the monochrome orange light emitting which has the main luminescence peak to an orange luminescence wavelength field.

[0040] The semi-conductor luminescence equipment of 1 operation gestalt is equipped with the closure resin which closes at least the part and the above-mentioned semi-conductor light emitting device of the above-mentioned base, and the above-mentioned closure resin contains the above-mentioned fluorescent substance.

[0041] Since the closure resin which closes the above-mentioned semi-conductor light emitting device contains the fluorescent substance according to the above-mentioned operation gestalt, since wavelength conversion is surely carried out, the outgoing radiation light from a semi-conductor light emitting device has the good utilization effectiveness of the light of a semi-conductor light emitting device. Moreover, since a fluorescent substance can be arranged while forming closure resin and the process which arranges a fluorescent substance separately is unnecessary, manufacture of semi-conductor luminescence equipment becomes easy.

[0042] Moreover, the semiconductor device which has desired luminescence wavelength is obtained, without changing the structure of a semi-conductor light emitting device and semi-conductor luminescence equipment, when this semi-conductor luminescence equipment combines the semi-conductor light emitting device which has the wavelength field where luminescence wavelength is fixed, and a predetermined fluorescent substance. That is, by the same production process, since the semi-conductor luminescence luminescence equipment which has desired luminescence wavelength is obtained, the manufacturing cost of semi-conductor luminescence equipment is substantially reducible only only changing a fluorescent substance.

[0043] The semi-conductor luminescence equipment of 1 operation gestalt is a leadframe in which the above-mentioned base has the mounting section of a cup configuration, the above-mentioned semi-conductor light emitting device is arranged at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe, and wire bonding connects with another leadframe electrically, and at least the part and the above-mentioned semi-conductor light emitting device of the two above-mentioned leadframes are closed by the above-mentioned closure resin.

[0044] Since wavelength conversion of the outgoing radiation light from the above-mentioned semi-conductor light emitting device collected by the mounting section of the above-mentioned cup configuration is certainly carried out

with the closure resin containing the above-mentioned fluorescent substance according to the above-mentioned operation gestalt, semi-conductor luminescence equipment with a color tone good luminous efficiency and sufficient is obtained with sufficient directivity.

[0045] The semi-conductor luminescence equipment of 1 operation gestalt is the insulator with which the above-mentioned base was connected at the head of the leadframe of a couple, the above-mentioned semi-conductor light emitting device is connected to metal wiring formed in the above-mentioned insulator, and at least the part, the above-mentioned insulator, and the above-mentioned semi-conductor light emitting device of a leadframe of a up Norikazu pair are closed by the above-mentioned closure resin.

[0046] According to the above-mentioned operation gestalt, since direct continuation of the above-mentioned semi-conductor light emitting device is carried out to metal wiring of the above-mentioned substrate for example, by a metal bump etc., the time and effort which connects a semi-conductor light emitting device and a leadframe with a metal wire etc. is saved. Moreover, wavelength conversion of the outgoing radiation light from a semi-conductor light emitting device is certainly carried out with the fluorescent substance contained in the above-mentioned closure resin. Therefore, manufacture effectiveness is good and, moreover, semi-conductor luminescence equipment with a color tone good luminous efficiency and sufficient is obtained.

[0047] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the leadframe which has the mounting section of a cup configuration. The above-mentioned semi-conductor light emitting device It is arranged at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe. And while wire bonding connects with another leadframe electrically and the mounting section of the above-mentioned cup configuration is filled up with the above-mentioned fluorescent substance At least the part, the above-mentioned semi-conductor light emitting device, and the above-mentioned fluorescent substance of the two above-mentioned leadframes are closed by closure resin.

[0048] Since the mounting section of the cup configuration for which the light from the above-mentioned semi-conductor light emitting device gathers is filled up with a fluorescent substance according to the above-mentioned operation gestalt, wavelength conversion is carried out certainly and the utilization effectiveness of light from a semi-conductor light emitting device of light improves. Moreover, since the field which arranges a fluorescent substance is small as compared with the semi-conductor luminescence equipment which does not collect the light from a semi-conductor light emitting device, the amount of the above-mentioned fluorescent substance used can be lessened.

[0049] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the leadframe which has the mounting section of a cup configuration. The above-mentioned semi-conductor light emitting device It is arranged at the bottom of the mounting section of the cup configuration of the above-mentioned leadframe. And while wire bonding connects with another leadframe electrically, filling up the mounting section of the above-mentioned cup configuration with a coating member and arranging the above-mentioned fluorescent substance on the above-mentioned coating member At least the part, the above-mentioned semi-conductor light emitting device, the above-mentioned coating member, and the above-mentioned fluorescent substance of the two above-mentioned leadframes are closed by closure resin.

[0050] Since the above-mentioned fluorescent substance is arranged on the coating member filled up by the above-mentioned mounting section according to the above-mentioned operation gestalt, compared with the case where all the above-mentioned mounting circles are filled up with a fluorescent substance, the amount of the above-mentioned fluorescent substance used is reduced. Moreover, by the above-mentioned coating member, since the distance between the light-emitting part of the above-mentioned semi-conductor light emitting device and a fluorescent substance becomes abbreviation homogeneity, the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color is obtained. Furthermore, since the above-mentioned semi-conductor light emitting device and a fluorescent substance are estranged by the above-mentioned coating member, there is almost no electric and thermal degradation of the fluorescent substance by the semi-conductor light emitting device.

[0051] The above-mentioned base is the substrate with which metal wiring was given, the above-mentioned semi-conductor light emitting device is electrically connected to metal wiring of the above-mentioned substrate, the semi-conductor luminescence equipment of 1 operation gestalt is equipped with the closure resin which closes the above-mentioned semi-conductor light emitting device, and the above-mentioned closure resin contains the above-mentioned fluorescent substance.

[0052] According to the above-mentioned operation gestalt, direct continuation of the above-mentioned semi-conductor light emitting device is done by the metal bump etc., without using metal wires, such as Au, and aluminum, Cu, for the semi-conductor light emitting device of the same configuration or a single class, connecting on metal wiring or using a metal wire etc. for the above-mentioned substrate. Therefore, the manufacture process of semi-conductor luminescence equipment is easy rather than it manufactures the semi-conductor luminescence equipment of a different configuration using the semi-conductor light emitting device of a different configuration [as / in the former] corresponding to the luminescent color. In this semi-conductor luminescence equipment, since the semi-conductor luminescence equipment which has desired luminescence wavelength only by arranging the predetermined fluorescent substance corresponding to desired wavelength is obtained, compared with the former, manufacture of semi-conductor luminescence equipment becomes simplicity and low cost.

[0053] The semi-conductor luminescence equipment of 1 operation gestalt is arranged in the crevice while the above-mentioned base is the substrate with which metal wiring was given and is connected electrically [the above-

mentioned semi-conductor light emitting device] to metal wiring of the above-mentioned substrate, and it fills up with the above-mentioned fluorescent substance in the above-mentioned crevice.

[0054] According to the above-mentioned operation gestalt, since the crevice of the above-mentioned substrate is filled up with the above-mentioned fluorescent substance, the amount of this fluorescent substance used becomes little, a manufacturing cost is cheap, luminous efficiency is good, and, moreover, semi-conductor luminescence equipment with a sufficient color tone is obtained by monochrome luminescence.

[0055] The semi-conductor luminescence equipment of 1 operation gestalt is formed with the frame with which the above-mentioned crevice has been arranged at the above-mentioned substrate.

[0056] Since according to the above-mentioned operation gestalt a frame is arranged to the above-mentioned substrate and the above-mentioned crevice is formed, the time and effort of processing which cuts a substrate, for example and forms a crevice is reduced. Moreover, in the configuration of the side face for example, by the side of the above-mentioned semi-conductor light emitting device, by processing the outgoing radiation light from the above-mentioned semi-conductor light emitting device into the condensing configuration, while the conversion efficiency of the wavelength of the above-mentioned outgoing radiation light improves further, the directivity of semi-conductor luminescence equipment improves the above-mentioned frame. Consequently, luminous efficiency is good and, moreover, semi-conductor luminescence equipment with a sufficient color tone is obtained by monochrome luminescence.

[0057] While in the semi-conductor luminescence equipment of 1 operation gestalt it is the given substrate, metal wiring is arranged in the crevice while the above-mentioned semi-conductor light emitting device is electrically connected to metal wiring of the above-mentioned substrate, and the above-mentioned base fills up the above-mentioned crevice with closure resin, the above-mentioned fluorescent substance is arranged on the above-mentioned closure resin.

[0058] According to the above-mentioned operation gestalt, since the above-mentioned fluorescent substance is arranged on the above-mentioned closure resin, the semi-conductor luminescence equipment which has desired luminescence wavelength is obtained by the amount of the still more nearly little fluorescent substance used rather than it is filled up with a fluorescent substance inside the crevice of the above-mentioned substrate. Moreover, with the above-mentioned closure resin, since the distance between the light-emitting part of a semi-conductor light emitting device and a fluorescent substance becomes abbreviation homogeneity, the semi-conductor luminescence equipment of homogeneity luminescence which does not almost have an irregular color is obtained. Moreover, since the above-mentioned closure resin makes a high order semi-conductor light emitting device and a fluorescent substance estrange, it can reduce the electric and thermal effect of a semi-conductor light emitting device to the above-mentioned fluorescent substance, and its engine performance of semi-conductor luminescence equipment is stable.

[0059] It is connected with metal wiring and the electric target of the above-mentioned substrate, and the above-mentioned semi-conductor light emitting device is equipped with the reflector which reflects a part of outgoing-radiation light [at least] from the above-mentioned semi-conductor light emitting device, the semi-conductor luminescence equipment of 1 operation gestalt is the substrate with which, as for the above-mentioned base, metal wiring was given, while closing the above-mentioned semi-conductor light emitting device, it has closure resin which the reflected light from the above-mentioned reflector penetrates, and the above-mentioned fluorescent substance is contained in the above-mentioned closure resin.

[0060] According to the above-mentioned operation gestalt, direct continuation of the above-mentioned semi-conductor light emitting device is done by the metal bump etc., without using metal wires, such as Au, and aluminum, Cu, for the semi-conductor light emitting device of the same configuration or a single class, connecting on metal wiring or using a metal wire etc. for the above-mentioned substrate. Therefore, the manufacture process of semi-conductor luminescence equipment is easy rather than it manufactures the semi-conductor luminescence equipment of a different configuration using the semi-conductor light emitting device of a different configuration [as / in the former] corresponding to the luminescent color. In this semi-conductor luminescence equipment, since the semi-conductor luminescence equipment which has desired luminescence wavelength only by arranging the predetermined fluorescent substance corresponding to desired wavelength is obtained, compared with the former, manufacture of semi-conductor luminescence equipment becomes simplicity and low cost.

[0061] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and it has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. The exterior of semi-conductor luminescence equipment is equipped with the screen which interrupts the light which carries out direct outgoing radiation from the above-mentioned semi-conductor light emitting device, while closing the above-mentioned semi-conductor light emitting device, it has closure resin which the reflected light from the above-mentioned reflector penetrates, and the layer of the above-mentioned fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector.

[0062] Since the layer of the above-mentioned fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector according to the above-mentioned operation gestalt, wavelength conversion of the light reflected by this reflector is carried out certainly. And since it is reflected in the above-mentioned reflector and outgoing radiation of the outgoing radiation light from the above-mentioned semi-conductor light emitting device is carried out to the semi-conductor luminescence equipment exterior, without leaking to the exterior of semi-

conductor luminescence equipment by the above-mentioned screen, they is the light by which wavelength conversion of all was carried out. [most] Therefore, this semi-conductor luminescence equipment is formed only in a reflector, it is the amount of few fluorescent substances used, and the desired luminescent color is obtained efficiently. Furthermore, since the layer of the above-mentioned fluorescent substance is formed in the reflector of the reflector which makes a predetermined distance from a semi-conductor light emitting device, the distance between the light-emitting part of a semi-conductor light emitting device and a fluorescent substance becomes abbreviation homogeneity, and the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color is obtained. Furthermore, since a semi-conductor light emitting device and a fluorescent substance are estranged, the electric and thermal effect of a semi-conductor light emitting device to a fluorescent substance is eased, and the engine performance of semi-conductor luminescence equipment is stabilized.

[0063] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and a part for the light-emitting part of the above-mentioned semi-conductor light emitting device is arranged in the crevice of the above-mentioned substrate at least. It has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device, while closing the above-mentioned semi-conductor light emitting device, it has closure resin which the reflected light from the above-mentioned reflector penetrates, and the layer of the above-mentioned fluorescent substance is prepared in the field which light reflects in the above-mentioned reflector.

[0064] According to the above-mentioned operation gestalt, since the semi-conductor light emitting device is arranged in the above-mentioned crevice, after wavelength conversion is surely reflected and carried out by the above-mentioned reflector in the exterior of semi-conductor luminescence equipment, without carrying out direct outgoing radiation, outgoing radiation of the light from a semi-conductor light emitting device is carried out to the exterior of semi-conductor luminescence equipment. Therefore, as for this semi-conductor luminescence equipment, the color tone of outgoing radiation light becomes good.

[0065] The semi-conductor luminescence equipment of 1 operation gestalt the above-mentioned base It is the substrate with which metal wiring was given. The above-mentioned semi-conductor light emitting device Connect with the above-mentioned metal wiring and the electric target of the above-mentioned substrate, and it has the reflector which reflects a part of outgoing radiation light [at least] from the above-mentioned semi-conductor light emitting device. While closing the above-mentioned semi-conductor light emitting device, it has closure resin which the reflected light from the above-mentioned reflector penetrates, and the layer of the above-mentioned fluorescent substance is prepared in the field as for which the light of the above-mentioned closure resin carries out outgoing radiation.

[0066] According to the above-mentioned operation gestalt, just before outgoing radiation is carried out from semi-conductor luminescence equipment, wavelength conversion of the outgoing radiation light from a semi-conductor light emitting device is carried out by the layer of the fluorescent substance prepared in the field as for which the light of the above-mentioned closure resin carries out outgoing radiation. That is, since wavelength conversion of all the light from this semi-conductor luminescence equipment is carried out, it becomes semi-conductor luminescence equipment of the utilization effectiveness of a good light. Moreover, since the layer of the above-mentioned fluorescent substance is in the location which kept a predetermined distance from the semi-conductor light emitting device, the distance between the light-emitting part of a semi-conductor light emitting device and a fluorescent substance becomes abbreviation homogeneity, and the semi-conductor luminescence equipment of homogeneity luminescence without an irregular color is obtained. Furthermore, since a semi-conductor light emitting device and a fluorescent substance are estranged, the electric and thermal effect of a semi-conductor light emitting device to a fluorescent substance is eased, and the engine performance of semi-conductor luminescence equipment is stabilized.

[0067] In the semi-conductor luminescence equipment with which the semi-conductor luminescence equipment of this invention comes to carry a semi-conductor light emitting device on a base the above-mentioned semi-conductor light emitting device It has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, and has the 1st fluorescent substance, the 2nd fluorescent substance, and the 3rd fluorescent substance. The 1st fluorescent substance of the above It has a red outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 600nm thru/or 670nm. The 2nd fluorescent substance of the above It has a green outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 500nm thru/or 540nm. The 3rd fluorescent substance of the above It has a blue outgoing radiation light which has the main luminescence peak to the wavelength field whose luminescence wavelength is 410nm thru/or 480nm, and the sum of the color of the outgoing radiation style from the 1st, 2nd, and 3rd fluorescent substance of the above is characterized by being a white system.

[0068] According to the above-mentioned configuration, the light in which the above-mentioned semi-conductor light emitting device has upwards the short wavelength field where human being's visibility is very low, and the above 1st thru/or the 3rd fluorescent substance carry out outgoing radiation Since it is the light of red, green, and the monochrome that has the main peak of luminescence wavelength respectively to a blue wavelength field Even if the above 1st thru/or the outgoing radiation light from the 3rd fluorescent substance and a direct outgoing radiation light from the above-mentioned semi-conductor light emitting device are mixed, if human being's visibility is taken into consideration, the color tone of the outgoing radiation light of semi-conductor luminescence equipment will

hardly change seemingly. That is, the above 1st thru/or the light from which [3rd] fluorescent substance are not influenced of the direct light from the above-mentioned semi-conductor light emitting device, either. Therefore, the semi-conductor luminescence equipment with which a color tone has the luminescent color of a good white system is obtained. Moreover, since color mixture is not carried out to the light from a fluorescent substance in human being's visible region, even if, as for the light by which direct outgoing radiation is carried out to the semi-conductor luminescence equipment exterior from a semi-conductor light emitting device about the outgoing radiation light of semi-conductor luminescence equipment, the luminescence engine performance of a semi-conductor light emitting device falls according to secular change after the activity of the long duration of semi-conductor luminescence equipment, it is only that the brightness of semi-conductor luminescence equipment falls, and a color tone does not change. Therefore, the light of a white system with a good color tone is stabilized by the above-mentioned semi-conductor luminescence equipment, and it is obtained.

[0069] Moreover, in the above-mentioned semi-conductor luminescence equipment, since the above-mentioned semi-conductor light emitting device has the outgoing radiation light whose luminescence wavelength is 390nm thru/or 420nm, it cannot damage the component part of semi-conductor luminescence equipments, such as closure resin, easily, for example, and does not almost have an operation harmful to the body. If the luminescence wavelength of a semi-conductor light emitting device is shorter than 390nm, the above-mentioned closure resin is damaged, for example, and inconvenience, such as opacification and melanism, may be produced. Therefore, by setting luminescence wavelength of the above-mentioned semi-conductor light emitting device to 390nm thru/or 420nm, degradation of the component part of semi-conductor luminescence equipment can be lessened, and there is almost no adverse effect in the body, and, moreover, semi-conductor luminescence equipment with a good color tone is obtained.

[0070] The semi-conductor luminescence equipment of 1 operation gestalt the 1st fluorescent substance of the above M2O2 S:Eu (however, any one or two or more elements with which M is chosen from La, Gd, and Y), 0.5MgF2 and 3.5 MgO-GeO2:Mn, Y2O3:Eu, It consists of any one or 2 or more Y(P, V) O4:Eu, YVO4:Eu, and among the groups of a fluorescent substance come out of and expressed. the 2nd fluorescent substance of the above RMg2aluminum16O27: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — RMgAl10O17: — Eu and Mn (however, any one as which R is chosen from Sr and Ba or both elements) — It Eu(s) and D(ies). ZnS:Cu, SrAl2O4:Eu, and SrAl2O4: — ZnO:Zn, Zn2germanium2O4:Mn, Zn2SiO4:Mn, and Q3MgSi2O8:Eu — Mn It consists of any one or 2 or more however, (any one or two or more elements) with which Q is chosen from Sr, Ba, and calcium, and among the groups of a fluorescent substance come out of and expressed. the 3rd fluorescent substance of the above A10(PO4) 6Cl2:Eu (however, any one or two or more elements with which A is chosen from Sr, calcium, Ba, Mg, and Ce), XMg2aluminum16O27:Eu (however, any one as which X is chosen from Sr and Ba or both elements), XMgAl10O17:Eu (however, any one as which X is chosen from Sr and Ba or both elements), ZnS:Ag, Sr10(PO4) 6Cl2:Eu, calcium10(PO4) 6F2:Sb, Z3MgSi2O8:Eu (however, any one or two or more elements with which Z is chosen from Sr, Ba, and calcium), SrMgSi2O8:Eu, Sr2P2O7:Eu, and CaAl2O4: — it consists of any one or 2 or more Eu, Nd, and among the groups of a fluorescent substance come out of and expressed.

[0071] According to the above-mentioned operation gestalt, even if it uses the semi-conductor light emitting device which has which luminescence wavelength of the inside whose luminescence wavelength is 390nm thru/or 420nm, red, monochromatic green, and a monochromatic blue luminescence light are respectively obtained by choosing a suitable fluorescent substance from two or more above-mentioned fluorescent substances corresponding to the luminescence wavelength of this semi-conductor light emitting device. Color mixture of the light of red and green and blue wavelength is respectively carried out appropriately by this, and the luminescent color of the white system of a good color tone is obtained. Moreover, since the light of the wavelength of all abbreviation for the wavelength field which a semi-conductor light emitting device has by combining two or more fluorescent substances is respectively convertible for red and green and blue wavelength, the utilization effectiveness of the outgoing radiation light of a semi-conductor light emitting device improves, and the semi-conductor luminescence equipment of efficient white system luminescence is obtained.

[0072] As for the 1st, 2nd, and 3rd fluorescent substance of the above, for the 1st fluorescent substance of the above, the 2nd fluorescent substance of the above is [the 3rd fluorescent substance of the above of the semi-conductor luminescence equipment of 1 operation gestalt] 30 or less % of the weight 20 % of the weight or more 70 or less % of the weight 50 % of the weight or more 20 or less % of the weight 7 % of the weight or more noting that a total amount is 100 % of the weight.

[0073] According to the above-mentioned operation gestalt, since 50-% of the weight or more 70 or less % of the weight and the 2nd fluorescent substance of the above are [7 % of the weight or more 20 or less % of the weight and the 3rd fluorescent substance of the above] 30 or less % of the weight 20 % of the weight or more for the 1st fluorescent substance of the above, the red in which the 1st fluorescent substance with low visibility carries out outgoing radiation compared with a green light in which the 2nd fluorescent substance of the above carries out outgoing radiation, and the blue luminous intensity the 3rd fluorescent substance carries out [luminous intensity] outgoing radiation are strengthened. Therefore, human being's visibility is taken into consideration and the semi-conductor luminescence equipment of white system luminescence of a good color tone is obtained.

[0074] In here, if there are more mixed ratios of the 1st fluorescent substance of the above than 70 % of the weight while it will turn into white of the color tone which green cut, if the luminescent color of semi-conductor luminescence equipment has few mixed ratios of the 1st fluorescent substance than 50 % of the weight, it will turn into white of the color tone which red cut. Moreover, the luminescent color of the above-mentioned semi-conductor

luminescence equipment turns into white of the color tone which red cut when there were few mixed ratios of the 2nd fluorescent substance than 7 % of the weight, and if there are more mixed ratios of the 2nd fluorescent substance of the above than 20 % of the weight, it will turn into white of the color tone which green cut. Moreover, the luminescent color of the above-mentioned semi-conductor luminescence equipment turns into white of the color tone which red cut when there were few mixed ratios of the 3rd fluorescent substance than 20 % of the weight, and if there are more mixed ratios of the 3rd fluorescent substance of the above than 30 % of the weight, it will turn into white of the color tone which green cut.

[0075] As for the above-mentioned closure resin, the semi-conductor luminescence equipment of 1 operation gestalt contains the 1st, 2nd, and 3rd fluorescent substance of the above, and the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is one or less [0.5 or more].

[0076] According to the above-mentioned operation gestalt, the semi-conductor luminescence equipment which carries out outgoing radiation of the light of the white system near the natural light is obtained by making the ratio of the AUW of the above-mentioned fluorescent substance to the weight of the above-mentioned closure resin or less [0.5 or more] into one. In addition, if the above-mentioned ratio becomes smaller than 0.5 while the brightness of the outgoing radiation light of semi-conductor luminescence equipment becomes bright and a color tone will become pale, if the above-mentioned ratio becomes larger than 1, while the brightness of the outgoing radiation light of semi-conductor luminescence equipment becomes dark, a color tone will wear redness.

[0077] The luminescence display of 1 operation gestalt is equipped with the light source which used the above-mentioned semi-conductor luminescence equipment, the light guide plate to which the light from the above-mentioned light source is led, and the light filter of green [which are made to penetrate the light from the above-mentioned light guide plate, and carry out a spectrum / the red and green], and blue, and the outgoing radiation light of the above-mentioned semi-conductor luminescence equipment has the wavelength distribution which suited the spectral characteristic of the above-mentioned light filter.

[0078] According to the above-mentioned operation gestalt, the outgoing radiation light from the above-mentioned semi-conductor luminescence equipment Since it has the above-mentioned red, green, and the wavelength distribution that suited the spectral characteristic of a blue light filter The light to which luminescence wavelength has a peak to a red wavelength field with this light filter, the light which has a peak to the wavelength field where luminescence wavelength is green, and the light which has a peak to the wavelength field where luminescence wavelength is blue — each — since it has suitable reinforcement and a spectrum is carried out — the utilization effectiveness of the light of semi-conductor luminescence equipment — good — moreover — high — it becomes a brightness luminescence display.

[0079] The luminescence display of 1 operation gestalt so that wavelength distribution of the outgoing radiation light of semi-conductor luminescence equipment may suit the spectral characteristic of the above-mentioned light filter The luminescence wavelength of the above-mentioned semi-conductor light emitting device, and the luminescence wavelength of the 1st fluorescent substance of the above, At least one of the luminescence wavelength of the 2nd fluorescent substance of the above, the luminescence wavelength of the 3rd fluorescent substance of the above, the mixed ratio of the 1st, 2nd, and 3rd fluorescent substance of the above, and the ratios of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is adjusted.

[0080] Since according to the above-mentioned operation gestalt it is adjusted certainly and effectively so that the outgoing radiation light from the above-mentioned semi-conductor luminescence equipment may suit the spectral characteristic of the above-mentioned light filter, and the outgoing radiation light from the above-mentioned luminescence display has comparatively large reinforcement by the above-mentioned light filter and a spectrum is carried out to the red of abbreviation monochrome, green, and blue, the above-mentioned luminescence display does not have a color omission etc., and becomes the full color display of high brightness and high contrast.

[0081] The above-mentioned luminescence display of the luminescence display of 1 operation gestalt is a liquid crystal display.

[0082] According to the above-mentioned operation gestalt, there is almost no color omission and the liquid crystal display of high brightness and high contrast is obtained.

[0083]

[Embodiment of the Invention] Hereafter, the operation gestalt of a graphic display explains this invention to a detail.

[0084] Drawing 1 (a), (b), and (c) are the sectional views showing the semi-conductor light emitting device used in the operation gestalt of this invention.

[0085] Drawing 1 (a) is the sectional view showing the semi-conductor light emitting device which has the substrate which consists of an insulating semiconductor material. This semi-conductor light emitting device 7a is carrying out the laminating of the N type gallium nitride system compound semiconductor layer 2, the P type gallium nitride system compound semiconductor layer 3, and the electrode 4 for P type layers that consists of a metal thin film or transparence electric conduction film to order on insulating silicon-on-sapphire 1a. While the pad electrode 5 for N type is formed on the exposed surface formed in right-hand side in drawing 1 (a) of the above-mentioned N type gallium nitride system compound semiconductor layer 2, the pad electrode 6 for P type is formed on the above-mentioned electrode 4 front face for P type layers. If a current is passed between the above-mentioned pad electrode 5 for N type, and the pad electrode 6 for P type, light will be emitted from luminescence field 8a.

[0086] Drawing 1 (b) is the sectional view showing the semi-conductor light emitting device which has the substrate

which consists of a conductive semiconductor material. On conductive gallium nitride semi-conductor substrate 1b, this semi-conductor light emitting device 7b carries out the laminating of the electrode 4 for P type layers which consists of the N type gallium nitride system compound semiconductor layer 2, the P type gallium nitride system compound semiconductor layer 3, a metal thin film, or transference electric conduction film one by one, and is formed. While the pad electrode 5 for N type is formed in the underside of the above-mentioned semi-conductor substrate 1b, the pad electrode 6 for P type is formed in the top face of the above-mentioned electrode 4 for P type layers. If a current is passed between the above-mentioned pad electrode 5 for N type, and the pad electrode 6 for P type, light will be emitted from luminescence field 8b.

[0087] Drawing 1 (c) is the sectional view showing the semi-conductor light emitting device of the type which is made to penetrate a substrate and takes out light. This semi-conductor light emitting device 7c on insulating silicon-on-sapphire 1a (it sets to drawing 1 (c) and is the lower part of silicon-on-sapphire 1a) The laminating of the electrode 4 for P type layers which consists of the N type gallium nitride system compound semiconductor layer 2, the P type gallium nitride system compound semiconductor layer 3, a metal thin film, or transference electric conduction film is carried out one by one. While forming the pad electrode 5 for N type in the exposed surface of the above-mentioned N type gallium nitride system compound semiconductor layer 2, the pad electrode 6 for P type is formed in the front face of the electrode 4 for P type layers. And as shown in drawing 1 (c), direct ball bonding of the above-mentioned pad electrode 5 for N type and the pad electrode 6 for P type is carried out to metal wiring of submounting which has been arranged under the semi-conductor light emitting device 7c and which is not illustrated etc. by the metal bumps 16a and 16b who consist of Au etc. If a current is passed between the above-mentioned pad electrode 5 for N type, and the pad electrode 6 for P type, light is emitted from the luminescence field 8, and this luminescence light will penetrate the above-mentioned silicon-on-sapphire 1a, and will be emitted up in drawing 1 (c).

[0088] In addition, other ingredients, such as ZnO, GaN, SiC, and ZnSe, may be used for insulating silicon-on-sapphire 1a of the above-mentioned semi-conductor light emitting devices 7a and 7c. Moreover, other ingredients, such as SiC, ZnSe, and Si, may be used for conductive gallium nitride semi-conductor substrate 1b in the above-mentioned semi-conductor light emitting device 7b. Semi-conductor light emitting device 7b equipped with this conductive semi-conductor substrate 1b Since an electrode is formed also in the underside of the above-mentioned semi-conductor substrate 1b and an electrode can be formed in vertical both sides of semi-conductor light emitting device 7b Compared with the semi-conductor light emitting devices 7a and 7b which have insulator substrate 1a and arrange two electrodes on one side, while being able to form the luminescence field of a semi-conductor layer widely in the same size, there is an advantage that mounting to a leadframe or a mounting substrate is easy.

[0089] As an ingredient of the semi-conductor layer in the above-mentioned semi-conductor light emitting devices 7a, 7b, and 7c, although a nitride system compound semiconductor ($\text{In}_x\text{Ga}_y\text{Al}_z\text{N}$ ($x+y+z=1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$)) can use suitably, semiconductor materials, such as SiC and ZnSe, may be used in addition to it.

[0090] As for the above-mentioned semi-conductor light emitting devices 7a, 7b, and 7c, a wavelength field emits light in the light from 390nm to 420nm. Since human being's visibility to the light of this wavelength field is very low, if the fluorescent substance which changes the light of this wavelength field into the light of other wavelength is used, only the color of the light changed by this fluorescent substance will be recognized as the luminescent color, and the semi-conductor luminescence equipment which has a good color tone will be obtained. If the wavelength of a semi-conductor light emitting device is longer than 420nm, it becomes human being's eyes that it is easy to be recognized as the light, and the light by which wavelength conversion was carried out with the fluorescent substance will be mixed with a direct outgoing radiation light from a semi-conductor light emitting device, and the color tone of the luminescent color will worsen. Moreover, if the wavelength of a semi-conductor light emitting device is shorter than 390nm, this light will carry out melanism of the mould resin as opposed to the resin part currently used for semi-conductor luminescence equipment, and will do the adverse effect of reducing brightness, or deteriorating resin and reducing dependability while it becomes ultraviolet rays harmful to the body.

[0091] Next, the fluorescent substance used for the semi-conductor luminescence equipment of this invention is stated to a detail.

[0092] A following table 1 and a following table 2 are a table having shown the result of having excited various fluorescent substances and having evaluated luminescence brightness using the semi-conductor light emitting device which created the gallium nitride system compound semiconductor whose peak of luminescence wavelength is 410nm as a light emitting device. Moreover, the peak wavelength (nm) of luminescence which excited the above-mentioned fluorescent substance and was obtained is shown simultaneously. In red, green, blue, a bluish green color, and each orange luminescent color, assessment of the brightness of luminescence measured the luminescence brightness for every fluorescent substance, evaluated superiority or inferiority, and gave x to what is inferior to what luminescence brightness is inferior to an excellent thing in O, and is a little inferior to an ordinary thing in O in **. The luminescent color shows red, the peak wavelength about a green fluorescent substance, and the assessment result of brightness, and, as for a table 1, the luminescent color shows blue and a bluish green color, the peak wavelength about an orange fluorescent substance, and the assessment result of brightness, as for a table 2.

[0093]

[A table 1]

発光色	蛍光体	発光ピーク 波長 (nm)	評価
赤色	$\text{La}_2\text{O}_2\text{S}:\text{Eu}$	623	◎
	$\text{Gd}_2\text{O}_2\text{S}:\text{Eu}$	625	○
	$\text{Y}_2\text{O}_2\text{S}:\text{Eu}$	626	△
	$0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2:\text{Mn}$	658	◎
	$\text{Y}_2\text{O}_3:\text{Eu}$	611	△
	$\text{Y}(\text{P}, \text{V})\text{O}_4:\text{Eu}$	618	△
	$\text{YVO}_4:\text{Eu}$	618	△
	$\text{CaS}:\text{Eu}$	655	○
	$\text{CaS}:\text{Eu}, \text{Tm}$	650	◎
緑色	$\text{BaMg}_2\text{Al}_{10}\text{O}_{27}:\text{Eu}, \text{Mn}$	515	○
	$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}, \text{Mn}$	512	○
	$\text{ZnS}:\text{Cu}$	527	△
	$\text{SrAl}_2\text{O}_4:\text{Eu}$	522	◎
	$\text{SrAl}_2\text{O}_4:\text{Eu}, \text{Dy}$	522	○
	$\text{ZnO}:\text{Zn}$	508	△
	$\text{Zn}_2\text{Ge}_2\text{O}_4:\text{Mn}$	537	○
	$\text{Zn}_2\text{SiO}_4:\text{Mn}$	525	○
	$\text{Ba}_3\text{MgSi}_2\text{O}_8:\text{Eu}, \text{Mn}$	512	○
	$\text{Sr}_3\text{MgSi}_2\text{O}_8:\text{Eu}, \text{Mn}$	532	○

[0094]

[A table 2]

発光色	蛍光体	発光ピーク波長 (nm)	評価
青色	$(\text{Sr}, \text{Ca}, \text{Ba}, \text{Ce})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	457	◎
	$\text{BaMg}_2\text{Al}_{16}\text{O}_{27}:\text{Eu}$	455	◎
	$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}$	452	○
	$\text{ZnS}:\text{Ag}$	450	△
	$\text{Sr}_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	447	○
	$\text{Ca}_{10}(\text{PO}_4)_6\text{F}_2:\text{Sb}$	480	△
	$\text{Sr}_3\text{MgSi}_2\text{O}_8:\text{Eu}$	462	○
	$\text{SrMgSi}_2\text{O}_8:\text{Eu}$	460	△
	$\text{SrAl}_{12}\text{O}_{19}:\text{Eu}$	400	×
	$\text{Sr}_2\text{P}_2\text{O}_7:\text{Eu}$	420	△
	$\text{CaAl}_2\text{O}_4:\text{Eu}, \text{Nd}$	440	△
	$\text{Sr}_4\text{Al}_{14}\text{O}_{26}:\text{Eu}$	492	◎
青緑色	$\text{Sr}_4\text{Al}_{14}\text{O}_{26}:\text{Eu}, \text{Dy}$	492	◎
	$(\text{Ba}, \text{Ca}, \text{Mg})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	482	○
	$\text{Sr}_2\text{Si}_3\text{O}_8 \cdot 2\text{SrCl}_2:\text{Eu}$	490	△
橙色	$\text{ZnS}:\text{Mn}$	586	○
	$\text{ZnS}:\text{Cu}, \text{Mn}, \text{Co}$	580	○

As shown in a table 1, in order to obtain the luminescent color of the red of high brightness, the fluorescent substance of $\text{La}_2\text{O}_2\text{S}:\text{Eu}$, 0.5MgF_2 and $3.5 \text{MgO}-\text{GeO}_2:\text{Mn}$, $\text{CaS}:\text{Eu}$, and Tm is suitable, and in order to obtain the green luminescent color of high brightness, the fluorescent substance of $\text{SrAl}_2\text{O}_4:\text{Eu}$ is suitable. moreover — as shown in a table 2, in order the fluorescent substance of $10(\text{Sr}, \text{calcium}, \text{Ba}, \text{Ce}) (\text{PO}_4)_6\text{Cl}_2:\text{Eu}$ is suitable in order to obtain the blue luminescent color of high brightness and to obtain the luminescent color of the bluish green color of high brightness — $\text{Sr}_4\text{aluminum}_{14}\text{O}_{25}:\text{Eu}$ and $\text{Sr}_4\text{aluminum}_{14}\text{O}_{25}:$ — the fluorescent substance of Eu and Dy is suitable.

[0095] Drawing 2 thru/or 7 are drawings having shown the emission spectrum and excitation spectrum of the main fluorescent substances which are used for the operation gestalt of this invention. An axis of abscissa is wavelength (nm) and any drawing of an axis of ordinate is relative intensity (%).

[0096] The luminescence wavelength of the semi-conductor light emitting device used for this invention is 390nm thru/or 420nm. The more nearly optimal luminescence wavelength range changes with the class of fluorescent substance excited by the luminescence wavelength of a semi-conductor light emitting device, and the luminescent color of a fluorescent substance.

[0097] For example, when it is going to obtain the luminescent color of the red which has a luminescence wavelength peak in 658nm by fluorescent substance 0.5MgF_2 and $3.5 \text{MgO}-\text{GeO}_2:\text{Mn}$ shown in drawing 2 (a), it is effective for the wavelength range of 410nm thru/or 420nm to excite the above-mentioned fluorescent substance by the semi-conductor light emitting device which has the peak of luminescence wavelength so that clearly from drawing 2 (b).

[0098] It is effective to, excite the above-mentioned fluorescent substance on the other hand, by the semi-conductor light emitting device which has the luminescence wavelength of 390nm so that clearly from drawing 3 (b) when it is going to obtain the luminescent color of the red which is fluorescent substance $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ shown in drawing 3 (a), and has a luminescence wavelength peak in 623nm.

[0099] Originally, although the peak of the excitation wavelength of fluorescent substance 0.5MgF_2 , $3.5 \text{MgO}-\text{GeO}_2:\text{Mn}$, and $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ is in a short wavelength side from 390nm If the luminescence wavelength of the semi-conductor light emitting device which excites a fluorescent substance is shorter than 390nm Since ultraviolet rays harmful to the body will be emitted, it is not practical, and ***** is also given to the resin part currently used for semi-conductor luminescence equipment, and it becomes the cause of lowering of the brightness by the melanism. of closure resin, or lowering of the dependability by deterioration of resin.

[0100] Besides the above-mentioned fluorescent substance, $\text{Gd}_2\text{O}_2\text{S}:\text{Eu}$, $\text{Y}_2\text{O}_2\text{S}:\text{Eu}$, $\text{Y}_2\text{O}_3:\text{Eu}$, $\text{Y}(\text{P}, \text{V})\text{O}_4:\text{Eu}$, $\text{YVO}_4:\text{Eu}$, etc. are available with the operation gestalt of this invention. Moreover, these fluorescent substances can be more effectively changed into the light of the red whose peaks of luminescence wavelength are 600nm thru/or 670nm by using more than one using the outgoing radiation light of a semi-conductor light emitting device.

[0101] moreover, fluorescent substance BaMg₂aluminum₁₆O₂₇: shown in drawing 4 (a) — it is Eu and Mn, and when it is going to obtain the green luminescent color which has a luminescence wavelength peak in 515nm, it is effective to excite the above-mentioned fluorescent substance by the semi-conductor light emitting device which has the luminescence wavelength of 390nm so that clearly from drawing 4 (b).

[0102] It is effective for the wavelength range of 390nm thru/or 420nm to excite the above-mentioned fluorescent substance by the semi-conductor light emitting device which has the peak of luminescence wavelength so that clearly [, on the other hand, it is fluorescent substance SrAl₂O₄:Eu shown in drawing 5 (a), and] from drawing 5 (b), when it is going to obtain the green luminescent color which has a luminescence wavelength peak in 522nm.

[0103] original — fluorescent substance BaMg₂aluminum₁₆O₂₇:, although the peak of the excitation wavelength of Eu, Mn, and SrAl₂O₄:Eu is in a short wavelength side from 390nm If the luminescence wavelength of the semi-conductor light emitting device which excites a fluorescent substance is shorter than 390nm Since ultraviolet rays harmful to the body will be emitted, it is not practical, and it has an adverse effect also on the resin part currently used for semi-conductor luminescence equipment, and becomes the cause of lowering of the brightness by the melanism of closure resin, or lowering of the dependability by deterioration of resin.

[0104] except for the above-mentioned fluorescent substance — the operation gestalt of this invention — ZnS:Cu and SrAl₂O₄: — Eu, Dy, ZnO:Zn, Zn₂germanium₂O₄:Mn, Zn₂SiO₄:Mn, and Ba₃MgSi₂O₈: — Eu, Mn, and Sr₃MgSi₂O₈: — Eu, Mn, etc. are available. Moreover, these fluorescent substances can be more effectively changed into a green light whose peaks of luminescence wavelength are 500nm thru/or 540nm by using more than one using the outgoing radiation light of a semi-conductor light emitting device.

[0105] Moreover, when it is going to obtain the blue luminescent color which has a luminescence wavelength peak in 457nm, it is effective [it is fluorescent substance (Sr, calcium, Ba, Ce) 10(PO₄) 6Cl₂:Eu shown in drawing 6 (a), and] for the wavelength range of 390nm thru/or 400nm to excite the above-mentioned fluorescent substance by the semi-conductor light emitting device which has the peak of luminescence wavelength so that clearly from drawing 6 (b). Originally, although the peak of the excitation wavelength of fluorescent substance (Sr, calcium, Ba, Ce) 10(PO₄) 6Cl₂:Eu is in a short wavelength side from 390nm If the luminescence wavelength of the semi-conductor light emitting device which excites a fluorescent substance is shorter than 390nm Since ultraviolet rays harmful to the body will be emitted, it is not practical, and it has an adverse effect also on the resin part currently used for semi-conductor luminescence equipment, and becomes the cause of lowering of the brightness by the melanism of closure resin, or lowering of the dependability by deterioration of resin.

[0106] It is effective to, excite the above-mentioned fluorescent substance on the other hand, by the semi-conductor light emitting device which has the luminescence wavelength of 390nm so that clearly [it is fluorescent substance BaMgAl₁₀O₁₇:Eu shown in drawing 7 (a), and] from drawing 7 (b), when it is going to obtain the blue luminescent color which has a luminescence wavelength peak in 452nm. Since ultraviolet rays harmful to the body will be emitted when the luminescence wavelength of the semi-conductor light emitting device which excites a fluorescent substance is originally shorter than 390nm, although the peak of the excitation wavelength of fluorescent substance BaMgAl₁₀O₁₇:Eu is in 390nm, it is not practical, and it has an adverse effect also on the resin part currently used for semi-conductor luminescence equipment, and becomes the cause of lowering of the brightness by the melanism of closure resin, or lowering of the dependability by deterioration of resin.

[0107] except for the above-mentioned fluorescent substance — the operation gestalt of this invention — BaMg₂aluminum₁₆O₂₇:Eu, ZnS:Ag, and Sr₁₀(PO₄) 6Cl₂: — Eu, calcium₁₀(PO₄) 6F₂:Sb, Sr₃MgSi₂O₈:Eu, SrMgSi₂O₈:Eu, Sr₂P₂O₇:Eu, and CaAl₂O₄: — Eu, Nd, etc. are available. Moreover, the outgoing radiation light of a semi-conductor light emitting device can be more effectively changed into a blue light whose peaks of luminescence wavelength are 410nm thru/or 480nm by using two or more these fluorescent substances.

[0108] It Eu(s) and D(ies). furthermore, an activity application — responding — Sr₄aluminum₁₄O₂₅:Eu and Sr₄aluminum₁₄O₂₅: — Any one of fluorescent substances, such as 10(PO₄) 6Cl₂:Eu, and Sr₂Si₃O₈, 2SrCl₂:Eu, (Ba, calcium, Mg) Or the outgoing radiation light of a semi-conductor light emitting device is effectively convertible for the light of the bluish green color whose peaks of luminescence wavelength are 480nm thru/or 500nm by using plurality.

[0109] Moreover, the outgoing radiation light of a semi-conductor light emitting device is convertible for a fluorescent substance by using ZnS:Mn, ZnS:Cu, and Mn and Co at an orange light whose peaks of luminescence wavelength are 570nm thru/or 600nm.

[0110] Hereafter, the semi-conductor luminescence equipment of the operation gestalt of this invention is explained in detail with reference to a drawing.

[0111] (1st operation gestalt) Drawing 8 (a) thru/or (c) are the sectional views showing the semi-conductor luminescence equipment of the 1st operation gestalt of this invention.

[0112] Drawing 8 (a) is the sectional view of the ramp-type semi-conductor luminescence equipment which closed the above-mentioned semi-conductor light emitting device 7a with the mould resin as closure resin of the shape of ramp type which it had [shape] semi-conductor light emitting device 7a which has an insulating substrate, and distributed the fluorescent substance.

[0113] This semi-conductor luminescence equipment has mounting section 10a which is the depression of a cup configuration at the head of the leadframe 101 as a base. The above-mentioned semi-conductor light emitting device 7a is being fixed to mounting section 10a of this cup configuration with the adhesives 11 which consist of an epoxy resin etc. P lateral electrode 6a prepared in the top face of the above-mentioned semi-conductor light emitting device 7a is connected to polar-zone 10b of a leadframe 101 by metal wire 6p which consists of Au,

aluminum, Cu, etc. Moreover, N lateral electrode 5a prepared in the top face of the above-mentioned semi-conductor light emitting device 7a is connected to polar-zone 10c of the right-hand side leadframe 102 by metal wire 5n. And the upper part of above-mentioned semi-conductor light emitting device 7a and a leadframe 101,102 is closed with the mould resin 130 which distributed the fluorescent substance, such as an epoxy resin of translucency, and ramp type-like semi-conductor luminescence equipment is formed. In addition, the adhesives 11 which join the above-mentioned semi-conductor light emitting device 7a and mounting section 10a of a leadframe 101 will not be limited especially if it is the ingredient which does not absorb the light from semi-conductor light emitting device 7a. For example, the resin ingredient containing the ingredient which reflects and scatters the other light efficiently etc. may be used for mounting section 10a of a leadframe 101 from the resin ingredient which mixed the thermally conductive good metallic material for the heat-characteristic improvement of the above-mentioned semi-conductor light emitting device 7a, and above-mentioned semi-conductor light emitting device 7a.

[0114] Drawing 8 (b) is the sectional view of the ramp-type semi-conductor luminescence equipment which closed the above-mentioned semi-conductor light emitting device 7b with the mould resin 130 as closure resin of the shape of ramp type which it had [shape] semi-conductor light emitting device 7b which has a conductive substrate, and distributed the fluorescent substance. Among drawing, the part which has the same function as the semi-conductor luminescence equipment shown in drawing 8 (a) attaches the same reference number, and omits detailed explanation.

[0115] As for this semi-conductor luminescence equipment, direct continuation of the N lateral electrode section 5 of above-mentioned semi-conductor light emitting device 7b is carried out to mounting section 10a of a leadframe 101 by the adhesives 15 which consist of the conductive wax material or Au-epoxy resin which consists of metal systems, such as an indium, an Ag-epoxy resin, etc. On the other hand, P lateral electrode 6b prepared in the top face of the above-mentioned semi-conductor light emitting device 7b is connected to polar-zone 10c of the right-hand side leadframe 102 by metal wire 6p in drawing 8 (b). And the upper part of above-mentioned semi-conductor light emitting device 7b and a leadframe 101,102 is closed with the mould resin 130 which distributed the fluorescent substance, and forms ramp type-like semi-conductor luminescence equipment. Since the electrodes 6b and 5b with which semi-conductor light emitting device 7b was prepared up and down are the same as that of the semi-conductor light emitting device of the conventional GaAs system or a GaP system, the leadframe used for conventional semi-conductor luminescence equipment can be used as it is.

[0116] Drawing 8 (c) is the sectional view of the ramp-type semi-conductor luminescence equipment which closed the above-mentioned semi-conductor light emitting device 7c with the mould resin 130 as closure resin of the shape of ramp type which it had [shape] semi-conductor light emitting device 7c which has an insulating substrate, and this semi-conductor light emitting device 7c and leadframe 103,103 were connected [shape], without using a metal wire, and distributed the fluorescent substance.

[0117] This semi-conductor luminescence equipment has connected the submounting 17 as a base at the head of the leadframe 103,103 which countered mutually and has been arranged. This submounting 17 consists of Si, it is insulation and the electrode wiring 17a and 17b is formed in the top face of the submounting 17. The above-mentioned semi-conductor light emitting device 7c makes a semi-conductor layer side face (bottom side of semi-conductor light emitting device 7c in drawing 1 (c)) counter the top face of this submounting 17, and is carried in it. P lateral electrode 6c and N lateral electrode 5c which were prepared in the bottom side of the above-mentioned semi-conductor light emitting device 7c are connected to the electrode wiring 17a and 17b formed in the top face of the above-mentioned submounting 17 using Au bump etc. It connected with the points 10d and 10e of a leadframe, and the electrode wiring 17a and 17b formed in the top face of the above-mentioned submounting 17 is connected to the exterior and an electric target. And it closes with the mould resin 130 which consists a fluorescent substance of a distributed epoxy resin in above-mentioned semi-conductor light emitting device 7c and the submounting 17, and the upper part of a leadframe 103,103, and ramp type-like semi-conductor luminescence equipment is formed. Since this semi-conductor luminescence equipment is carrying out direct continuation of the above-mentioned semi-conductor light emitting device 7c to the submounting 17, it has the advantage that the heat from the luminescence field of the above-mentioned semi-conductor light emitting device 7c can be quickly missed to the exterior of semi-conductor luminescence equipment through the submounting 17 and a leadframe 103,103.

[0118] The semi-conductor luminescence equipment of the shape of ramp type shown in drawing 8 (a), (b), and (c) The light emitted has the other directivity above drawing 8 (a), (b), and (c). Especially the semi-conductor luminescence equipment of drawing 8 (a) and (b) Since the light by which outgoing radiation was carried out from the semi-conductor light emitting devices 7a and 7b is condensed efficiently, mounting section 10a of a leadframe 101 is formed in the cup configuration. The thermosetting which has the translucency of silicon resin, urethane resin, polycarbonate resin, etc. in addition to an epoxy resin, and thermoplastic resin may be used for the above-mentioned mould resin 130. Moreover, although the mould resin 130 whole may be made to distribute the above-mentioned fluorescent substance to homogeneity, if the content ratio of a fluorescent substance is gradually made high toward the semi-conductor light emitting devices 7a, 7b, and 7c from the front face of mould resin 130, degradation of the fluorescent substance under the effect of the moisture from the outside of mould resin 130 etc. can be reduced. moreover, the fluorescent substance by the semi-conductor light emitting devices 7a, 7b, and 7c if the content ratio of a fluorescent substance is gradually made high toward the front face of mould resin 130 from the semi-conductor light emitting devices 7a, 7b, and 7c — electric and thermal effect can also be eased. Thus, distribution of the fluorescent substance in mould resin 130 can make various gestalten according to the class of mould resin, the class of fluorescent substance, an operating environment, conditions, or an application.

[0119] (2nd operation gestalt) Drawing 9 (a) and (b) are the sectional views having shown the semi-conductor luminescence equipment in the 2nd operation gestalt of this invention. The semi-conductor luminescence equipment of drawing 9 (a) is the same as the semi-conductor luminescence equipment shown in drawing 8 (a) except mould resin 131 not containing a fluorescent substance while being filled up with a fluorescent substance in mounting section 10a of a leadframe 101. Also about the semi-conductor luminescence equipment of drawing 9 (b), while being filled up with a fluorescent substance in mounting section 10a of a leadframe 101, it is the same as that of the semi-conductor luminescence equipment shown in drawing 8 (b) except mould resin 131 not containing a fluorescent substance. Therefore, the same reference number is given to the part which has the same function as the semi-conductor luminescence equipment shown in drawing 8 (a) and (b), and detailed explanation is omitted. Also in other following operation gestalten, it is the same.

[0120] While the semi-conductor luminescence equipment shown in drawing 9 (a) and (b) arranges the semi-conductor light emitting devices 7a and 7b at the bottom of mounting section 10a of a cup configuration, it fills up this mounting section 10a with a fluorescent substance 12, and he is trying to change the wavelength of the light from the semi-conductor light emitting devices 7a and 7b with this fluorescent substance 12. That is, by arranging the above-mentioned fluorescent substance 12 to mounting section 10a which collects the light from the semi-conductor light emitting devices 7a and 7b, it does not leak, the light from the semi-conductor light emitting devices 7a and 7b is transformed, and the conversion efficiency of light is raised. Therefore, compared with the case where the whole mould resin [as / in the operation gestalt of the above 1st] is made to distribute a fluorescent substance, the color tone of semi-conductor luminescence equipment is good, and since what is necessary is to arrange a fluorescent substance only in mounting section 10a moreover, the amount of the fluorescent substance used is reduced.

[0121] In the above-mentioned operation gestalt, although filled up with the fluorescent substance 12 in [of a leadframe 101 / whole] mounting section 10a, as long as the bleedoff light from the semi-conductor light emitting devices 7a and 7b is convertible for wavelength predetermined enough, you do not need to make it filled up with a fluorescent substance 12 in [whole] mounting section 10a not necessarily, and a concave may be filled up with a fluorescent substance 12 in mounting section 10a. Or what is necessary is to have been filled up with the fluorescent substance 12 so that it might rise to convex rather than the above-mentioned mounting section 10a upper bed, and just to, have filled up mounting section 10a with the fluorescent substance 12 of an amount which can change the wavelength of the light from the semi-conductor light emitting devices 7a and 7b into desired wavelength in short.

[0122] (3rd operation gestalt) Drawing 10 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment of the 3rd operation gestalt of this invention. The semi-conductor luminescence equipment of drawing 10 (a) is the same as the semi-conductor luminescence equipment shown in drawing 9 (a) in mounting section 10a of a leadframe 101 except having arranged pre coating 13a so that the whole semi-conductor light emitting device 7a may be covered, and having arranged the fluorescent substance 12 on it. It is the same as that of the semi-conductor luminescence equipment shown in drawing 9 (b) except having arranged pre coating 13a so that the whole semi-conductor light emitting device 7a may be covered in mounting section 10a of a leadframe 101, and having arranged the fluorescent substance 12 on it also about the semi-conductor luminescence equipment of drawing 10 (b). Therefore, the same reference number is given to the part which has the same function as the semi-conductor luminescence equipment shown in drawing 9 (a) and (b), and detailed explanation is omitted.

[0123] In drawing 10 (a) and (b), pre coating 13a which consists of an epoxy resin, silicon resin, urethane resin, etc. so that the semi-conductor light emitting devices 7a and 7b may be arranged and this semi-conductor light emitting device 7a and the whole 7b may be covered is formed in the bottom of mounting section 10a of the cup configuration formed at left-hand side leadframe 101 head. The fluorescent substance 12 is arranged in the shape of a layer so that the above-mentioned mounting section 10a inside may be filled on this pre coating 13. The above-mentioned fluorescent substance 12 carries out dipping of the mounting section 10a in which pre coating 13a was formed, or forms it on the pre coating 13 potting or the fuel spray, and by vapor-depositing on pre coating 13a in mounting section 10a. In drawing 10 (a) and (b), although the fluorescent substance 12 was formed only inside [mounting section 10a] the leadframe 101, you may form so that all the top faces of a leadframe 101 may be covered.

[0124] The above-mentioned fluorescent substance 12 sets the abbreviation equal distance by pre coating 13a from the luminescence field of the semi-conductor light emitting devices 7a and 7b, and the semi-conductor luminescence equipment shown in drawing 10 (a) and (b) is formed in homogeneity thickness. Therefore, a uniform luminescence light in which this semi-conductor luminescence equipment does not have nonuniformity is obtained by that abbreviation etc. requires the quantity of light passed in all the fields of a fluorescent substance 12 by carrying out. Moreover, since a fluorescent substance 12 is arranged in the location estranged from the semi-conductor light emitting devices 7a and 7b, the electric and thermal effect of a semi-conductor light emitting device to a fluorescent substance 12 can be eased. Consequently, a luminescence property is good and, moreover, semi-conductor luminescence equipment with sufficient endurance is obtained.

[0125] (4th operation gestalt) Drawing 11 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment by the 4th operation gestalt of this invention.

[0126] Drawing 11 (a) carries semi-conductor light emitting device 7a which has an insulating substrate on the printed-circuit board 18 as a base, and is closing the above-mentioned semi-conductor light emitting device 7a with the mould resin 132 as closure resin which distributed the fluorescent substance.

[0127] This semi-conductor luminescence equipment has pasted up semi-conductor light emitting device 7a with the adhesives 11 which consist of an epoxy resin on the printed-circuit board 18 of the rectangular parallelepiped configuration which consists of glass epoxy which has thermal resistance. P lateral electrode 6a and N lateral electrode 5a which were prepared in the top face of this semi-conductor light emitting device 7a are respectively connected to the polar zone 18a and 18b of printed-circuit board 18 top face by the metal wires 6p and 5n. Through the through hole of the shape of cross-section radii which connects the top face and underside of a printed-circuit board 18 which is not illustrated, these polar zone 18a and 18b was taken about on the underside of the printed-circuit board 18 as a component side, and is prolonged even to the both ends of this component side. In addition, an insulating film may be used for the above-mentioned printed-circuit board 18.

[0128] And on the above-mentioned printed-circuit board 18, it forms so that a parabolic edge section as shows the mould resin 132 which distributed the fluorescent substance, such as an epoxy resin as closure resin (for example, translucency), to drawing 11 (a) may be made, and the semi-conductor luminescence equipment of a chip part shape is formed so that the above-mentioned whole semi-conductor light emitting device 7a may be covered.

[0129] The adhesives 11 on which the above-mentioned semi-conductor light emitting device 7a and a printed-circuit board 18 are pasted up will not be limited especially if it is the ingredient with which the light from semi-conductor light emitting device 7a is not absorbed. For example, the resin ingredient which mixed the thermally conductive good metallic material for the heat-characteristic improvement of semi-conductor light emitting device 7a, the resin ingredient containing the ingredient which reflects and scatters efficiently the light emitted toward the printed-circuit board 18 from semi-conductor light emitting device 7a, etc. may be used. However, to use the resin ingredient containing a metallic material, it is necessary to take care that P lateral electrode 6a and N lateral electrode 5a do not connect too hastily.

[0130] Drawing 11 (b) is the same as that of the semi-conductor luminescence equipment of drawing 11 (a) except having semi-conductor light emitting device 7c which changes to semi-conductor light emitting device 7a in drawing 11 (a), and has an insulating substrate. Therefore, the same reference number is given to the part which has the same function as drawing 11 (a), and detailed explanation is omitted.

[0131] In the semi-conductor luminescence equipment of drawing 11 (b), semi-conductor light emitting device 7c carries out outgoing radiation of the light through the insulating substrate located in an upside in drawing 11 (b) of semi-conductor light emitting device 7c. The above-mentioned semi-conductor light emitting device 7c is carrying out direct continuation of P lateral electrode 6c and N lateral electrode 5c which were formed in the semi-conductor laminating side which is the bottom in drawing 11 (b) to the polar zone 18a and 18b on a printed-circuit board 18 respectively through Au bump. In addition, semi-conductor light emitting device 7c may be carried in submounting which consists of Si beforehand given to metal wiring, and this submounting may be electrically connected to a printed-circuit board 18 with die bond, wire bond, etc. Since this semi-conductor luminescence equipment turns the field by the side of a semi-conductor laminating to a printed-circuit board 18 and mounts semi-conductor light emitting device 7c, it can miss quickly the heat from the luminescence field of the above-mentioned semi-conductor light emitting device 7c to the exterior.

[0132] The thermosetting which has the translucency of silicon resin, urethane resin, Pori force-BONETO resin, etc. in addition to an epoxy resin, and thermoplastic resin may be used for the mould resin 132 in the semi-conductor luminescence equipment of drawing 11 (a) and (b). Moreover, although the mould resin 132 whole may be made to distribute a fluorescent substance to homogeneity, if the content ratio of a fluorescent substance is gradually made high toward a semi-conductor light emitting device from the front face of mould resin 132, degradation of the fluorescent substance under the effect of moisture etc. can be reduced. Moreover, if the content ratio of a fluorescent substance is gradually made high toward the front face of mould resin 132 from the semi-conductor light emitting devices 7a and 7c, the electric and thermal effect of the semi-conductor light emitting devices 7a and 7c to a fluorescent substance can be eased. Thus, distribution of the fluorescent substance in mould resin 132 can make various gestalten according to the class of mould resin, the class of fluorescent substance, an operating environment, conditions, an application, etc.

[0133] In addition, it may change to the above-mentioned semi-conductor light emitting devices 7a and 7c, and semi-conductor light emitting device 7b which has a conductive substrate may be used. In this case, direct continuation of the N type electrode formed in the underside of semi-conductor light emitting device 7b is carried out to one electrode on a printed-circuit board with the adhesives which have conductivity. P lateral electrode prepared in the top face of the above-mentioned semi-conductor light emitting device 7b is connected to the polar zone of another side on a printed-circuit board with a metal wire. Like the semi-conductor luminescence equipment of the conventional GaAs system or a GaP system, since the above-mentioned semi-conductor light emitting device 7b has an electrode to vertical both sides of semi-conductor light emitting device 7b, it has the advantage that the conventional leadframe can be used as it is.

[0134] (5th operation gestalt) Drawing 12 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment of the 5th operation gestalt of this invention. The semi-conductor luminescence equipment of drawing 12 (a) is equipped with the frame 19 which consists of resin on the printed-circuit board 18 as a base. Semi-conductor light emitting device 7b which is on this printed-circuit board 18, and has a conductive substrate inside the above-mentioned resin frame 19 is arranged. And it is filled up with the mould resin 134 as closure resin which contains a fluorescent substance inside the above-mentioned resin frame 19, and semi-conductor light emitting device 7b is closed.

[0135] This semi-conductor luminescence equipment has formed the frame 19 which consists of resin on the

printed circuit board 18 of the rectangular parallelepiped configuration which consists of glass epoxy which has thermal resistance. When this resin frame 19 is filled up with mould resin 134 inside, it has the height whose resin 134 is fully wrap extent about semi-conductor light emitting device 7b. In the inside of this frame 19, one polar-zone 18a on a printed-circuit board 18 and N lateral electrode 5b under semi-conductor light emitting device 7b are pasted up and connected with the adhesives which have conductivity. On the other hand, P lateral electrode 6b on a printed-circuit board 18 by metal wire 6p. Through the through hole of the shape of cross-section radii which penetrates a printed-circuit board 18 which is not illustrated, these polar zone 18a and 18b was taken about in three dimensions from the top face of a printed-circuit board 18 to the underside which is a component side, and is prolonged even to the ends of printed-circuit board 18 underside, respectively. The above-mentioned printed-circuit board 18 top and inside the resin frame 19, it fills up with the mould resin 134 which consists of an epoxy resin of the translucency which distributed the fluorescent substance so that the whole semi-conductor light emitting device 7b may be covered. Since the above-mentioned semi-conductor light emitting device 7b has Electrodes 6b and 5b to vertical both sides like the semi-conductor light emitting device of the conventional GaAs system or a GaP system, it has the advantage that it is common and the conventional leadframe can be used. In addition, as a base, the insulating film other than the above-mentioned printed-circuit board may be used.

[0136] The semi-conductor luminescence equipment of drawing 12 (b) is filled up with the mould resin 134 as closure resin which distributed the fluorescent substance while it is equipped with resin frame 19a on the printed circuit board 18 as a base and is equipped with semi-conductor light emitting device 7c which has an insulating substrate inside this resin frame 19a. The above-mentioned resin frame 19a inclines so that the side face facing semi-conductor light emitting device 7c may reflect the light by which outgoing radiation was carried out to the longitudinal direction from the side face of semi-conductor light emitting device 7c in the direction of a right angle of a printed circuit board 18.

[0137] This semi-conductor luminescence equipment is equipped with resin frame 19a toward which the side face which faces at semi-conductor light emitting device 7c on the printed circuit board 18 of the rectangular parallelepiped configuration which consists of glass epoxy inclined. The above-mentioned semi-conductor light emitting device 7c turns a semi-conductor laminating side face downward, and is carried in the printed-circuit board 18. P lateral electrode 6c and N lateral electrode 5c with which semi-conductor light emitting device 7c is equipped are respectively connected to the polar zone 18a and 18b on a printed-circuit board 18 through Au bump. The above-mentioned polar zone 18a and 18b is taken about in three dimensions to an underside like the semi-conductor luminescence equipment shown in drawing 12 (a) through the through hole which is not illustrated from the top face of a printed-circuit board 18, and is extended even to the underside ends of a printed-circuit board 18. In addition, as a base, the insulating film other than the above-mentioned printed-circuit board 18 may be used. Moreover, although direct continuation of the above-mentioned semi-conductor light emitting device 7c was carried out to the printed-circuit board 18, it may carry semi-conductor light emitting device 7c in submounting which gives metal wiring beforehand and consists of Si, and may connect this submounting to a printed-circuit board 18 electrically with die bond, wire bond, etc.

[0138] Since this semi-conductor luminescence equipment mounts the semi-conductor laminating side face of semi-conductor light emitting device 7c in the immediate printing wiring substrate 18, it has the advantage that the heat from the luminescence field of semi-conductor light emitting device 7c can be quickly missed to the exterior through submounting and a leadframe.

[0139] The mould resin 134 in the semi-conductor luminescence equipment of drawing 12 (a) and (b) is the same ingredient as the mould resin 13 of drawing 8 (a), (b), and (c), and distribution of the fluorescent substance in the above-mentioned mould resin can take various gestalten according to the class of mould resin, the class of fluorescent substance, an operating environment, conditions, an application, etc.

[0140] In drawing 12 (a) and (b), although the above-mentioned resin frames 19 and 19a were stuck on the printed-circuit board 18 after forming them apart from a printed-circuit board 18, they may remove some thicker printed-circuit boards, may form a crevice, and may use the surroundings of this crevice as a frame. Furthermore, while forming a through hole in a printed-circuit board, arranging an electrode-cum-wiring by the metallic foil on the base of this printed-circuit board and arranging a semi-conductor light emitting device after an electrode-cum-this wiring, the above-mentioned through hole part may be closed by closure resin.

[0141] Moreover, in the semi-conductor luminescence equipment of drawing 12 (a) and (b), semi-conductor light emitting device 7a shown in drawing 1 (a) is sufficient as the semi-conductor light emitting devices 7b and 7c, and when this semi-conductor light emitting device 7a is used, they connect the electrode of semi-conductor light emitting device 7a, and the polar zone of a printed-circuit board with a metal wire.

[0142] (6th operation gestalt) Drawing 13 is the sectional view showing the semi-conductor luminescence equipment in the 6th operation gestalt of this invention.

[0143] This semi-conductor luminescence equipment has the same frame 19a as the frame with which the semi-conductor luminescence equipment shown in drawing 12 (b) is equipped. This frame 19a is installed on the printed circuit board 18 as a base of the shape of a rectangular parallelepiped which consists of glass epoxy, and the side face facing semi-conductor light emitting device 7c of this frame 19a inclines so that the light from the side face of semi-conductor light emitting device 7c may be reflected in the direction of a right angle of a printed circuit board 18. The above-mentioned semi-conductor light emitting device 7c is carried on the printed-circuit board 18 so that outgoing radiation of the light may be carried out [in / for a semi-conductor laminating side / drawing 13] from an

upper substrate side towards the bottom in drawing 13. The electrodes 6c and 5c of this semi-conductor light emitting device 7c are being connected to the polar zone 18a and 18b of a printed-circuit board 18 by the bump like the semi-conductor luminescence equipment shown in drawing 12 (b). It is filled up with the mould resin 135 as closure resin of the translucency which consists of an epoxy resin inside frame 19a arranged on the above-mentioned printed-circuit board 18, and the above-mentioned semi-conductor light emitting device 7c is closed. And on above-mentioned frame 19a and mould resin 13, a fluorescent substance 12 has predetermined thickness and is formed in the shape of a layer.

[0144] Since the fluorescent substance 12 is formed in the location of the abbreviation equal distance by the thickness of homogeneity from the luminescence field of semi-conductor light emitting device 7c, in the location of all the fluorescent substances 12, uniform luminescence which does not have nonuniformity by the quantity of light which passes a fluorescent substance 12 becoming abbreviation regularity is possible for the semi-conductor luminescence equipment in this operation gestalt. Moreover, since the above-mentioned fluorescent substance 12 keeps a predetermined distance and is formed from semi-conductor light emitting device 7c, it can ease the electric and thermal effect of a semi-conductor light emitting device to a fluorescent substance 12.

[0145] With the above-mentioned operation gestalt, although the fluorescent substance 12 was formed also in the top face of resin frame 19a, as long as resin frame 19a is formed with the ingredient of protection-from-light nature, it may form a fluorescent substance 12 in the upper chisel of mould resin 135. Moreover, the height of resin frame 19a is made high, after filling up extent slightly exceeding the upper bed of semi-conductor light emitting device 7c with mould resin 13, it is in the above-mentioned resin frame 19a, and a fluorescent substance may be arranged by potting etc. on the above-mentioned mould resin 135.

[0146] The above-mentioned resin frame 19a may use as a frame the heights which removed some thicker printed-circuit boards 18 like the time of describing the semi-conductor luminescence equipment of drawing 12 (b), and remained. Furthermore, an electrode-cum-wiring by the metallic foil may be prepared in the pars basilaris ossis occipitalis of a printed-circuit board which has a through hole, and a crevice may be formed in it.

[0147] Moreover, although the optical drawing effectiveness to the exterior falls, the resin frame in which the side face facing semi-conductor light emitting device 7c was formed vertically may be used.

[0148] In addition, the semi-conductor light emitting devices 7a and 7b shown in drawing 1 may be used for the above-mentioned semi-conductor light emitting device 7c. Especially semi-conductor light emitting device 7b that has a conductive substrate equips an upside and the bottom with an electrode, and since it is the same electrode structure as the semi-conductor light emitting device of the conventional GaAs system or a GaP system, it has the advantage that the conventional leadframe can be used as it is.

[0149] (7th operation gestalt) Drawing 14 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment in the 7th operation gestalt of this invention.

[0150] Drawing 14 (a) is the sectional view which looked at this semi-conductor luminescence equipment from luminescence, and drawing 14 (b) is the sectional view seen from the right angle to the luminescence direction.

[0151] P lateral electrode 6a and N lateral electrode 5a which semi-conductor light emitting device 7a pasted up this semi-conductor luminescence equipment with the adhesives 11, such as an epoxy resin, on the printed-circuit board 18 as a base of the shape of a rectangular parallelepiped which consists of glass epoxy, and were prepared on the top face of this semi-conductor light emitting device 7a are respectively connected to the polar zone 18a and 18b of a printed-circuit board 18 by the metal wires 6p and 5n. These polar zone 18a and 18b was taken about in three dimensions on the underside of a printed-circuit board 18 through the through holes 19 and 19 of the shape of cross-section radii formed by penetrating a printed-circuit board 18, and is prolonged to the ends of the component side which is an underside of this printed-circuit board 18. In addition, it may change to the above-mentioned printed-circuit board 18, and an insulating film may be used.

[0152] Furthermore, the above-mentioned whole semi-conductor light emitting device 7a is closed with the mould resin 136 as closure resin which consists of an epoxy resin of the translucency which distributed the fluorescent substance. While this mould resin 136 has the abbreviation quadrant elliptical cross section where a left side edge and a bottom edge make a straight line in drawing 14 (b), it has the rectangle cross section where the cross direction is longer than the height direction in drawing 14 (a). And the reflector 20 for reflecting the light from above-mentioned semi-conductor light emitting device 7a on the above-mentioned mould resin 136 is formed.

[0153] As for the above-mentioned mould resin 136, it is desirable to use the thermosetting resin which has translucency and can also bear the elevated temperature in the case of a solder reflow in a mounting process, and it forms it by the resin potting method, the transfermold method, the injection molding method, etc. on a printed-circuit board 18. The top face of the above-mentioned mould resin 136 arranges semi-conductor light emitting device 7a more nearly up than center line I-I of this parabola while a parabola is made and it curves, as shown in drawing 14 (b). Moreover, the outgoing radiation side face A of the light of the above-mentioned mould resin 136 is formed evenly, and is made into the side face and abbreviation same side of a printed-circuit board 18. In addition, the curved surface of the above-mentioned mould resin 136 may be formed so that the above-mentioned semi-conductor light emitting device 7a may be caudad located rather than center line I-I of the parabola of a curved surface.

[0154] Including at least the ingredient which reflects the light by which wavelength conversion was carried out with the light and the fluorescent substance 12 of semi-conductor light emitting device 7a, like the above-mentioned mould resin 136, using the thermosetting resin or thermoplastics which can also bear the elevated temperature in the case of a solder reflow, the above-mentioned reflector 20 is formed by the resin potting method, the

transfermold method, the injection molding method, etc. so that the upside side of the above-mentioned mould resin 136 may be covered. The right side edge of a reflector 20 makes a straight line, and as shown in the cross section of drawing 14 (b), while the bottom edge curves in contact with the upside edge of mould resin 136, this reflector 20 is formed so that the right side edge side of the above-mentioned printed-circuit board 18 may be followed, so that the flat surface as the optical outgoing radiation side A of mould resin 136 where a left side edge edge is the same may be made. And the upper bed edge of the above-mentioned reflector is formed in parallel at the above-mentioned printed-circuit board 18. As for this semi-conductor luminescence equipment, the interface of the top face of mould resin 136 and the underside of a reflector 20 is a reflector. While diffusing the light which reflects and carries out outgoing radiation in this reflector on the left-hand side of horizontal in drawing 14 (a), it is interrupted with a reflector 20 and a printed-circuit board 18 in the vertical direction. Therefore, the direct light and the reflected light from semi-conductor light emitting device 7a serve as directional characteristics extracted horizontally. Specifically, the horizontal half power angle in exposure light has ≈ 65 degrees and the directional characteristics whose vertical half power angle is ≈ 30 degrees. therefore — since wavelength conversion is carried out with the fluorescent substance 12 in mould resin 136, it is reflected by the reflector 20 and outgoing radiation of it is carried out from the lateral portion of mould resin 136 to the exterior, while the light from semi-conductor light emitting device 7a carries out direct outgoing radiation — horizontal — an effective exposure field — large — and high — brightness side luminescence mold semi-conductor luminescence equipment can be offered.

[0155] In addition, since the reflector 20 should have reflex action only into the part which touches mould resin 136, it is good to prepare the reflecting layer which becomes either the upside side where mould resin 136 curved, or the bottom side as for which the reflector 20 carried out the bend from a metal, a white coating, etc.

[0156] The resin which pastes up the above-mentioned semi-conductor light emitting device 7a on a printed-circuit board 18 is [that there is especially no definition] available if the light from semi-conductor light emitting device 7a is not absorbed. For example, the resin which mixed the thermally conductive good metal for the heat-characteristic improvement of semi-conductor light emitting device 7a, the resin containing the ingredient which reflects and scatters efficiently the light emitted in the direction of the leadframe mounting section, etc. may be used. However, to use the resin containing a metal, it is necessary to take care that P lateral electrode and N lateral electrode do not short-circuit.

[0157] In addition, in the semi-conductor luminescence equipment in this operation gestalt, it may change to the above-mentioned semi-conductor light emitting device 7a, and semi-conductor light emitting device 7b which equips with an electrode the top face and underside which were shown in drawing 1 (b), respectively, and semi-conductor light emitting device 7c of the type which carries out outgoing radiation of the light from the substrate side shown in drawing 1 (c) may be used. Since the above-mentioned semi-conductor light emitting device 7b has the same electrode structure as the semi-conductor luminescence equipment of the conventional GaAs system or a GaP system, it has the advantage that the conventional leadframe can be used as it is. Since the above-mentioned semi-conductor light emitting device 7c mounts a semi-conductor laminating side face in direct electric wiring, it has the advantage that the heat from a luminescence field can be promptly missed to the exterior through a submounting leadframe.

[0158] (8th operation gestalt) Drawing 15 (a) and (b) are the sectional views showing the side luminescence mold semi-conductor luminescence equipment as 8th operation gestalt of this invention.

[0159] Drawing 15 (a) shows the sectional view which looked at this semi-conductor luminescence equipment from luminescence, and drawing 15 (b) is the sectional view seen from the right angle to the luminescence direction. The semi-conductor luminescence equipment of drawing 15 (a) and (b) used semi-conductor light emitting device 7b which has an electrode for the top face and the underside, Except having formed the fluorescent substance 12 in the outgoing radiation side A side of the light of the mould resin 137 as closure resin in the shape of a layer, without distributing a fluorescent substance in closure resin It is the same as that of the semi-conductor luminescence equipment of drawing 14 (a) and (b), and the same reference number is given to the part which has the same function, and detailed explanation is omitted.

[0160] The amount of the light which passes in the abbreviation whole region of a fluorescent substance 12 becomes always fixed [equipment], since this side luminescence mold semi-conductor luminescence equipment formed the fluorescent substance 12 in the location of the abbreviation equal distance from the luminescence field of semi-conductor light emitting device 7b at the thickness of homogeneity, and uniform luminescence without nonuniformity is attained. Moreover, since the fluorescent substance 12 has been arranged in the location estranged from semi-conductor light emitting device 7b, the effect by the current and heat of semi-conductor light emitting device 7b to a fluorescent substance 12 can be eased. Moreover, since the type which has arranged Electrodes 6b and 5b on the top face and the underside in the above-mentioned semi-conductor light emitting device 7b has same semi-conductor light emitting device and electrode structure of the conventional GaAs system or a GaP system, it has the advantage that the conventional leadframe can be used as it is.

[0161] In the operation gestalt of this invention, the above-mentioned semi-conductor light emitting device 7b may use semi-conductor light emitting device 7a of drawing 1 (a), and semi-conductor light emitting device 7c of drawing 1 (c).

[0162] (9th operation gestalt) Drawing 16 (a) and (b) are drawings showing the side luminescence mold semi-conductor luminescence equipment which is the 9th operation gestalt of this invention.

[0163] Drawing 16 (a) is the sectional view which looked at this semi-conductor luminescence equipment from luminescence, and (b) is the sectional view seen from the right angle to the luminescence direction. This semi-

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which wavelength was changed by fluorescent substance layer 12a as a fluorescent substance is carried out to the exterior of semi-conductor luminescence equipment, the color tone of semi-conductor luminescence equipment becomes still better. In addition, the depth of the above-mentioned breakthrough B should just be extent in which the luminescence field of semi-conductor light emitting device 7b sees and hides from the outgoing radiation side A (refer to drawing 17 (b)) side of light at least.

[0171] In addition, in the above-mentioned operation gestalt, the semi-conductor light emitting devices 7a and 7c shown in drawing 1 (a) and (c) may be used for semi-conductor light emitting device 7b. Since a luminescence field is located near the pars basilaris ossis occipitalis of a through hole B when it has arranged in Breakthrough B, semi-conductor luminescence equipment is further made especially as for the above-mentioned semi-conductor light emitting device 7c to a thin shape.

[0172] (11th operation gestalt) Drawing 18 (a), (b), (c) and drawing 19 (a), (b), and (c) are drawings having shown the wavelength distribution of light in which the semi-conductor luminescence equipment of the 11th operation gestalt of this invention carries out outgoing radiation. This semi-conductor luminescence equipment is equipped with a semi-conductor light emitting device on a base, and the outgoing radiation light of this semi-conductor light emitting device has the peak of luminescence wavelength in 410nm of a wavelength field (390nm thru/or 420nm).

Furthermore, this semi-conductor luminescence equipment is equipped with the 1st, 2nd, and 3rd fluorescent substance which changes the outgoing radiation light of the above-mentioned semi-conductor light emitting device. The above-mentioned semi-conductor light emitting device is closed by the closure resin which consists of resin which is not damaged by this semi-conductor light emitting device, and after the 1st, 2nd, and 3rd fluorescent substance of the above has been mixed by abbreviation homogeneity, it is contained in this closure resin. The 1st fluorescent substance of the above consists of a fluorescent substance of 0.5MgF₂ and 3.5 MgO-GeO₂:Mn, it is excited by the outgoing radiation light of the above-mentioned semi-conductor light emitting device, and luminescence wavelength carries out outgoing radiation of the red light which has the main peak in 658nm. The 2nd fluorescent substance of the above consists of a fluorescent substance of SrAl₂O₄:Eu, and luminescence wavelength carries out outgoing radiation of the green light which has the main peak in 522nm. The 3rd fluorescent substance of the above consists of a fluorescent substance of BaMgAl₁₀O₁₇:Eu, and luminescence wavelength carries out outgoing radiation of the blue light which has the main peak in 452nm. By carrying out color mixture of the outgoing radiation light from the 1st, 2nd, and 3rd fluorescent substance of the above, this semi-conductor luminescence equipment carries out outgoing radiation of the white light, and is used as the light source for back lights of indicating equipments, such as a cellular phone, and a Personal Digital Assistant, a personal computer. In addition, although it is in a wavelength field (390nm thru/or 420nm), if the peak of the luminescence wavelength of the above-mentioned semi-conductor light emitting device is in a wavelength field (400nm thru/or 420nm), it is more desirable.

[0173] In the above-mentioned semi-conductor luminescence equipment, drawing 18 (a), (b), and (c) are drawings having shown change produced in wavelength distribution of outgoing radiation light, when the mixed ratio of the 1st, 2nd, and 3rd fluorescent substance of the above is changed. An axis of abscissa is wavelength (nm) and all of an axis of ordinate are relative intensity (%). Moreover, also in any, the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance of the above to the weight of the above-mentioned closure resin is 0.5.

[0174] Drawing 18 (a) is drawing in which the 1st fluorescent substance showed wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case 47 % of the weight and the 2nd fluorescent substance are [13 % of the weight and the 3rd fluorescent substance] 40 % of the weight noting that the total amount of the 1st, 2nd, and 3rd fluorescent substance is 100 % of the weight. The outgoing radiation light of the semi-conductor luminescence equipment in this case becomes the white of the color tone which green cut a little.

[0175] Drawing 18 (b) is drawing in which the 1st fluorescent substance showed wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case 56 % of the weight and the 2nd fluorescent substance are [11 % of the weight and the 3rd fluorescent substance] 33 % of the weight noting that the total amount of the 1st, 2nd, and 3rd fluorescent substance is 100 % of the weight. The outgoing radiation light of the semi-conductor luminescence equipment in this case becomes the white of a good color tone.

[0176] Drawing 18 (c) is drawing in which the 1st fluorescent substance showed wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case 65 % of the weight and the 2nd fluorescent substance are [26 % of the weight and the 3rd fluorescent substance] 9 % of the weight noting that the total amount of the 1st, 2nd, and 3rd fluorescent substance is 100 % of the weight. The outgoing radiation light of the semi-conductor luminescence equipment in this case becomes the white of the color tone which red cut a little, and the so-called daytime white.

[0177] moreover, La₂O₂S:Eu as the 1st fluorescent substance and BaMg₂aluminum₁₆O₂₇: as the 2nd fluorescent substance — the semi-conductor luminescence equipment equipped with Eu, Mn, and 10(Sr, calcium, Mg, Ce) (PO₄)₆Cl₂:Eu as the 3rd fluorescent substance in order at 72 % of the weight, 7 % of the weight, and 21% of the weight of a rate was formed. The outgoing radiation light of this semi-conductor luminescence equipment was the good white light. Furthermore, a white outgoing radiation light also with the good semi-conductor luminescence equipment equipped with the 1st, 2nd, and 3rd fluorescent substance of the above in order at 58 % of the weight, 22 % of the weight, and 20% of the weight of a rate was obtained. While becoming the white of the color tone which green cut when the above experimental result was taken into consideration, and the luminescent color of the above-mentioned semi-conductor luminescence equipment had few mixed ratios of the 1st fluorescent substance, i.e., the

fluorescent substance of red luminescence, than 50 % of the weight, when there were more mixed ratios of the 1st fluorescent substance of the above than 70 % of the weight, it turned out that it becomes the white of the color tone which red cut. Moreover, it turned out that the luminescent color of the above-mentioned semi-conductor luminescence equipment turns into white of the color tone which red cut when there were few mixed ratios of the 2nd fluorescent substance, i.e., the fluorescent substance of green luminescence, than 7 % of the weight, and it will become the white of the color tone which green cut if there are more mixed ratios of the 2nd fluorescent substance of the above than 20 % of the weight. Moreover, it turned out that the luminescent color of the above-mentioned semi-conductor luminescence equipment turns into white of the color tone which red cut when there were few mixed ratios of the 3rd fluorescent substance, i.e., the fluorescent substance of blue luminescence, than 20 % of the weight, and it will become the white of the color tone which green cut if there are more mixed ratios of the 3rd fluorescent substance of the above than 30 % of the weight. therefore, the case where the ratio of the AUW of the 1st [as opposed to the weight of closure resin in the semi-conductor luminescence equipment of the 11th operation gestalt] thru/or the 3rd fluorescent substance is 0.5 — the 1st, 2nd, and 3rd fluorescent substance — 56 % of the weight of each, 11 % of the weight, and 33% of the weight of a mixing ratio — a good white outgoing radiation light is obtained with it being a rate.

[0178] In the above-mentioned semi-conductor luminescence equipment, drawing 19 (a), (b), and (c) are drawings having shown change produced in wavelength distribution of outgoing radiation light, when the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is changed. An axis of abscissa is wavelength (nm) and all of an axis of ordinate are relative intensity (%). Moreover, also in any, for the 1st fluorescent substance, the 2nd fluorescent substance is [the 3rd fluorescent substance] 9% of the weight of a mixed ratio 26% of the weight 65% of the weight noting that the total amount of the 1st, 2nd, and 3rd fluorescent substance is 100 % of the weight.

[0179] Drawing 19 (a) is drawing having shown wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 0.5. The outgoing radiation light of this semi-conductor luminescence equipment becomes the white of the color tone which red cut a little, and the so-called daytime white.

[0180] Drawing 19 (b) is drawing having shown wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 0.66. The outgoing radiation light of this semi-conductor luminescence equipment becomes the white of a good color tone.

[0181] Drawing 19 (c) is drawing having shown wavelength distribution of the outgoing radiation light by semi-conductor luminescence equipment in case the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 1.0. The outgoing radiation light of this semi-conductor luminescence equipment becomes the white of the color tone which green cut a little.

[0182] Drawing 19 (a), (b), and (c) show that a white outgoing radiation light of a color tone with the above-mentioned semi-conductor luminescence equipment good when the 1st, 2nd, and 3rd fluorescent substance of the above is 65 % of the weight, 26 % of the weight, and 9 % of the weight respectively and the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 1.0 or less [0.5 or more] is obtained.

[0183] Drawing 20 is drawing showing the emission spectrum 150 of the semi-conductor luminescence equipment shown in drawing 19 (a), and the effective emission spectrum 152 of the semi-conductor luminescence equipment in consideration of human being's relative luminous efficiency 151. An axis of abscissa is wavelength (nm) and an axis of ordinate is relative intensity (%).

[0184] Since it has a larger luminescence wavelength field than the wavelength field which human being's relative luminous efficiency 151 has and the effective emission spectrum 152 of the wavelength field which covers the wavelength field of the above-mentioned relative luminous efficiency 151 is obtained, in human being's vision, a color tone is made as for the emission spectrum 150 of the above-mentioned semi-conductor luminescence equipment to the good white luminescent color, so that drawing 20 may show.

[0185] Furthermore, since the above-mentioned semi-conductor luminescence equipment is resin which the above-mentioned closure resin does not damage by the outgoing radiation light from a semi-conductor light emitting device, inconvenience, such as melanism, does not produce this closure resin. Therefore, inconvenience, such as lowering of the brightness of semi-conductor luminescence equipment, can be prevented, it continues at a long period of time, and the engine performance of semi-conductor luminescence equipment is made to stability.

[0186] In the above-mentioned semi-conductor luminescence equipment, the wavelength field range of human being's relative luminous efficiency 151, abbreviation, etc. may spread and carry out the wavelength field of the above-mentioned effective emission spectrum 152 by using two or more fluorescent substances of a class for the 1st, 2nd, and 3rd fluorescent substance of the above respectively. Since the luminescence wavelength field of semi-conductor luminescence equipment is made by this only in human being's visible region while being able to make good the color tone of the luminescent color of semi-conductor luminescence equipment, the luminous efficiency of semi-conductor luminescence equipment can be improved.

[0187] Although the semi-conductor luminescence equipment of this operation gestalt mixed the 1st, 2nd, and 3rd fluorescent substance of the above at abbreviation homogeneity to the closure resin which closes a semi-conductor light emitting device Only the 1st, 2nd, and 3rd fluorescent substance of the above may be mixed, and this mixed fluorescent substance may be arranged in the shape of a layer on the front face of closure resin, and the 1st, 2nd, and 3rd fluorescent substance of the above may be respectively prepared in the front face of the above-mentioned

closure resin in the shape of a layer separately. In this case, it is desirable to arrange in consideration of luminescence / absorption wavelength of light etc. toward a side far from the side near a semi-conductor light emitting device in order with the short luminescence wavelength of the fluorescent substance with which that layer contains each layer. Moreover, the semiconductor device of this operation gestalt may be formed in the same structure as the semi-conductor luminescence equipment of the above 1st thru/or the operation gestalt of 10. By this, white luminescence of a good color tone can be obtained in the semi-conductor luminescence equipment of a ramp type, a chip mold, and a side luminescence mold.

[0188] (12th operation gestalt) Drawing 21 is the mimetic diagram showing the luminescence display of the 12th operation gestalt of this invention. This luminescence display 200 is a liquid crystal display which has the light source 201 which consists of semi-conductor luminescence equipment of the operation gestalt of the above 11th, the light guide plate 202 to which the light 205 from the light source 201 is led, and the liquid crystal panel 203 equipped with the light filter which carries out the spectrum of the light from this light guide plate 202.

[0189] The above-mentioned light source 201 may be formed using any of the semi-conductor luminescence equipment of the above 1st thru/or the operation gestalt of 11. Especially when the above-mentioned luminescence display 200 is used as displays, such as a cellular phone, and a Personal Digital Assistant, a personal computer, the semi-conductor luminescence equipment of white luminescence of the operation gestalt of the above 11th is suitable as the light source 201. Moreover, if the 1st, 2nd, and 3rd fluorescent substance with which the semi-conductor luminescence equipment of the operation gestalt of the above 11th is equipped is used as a fluorescent substance of the semi-conductor luminescence equipment of the above 4th thru/or the operation gestalt of 6, it will have a chip part shape and the semi-conductor luminescence equipment for which light can be emitted white will be obtained. Since this semi-conductor luminescence equipment has a chip part shape, the handling at the time of mounting in the luminescence display 200 becomes easy. Moreover, since the semi-conductor luminescence equipment which has the above-mentioned chip part shape can be attached to side-face 202a of the above-mentioned light guide plate 202 direct picking, it can lead luminescence light to a light guide plate 202 efficiently. Moreover, if the light source 201 is constituted using the semi-conductor luminescence equipment carrying the fluorescent substance of the 11th operation gestalt to the semi-conductor luminescence equipment of the above 7th thru/or the operation gestalt of 10. Since this semi-conductor luminescence equipment is a side luminescence mold, so that the printed-circuit board 18 as a base may turn into a light guide plate 202 to abbreviation parallel. By attaching semi-conductor luminescence equipment in side-face 202a of a light guide plate, thickness of the luminescence display 200 of the direction of optical outgoing radiation of this light guide plate 202 can be effectively made small. In addition, although two or more semi-conductor luminescence equipments were used for it, as long as the above-mentioned light source 201 has enough luminous intensity, one semi-conductor luminescence equipment may constitute it.

[0190] The above-mentioned light guide plate 202 is formed from a polycarbonate, acrylic resin, etc. Moreover, if the light reflex section is prepared in fields other than side-face 202a into which the light from the light source 201 is introduced, and light emission side 202b which emits the introduced light, the light from the light source 201 can be efficiently emitted from light emission side 202b. Moreover, you may introduce from two side faces which the light to a light guide plate 202 is not only from one side-face 202a, for example, counter, or may introduce from three and four side faces. Furthermore, in order to make bleedoff luminous intensity in light emission side 202b into homogeneity, a light-scattering agent may be mixed into a light guide plate 202, or the field by the side of the bottom in the above-mentioned light emission side 202b and drawing 21 which counters may be made to incline, the light introduced from side-face 202a of a light guide plate may be reflected on the above-mentioned bottom side face in which dip was carried out, and you may emit from light emission side 202b. If a light-scattering pattern is prepared in the above-mentioned bottom side face, reinforcement of the light 206 from light emission side 202b will be further made to homogeneity.

[0191] The above-mentioned liquid crystal panel 203 is equipped with the light filter stuck on the liquid crystal enclosed between two transparent substrates which prepared the transparent electrode, and these two substrates, the polarizing plate, and the above-mentioned substrate. Corresponding to two or more pixels by which the quantity of light which penetrates the above-mentioned liquid crystal is adjusted, red and a green and blue light filter are formed in the above-mentioned light filter by the signal impressed to the above-mentioned transparent electrode. It is a color or a pigment of light transmission nature etc., and it is colored red, green, and blue and red and a green and blue light filter are formed so that this light filter may make the pixel of a minute honeycomb configuration or a delta array configuration to a polycarbonate, polyethylene terephthalate, etc. which were formed in the shape of a sheet.

[0192] Drawing 22 is drawing having shown the spectral characteristic of the above-mentioned light filter, 210 is the spectral characteristic of a red light filter, and 212 is [211 is the spectral characteristic of a green light filter, and] the spectral characteristic of a blue light filter. Wavelength distribution of the light from the above-mentioned light source 201 is adjusted so that the spectral characteristic 210,211,212 of this light filter may be suited. In more detail, in the semi-conductor luminescence equipment which constitutes the light source 201, the luminescence wavelength of a semi-conductor light emitting device, the luminescence wavelength of the 1st, 2nd, and 2nd fluorescent substance and a mixed ratio, the rate of a compounding ratio of the AUW of the fluorescent substance of the 1st thru/or 3 and the weight of the resin for closure, etc. are adjusted, and wavelength distribution of the light 205 from the light source 201 is fitted to the spectral characteristic 210,211,212 of the above-mentioned light filter. For example, the semi-conductor luminescence equipment which has a good color tone and makes wavelength

distribution of drawing 19 (b) conforms to the spectral characteristic of drawing 22. This semi-conductor luminescence equipment is because the above 1st thru/or the rate of a compounding ratio of the AUW of the fluorescent substance of 3 and the weight of the resin for closure are adjusted so that the above-mentioned spectral characteristic may be suited. Thus, since the above-mentioned light source 201 has the wavelength distribution which suits the spectral characteristic of the above-mentioned light filter, if the light 205 from this light source 201 is led to a liquid crystal panel 203 through the above-mentioned light guide plate 202, with the light filter of this liquid crystal panel 203, its brightness will be high and a spectrum will be carried out to the red of an abbreviation single, and the green and blue light 207. Consequently, a deer with a color tone good [this luminescence display 200] can also display the image and image of high brightness and high contrast.

[0193]

[Translation done.]

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DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[Drawing 1] Drawing 1 (a), (b), and (c) are sectional views of a semi-conductor light emitting device used in this invention.

[Drawing 2] Drawing 2 (a) is drawing showing the emission spectrum of a fluorescent substance about the red luminescent color, and drawing 2 (b) is drawing showing the excitation spectrum of a fluorescent substance.

[Drawing 3] Drawing 3 (a) is drawing showing the emission spectrum of a different fluorescent substance from drawing 2 about the red luminescent color, and drawing 3 (b) is drawing showing the excitation spectrum of a fluorescent substance.

[Drawing 4] Drawing 4 (a) is drawing showing the emission spectrum of a fluorescent substance about the green luminescent color, and drawing 4 (b) is drawing showing the excitation spectrum of a fluorescent substance.

[Drawing 5] Drawing 5 (a) is drawing showing the emission spectrum of a different fluorescent substance from drawing 4 about the green luminescent color, and drawing 5 (b) is drawing showing the excitation spectrum of a fluorescent substance.

[Drawing 6] Drawing 6 (a) is drawing showing the emission spectrum of a fluorescent substance about the blue luminescent color, and drawing 6 (b) is drawing showing the excitation spectrum of a fluorescent substance.

[Drawing 7] Drawing 7 (a) is drawing showing the emission spectrum of a different fluorescent substance from drawing 6 about the blue luminescent color, and drawing 7 (b) is drawing showing the excitation spectrum of a fluorescent substance.

[Drawing 8] Drawing 8 (a), (b), and (c) are the sectional views showing the semi-conductor luminescence equipment in the 1st operation gestalt of this invention.

[Drawing 9] Drawing 9 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment in the 2nd operation gestalt of this invention.

[Drawing 10] Drawing 10 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment in the 3rd operation gestalt of this invention.

[Drawing 11] Drawing 11 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment in the 4th operation gestalt of this invention.

[Drawing 12] Drawing 12 (a) and (b) are the sectional views showing the semi-conductor luminescence equipment in the 5th operation gestalt of this invention.

[Drawing 13] It is the sectional view showing the semi-conductor luminescence equipment in the 6th operation gestalt of this invention.

[Drawing 14] Drawing 14 (a) is the sectional view seen from the transverse plane of the semi-conductor luminescence equipment in the 7th operation gestalt of this invention, and drawing 14 (b) is the sectional view seen from the side face.

[Drawing 15] Drawing 15 (a) is the sectional view seen from the transverse plane of the semi-conductor luminescence equipment in the 8th operation gestalt of this invention, and drawing 15 (b) is the sectional view seen from the side face.

[Drawing 16] Drawing 16 (a) is the sectional view seen from the transverse plane of the semi-conductor luminescence equipment in the 9th operation gestalt of this invention, and drawing 16 (b) is the sectional view seen from the side face.

[Drawing 17] Drawing 17 (a) is the sectional view seen from the transverse plane of the semi-conductor luminescence equipment in the 10th operation gestalt of this invention, and drawing 17 (b) is the sectional view seen from the side face.

[Drawing 18] When the 1st fluorescent substance is [the 3rd fluorescent substance] 40 % of the weight, the 2nd fluorescent substance drawing 18 (a) 13% of the weight 47% of the weight drawing 18 (b) When 56 % of the weight and the 2nd fluorescent substance are [11 % of the weight and the 3rd fluorescent substance] 33 % of the weight for the 1st fluorescent substance, drawing 18 (c) is drawing in which the 1st fluorescent substance showed wavelength distribution of the outgoing radiation light of semi-conductor luminescence equipment in case 65 % of the weight and the 2nd fluorescent substance are [26 % of the weight and the 3rd fluorescent substance] 9 % of the weight.

[Drawing 19] Drawing 19 (a) is drawing having shown wavelength distribution of the outgoing radiation light of semi-conductor luminescence equipment in case drawing 19 (c) is 1.0, when the ratio of the AUW of the 1st, 2nd, and 3rd fluorescent substance to the weight of closure resin is 0.5, and drawing 19 (b) is 0.66.

[Drawing 20] It is drawing showing the emission spectrum 150 of the semi-conductor luminescence equipment shown in drawing 19 (a), and the effective emission spectrum 152 of the semi-conductor luminescence equipment in consideration of human being's relative luminous efficiency 151.

[Drawing 21] It is the mimetic diagram showing the luminescence display of the 12th operation gestalt of this invention.

[Drawing 22] It is drawing having shown the spectral characteristic of the light filter with which the luminescence display of this invention is equipped.

[Description of Notations]

7a Semi-conductor light emitting device

7b Semi-conductor light emitting device

7c Semi-conductor light emitting device

10 Leadframe

12 Fluorescent Substance

[Translation done.]

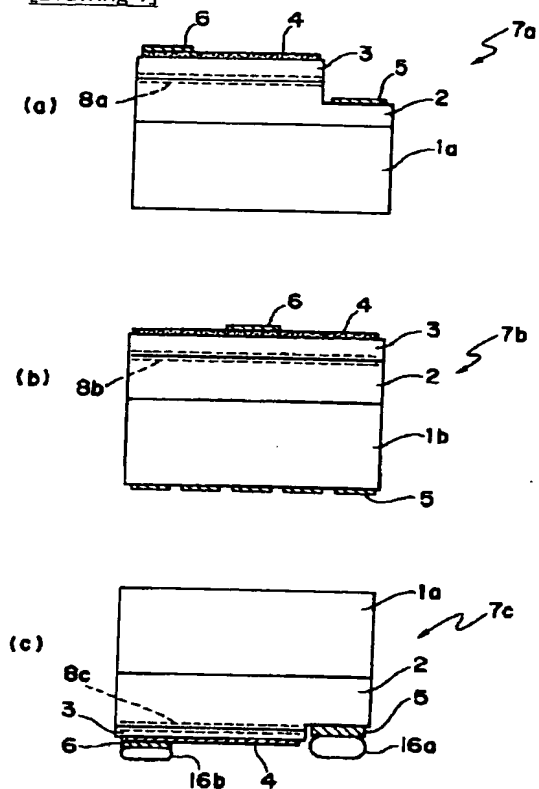
* NOTICES *

JPO and NCIPJ are not responsible for any damages caused by the use of this translation.

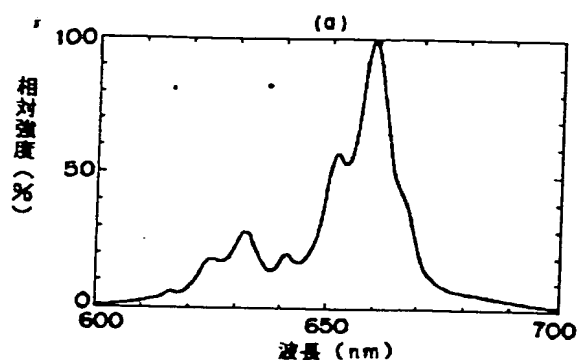
1. This document has been translated by computer. So the translation may not reflect the original precisely.
2. **** shows the word which can not be translated.
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DRAWINGS

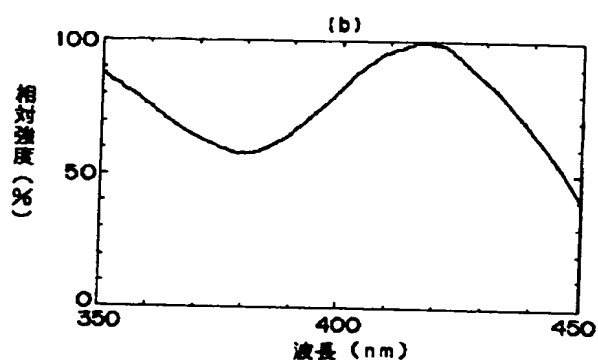
[Drawing 1]



[Drawing 2]

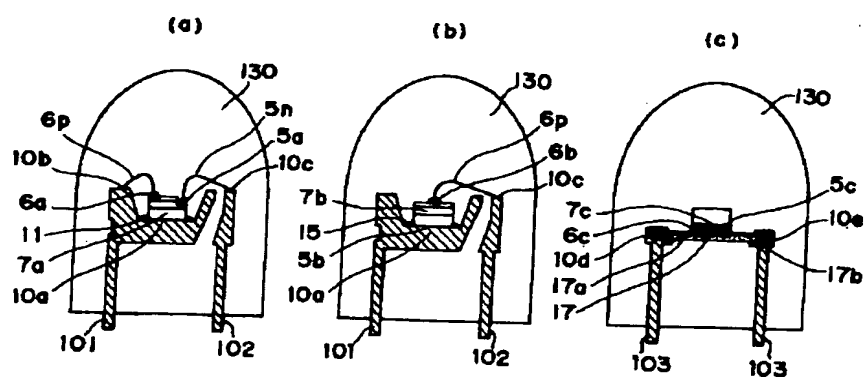


蛍光体 $0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2 \cdot \text{Mn}$ の
発光スペクトル

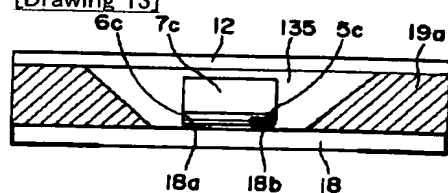


蛍光体 $0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2 \cdot \text{Mn}$ の
励起スペクトル

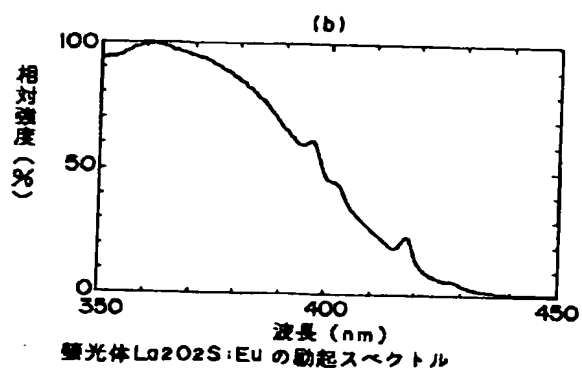
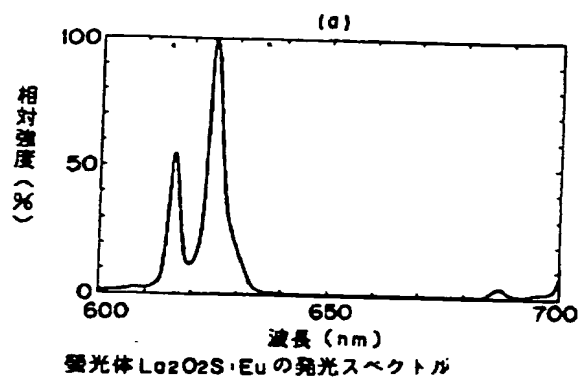
[Drawing 8]



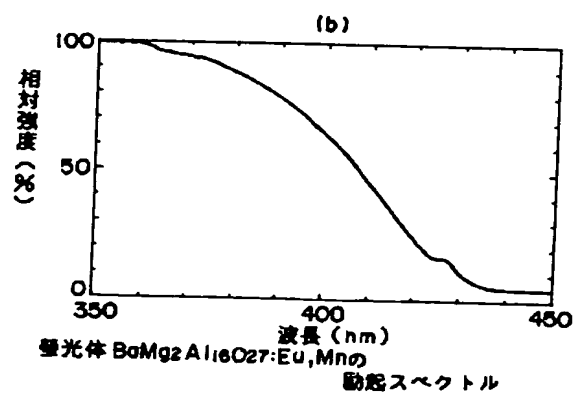
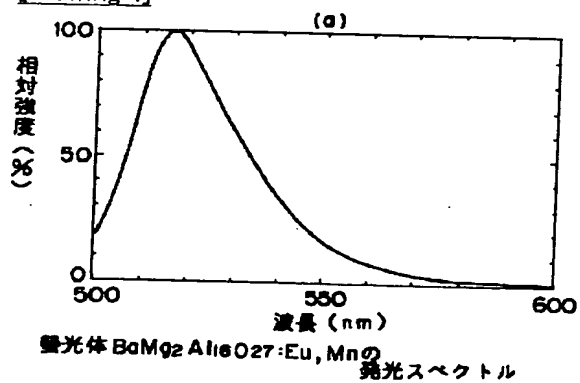
[Drawing 13]



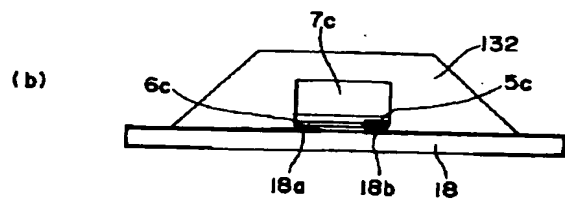
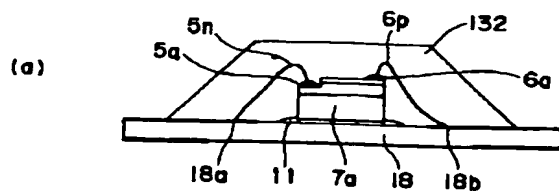
[Drawing 3]



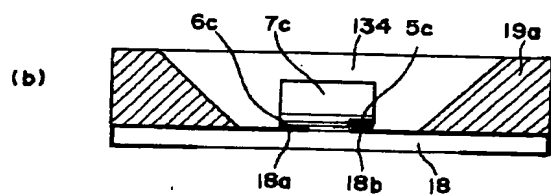
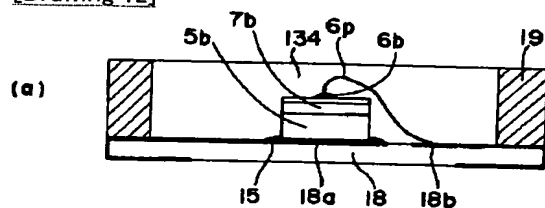
[Drawing 4]



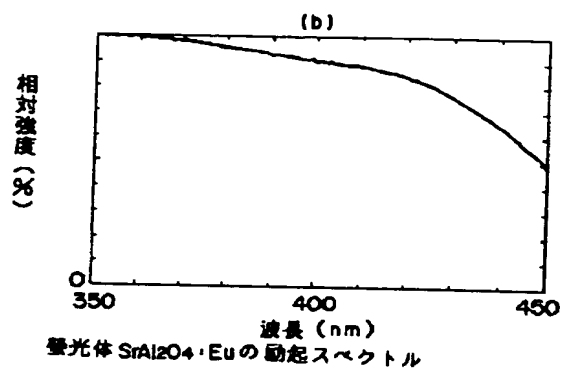
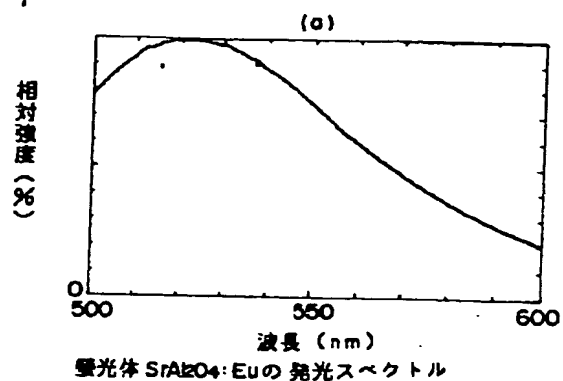
[Drawing 11]



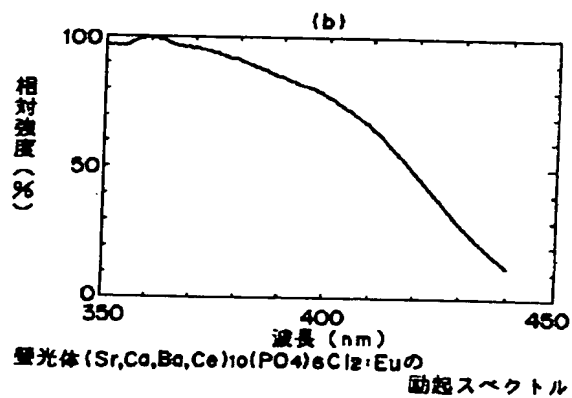
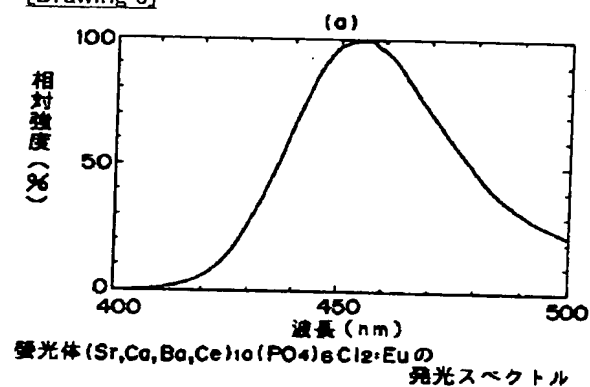
[Drawing 12]



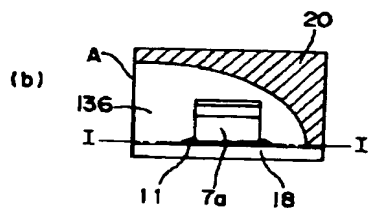
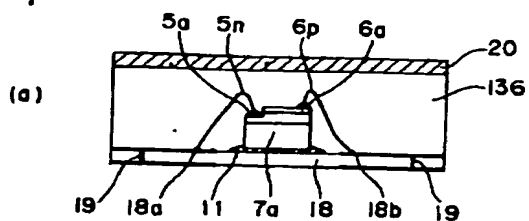
[Drawing 5]



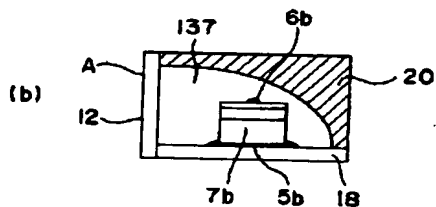
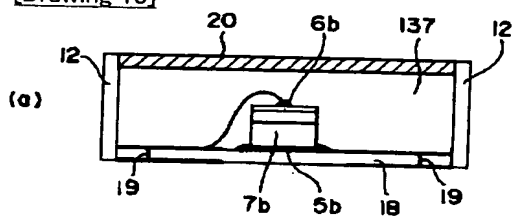
[Drawing 6]



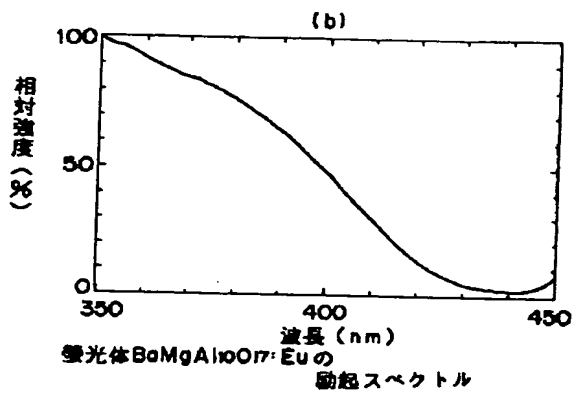
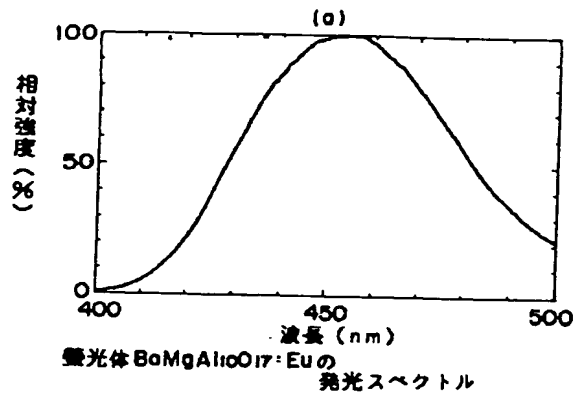
[Drawing 14]



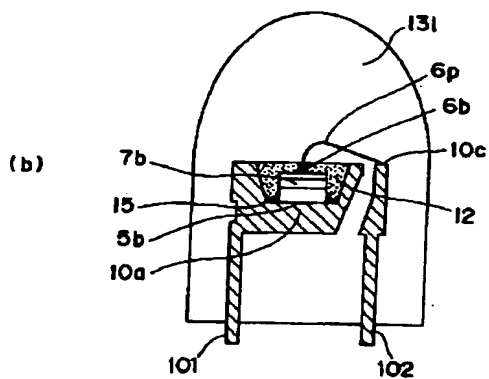
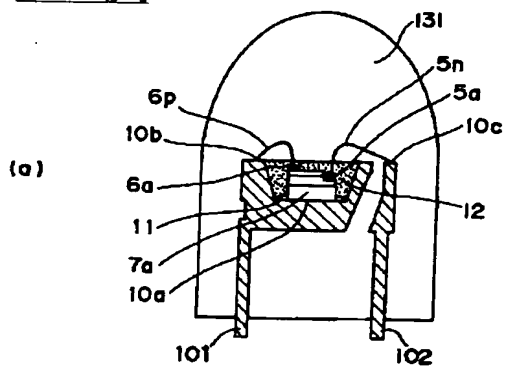
[Drawing 15]



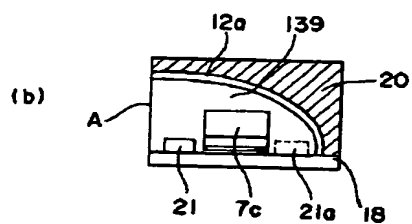
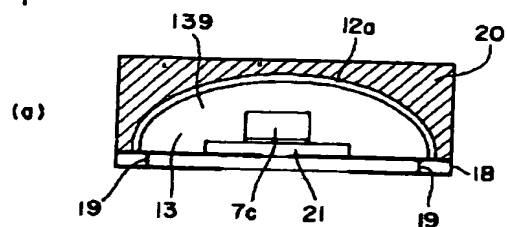
[Drawing 7]



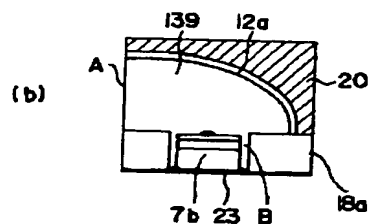
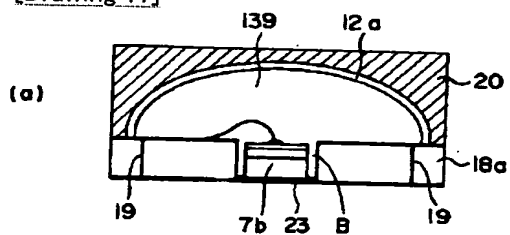
[Drawing 9]



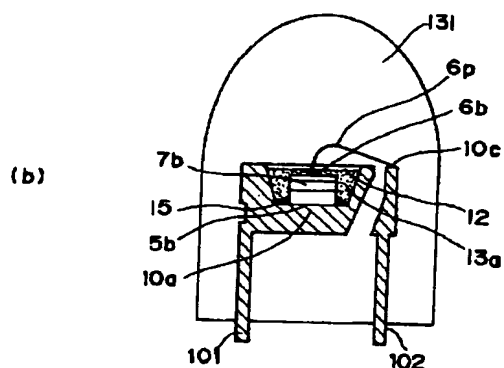
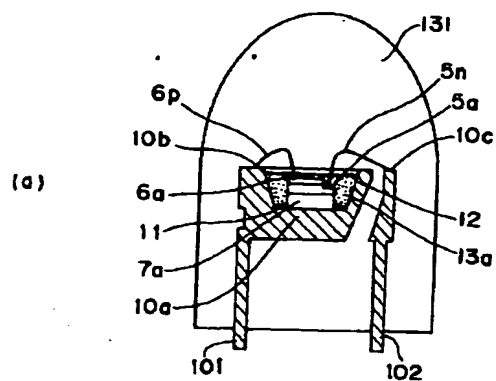
[Drawing 16]



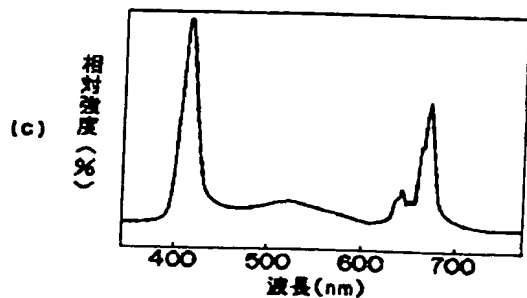
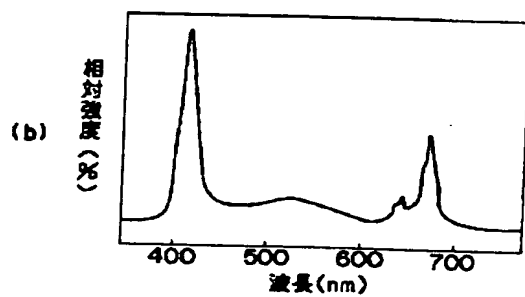
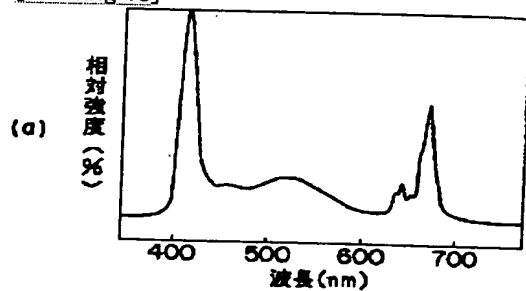
[Drawing 17]



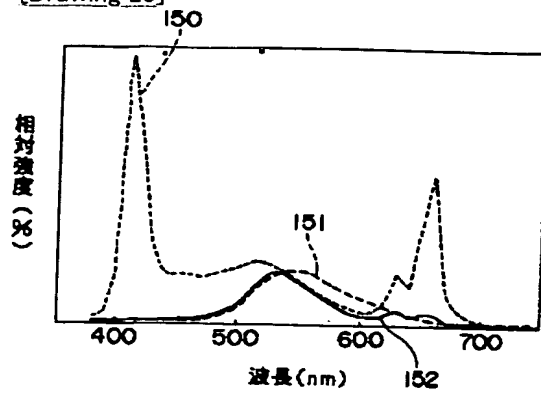
[Drawing 10]



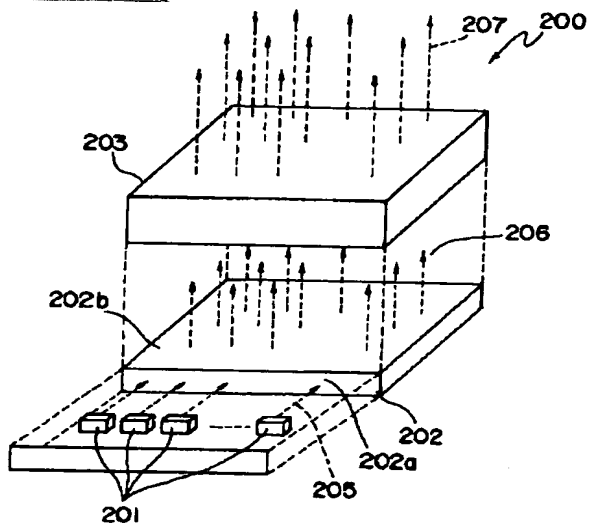
[Drawing 18]



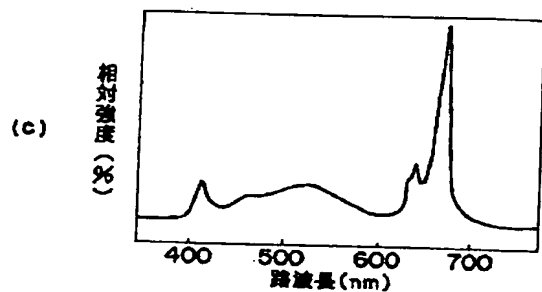
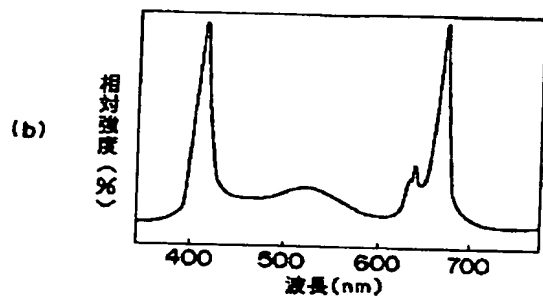
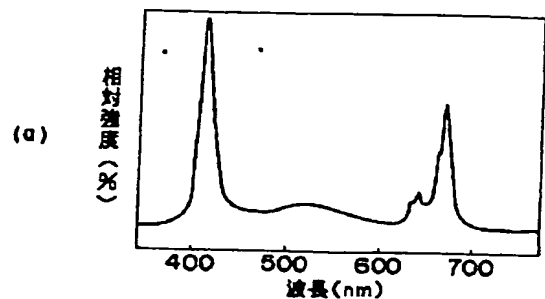
[Drawing 20]



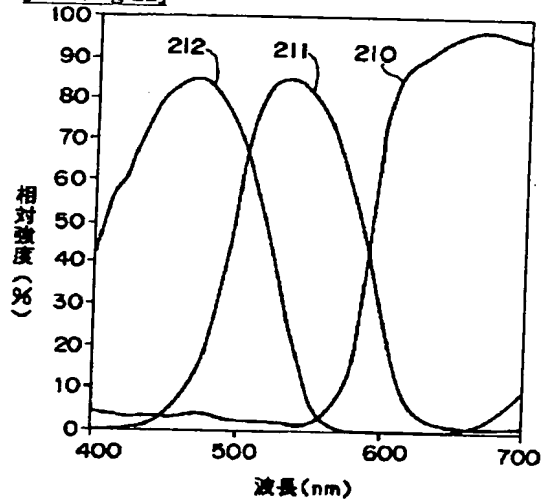
[Drawing 21]



[Drawing 19]



[Drawing 22]



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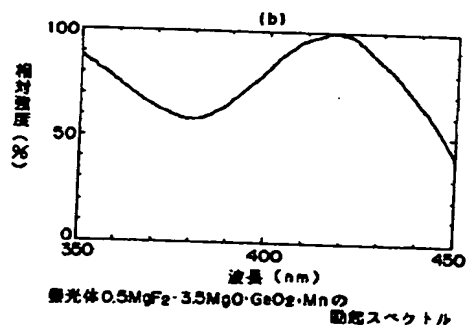
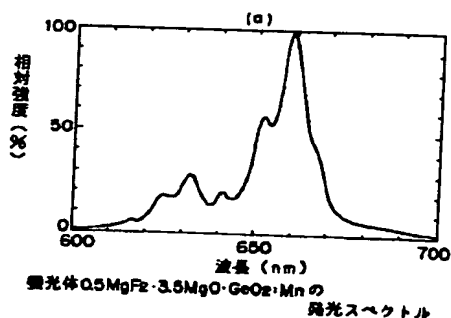
最終頁に続く

(54) 【発明の名称】 半導体発光装置およびそれを用いた発光表示装置

(57) 【要約】

【課題】 半導体発光素子からの出射光の影響が無く色調の良好な単色発光の半導体発光装置を提供すること。

【解決手段】 発光波長が390nm乃至420nmで、人間の視感度が低い近紫外から紫青色の発光色を有する半導体発光素子を備え、この半導体発光素子の光の波長を、単色の発光ピークを有する蛍光体で変換する。蛍光体によって波長変換された光は、人間の視感度を考慮すると、見かけ上、半導体発光素子からの直接光の影響を殆ど受けないから、蛍光体からの光の色調は良好である。また、半導体発光装置の構造や半導体発光素子を変えることなく、蛍光体材料を変えるのみで所望の発光色を有する半導体発光装置が得られるので、半導体発光装置の製造コストを削減できる。



【特許請求の範囲】

【請求項1】 基体上に半導体発光素子を搭載してなる半導体発光装置において、

上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、

上記半導体発光素子からの出射光により励起されて、発光波長が600nm乃至670nmの波長領域に主発光ピークを有する赤色の光を出射する蛍光体を備えることを特徴とする半導体発光装置。

【請求項2】 上記蛍光体は、

$M_2O_2S : Eu$ (但し、MはLa, Gd, Yから選ばれるいずれか一つまたは2以上の元素)、

$0.5MgF_2 \cdot 3.5MgO \cdot GeO_2 : Mn$ 、

$Y_2O_3 : Eu$ 、

$Y(P, V)O_4 : Eu$ 、

$YVO_4 : Eu$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなることを特徴とする請求項1に記載の半導体発光装置。

【請求項3】 基体上に半導体発光素子を搭載してなる半導体発光装置において、

上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、

上記半導体発光素子からの出射光により励起されて、発光波長が500nm乃至540nmの波長領域に主発光ピークを有する緑色の光を出射する蛍光体を備えることを特徴とする半導体発光装置。

【請求項4】 上記蛍光体は、

$RMg_2Al_{16}O_{27} : Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$RMgAl_{10}O_{17} : Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$ZnS : Cu$ 、

$SrAl_2O_4 : Eu$ 、

$SrAl_2O_4 : Eu, Dy$ 、

$ZnO : Zn$ 、

$Zn_2Ge_2O_4 : Mn$ 、

$Zn_2SiO_4 : Mn$ 、

$Q_3MgSi_2O_8 : Eu, Mn$ (但し、QはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、で表される蛍光体の群のうち、いずれか一つまたは2以上からなることを特徴とする請求項3に記載の半導体発光装置。

【請求項5】 基体上に半導体発光素子を搭載してなる半導体発光装置において、

上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、

上記半導体発光素子からの出射光により励起されて、発光波長が410nm乃至480nmの波長領域に主発光ピークを有する青色の光を出射する蛍光体を備えることを特徴とする半導体発光装置。

【請求項6】 上記蛍光体は、

$A_{10}(PO_4)_6Cl_2 : Eu$ (但し、AはSr, Ca, Ba, Mg, Ceから選ばれるいずれか一つまたは2以上の元素)、

$XMg_2Al_{16}O_{27} : Eu$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$XMgAl_{10}O_{17} : Eu$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$ZnS : Ag$ 、

10 $Sr_{10}(PO_4)_6Cl_2 : Eu$ 、

$Ca_{10}(PO_4)_6F_2 : Sb$ 、

$Z_3MgSi_2O_8 : Eu$ (但し、ZはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、

$SrMgSi_2O_8 : Eu$ 、

$Sr_2P_2O_7 : Eu$ 、

$CaAl_2O_4 : Eu, Nd$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなることを特徴とする請求項5に記載の半導体発光装置。

【請求項7】 基体上に半導体発光素子を搭載してなる半導体発光装置において、

上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、

上記半導体発光素子からの出射光により励起されて、発光波長が480nm乃至500nmの波長領域に主発光ピークを有する青緑色の光を出射する蛍光体を備えることを特徴とする半導体発光装置。

【請求項8】 上記蛍光体は、

$Sr_4Al_{14}O_{25} : Eu$ 、

$Sr_4Al_{14}O_{25} : Eu, Dy$ 、

$L_{10}(PO_4)_6Cl_2 : Eu$ (但し、LはBa, Ca, Mgから選ばれるいずれか一つまたは2以上の元素)、

$Sr_2Si_3O_8 \cdot 2SrCl_2 : Eu$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなることを特徴とする請求項7に記載の半導体発光装置。

【請求項9】 基体上に半導体発光素子を搭載してなる半導体発光装置において、

上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、

上記半導体発光素子からの出射光により励起されて、発光波長が570nm乃至600nmの波長領域に主発光ピークを有する橙色の光を出射する蛍光体を備えることを特徴とする半導体発光装置。

【請求項10】 上記蛍光体は、

$ZnS : Mn$ 、

$ZnS : Cu, Mn, Co$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなることを特徴とする請求項9に記載の半導体発光装置。

【請求項11】 上記基体の少なくとも一部と、上記半導体発光素子とを封止する封止樹脂を備え、

50 上記封止樹脂が上記蛍光体を含んでいることを特徴とす

る請求項1乃至10のいずれか一つに記載の半導体発光装置。

【請求項12】 上記基板はカップ形状のマウント部を有するリードフレームであり、

上記半導体発光素子は、上記リードフレームのカップ形状のマウント部の底に配置されており、かつ、もう一つのリードフレームにワイヤーボンディングによって電気的に接続されている、

上記2つのリードフレームの少なくとも一部と上記半導体発光素子とが上記封止樹脂で封止されていることを特徴とする請求項11に記載の半導体発光装置。

【請求項13】 上記基板は、一対のリードフレームの先端に連結された絶縁体であり、

上記半導体発光素子は上記絶縁体に形成された金属配線に接続されている、

上記一対のリードフレームの少なくとも一部と、上記絶縁体と、上記半導体発光素子とが上記封止樹脂で封止されていることを特徴とする請求項11に記載の半導体発光装置。

【請求項14】 上記基板は、カップ形状のマウント部を有するリードフレームであり、

上記半導体発光素子は、上記リードフレームのカップ形状のマウント部の底に配置されており、かつ、もう一つのリードフレームにワイヤーボンディングによって電気的に接続されている、

上記カップ形状のマウント部に上記蛍光体が充填されていると共に、

上記2つのリードフレームの少なくとも一部と、上記半導体発光素子と、上記蛍光体とが封止樹脂で封止されていることを特徴とする請求項1乃至10のいずれか一つに記載の半導体発光装置。

【請求項15】 上記基板は、カップ形状のマウント部を有するリードフレームであり、

上記半導体発光素子は、上記リードフレームのカップ形状のマウント部の底に配置されており、かつ、もう一つのリードフレームにワイヤーボンディングによって電気的に接続されている、

上記カップ形状のマウント部にコーティング部材を充填して、上記コーティング部材の上に上記蛍光体が配置されていると共に、

上記2つのリードフレームの少なくとも一部と、上記半導体発光素子と、上記コーティング部材と、上記蛍光体とが封止樹脂で封止されていることを特徴とする請求項1乃至10のいずれか一つに記載の半導体発光装置。

【請求項16】 上記基板は、金属配線が施された基板であり、

上記半導体発光素子は、上記基板の金属配線に電気的に接続されている、

上記半導体発光素子を封止する封止樹脂を備え、

上記封止樹脂は上記蛍光体を含んでいることを特徴とする

る請求項1乃至10のいずれか一つに記載の半導体発光装置。

【請求項17】 上記基板は、金属配線が施された基板であり、

上記半導体発光素子は、上記基板の金属配線に電気的に接続されていると共に凹部内に配置されており、

上記蛍光体は上記凹部内に充填されていることを特徴とする請求項1乃至10のいずれか一つに記載の半導体発光装置。

10 【請求項18】 上記凹部は、上記基板に配置された枠によって形成されていることを特徴とする請求項17に記載の半導体発光装置。

【請求項19】 上記基板は、金属配線が施された基板であり、

上記半導体発光素子は、上記基板の金属配線に電気的に接続されていると共に凹部内に配置されており、

上記凹部に封止樹脂を充填すると共に、上記封止樹脂の上に上記蛍光体が配置されていることを特徴とする請求項1乃至10のいずれか一つに記載の半導体発光装置。

20 【請求項20】 上記基板は、金属配線が施された基板であり、

上記半導体発光素子は、上記基板の金属配線と電気的に接続されており、

上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、

上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、

上記蛍光体が上記封止樹脂に含まれていることを特徴とする請求項1乃至10のいずれか一つに記載の半導体発光装置。

30 【請求項21】 上記基板は、金属配線が施された基板であり、

上記半導体発光素子は、上記基板の上記金属配線と電気的に接続されており、

上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、

上記半導体発光素子から半導体発光装置の外部に直接出射する光を遮る遮蔽体を備え、

40 上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、

上記蛍光体の層が、上記反射体において光が反射する面に設けられていることを特徴とする請求項1乃至10のいずれか一つに記載の半導体発光装置。

【請求項22】 上記基板は、金属配線が施された基板であり、

上記半導体発光素子は、上記基板の上記金属配線と電気的に接続されており、

少なくとも上記半導体発光素子の発光部分が上記基板の凹部内に配置されており、

上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、

上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、

上記蛍光体の層が、上記反射体において光が反射する面に設けられていることを特徴とする請求項1乃至10のいずれか一つに記載の半導体発光装置。

【請求項23】 上記基板は、金属配線が施された基板であり、

上記半導体発光素子は、上記基板の上記金属配線と電気的に接続されており、

上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、

上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、

上記蛍光体の層が、上記封止樹脂の光が出射する面に設けられていることを特徴とする請求項1乃至10のいずれか一つに記載の半導体発光装置。

【請求項24】 基板上に半導体発光素子を搭載してなる半導体発光装置において、

上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、

第1の蛍光体と、第2の蛍光体と、第3の蛍光体とを備え、

上記第1の蛍光体は、発光波長が600nm乃至670nmの波長領域に主発光ピークを有する赤色の出射光を有し、

上記第2の蛍光体は、発光波長が500nm乃至540nmの波長領域に主発光ピークを有する緑色の出射光を有し、

上記第3の蛍光体は、発光波長が410nm乃至480nmの波長領域に主発光ピークを有する青色の出射光を有して、

上記第1、第2、第3の蛍光体からの出射光の色の和が、白色系であることを特徴とする半導体発光装置。

【請求項25】 上記第1の蛍光体は、

$M_2O_2S : Eu$ (但し、MはLa, Gd, Yから選ばれるいずれか一つまたは2以上の元素)、

$0.5MgF_2 \cdot 3.5MgO \cdot GeO_2 : Mn$ 、

$Y_2O_3 : Eu$ 、

$Y(P, V)O_4 : Eu$ 、

$YVO_4 : Eu$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなり、

上記第2の蛍光体は、

$RMg_2Al_{16}O_{27} : Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$RMgAl_{10}O_{17} : Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$ZnS : Cu$ 、

$SrAl_2O_4 : Eu$ 、

$SrAl_2O_4 : Eu, Dy$ 、

$ZnO : Zn$ 、

$Zn_2Ge_2O_4 : Mn$ 、

$Zn_2SiO_4 : Mn$ 、

$Q_3MgSi_2O_8 : Eu, Mn$ (但し、QはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、で表される蛍光体の群のうち、いずれか一つまたは2以上からなり、

上記第3の蛍光体は、

10 $A_{10}(PO_4)_6Cl_2 : Eu$ (但し、AはSr, Ca, Ba, Mg, Ceから選ばれるいずれか一つまたは2以上の元素)、

$XMg_2Al_{16}O_{27} : Eu$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$XMgAl_{10}O_{17} : Eu$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$ZnS : Ag$ 、

$Sr_{10}(PO_4)_6Cl_2 : Eu$ 、

$Ca_{10}(PO_4)_6F_2 : Sb$ 、

20 $Z_3MgSi_2O_8 : Eu$ (但し、ZはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、

$SrMgSi_2O_8 : Eu$ 、

$Sr_2P_2O_7 : Eu$ 、

$CaAl_2O_4 : Eu, Nd$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなることを特徴とする請求項24に記載の半導体発光装置。

【請求項26】 上記第1、第2、第3の蛍光体は、総量が100重量%であるとして、

上記第1の蛍光体が50重量%以上70重量%以下、

30 上記第2の蛍光体が7重量%以上20重量%以下、

上記第3の蛍光体が20重量%以上30重量%以下であることを特徴とする請求項24または25に記載の半導体発光装置。

【請求項27】 上記封止樹脂は、上記第1、第2、第3の蛍光体を含んでおり、

上記封止樹脂の重量に対する上記第1、第2、第3の蛍光体の総重量の比率が、0.5以上1以下であることを特徴とする請求項26に記載の半導体発光装置。

【請求項28】 請求項24乃至27のいずれか一つに記載の半導体発光装置を用いた光源と、

上記光源からの光を導く導光板と、

上記導光板からの光を透過させて分光する赤、緑、青のカラーフィルタとを備え、

上記半導体発光装置の出射光は、上記カラーフィルタの分光特性に適合した波長分布を有することを特徴とする発光表示装置。

【請求項29】 半導体発光装置の出射光の波長分布が上記カラーフィルタの分光特性に適合するように、

上記半導体発光素子の発光波長と、

50 上記第1の蛍光体の発光波長と、

上記第2の蛍光体の発光波長と、

上記第3の蛍光体の発光波長と、

上記第1、第2、第3の蛍光体の混合比率と、

上記封止樹脂の重量に対する上記第1、第2、第3の蛍光体の総重量の比率とをのうちの少なくとも一つを調節したことを特徴とする請求項28に記載の発光表示装置。

【請求項30】 上記発光表示装置は、液晶表示装置であることを特徴とする請求項28または29に記載の発光表示装置。

【発明の詳細な説明】

【0001】

【発明の属する技術分野】本発明は、液晶ディスプレイや携帯電話・携帯情報端末等のバックライト用光源や、屋内外公告等に利用されるLED（発光ダイオード）表示装置、各々種携帯機器のインジケータ、照光スイッチ、OA（オフィスオートメーション）機器用光源等利用される半導体発光装置に関するものであり、特に半導体発光素子からの出射光を、蛍光体を利用して波長変換し、様々な発光色の光源として利用可能な半導体発光装置と、それを用いた発光表示装置に関する。

【0002】

【従来の技術】半導体発光装置は、小型で消費電力が少なく高輝度発光を安定に行えるので、各種表示装置における光源として広く用いられている。また、半導体発光装置は、各種情報処理装置における情報記録読み取り用の光源としても利用されている。これまでに広く実用化されている長波長可視光半導体発光装置に用いられる半導体発光素子は、使用される発光層の半導体材料や形成条件等により、赤から緑色の高輝度発光が可能であった。これに対して、近年、青から紫色の短波長可視光を発光する半導体発光素子が開発され、一般に実用化され始めてきている。

【0003】これら様々な発光色の半導体発光装置を用いて、例えばR（赤）、G（緑）、B（青）の三原色の発光色を有する半導体発光装置を利用したLEDディスプレイが市場に出始めている。

【0004】さらに、青から紫色の短波長可視光を発光する半導体発光素子と蛍光体とを組み合わせ、半導体発光素子の出射光と蛍光体により波長変換された変換光との混色により白色を得る半導体発光装置が、例えば特許第2927279号に開示されている。

【0005】また、特開平10-163535号には、高輝度でコンパクトな白色の発光色を得るために、青色または青紫色の発光色を有する半導体発光素子と、この半導体発光素子からの光を吸収して可視領域の光を発光する1種または2種類以上の蛍光体とを組み合わせ、半導体発光装置が開示されている。上記半導体発光素子の発光色と蛍光体の発光色とが互いに補色の関係になって、この半導体発光素子の発光色と蛍光体の発光色とが加色されて白色に発光するように、上記蛍光体を選択し

ている。

【0006】また、特開平10-12925号には、紫外光および近紫外光を出射する半導体発光素子と、この半導体発光素子からの光によって蛍光を発する蛍光体とを備える半導体発光装置が開示されている。上記半導体発光素子は、通常は青色の光を発する半導体発光素子であり、パルス状の大電流を流すことによって、紫外光および近紫外光を出射させている。上記蛍光体の種類を変えるのみによって、単一種類の半導体発光素子を用いて複数の発光色を得ることが開示されている。

【0007】また、特開平9-153644号には、3族窒素化合物半導体を用いて形成されてピーク波長が380nmの紫外線を発光する発光層と、この発光層からの紫外線を受光して、赤、青、緑の3原色を各々発光する3種類の蛍光体層とを備えたドットマトリックスタイプの表示装置が開示されている。

【0008】

【発明が解決しようとする課題】しかしながら、上記従来の技術は、以下のような問題点がある。

【0009】長波長可視光半導体発光装置に用いられて赤から緑色の発光色を有する半導体発光素子や、青から紫色の短波長可視光を発光する半導体発光素子は、発光する波長に応じて使用される材料や素子形状が異なるので、互いに異なる波長の半導体素子を実装して半導体発光装置を得ようとする、互いに異なる複数の実装材料や実装工程が必要となって、製造工程が煩雑となると共にコストアップの要因になるという問題がある。

【0010】さらに、上記発光色が互いに異なる複数の半導体発光素子を用いて色彩が良好な白色光を得るためには、上記複数の半導体発光素子への電流を各々調整する必要がある半導体発光装置が複雑になるという問題がある。また、上記半導体発光装置を複数個用いて発光表示装置を形成すると、大量の半導体発光素子の色調の調整が必要になって製造工程が煩雑になるという問題点がある。

【0011】また、上記特許第2927279号や特開平10-163535号に開示されている半導体発光装置は、半導体発光素子の出射光と、この出射光と補色の関係にある蛍光体の発光光とを混色して白色の発光色を得るので、光の利用効率が悪く、また、色調も良くないという問題点があった。例えば、半導体発光素子の青色の出射光と蛍光体の黄色の出射光との混色によって白色光を得る半導体発光装置を、液晶表示装置のバックライトとして利用すると、この白色光は純緑および純赤色の光量が少ないので、上記液晶表示装置が備える赤色カラーフィルタを透過する光の量が少ないから、上記液晶表示装置がフルカラー表示をすると、色抜けしたような印象を与えるという問題点がある。

【0012】また、特開平10-12925号に開示されている半導体発光装置は、半導体発光素子にパルス状

の大電流を印加するので、半導体発光素子が破壊したり発熱して劣化して、寿命が短くて信頼性が低いという問題点がある。また、上記半導体発光素子は、紫外及び近紫外の波長に発光波長のピークを有すると共に、青色の波長にも発光波長のピークを有するので、この青色光が蛍光の発光光と混色して色調が悪いという問題点がある。さらに、半導体発光装置が劣化した場合には、複数の異なる発光色を有する半導体発光素子が、輝度が一律に劣化するのではなくて、青色の波長成分が特に急激に低下するので、半導体発光装置の色調が変化してしまうという問題点がある。さらに、上記半導体発光素子は、近紫外（390 nm）付近から短波長側の紫外領域の波長の光を出射するので、人体への影響を防止する施策が必要である。また、上記半導体発光素子の固定用およびモールド用の樹脂も、上記紫外領域の波長の光によって悪影響を受けるので、上記固定用樹脂の変質による信頼性の低下や、上記モールド用樹脂の黒化による発光輝度の低下を招く虞があるという問題点がある。

【0013】特開平9-153644号に開示された半導体発光装置もまた、380 nmという紫外領域の発光波長を利用しているため、人体への影響を防止するために紫外領域の光の漏洩防止を施策する必要があると共に、半導体発光素子の固定用およびモールド用の樹脂が悪影響を受けて、信頼性の低下や発光輝度の低下の原因になるという問題点がある。さらに、この半導体発光装置は、基板上に、赤、青、緑の3原色を発光する蛍光体層を半導体層と共に形成するので、半導体発光装置の製造工程が煩雑で歩留りや信頼性が低下するという問題点がある。

【0014】本発明は、上記の課題を解決するためになされたものであって、複数の発光波長の光を出射できるにも拘らず製造が容易で安価であり、色調が良好で、人体への影響が少なく、劣化が殆ど無い半導体発光装置と、それを用いた発光表示装置を提供することを目的とする。

【0015】

【課題を解決するための手段】上記目的を達成するため、本発明の半導体発光装置は、基体上に半導体発光素子を搭載してなる半導体発光装置において、上記半導体発光素子は、発光波長が390 nm乃至420 nmの出射光を有し、上記半導体発光素子からの出射光により励起されて、発光波長が600 nm乃至670 nmの波長領域に主発光ピークを有する赤色の光を出射する蛍光体を備えることを特徴としている。

【0016】本発明によれば、上記半導体発光装置において、上記半導体発光素子は人間の視感度が非常に低い短波長領域の出射光を有する上に、上記蛍光体は、発光波長が赤色の波長領域に主発光ピークを有して単色の赤色の光を出射するので、もし、上記蛍光体が出射する光と上記半導体発光素子からの直接の出射光とが混じって

も、人間の視感度を考慮すると、見かけ上、上記蛍光体の出射光の色調が殆ど変化することがない。つまり、上記蛍光体からの光が、上記半導体発光素子からの直接光の影響を受けることなく半導体発光装置から出射されるのである。したがって、色調が良好な単色赤色発光の半導体発光装置が得られる。

【0017】また、上記半導体発光装置において、上記半導体発光素子は発光波長が390 nm乃至420 nmの出射光を有するので、例えば封止樹脂などの半導体発光装置の構成部品を損傷し難く、また、人体に有害な作用が殆ど無い。もし、半導体発光素子の発光波長が390 nmよりも短いと、例えば上記封止樹脂を損傷して不透明化や黒化などの不都合を生じさせる場合がある。一方、上記半導体発光素子の発光波長が420 nmよりも長いと、この半導体発光素子からの出射光は、可視領域の発光波長を有するようになるから、上記蛍光体からの出射光と混色して、半導体発光装置の発光色の色調が変化してしまう。したがって、上記半導体発光素子の発光波長を390 nm乃至420 nmにすることによって、半導体発光装置の構成部品の劣化を少なくでき、また、人体に悪影響が殆どなく、しかも、色調が良好な半導体発光装置が得られる。

【0018】1実施形態の半導体発光装置は、上記蛍光体は、

$M_2O_2S : Eu$ （但し、MはLa, Gd, Yから選ばれ
るいずれか一つまたは2以上の元素）、

$0.5MgF_2 \cdot 3.5MgO \cdot GeO_2 : Mn$ 、

$Y_2O_3 : Eu$ 、

$Y(P, V)O_4 : Eu$ 、

$YVO_4 : Eu$ 、で表される蛍光体の群のうち、いずれ
か一つまたは2以上からなる。

【0019】上記実施形態によれば、発光波長が390 nm乃至420 nmのいずれの出射光を有する半導体発光素子を用いても、上記半導体発光素子からの出射光の波長に応じて上記蛍光体を選択できるので、発光波長が赤色の波長領域に良好な発光ピークを有する単色赤色発光の半導体発光装置が得られる。また、複数の蛍光体を組み合わせることによって、半導体発光素子からの出射光の波長領域の略全ての波長を赤色の波長に変換できるので、高効率な単色赤色発光の半導体発光装置が得られる。

【0020】本発明の半導体発光装置は、基体上に半導体発光素子を搭載してなる半導体発光装置において、上記半導体発光素子は、発光波長が390 nm乃至420 nmの出射光を有し、上記半導体発光素子からの出射光により励起されて、発光波長が500 nm乃至540 nmの波長領域に主発光ピークを有する緑色の光を出射する蛍光体を備えることを特徴としている。

【0021】本発明によれば、上記半導体発光装置において、上記半導体発光素子は人間の視感度が非常に低い短波長領域の出射光を有する上に、上記蛍光体は、発光

波長が緑色の波長領域に主発光ピークを有して単色の緑色の光を出射するので、もし、上記蛍光体が出射する光と上記半導体発光素子からの直接の出射光とが混じっても、人間の視感度を考慮すると、見かけ上、上記蛍光体の出射光の色調が殆ど変化することがない。つまり、上記蛍光体からの光が、上記半導体発光素子からの直接光の影響を受けることなく半導体発光装置から出射されるのである。したがって、色調が良好な単色緑色発光の半導体発光装置が得られる。

【0022】また、上記半導体発光装置において、上記半導体発光素子は発光波長が390nm乃至420nmの出射光を有するので、例えば封止樹脂などの半導体発光装置の構成部品を損傷し難く、また、人体に有害な作用が殆ど無い。もし、半導体発光素子の発光波長が390nmよりも短いと、例えば上記封止樹脂を損傷して不透明化や黒化などの不都合を生じさせる場合がある。一方、上記半導体発光素子の発光波長が420nmよりも長いと、この半導体発光素子からの出射光は、可視領域の発光波長を有するようになるから、上記蛍光体からの出射光と混色して、半導体発光装置の発光色の色調が変化してしまう。したがって、上記半導体発光素子の発光波長を390nm乃至420nmにすることによって、半導体発光装置の構成部品の劣化を少なくでき、また、人体に悪影響が殆どなく、しかも、色調が良好な半導体発光装置が得られる。

【0023】1実施形態の半導体発光装置は、上記蛍光体は、

$\text{RMg}_2\text{Al}_{16}\text{O}_{27} : \text{Eu, Mn}$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$\text{RMgAl}_{10}\text{O}_{17} : \text{Eu, Mn}$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$\text{ZnS} : \text{Cu}$ 、

$\text{SrAl}_2\text{O}_4 : \text{Eu}$ 、

$\text{SrAl}_2\text{O}_4 : \text{Eu, Dy}$ 、

$\text{ZnO} : \text{Zn}$ 、

$\text{Zn}_2\text{Ge}_2\text{O}_4 : \text{Mn}$ 、

$\text{Zn}_2\text{SiO}_4 : \text{Mn}$ 、

$\text{Q}_3\text{MgSi}_2\text{O}_8 : \text{Eu, Mn}$ (但し、QはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、で表される蛍光体の群のうち、いずれか一つまたは2以上からなる。

【0024】上記実施形態によれば、上記半導体発光素子の発光波長に応じて最適な蛍光体を選択できるので、発光波長が緑色の波長領域に良好な発光ピークを有する単色緑色発光の半導体発光装置が得られる。また、複数の蛍光体を組合わせることによって、半導体発光素子からの出射光の波長領域の略全ての波長を緑色の波長に変換できるので、高効率の単色緑色発光の半導体発光装置が得られる。

【0025】本発明の半導体発光装置は、基体上に半導

体発光素子を搭載してなる半導体発光装置において、上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、上記半導体発光素子からの出射光により励起されて、発光波長が410nm乃至480nmの波長領域に主発光ピークを有する青色の光を出射する蛍光体を備えることを特徴としている。

【0026】本発明によれば、上記半導体発光装置において、上記半導体発光素子は人間の視感度が非常に低い短波長領域の出射光を有する上に、上記蛍光体は、発光波長が青色の波長領域に主発光ピークを有して単色の青色の光を出射するので、もし、上記蛍光体が出射する光と上記半導体発光素子からの直接の出射光とが混じっても、人間の視感度を考慮すると、見かけ上、上記蛍光体の出射光の色調が殆ど変化することがない。つまり、上記蛍光体からの光が、上記半導体発光素子からの直接光の影響を受けることなく半導体発光装置から出射されるのである。したがって、色調が良好な単色青色発光の半導体発光装置が得られる。

【0027】また、上記半導体発光装置において、上記半導体発光素子は発光波長が390nm乃至420nmの出射光を有するので、例えば封止樹脂などの半導体発光装置の構成部品を損傷し難く、また、人体に有害な作用が殆ど無い。もし、半導体発光素子の発光波長が390nmよりも短いと、例えば上記封止樹脂を損傷して不透明化や黒化などの不都合を生じさせる場合がある。一方、上記半導体発光素子の発光波長が420nmよりも長いと、この半導体発光素子からの出射光は、可視領域の発光波長を有するようになるから、上記蛍光体からの出射光と混色して、半導体発光装置の発光色の色調が変化してしまう。したがって、上記半導体発光素子の発光波長を390nm乃至420nmにすることによって、半導体発光装置の構成部品の劣化を少なくでき、また、人体に悪影響が殆どなく、しかも、色調が良好な半導体発光装置が得られる。

【0028】1実施形態の半導体発光装置は、上記蛍光体は、

$\text{A}_{10}(\text{PO}_4)_6\text{Cl}_2 : \text{Eu}$ (但し、AはSr, Ca, Ba, Mg, Ceから選ばれるいずれか一つまたは2以上の元素)、

$\text{XMg}_2\text{Al}_{16}\text{O}_{27} : \text{Eu}$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$\text{XMgAl}_{10}\text{O}_{17} : \text{Eu}$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$\text{ZnS} : \text{Ag}$ 、

$\text{Sr}_{10}(\text{PO}_4)_6\text{Cl}_2 : \text{Eu}$ 、

$\text{Ca}_{10}(\text{PO}_4)_6\text{F}_2 : \text{Sb}$ 、

$\text{Z}_3\text{MgSi}_2\text{O}_8 : \text{Eu}$ (但し、ZはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、

$\text{SrMgSi}_2\text{O}_8 : \text{Eu}$ 、

$\text{Sr}_2\text{P}_2\text{O}_7 : \text{Eu}$ 、

$\text{CaAl}_2\text{O}_4 : \text{Eu}, \text{Nd}$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなる。

【0029】上記実施形態によれば、半導体発光素子の発光波長に応じて最適な蛍光体を選択できるので、発光波長が青色の波長領域に良好な発光ピークを有する単色青色発光の半導体発光装置が得られる。また、複数の蛍光体を組合わせることによって、上記半導体発光素子の出射光の波長領域の略全ての波長を青色の波長に変換できるので、高効率な単色青色発光の半導体発光装置が得られる。

【0030】本発明の半導体発光装置は、基体上に半導体発光素子を搭載してなる半導体発光装置において、上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、上記半導体発光素子からの出射光により励起されて、発光波長が480nm乃至500nmの波長領域に主発光ピークを有する青緑色の光を出射する蛍光体を備えることを特徴としている。

【0031】本発明によれば、上記半導体発光装置において、上記半導体発光素子は人間の視感度が非常に低い短波長領域の出射光を有する上に、上記蛍光体は、発光波長が青緑色の波長領域に主発光ピークを有して単色の青緑色の光を出射するので、もし、上記蛍光体が出射する光と上記半導体発光素子からの直接の出射光とが混じっても、人間の視感度を考慮すると、見かけ上、上記蛍光体の出射光の色調が殆ど変化することがない。つまり、上記蛍光体からの光が、上記半導体発光素子からの直接光の影響を受けることなく半導体発光装置から出射されるのである。したがって、色調が良好な単色青緑色発光の半導体発光装置が得られる。

【0032】また、上記半導体発光装置において、上記半導体発光素子は発光波長が390nm乃至420nmの出射光を有するので、例えば封止樹脂などの半導体発光装置の構成部品を損傷し難く、また、人体に有害な作用が殆ど無い。もし、半導体発光素子の発光波長が390nmよりも短いと、例えば上記封止樹脂を損傷して不透明化や黒化などの不都合を生じさせる場合がある。一方、上記半導体発光素子の発光波長が420nmよりも長いと、この半導体発光素子からの出射光は、可視領域の発光波長を有するようになるから、上記蛍光体からの出射光と混色して、半導体発光装置の発光色の色調が変化してしまう。したがって、上記半導体発光素子の発光波長を390nm乃至420nmにすることによって、半導体発光装置の構成部品の劣化を少なくでき、また、人体に悪影響が殆どなく、しかも、色調が良好な半導体発光装置が得られる。

【0033】1実施形態の半導体発光装置は、上記蛍光体は、

$\text{Sr}_4\text{Al}_{14}\text{O}_{25} : \text{Eu}$ 、

$\text{Sr}_4\text{Al}_{14}\text{O}_{25} : \text{Eu}, \text{Dy}$ 、

$\text{Li}_6(\text{PO}_4)_3\text{Cl}_2 : \text{Eu}$ (但し、LはBa, Ca,

Mgから選ばれるいずれか一つまたは2以上の元素)、 $\text{Sr}_2\text{Si}_3\text{O}_8 \cdot 2\text{SrCl}_2 : \text{Eu}$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなる。

【0034】上記実施形態によれば、上記半導体発光素子の発光波長に応じて最適な蛍光体を選択できるので、発光波長が青緑色の波長領域に良好な発光ピークを有する単色青緑色発光の半導体発光装置が得られる。また、複数の蛍光体を組合わせることによって、上記半導体発光素子が出射する光の波長領域の略全ての波長を青緑色の波長に変換できるので、高効率な単色青緑色発光の半導体発光装置が得られる。

【0035】本発明の半導体発光装置は、基体上に半導体発光素子を搭載してなる半導体発光装置において、上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、上記半導体発光素子からの出射光により励起されて、発光波長が570nm乃至600nmの波長領域に主発光ピークを有する橙色の光を出射する蛍光体を備えることを特徴としている。

【0036】本発明によれば、上記半導体発光装置において、上記半導体発光素子は人間の視感度が非常に低い短波長領域の出射光を有する上に、上記蛍光体は、発光波長が橙色の波長領域に主発光ピークを有して単色の橙色の光を出射するので、もし、上記蛍光体が出射する光と上記半導体発光素子からの直接の出射光とが混じっても、人間の視感度を考慮すると、見かけ上、上記蛍光体の出射光の色調が殆ど変化することがない。つまり、上記蛍光体からの光が、上記半導体発光素子からの直接光の影響を受けることなく半導体発光装置から出射されるのである。したがって、色調が良好な単色橙色発光の半導体発光装置が得られる。

【0037】また、上記半導体発光装置において、上記半導体発光素子は発光波長が390nm乃至420nmの出射光を有するので、例えば封止樹脂などの半導体発光装置の構成部品を損傷し難く、また、人体に有害な作用が殆ど無い。もし、半導体発光素子の発光波長が390nmよりも短いと、例えば上記封止樹脂を損傷して不透明化や黒化などの不都合を生じさせる場合がある。一方、上記半導体発光素子の発光波長が420nmよりも長いと、この半導体発光素子からの出射光は、可視領域の発光波長を有するようになるから、上記蛍光体からの出射光と混色して、半導体発光装置の発光色の色調が変化してしまう。したがって、上記半導体発光素子の発光波長を390nm乃至420nmにすることによって、半導体発光装置の構成部品の劣化を少なくでき、また、人体に悪影響が殆どなく、しかも、色調が良好な半導体発光装置が得られる。

【0038】1実施形態の半導体発光装置は、上記蛍光体は、

$\text{ZnS} : \text{Mn}$ 、

$\text{ZnS} : \text{Cu}, \text{Mn}, \text{Co}$ 、で表される蛍光体の群のう

ち、いずれか一つまたは2以上からなる。

【0039】上記実施形態によれば、半導体発光素子の波長領域に応じて最適な蛍光体を選択できるので、発光波長が橙色の発光波長領域に主発光ピークを有する単色橙色発光の半導体発光装置を得ることができる。

【0040】1実施形態の半導体発光装置は、上記基体の少なくとも一部と、上記半導体発光素子とを封止する封止樹脂を備え、上記封止樹脂が上記蛍光体を含んでいる。

【0041】上記実施形態によれば、上記半導体発光素子を封止する封止樹脂が蛍光体を含んでいるので、半導体発光素子からの出射光は必ず波長変換されるから、半導体発光素子の光の利用効率がよい。また、封止樹脂を形成すると共に蛍光体を配置できるので、蛍光体を別個に配置する工程が不要であるから、半導体発光装置の製造が容易になる。

【0042】また、この半導体発光装置は、発光波長が一定の波長領域を有する半導体発光素子と、所定の蛍光体とを組み合わせることによって、半導体発光素子および半導体発光装置の構造を変えることなく、所望の発光波長を有する半導体装置が得られる。すなわち、同一の製造工程で、蛍光体を変えることのみで、所望の発光波長を有する半導体発光装置が得られるので、半導体発光装置の製造コストを大幅に削減できる。

【0043】1実施形態の半導体発光装置は、上記基体は、カップ形状のマウント部を有するリードフレームであり、上記半導体発光素子は、上記リードフレームのカップ形状のマウント部の底に配置されており、かつ、もう一つのリードフレームにワイヤーボンディングによって電気的に接続されていて、上記2つのリードフレームの少なくとも一部と上記半導体発光素子とが上記封止樹脂で封止されている。

【0044】上記実施形態によれば、上記蛍光体を含む封止樹脂によって、上記カップ形状のマウント部によって集められた上記半導体発光素子からの出射光が、確実に波長変換されるので、指向性が良く、かつ、発光効率が良くて色調の良い半導体発光装置が得られる。

【0045】1実施形態の半導体発光装置は、上記基体は、一対のリードフレームの先端に連結された絶縁体であり、上記半導体発光素子は上記絶縁体に形成された金属配線に接続されていて、上記一対のリードフレームの少なくとも一部と、上記絶縁体と、上記半導体発光素子とが上記封止樹脂で封止されている。

【0046】上記実施形態によれば、上記半導体発光素子を、例えば金属バンプ等によって上記基板の金属配線に直接接続するので、半導体発光素子とリードフレームとを金属ワイヤー等で接続する手間が省かれる。また、上記封止樹脂に含まれる蛍光体によって、半導体発光素子からの出射光が確実に波長変換される。したがって、製造効率が良好で、しかも発光効率が良くて色調のよい

半導体発光装置が得られる。

【0047】1実施形態の半導体発光装置は、上記基体は、カップ形状のマウント部を有するリードフレームであり、上記半導体発光素子は、上記リードフレームのカップ形状のマウント部の底に配置されており、かつ、もう一つのリードフレームにワイヤーボンディングによって電気的に接続されていて、上記カップ形状のマウント部に上記蛍光体が充填されていると共に、上記2つのリードフレームの少なくとも一部と、上記半導体発光素子と、上記蛍光体とが封止樹脂で封止されている。

【0048】上記実施形態によれば、上記半導体発光素子からの光が集まるカップ形状のマウント部に蛍光体を充填するので、半導体発光素子からの光は確実に波長変換されて、光の利用効率が向上する。また、半導体発光素子からの光を集めない半導体発光装置と比較して、蛍光体を配置する領域が小さいので、上記蛍光体の使用量を少なくできる。

【0049】1実施形態の半導体発光装置は、上記基体は、カップ形状のマウント部を有するリードフレームであり、上記半導体発光素子は、上記リードフレームのカップ形状のマウント部の底に配置されており、かつ、もう一つのリードフレームにワイヤーボンディングによって電気的に接続されていて、上記カップ形状のマウント部にコーティング部材を充填して、上記コーティング部材の上に上記蛍光体が配置されていると共に、上記2つのリードフレームの少なくとも一部と、上記半導体発光素子と、上記コーティング部材と、上記蛍光体とが封止樹脂で封止されている。

【0050】上記実施形態によれば、上記蛍光体を、上記マウント部に充填されたコーティング部材の上に配置するので、上記マウント部内の全てに蛍光体を充填する場合に比べて、上記蛍光体の使用量が削減される。また、上記コーティング部材によって、上記半導体発光素子の発光部と蛍光体との間の距離が略均一になるので、色むらの無い均一発光の半導体発光装置が得られる。さらに、上記コーティング部材によって、上記半導体発光素子と蛍光体とが離間されるので、半導体発光素子による蛍光体の電気的および熱的劣化が殆どない。

【0051】1実施形態の半導体発光装置は、上記基体は、金属配線が施された基板であり、上記半導体発光素子は、上記基板の金属配線に電気的に接続されていて、上記半導体発光素子を封止する封止樹脂を備え、上記封止樹脂は上記蛍光体を含んでいる。

【0052】上記実施形態によれば、上記半導体発光素子は上記基板に、同一形状または単一種類の半導体発光素子を、例えばAuやAl、Cu等の金属ワイヤーを用いて金属配線に接続したり、あるいは、金属ワイヤー等を用いることなく金属バンプ等によって直接接続される。したがって、従来におけるように、発光色に対応して異なる形状の半導体発光素子を用いて異なる形状の半

導体発光装置を製造するよりも、半導体発光装置の製造過程が容易である。この半導体発光装置において、所望の波長に対応する所定の蛍光体を配置するのみによって、所望の発光波長を有する半導体発光装置が得られるので、従来に比べて半導体発光装置の製造が簡単、かつ、低コストになる。

【0053】1実施形態の半導体発光装置は、上記基板は、金属配線が施された基板であり、上記半導体発光素子は、上記基板の金属配線に電気的に接続されると共に凹部内に配置されており、上記蛍光体は上記凹部内に充填されている。

【0054】上記実施形態によれば、上記基板の凹部に上記蛍光体を充填するので、この蛍光体の使用量が少量になって、製造コストが安価で発光効率が良く、しかも、単色発光で色調が良い半導体発光装置が得られる。

【0055】1実施形態の半導体発光装置は、上記凹部は、上記基板に配置された枠によって形成されている。

【0056】上記実施形態によれば、上記基板に枠を配置して上記凹部を形成するので、基板を例えば切削して凹部を形成する加工の手間が削減される。また、上記枠を、例えば上記半導体発光素子側の側面の形状を、上記半導体発光素子からの出射光を集光する形状に加工することによって、上記出射光の波長の変換効率がさらに向上すると共に半導体発光装置の指向性が向上する。その結果、発光効率が良く、しかも単色発光で色調が良い半導体発光装置が得られる。

【0057】1実施形態の半導体発光装置は、上記基板は、金属配線が施された基板であり、上記半導体発光素子は、上記基板の金属配線に電気的に接続されていると共に凹部内に配置されており、上記凹部に封止樹脂を充填すると共に、上記封止樹脂の上に上記蛍光体が配置されている。

【0058】上記実施形態によれば、上記蛍光体を上記封止樹脂の上に配置するので、上記基板の凹部の内側に蛍光体を充填するよりも、さらに少量の蛍光体の使用量で、所望の発光波長を有する半導体発光装置が得られる。また、上記封止樹脂によって、半導体発光素子の発光部と蛍光体との間の距離が略均一になるので、色むらが殆ど無い均一発光の半導体発光装置が得られる。また、上記封止樹脂は、上位半導体発光素子と蛍光体とを離間させるので、上記蛍光体に対する半導体発光素子の電気的および熱的影響を低減できて、半導体発光装置の性能が安定する。

【0059】1実施形態の半導体発光装置は、上記基板は、金属配線が施された基板であり、上記半導体発光素子は、上記基板の金属配線と電気的に接続されており、上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、上記蛍光体が上記封止樹脂に含まれている。

【0060】上記実施形態によれば、上記半導体発光素子は上記基板に、同一形状または単一種類の半導体発光素子を、例えばAuやAl、Cu等の金属ワイヤーを用いて金属配線上に接続したり、あるいは、金属ワイヤー等を用いることなく金属バンプ等によって直接接続される。したがって、従来におけるように、発光色に対応して異なる形状の半導体発光素子を用いて異なる形状の半導体発光装置を製造するよりも、半導体発光装置の製造過程が容易である。この半導体発光装置において、所望の波長に対応する所定の蛍光体を配置するのみによって、所望の発光波長を有する半導体発光装置が得られるので、従来に比べて半導体発光装置の製造が簡単、かつ、低コストになる。

【0061】1実施形態の半導体発光装置は、上記基板は、金属配線が施された基板であり、上記半導体発光素子は、上記基板の上記金属配線と電気的に接続されており、上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、上記半導体発光素子から半導体発光装置の外部に直接出射する光を遮る遮蔽体を備え、上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、上記蛍光体の層が、上記反射体において光が反射する面に設けられている。

【0062】上記実施形態によれば、上記蛍光体の層は上記反射体において光が反射する面に設けられているので、この反射体で反射される光は確実に波長変換される。そして、上記半導体発光素子からの出射光は、上記遮蔽体によって半導体発光装置の外部に漏れることなく上記反射面で反射されて半導体発光装置外部に出射するので、殆ど全てが波長変換された光である。したがって、この半導体発光装置は、反射面のみに設けられて少ない蛍光体の使用量で、効率良く所望の発光色が得られる。さらに、上記蛍光体の層は、半導体発光素子から所定の距離をなす反射体の反射面に形成されるので、半導体発光素子の発光部と蛍光体との間の距離が略均一になって、色むらの無い均一発光の半導体発光装置が得られる。さらに、半導体発光素子と蛍光体とが離間されるので、蛍光体に対する半導体発光素子の電気的および熱的影響が緩和されて、半導体発光装置の性能が安定する。

【0063】1実施形態の半導体発光装置は、上記基板は、金属配線が施された基板であり、上記半導体発光素子は、上記基板の上記金属配線と電気的に接続されており、少なくとも上記半導体発光素子の発光部分が上記基板の凹部内に配置されており、上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、上記蛍光体の層が、上記反射体において光が反射する面に設けられている。

【0064】上記実施形態によれば、半導体発光素子は上記凹部内に配置されているので、半導体発光素子から

の光は半導体発光装置の外部へ直接出射されずに、必ず上記反射体で反射されて波長変換されてから半導体発光装置の外部に出射される。したがって、この半導体発光装置は、出射光の色調が良好になる。

【0065】1実施形態の半導体発光装置は、上記基体は、金属配線が施された基板であり、上記半導体発光素子は、上記基板の上記金属配線と電気的に接続されており、上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、上記蛍光体の層が、上記封止樹脂の光が出射する面に設けられている。

【0066】上記実施形態によれば、上記封止樹脂の光が出射する面に設けられた蛍光体の層によって、半導体発光素子からの出射光が、半導体発光装置から出射される直前に波長変換される。すなわち、この半導体発光装置からの光は全て波長変換されているので、良好な光の利用効率の半導体発光装置になる。また、上記蛍光体の層は、半導体発光素子から所定の距離をおいた位置にあるので、半導体発光素子の発光部と蛍光体との間の距離が略均一になって、色むらの無い均一発光の半導体発光装置が得られる。さらに、半導体発光素子と蛍光体とが離間されるので、蛍光体に対する半導体発光素子の電気的および熱的影響が緩和されて、半導体発光装置の性能が安定する。

【0067】本発明の半導体発光装置は、基体上に半導体発光素子を搭載してなる半導体発光装置において、上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有し、第1の蛍光体と、第2の蛍光体と、第3の蛍光体とを備え、上記第1の蛍光体は、発光波長が600nm乃至670nmの波長領域に主発光ピークを有する赤色の出射光を有し、上記第2の蛍光体は、発光波長が500nm乃至540nmの波長領域に主発光ピークを有する緑色の出射光を有し、上記第3の蛍光体は、発光波長が410nm乃至480nmの波長領域に主発光ピークを有する青色の出射光を有して、上記第1、第2、第3の蛍光体からの出射光の色の和が、白色系であることを特徴としている。

【0068】上記構成によれば、上記半導体発光素子は人間の視感度が非常に低い短波長領域を有する上に、上記第1乃至第3の蛍光体が出射する光は、赤色、緑色、青色波長領域に各々発光波長の主ピークを有する単色の光であるので、もし、上記第1乃至第3の蛍光体からの出射光と上記半導体発光素子からの直接の出射光とが混じっても、人間の視感度を考慮すると、見かけ上、半導体発光装置の出射光の色調は殆ど変化しない。つまり、上記第1乃至第3のいずれの蛍光体からの光も、上記半導体発光素子からの直接光の影響を受けることが無い。したがって、色調が良好な白色系の発光色を有する半導体発光装置が得られる。また、半導体発光装置の出射光

に関して、半導体発光素子から半導体発光装置外部に直接出射される光は、人間の可視領域において、蛍光体からの光と混色されていないから、半導体発光装置の長時間の使用の後に、経年変化によって半導体発光素子の発光性能が低下しても、半導体発光装置の輝度が低下するのみであって、色調が変化することがない。したがって、上記半導体発光装置は、色調が良好な白色系の光が安定して得られる。

【0069】また、上記半導体発光装置において、上記半導体発光素子は発光波長が390nm乃至420nmの出射光を有するので、例えば封止樹脂などの半導体発光装置の構成部品を損傷し難く、また、人体に有害な作用が殆ど無い。もし、半導体発光素子の発光波長が390nmよりも短いと、例えば上記封止樹脂を損傷して不透明化や黒化などの不都合を生じさせる場合がある。したがって、上記半導体発光素子の発光波長を390nm乃至420nmにすることによって、半導体発光装置の構成部品の劣化を少なくでき、また、人体に悪影響が殆どなく、しかも、色調が良好な半導体発光装置が得られる。

【0070】1実施形態の半導体発光装置は、上記第1の蛍光体は、

$M_2O_2S : Eu$ (但し、MはLa, Gd, Yから選ばれるいずれか一つまたは2以上の元素)、

$0.5MgF_2 \cdot 3.5MgO \cdot GeO_2 : Mn$ 、
 $Y_2O_3 : Eu$ 、

$Y(P, V)O_4 : Eu$ 、

$YVO_4 : Eu$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなり、上記第2の蛍光体は、

$RMg_2Al_{16}O_{27} : Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$RMgAl_{10}O_{17} : Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$ZnS : Cu$ 、

$SrAl_2O_4 : Eu$ 、

$SrAl_2O_4 : Eu, Dy$ 、

$ZnO : Zn$ 、

$Zn_2Ge_2O_4 : Mn$ 、

$Zn_2SiO_4 : Mn$ 、

$Q_3MgSi_2O_8 : Eu, Mn$ (但し、QはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、

で表される蛍光体の群のうち、いずれか一つまたは2以上からなり、上記第3の蛍光体は、

$A_{10}(PO_4)_6Cl_2 : Eu$ (但し、AはSr, Ca, Ba, Mg, Ceから選ばれるいずれか一つまたは2以上の元素)、

$XMg_2Al_{16}O_{27} : Eu$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、

$XMgAl_{10}O_{17} : Eu$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、

ZnS:Ag、
 Sr₁₀(PO₄)₆Cl₂:Eu、
 Ca₁₀(PO₄)₆F₂:Sb、
 Z₃MgSi₂O₈:Eu (但し、ZはSr, Ba, Ca
 から選ばれるいずれか一つまたは2以上の元素)、
 SrMgSi₂O₈:Eu、
 Sr₂P₂O₇:Eu、
 CaAl₂O₄:Eu, Nd、で表される蛍光体の群の
 うち、いずれか一つまたは2以上からなる。

【0071】上記実施形態によれば、発光波長が390
 nm乃至420nmのうちのいずれの発光波長を有する
 半導体発光素子を用いても、この半導体発光素子の発光
 波長に対応して上記複数の蛍光体から適切な蛍光体を選
 択することによって、単色の赤色、および、緑色、およ
 び、青色の発光光が各々得られる。これによって、赤
 色、緑色、青色の波長の光が各々適切に混色されて、良
 好な色調の白色系の発光色が得られる。また、複数の蛍
 光体を組合わせることによって、半導体発光素子が有す
 る波長領域の略全ての波長の光を、赤色、緑色、青色の
 波長に各々変換することができるので、半導体発光素子
 の出射光の利用効率が向上して、高効率な白色系発光の
 半導体発光装置が得られる。

【0072】1実施形態の半導体発光装置は、上記第
 1、第2、第3の蛍光体は、総量が100重量%である
 として、上記第1の蛍光体が50重量%以上70重量%
 以下、上記第2の蛍光体が7重量%以上20重量%以
 下、上記第3の蛍光体が20重量%以上30重量%以下
 である。

【0073】上記実施形態によれば、上記第1の蛍光体
 が50重量%以上70重量%以下、上記第2の蛍光体が
 7重量%以上20重量%以下、上記第3の蛍光体が20
 重量%以上30重量%以下であるので、上記第2の蛍光
 体が出射する緑色の光に比べて視感度が低い第1の蛍光
 体が出射する赤色、および第3の蛍光体が出射する青色
 の光の強度が強められる。したがって、人間の視感度が
 考慮されて、良好な色調の白色系発光の半導体発光装置
 が得られる。

【0074】ここにおいて、半導体発光装置の発光色
 は、第1の蛍光体の混合比率が50重量%より少ない
 と、緑色がかった色調の白色になる一方、上記第1の蛍
 光体の混合比率が70重量%より多いと、赤色がかった
 色調の白色になる。また、上記半導体発光装置の発光色
 は、第2の蛍光体の混合比率が7重量%より少ないと、
 赤色がかった色調の白色になり、上記第2の蛍光体の混
 合比率が20重量%より多いと、緑色がかった色調の白
 色になる。また、上記半導体発光装置の発光色は、第3
 の蛍光体の混合比率が20重量%より少ないと、赤色か
 かった色調の白色になり、上記第3の蛍光体の混合比率
 が30重量%より多いと、緑色がかった色調の白色にな
 る。

【0075】1実施形態の半導体発光装置は、上記封止
 樹脂は、上記第1、第2、第3の蛍光体を含んでおり、
 上記封止樹脂の重量に対する上記第1、第2、第3の蛍
 光体の総重量の比率が、0.5以上1以下である。

【0076】上記実施形態によれば、上記封止樹脂の重
 量に対する上記蛍光体の総重量の比率を、0.5以上1
 以下にすることによって、自然光に近い白色系の光を出
 射する半導体発光装置が得られる。なお、上記比率が1
 より大きくなると、半導体発光装置の出射光の輝度は明
 るくなると共に色調が青白くなる一方、上記比率が0.
 5より小さくなると、半導体発光装置の出射光の輝度が
 暗くなると共に色調が赤味を帯びてしまう。

【0077】1実施形態の発光表示装置は、上記半導体
 発光装置を用いた光源と、上記光源からの光を導く導光
 板と、上記導光板からの光を透過させて分光する赤、
 緑、青のカラーフィルタとを備え、上記半導体発光装置
 の出射光は、上記カラーフィルタの分光特性に適合した
 波長分布を有する。

【0078】上記実施形態によれば、上記半導体発光装
 置からの出射光は、上記赤、緑、青のカラーフィルタの
 分光特性に適合した波長分布を有するので、このカラー
 フィルタによって、発光波長が赤色の波長領域にピーク
 を有する光と、発光波長が緑色の波長領域にピークを有
 する光と、発光波長が青色の波長領域にピークを有する
 光とに、各々適切な強度を有して分光されるから、半導
 体発光装置の光の利用効率が良好で、しかも、高輝度な
 発光表示装置になる。

【0079】1実施形態の発光表示装置は、半導体発光
 装置の出射光の波長分布が上記カラーフィルタの分光特
 性に適合するように、上記半導体発光素子の発光波長
 と、上記第1の蛍光体の発光波長と、上記第2の蛍光体
 の発光波長と、上記第3の蛍光体の発光波長と、上記第
 1、第2、第3の蛍光体の混合比率と、上記封止樹脂の
 重量に対する上記第1、第2、第3の蛍光体の総重量の
 比率とのうちの少なくとも一つを調節している。

【0080】上記実施形態によれば、上記半導体発光装
 置からの出射光が上記カラーフィルタの分光特性に適合
 するように確実かつ効果的に調節されるので、上記発光
 表示装置からの出射光は、上記カラーフィルタによっ
 て、強度が比較的大きくて略単色の赤色と、緑色と、青
 色とに分光されるから、上記発光表示装置は、色抜けな
 どが無く高輝度かつ高コントラストのフルカラー表示
 になる。

【0081】1実施形態の発光表示装置は、上記発光表
 示装置は、液晶表示装置である。

【0082】上記実施形態によれば、色抜けが殆ど無
 く、高輝度かつ高コントラストの液晶表示装置が得られ
 る。

【0083】

【発明の実施形態】以下、本発明を図示の実施形態によ

り詳細に説明する。

【0084】図1(a), (b), (c)は、本発明の実施形態において用いられる半導体発光素子を示す断面図である。

【0085】図1(a)は、絶縁性の半導体材料からなる基板を有する半導体発光素子を示す断面図である。この半導体発光素子7aは、絶縁性のサファイア基板1a上に、N型窒化ガリウム系化合物半導体層2、P型窒化ガリウム系化合物半導体層3と、金属薄膜または透明導電膜からなるP型層用電極4とを順に積層している。上記N型窒化ガリウム系化合物半導体層2の図1(a)において右側に形成された露出面上にN型用パッド電極5が形成されていると共に、上記P型層用電極4表面上にP型用パッド電極6が形成されている。上記N型用パッド電極5およびP型用パッド電極6の間に電流を流すと、発光領域8aから発光する。

【0086】図1(b)は、導電性の半導体材料からなる基板を有する半導体発光素子を示す断面図である。この半導体発光素子7bは、導電性の窒化ガリウム半導体基板1b上に、N型窒化ガリウム系化合物半導体層2、P型窒化ガリウム系化合物半導体層3、金属薄膜または透明導電膜からなるP型層用電極4を順次積層して形成されている。上記半導体基板1bの下面にN型用パッド電極5が形成されていると共に、上記P型層用電極4の上面にP型用パッド電極6が形成されている。上記N型用パッド電極5とP型用パッド電極6との間に電流を流すと、発光領域8bから発光する。

【0087】図1(c)は、基板を透過させて光を取り出すタイプの半導体発光素子を示す断面図である。この半導体発光素子7cは、絶縁性のサファイア基板1a上(図1(c)においてはサファイア基板1aの下方)に、N型窒化ガリウム系化合物半導体層2、P型窒化ガリウム系化合物半導体層3、金属薄膜または透明導電膜からなるP型層用電極4を順次積層して、上記N型窒化ガリウム系化合物半導体層2の露出面上にN型用パッド電極5を形成すると共に、P型層用電極4の表面にP型用パッド電極6を形成している。そして、図1(c)に示すように、上記N型用パッド電極5およびP型用パッド電極6を、例えばAu等からなる金属バンプ16a, 16bによって、半導体発光素子7cの下方に配置した図示しないサブマウントの金属配線等に直接ボールボンディングする。上記N型用パッド電極5とP型用パッド電極6との間に電流を流すと、発光領域8から発光し、この発光光は上記サファイア基板1aを透過して図1(c)において上方に放射される。

【0088】なお、上記半導体発光素子7a, 7cの絶縁性サファイア基板1aは、ZnO, GaN, SiC, ZnSe等の他の材料を用いてもよい。また、上記半導体発光素子7bにおける導電性の窒化ガリウム半導体基

板1bは、SiC, ZnSe, Si等の他の材料を用いてもよい。この導電性の半導体基板1bを備えた半導体発光素子7bは、上記半導体基板1bの下面にも電極を形成して、半導体発光素子7bの上下両面に電極を形成できるので、絶縁体基板1aを有して片面に2つの電極を配置する半導体発光素子7a, 7bに較べて、同一のサイズで半導体層の発光領域を広く形成できると共にリードフレームや実装基板への実装が容易であるという利点がある。

10 【0089】上記半導体発光素子7a, 7b, 7cにおける半導体層の材料としては、窒化物系化合物半導体($\text{In}_x\text{Ga}_y\text{Al}_z\text{N}$ ($x+y+z=1$, $0\leq x\leq 1$, $0\leq y\leq 1$, $0\leq z\leq 1$))が好適に利用できるが、それ以外にSiCやZnSe等の半導体材料を用いてもよい。

【0090】上記半導体発光素子7a, 7b, 7cは、波長領域が390nmから420nmまでの光を発光する。この波長領域の光に対する人間の視感度は非常に低いため、この波長領域の光を他の波長の光に変換する蛍光体を用いると、この蛍光体によって変換された光の色のみが発光色として認識されて、良好な色調を有する半導体発光装置が得られる。半導体発光素子の波長が420nmよりも長いと、人間の目には可視光として認識され易くなり、蛍光体によって波長変換された光が半導体発光素子からの直接の出射光と混ざって、発光色の色調が悪くなってしまう。また、半導体発光素子の波長が390nmよりも短いと、この光は人体に有害な紫外線になると共に、半導体発光装置に使用されている樹脂部分に対して例えばモールド樹脂を黒化して輝度を低下させたり、樹脂を変質させて信頼性を低下させるといった悪影響を及ぼす。

【0091】次に、本発明の半導体発光装置に用いられる蛍光体に関して詳細に述べる。

【0092】下記の表1および表2は、発光波長のピークが410nmの窒化ガリウム系化合物半導体を発光素子として作成した半導体発光素子を用いて、各種蛍光体を励起して発光輝度を評価した結果を示した表である。また、上記蛍光体を励起して得られた発光のピーク波長(nm)も同時に示している。発光の輝度の評価は、赤色、緑色、青色、青緑色、橙色の各発光色において、蛍光体毎の発光輝度を比較して優劣を評価し、発光輝度が優秀なものには◎を、普通のものには○を、やや劣るものには△を、劣るものには×を付した。表1は、発光色が赤色および緑色の蛍光体についてのピーク波長および輝度の評価結果を示し、表2は、発光色が青色および青緑色、橙色の蛍光体についてのピーク波長および輝度の評価結果を示している。

【0093】

【表1】

発光色	蛍光体	発光ピーク 波長 (nm)	評価
赤色	$\text{La}_2\text{O}_2\text{S}:\text{Eu}$	623	◎
	$\text{Gd}_2\text{O}_2\text{S}:\text{Eu}$	625	○
	$\text{Y}_2\text{O}_2\text{S}:\text{Eu}$	626	△
	$0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2:\text{Mn}$	658	◎
	$\text{Y}_2\text{O}_3:\text{Eu}$	611	△
	$\text{Y}(\text{P}, \text{V})\text{O}_4:\text{Eu}$	618	△
	$\text{YVO}_4:\text{Eu}$	618	△
	$\text{CaS}:\text{Eu}$	655	○
	$\text{CaS}:\text{Eu}, \text{Tm}$	650	◎
	$\text{BaMg}_2\text{Al}_{10}\text{O}_{17}:\text{Eu}, \text{Mn}$	515	○
緑色	$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}, \text{Mn}$	512	○
	$\text{ZnS}:\text{Cu}$	527	△
	$\text{SrAl}_2\text{O}_4:\text{Eu}$	522	◎
	$\text{SrAl}_2\text{O}_4:\text{Eu}, \text{Dy}$	522	○
	$\text{ZnO}:\text{Zn}$	508	△
	$\text{Zn}_2\text{Ge}_2\text{O}_4:\text{Mn}$	537	○
	$\text{Zn}_2\text{SiO}_4:\text{Mn}$	525	○
	$\text{Ba}_3\text{MgSi}_2\text{O}_8:\text{Eu}, \text{Mn}$	512	○
	$\text{Sr}_3\text{MgSi}_2\text{O}_8:\text{Eu}, \text{Mn}$	532	○

【0094】

【表2】

発光色	蛍光体	発光ピーク波長 (nm)	評価
青色	$(\text{Sr}, \text{Ca}, \text{Ba}, \text{Ce})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	457	◎
	$\text{BaMg}_2\text{Al}_{16}\text{O}_{27}:\text{Eu}$	455	◎
	$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}$	452	○
	$\text{ZnS}:\text{Ag}$	450	△
	$\text{Sr}_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	447	○
	$\text{Ca}_{10}(\text{PO}_4)_6\text{F}_2:\text{Sb}$	480	△
	$\text{Sr}_3\text{MgSi}_4\text{O}_8:\text{Eu}$	462	○
	$\text{SrMgSi}_2\text{O}_6:\text{Eu}$	460	△
	$\text{SrAl}_{12}\text{O}_{19}:\text{Eu}$	400	×
	$\text{Sr}_2\text{P}_2\text{O}_7:\text{Eu}$	420	△
	$\text{CaAl}_2\text{O}_4:\text{Eu}, \text{Nd}$	440	△
	$\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}$	492	◎
	$\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}, \text{Dy}$	492	◎
青緑色	$(\text{Ba}, \text{Ca}, \text{Mg})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$	482	○
	$\text{Sr}_2\text{Si}_3\text{O}_8 \cdot 2\text{SrCl}_2:\text{Eu}$	490	△
	$\text{ZnS}:\text{Mn}$	586	○
橙色	$\text{ZnS}:\text{Cu}, \text{Mn}, \text{Co}$	580	○

表1から分かるように、高い輝度の赤色の発光色を得るためには、 $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ 、 $0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2:\text{Mn}$ 、 $\text{CaS}:\text{Eu}$ 、 Tm の蛍光体が好適であり、高い輝度の緑色の発光色を得るためには、 $\text{SrAl}_2\text{O}_4:\text{Eu}$ の蛍光体が好適である。また、表2から分かるように、高い輝度の青色の発光色を得るためには、 $(\text{Sr}, \text{Ca}, \text{Ba}, \text{Ce})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$ の蛍光体が好適であり、高い輝度の青緑色の発光色を得るためには、 $\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}$ 、 $\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}, \text{Dy}$ の蛍光体が好適である。

【0095】図2乃至7は、本発明の実施形態に用いられる主な蛍光体の発光スペクトル及び励起スペクトルを示した図である。いずれの図も、横軸は波長 (nm) であり、縦軸は相対強度 (%) である。

【0096】本発明に用いられる半導体発光素子の発光波長は、390nm乃至420nmである。より最適な発光波長範囲は、半導体発光素子の発光波長により励起される蛍光体の種類や、蛍光体の発光色により変わってくる。

【0097】例えば、図2(a)に示す蛍光体 $0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2:\text{Mn}$ によって、658nmに発光波長ピークを有する赤色の発光色を得ようとする場合、図2(b)から明らかなように、410nm乃至420nmの波長範囲に発光波長のピークを有する半導体発光素子によって上記蛍光体を励起するのが効果的である。

【0098】一方、図3(a)に示す蛍光体 $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ で、623nmに発光波長ピークを有する赤色の発光色を得ようとする場合、図3(b)から明らかなように、390nmの発光波長を有する半導体発光素子によって上記蛍光体を励起するのが効果的である。

【0099】本来、蛍光体 $0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2:\text{Mn}$ および $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ の励起波長のピークは390nmより短波長側にあるが、蛍光体を励起する半導体発光素子の発光波長が390nmより短いと、人体に有害な紫外線を放出することとなるので実用的ではなく、また、半導体発光装置に使用されている樹脂部分にも悪影響を与え、封止樹脂の黒化による輝度の低下や樹脂の変質による信頼性の低下の原因となる。

【0100】上記蛍光体以外にも、本発明の実施形態では、 $\text{Gd}_2\text{O}_2\text{S}:\text{Eu}$ 、 $\text{Y}_2\text{O}_2\text{S}:\text{Eu}$ 、 $\text{Y}_2\text{O}_3:\text{Eu}$ 、 $\text{Y}(\text{P}, \text{V})\text{O}_4:\text{Eu}$ 、 $\text{YVO}_4:\text{Eu}$ 等が利用可能である。また、これらの蛍光体を複数用いることで、より効果的に半導体発光素子の出射光を用いて、発光波長のピークが600nm乃至670nmの赤色の光に変換することができる。

【0101】また、図4(a)に示す蛍光体 $\text{BaMg}_2\text{Al}_{16}\text{O}_{27}:\text{Eu}, \text{Mn}$ で、515nmに発光波長ピークを有する緑色の発光色を得ようとする場合、図4

(b)から明らかなように、390nmの発光波長を有する半導体発光素子によって上記蛍光体を励起するのが

効果的である。

【0102】一方、図5(a)に示す蛍光体 $\text{SrAl}_2\text{O}_4:\text{Eu}$ で、522nmに発光波長ピークを有する緑色の発光色を得ようとする場合、図5(b)から明らかなように、390nm乃至420nmの波長範囲に発光波長のピークを有する半導体発光素子によって上記蛍光体を励起するのが効果的である。

【0103】本来、蛍光体 $\text{BaMg}_2\text{Al}_{16}\text{O}_{27}:\text{Eu}$ 、 Mn 及び $\text{SrAl}_2\text{O}_4:\text{Eu}$ の励起波長のピークは390nmより短波長側にあるが、蛍光体を励起する半導体発光素子の発光波長が390nmより短いと、人体に有害な紫外線を放出することとなるので実用的ではなく、また、半導体発光装置に使用されている樹脂部分にも悪影響を与え、封止樹脂の黒化による輝度の低下や樹脂の変質による信頼性の低下の原因となる。

【0104】上記蛍光体以外にも、本発明の実施形態では、 $\text{ZnS}:\text{Cu}$ 、 $\text{SrAl}_2\text{O}_4:\text{Eu}$ 、 Dy 、 $\text{ZnO}:\text{Zn}$ 、 $\text{Zn}_2\text{Ge}_2\text{O}_4:\text{Mn}$ 、 $\text{Zn}_2\text{SiO}_4:\text{Mn}$ 、 $\text{Ba}_3\text{MgSi}_2\text{O}_8:\text{Eu}$ 、 Mn 、 $\text{Sr}_3\text{MgSi}_2\text{O}_8:\text{Eu}$ 、 Mn 等が利用可能である。また、これらの蛍光体を複数用いることで、より効果的に半導体発光素子の出射光を用いて、発光波長のピークが500nm乃至540nmの緑色の光に変換することができる。

【0105】また、図6(a)に示す蛍光体 $(\text{Sr}, \text{Ca}, \text{Ba}, \text{Ce})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$ で、457nmに発光波長ピークを有する青色の発光色を得ようとする場合、図6(b)から明らかなように、390nm乃至400nmの波長範囲に発光波長のピークを有する半導体発光素子によって上記蛍光体を励起するのが効果的である。本来、蛍光体 $(\text{Sr}, \text{Ca}, \text{Ba}, \text{Ce})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$ の励起波長のピークは390nmより短波長側にあるが、蛍光体を励起する半導体発光素子の発光波長が390nmより短いと、人体に有害な紫外線を放出することとなるので実用的ではなく、また、半導体発光装置に使用されている樹脂部分にも悪影響を与え、封止樹脂の黒化による輝度の低下や樹脂の変質による信頼性の低下の原因となる。

【0106】一方、図7(a)に示す蛍光体 $\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}$ で、452nmに発光波長ピークを有する青色の発光色を得ようとする場合、図7(b)から明らかなように、390nmの発光波長を有する半導体発光素子によって上記蛍光体を励起するのが効果的である。本来、蛍光体 $\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}$ の励起波長のピークは390nmにあるが、蛍光体を励起する半導体発光素子の発光波長が390nmより短いと、人体に有害な紫外線を放出することとなるので実用的ではなく、また、半導体発光装置に使用されている樹脂部分にも悪影響を与え、封止樹脂の黒化による輝度の低下や樹脂の変質による信頼性の低下の原因となる。

【0107】上記蛍光体以外にも、本発明の実施形態で

は、 $\text{BaMg}_2\text{Al}_{16}\text{O}_{27}:\text{Eu}$ 、 $\text{ZnS}:\text{Ag}$ 、 $\text{Sr}_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$ 、 $\text{Ca}_{10}(\text{PO}_4)_6\text{F}_2:\text{Sb}$ 、 $\text{Sr}_3\text{MgSi}_2\text{O}_8:\text{Eu}$ 、 $\text{SrMgSi}_2\text{O}_8:\text{Eu}$ 、 $\text{Sr}_2\text{P}_2\text{O}_7:\text{Eu}$ 、 $\text{CaAl}_2\text{O}_4:\text{Eu}$ 、 Nd 等が利用可能である。また、これらの蛍光体を複数用いることで、より効果的に半導体発光素子の出射光を、発光波長のピークが410nm乃至480nmの青色の光に変換することができる。

【0108】さらに、使用用途に応じて、 $\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}$ 、 $\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}$ 、 Dy 、 $(\text{Ba}, \text{Ca}, \text{Mg})_{10}(\text{PO}_4)_6\text{Cl}_2:\text{Eu}$ 、 $\text{Sr}_2\text{Si}_3\text{O}_8 \cdot 2\text{SrCl}_2:\text{Eu}$ 等の蛍光体のうちのいずれか一つ、または、複数を用いることによって、効果的に半導体発光素子の出射光を、発光波長のピークが480nm乃至500nmの青緑色の光に変換することができる。

【0109】また、蛍光体に、 $\text{ZnS}:\text{Mn}$ 、 $\text{ZnS}:\text{Cu}$ 、 Mn 、 Co を用いることにより、半導体発光素子の出射光を、発光波長のピークが570nm乃至600nmの橙色の光に変換することができる。

【0110】以下、本発明の実施形態の半導体発光装置について図面を参照して詳しく説明する。

【0111】(第1の実施形態)図8(a)乃至(c)は、本発明の第1の実施形態の半導体発光装置を示す断面図である。

【0112】図8(a)は、絶縁性基板を有する半導体発光素子7aを備え、蛍光体を分散させたランプ形状の封止樹脂としてのモールド樹脂によって、上記半導体発光素子7aを封止したランプ型半導体発光装置の断面図である。

【0113】この半導体発光装置は、基体としてのリードフレーム101の先端に、カップ形状の凹みであるマウント部10aを有する。このカップ形状のマウント部10aに、上記半導体発光素子7aが例えばエポキシ樹脂等からなる接着剤11で固定されている。上記半導体発光素子7aの上面に設けられたP側電極6aが、例えば Au 、 Al 、 Cu 等からなる金属ワイヤー6pによってリードフレーム101の電極部10bに接続されている。また、上記半導体発光素子7aの上面に設けられたN側電極5aが、金属ワイヤー5nによって右側のリードフレーム102の電極部10cに接続されている。そして、上記半導体発光素子7aおよびリードフレーム101、102の上部を、蛍光体を分散させた例えば透光性のエポキシ樹脂等のモールド樹脂130によって封止して、ランプ形状の半導体発光装置を形成している。なお、上記半導体発光素子7aとリードフレーム101のマウント部10aとを接合する接着剤11は、半導体発光素子7aからの光を吸収しない材料であれば特に限定されない。例えば、上記半導体発光素子7aの熱特性改善のために熱伝導性の良い金属材料を混合した樹脂材料や、上記半導体発光素子7aからリードフレーム101

のマウント部10aに向う光を効率よく反射・散乱させる材料を含有した樹脂材料等を用いてもよい。

【0114】図8(b)は、導電性基板を有する半導体発光素子7bを備え、蛍光体を分散させたランプ形状の封止樹脂としてのモールド樹脂130によって上記半導体発光素子7bを封止したランプ型半導体発光装置の断面図である。図中、図8(a)に示した半導体発光装置と同一の機能を有する部分は、同一の参照番号を付して、詳細な説明を省く。

【0115】この半導体発光装置は、上記半導体発光素子7bのN側電極部5bが、リードフレーム101のマウント部10aに、例えばインジウム等の金属系からなる導電性のろう材またはAu-エポキシ樹脂、Ag-エポキシ樹脂等からなる接着剤15によって直接接続されている。一方、上記半導体発光素子7bの上面に設けられたP側電極6bは、金属ワイヤー6pによって図8

(b)において右側のリードフレーム102の電極部10cに接続されている。そして、上記半導体発光素子7bおよびリードフレーム101、102の上部が、蛍光体を分散させたモールド樹脂130によって封止されて、ランプ形状の半導体発光装置を形成している。半導体発光素子7bの上下に設けられた電極6b、5bは、従来のGaAs系やGaP系の半導体発光素子と同様であるので、従来の半導体発光装置に用いられたリードフレームをそのまま利用できる。

【0116】図8(c)は、絶縁性基板を有する半導体発光素子7cを備え、この半導体発光素子7cとリードフレーム103、103とを金属ワイヤーを用いずに接続して、蛍光体を分散させたランプ形状の封止樹脂としてのモールド樹脂130によって上記半導体発光素子7cを封止したランプ型半導体発光装置の断面図である。

【0117】この半導体発光装置は、互いに対向して配置されたリードフレーム103、103の先端に、基板としてのサブマウント17を連結している。このサブマウント17はSiからなって絶縁性であり、サブマウント17の上面には電極配線17a、17bが形成されている。このサブマウント17の上面に、上記半導体発光素子7cが半導体層側面(図1(c)における半導体発光素子7cの下側面)を対向させて搭載されている。上記半導体発光素子7cの下側面に設けられたP側電極6cとN側電極5cは、例えばAuバンプ等を用いて上記サブマウント17の上面に形成された電極配線17a、17bに接続されている。上記サブマウント17の上面に形成された電極配線17a、17bは、リードフレームの先端部10d、10eに接続して、外部と電気的に接続している。そして、上記半導体発光素子7cおよびサブマウント17と、リードフレーム103、103の上部を、蛍光体を分散させたエポキシ樹脂からなるモールド樹脂130によって封止して、ランプ形状の半導体発光装置を形成している。この半導体発光装置は、上記

半導体発光素子7cをサブマウント17に直接接続している。上記半導体発光素子7cの発光領域からの熱をサブマウント17とリードフレーム103、103を介して半導体発光装置の外部に素早く逃がすことができるという利点がある。

【0118】図8(a)、(b)、(c)に示したランプ形状の半導体発光装置は、放射される光が図8

(a)、(b)、(c)の上方に向う指向性を有しており、特に図8(a)、(b)の半導体発光装置は、半導体発光素子7a、7bから出射された光を効率良く集光するために、リードフレーム101のマウント部10aがカップ形状に形成されている。上記モールド樹脂130は、エポキシ樹脂以外に例えばシリコン樹脂、ウレタン樹脂、ポリカーボネート樹脂等の透光性を有する熱硬化性、熱可塑性の樹脂を用いてもよい。また、上記蛍光体はモールド樹脂130全体に均一に分散させてもよいが、モールド樹脂130の表面から半導体発光素子7a、7b、7cに向って漸次蛍光体の含有比率を高くすると、モールド樹脂130の外側からの水分等の影響による蛍光体の劣化を低減できる。また、半導体発光素子7a、7b、7cからモールド樹脂130の表面に向って漸次蛍光体の含有比率を高くすると、半導体発光素子7a、7b、7cによる蛍光体への電気的および熱的影響を緩和することもできる。このように、モールド樹脂130中の蛍光体の分布は、モールド樹脂の種類、蛍光体の種類、使用環境、条件または用途等に応じて、様々な形態をなすことができる。

【0119】(第2の実施形態)図9(a)、(b)は、本発明の第2の実施形態における半導体発光装置を示した断面図である。図9(a)の半導体発光装置は、リードフレーム101のマウント部10a内に蛍光体を充填すると共に、モールド樹脂131が蛍光体を含まないこと以外は、図8(a)に示した半導体発光装置と同一である。図9(b)の半導体発光装置についても、リードフレーム101のマウント部10a内に蛍光体を充填すると共に、モールド樹脂131が蛍光体を含まないこと以外は、図8(b)に示した半導体発光装置と同一である。したがって、図8(a)、(b)に示した半導体発光装置と同一の機能を有する部分には同一の参照番号を付して、詳細な説明を省略する。以下の他の実施形態においても同様である。

【0120】図9(a)、(b)に示した半導体発光装置は、半導体発光素子7a、7bを、カップ形状のマウント部10aの底に配置すると共に、このマウント部10aに蛍光体12を充填して、この蛍光体12によって半導体発光素子7a、7bからの光の波長を変換するようにしている。すなわち、半導体発光素子7a、7bからの光を集めるマウント部10aに上記蛍光体12を配置することによって、半導体発光素子7a、7bからの光をもれなく変換させて、光の変換効率を高めているの

である。したがって、上記第1の実施形態におけるようなモールド樹脂全体に蛍光体を分散させる場合に比べて、半導体発光装置の色調が良く、しかも蛍光体はマウント部10a内のみに配置すればよいので、蛍光体の使用量が低減される。

【0121】上記実施形態において、蛍光体12はリードフレーム101のマウント部10a内全体に充填したが、半導体発光素子7a、7bからの放出光を十分に所定の波長に変換できるのであれば、必ずしもマウント部10a内全体に蛍光体12を充填させる必要はなく、マウント部10aにおいて蛍光体12を凹状に充填してもよい。あるいは、蛍光体12を上記マウント部10a上端よりも凸状に盛り上がるように充填してもよく、要は、半導体発光素子7a、7bからの光の波長を所望の波長に変換可能な量の蛍光体12をマウント部10aに充填していればよい。

【0122】(第3の実施形態)図10(a)、(b)は、本発明の第3の実施形態の半導体発光装置を示す断面図である。図10(a)の半導体発光装置は、リードフレーム101のマウント部10aにおいて、半導体発光素子7a全体を覆うようにプレコーティング13aを配置して、その上に蛍光体12を配置した以外は、図9(a)に示した半導体発光装置と同一である。図10(b)の半導体発光装置についても、リードフレーム101のマウント部10aにおいて、半導体発光素子7a全体を覆うようにプレコーティング13aを配置して、その上に蛍光体12を配置した以外は、図9(b)に示した半導体発光装置と同一である。したがって、図9(a)、(b)に示した半導体発光装置と同一の機能を有する部分には同一の参照番号を付して、詳細な説明を省略する。

【0123】図10(a)、(b)において、左側リードフレーム101先端に形成されたカップ形状のマウント部10aの底に、半導体発光素子7a、7bを配置して、この半導体発光素子7a、7b全体を覆うように例えばエポキシ樹脂、シリコン樹脂、ウレタン樹脂等からなるプレコーティング13aを形成している。このプレコーティング13aの上に、上記マウント部10a内側を満たすように蛍光体12を層状に配置している。上記蛍光体12は、プレコーティング13aが形成されたマウント部10aをディッピングして、または、マウント部10a内のプレコーティング13a上にポッティング、あるいは噴霧、蒸着することによって、プレコーティング13a上に形成する。図10(a)、(b)において、蛍光体12はリードフレーム101のマウント部10a内側にのみ形成したが、リードフレーム101の上面全体を覆うように形成してもよい。

【0124】図10(a)、(b)に示す半導体発光装置は、上記蛍光体12は、プレコーティング13aによって、半導体発光素子7a、7bの発光領域から略等距

離をおいて均一厚さに形成されている。したがって、蛍光体12の全ての領域において通過する光量が略等しいので、この半導体発光装置はムラの無い均一な発光光が得られる。また、半導体発光素子7a、7bから離間した位置に蛍光体12を配置するので、蛍光体12に対する半導体発光素子の電気的および熱的影響を緩和できる。その結果、発光特性が良好で、しかも耐久性の良い半導体発光装置が得られる。

【0125】(第4の実施形態)図11(a)、(b)は、本発明の第4の実施形態による半導体発光装置を示す断面図である。

【0126】図11(a)は、絶縁性基板を有する半導体発光素子7aを、基板としてのプリント配線基板18上に搭載して、上記半導体発光素子7aを、蛍光体を分散させた封止樹脂としてのモールド樹脂132によって封止している。

【0127】この半導体発光装置は、耐熱性を有するガラスエポキシからなる直方体形状のプリント配線基板18上に、エポキシ樹脂からなる接着剤11によって半導体発光素子7aを接着している。この半導体発光素子7aの上面に設けられたP側電極6aとN側電極5aは、金属ワイヤー6p、5nによって、プリント配線基板18上面の電極部18a、18bに各々接続されている。これらの電極部18a、18bは、プリント配線基板18の上面と下面とを接続する図示しない断面円弧状のスルーホールを介して、実装面としてのプリント配線基板18の下面に引き回されて、この実装面の両端部にまで延びている。なお、上記プリント配線基板18は、絶縁性フィルムを用いてもよい。

【0128】そして、上記プリント配線基板18上に、上記半導体発光素子7a全体を覆うように、蛍光体を分散させた封止樹脂としての例えば透光性のエポキシ樹脂等のモールド樹脂132を図11(a)に示すような台形断面をなすように形成して、チップ部品形状の半導体発光装置を形成している。

【0129】上記半導体発光素子7aとプリント配線基板18とを接着する接着剤11は、半導体発光素子7aからの光が吸収されない材料であれば特に限定されない。例えば、半導体発光素子7aの熱特性改善のために熱伝導性の良い金属材料を混合した樹脂材料や、半導体発光素子7aからプリント配線基板18に向かって放出された光を効率よく反射・散乱させる材料を含有した樹脂材料等を用いてもよい。しかし、金属材料を含む樹脂材料を使用する場合は、P側電極6aとN側電極5aとが短絡しないように注意する必要がある。

【0130】図11(b)は、図11(a)における半導体発光素子7aに換えて、絶縁性基板を有する半導体発光素子7cを備える以外は、図11(a)の半導体発光装置と同一である。したがって、図11(a)と同様の機能を有する部分には同一の参照番号を付して、詳細

な説明を省略する。

【0131】図11(b)の半導体発光装置において、半導体発光素子7cは、半導体発光素子7cの図11

(b)において上側に位置する絶縁性基板を通して光を出射する。上記半導体発光素子7cは、図11(b)において下側である半導体積層側に形成されたP側電極6cとN側電極5cを、Auバンプを介してプリント配線基板18上の電極部18aと18bに各々直接接続している。なお、半導体発光素子7cを、予め金属配線が施されたSiからなるサブマウント等に搭載し、このサブマウントをプリント配線基板18にダイボンドやワイヤーボンド等によって電気的に接続してもよい。この半導体発光装置は、半導体発光素子7cを、半導体積層側の面をプリント配線基板18に向けて実装するので、上記半導体発光素子7cの発光領域からの熱を外部へ素早く逃がすことができる。

【0132】図11(a), (b)の半導体発光装置におけるモールド樹脂132は、エポキシ樹脂以外に例えばシリコン樹脂、ウレタン樹脂、ポリカーボネート樹脂等の透光性を有する熱硬化性、熱可塑性の樹脂を用いてもよい。また、蛍光体はモールド樹脂132全体に均一に分散させてもよいが、モールド樹脂132の表面から半導体発光素子7cに向って漸次蛍光体の含有比率を高くすると、水分等の影響による蛍光体の劣化を低減できる。また、半導体発光素子7a, 7cからモールド樹脂132の表面に向って漸次蛍光体の含有比率を高くすると、蛍光体に対する半導体発光素子7a, 7cの電気的および熱的影響を緩和することができる。このように、モールド樹脂132中の蛍光体の分布は、モールド樹脂の種類、蛍光体の種類、使用環境、条件、用途等に応じて様々な形態をなし得る。

【0133】なお、上記半導体発光素子7a, 7cに換えて、導電性基板を有する半導体発光素子7bを使用してもよい。この場合は、プリント配線基板上の一方の電極に、半導体発光素子7bの下面に形成されたN型電極を、導電性を有する接着剤によって直接接続する。上記半導体発光素子7bの上面に設けられたP側電極は、金属ワイヤーによってプリント配線基板上の他方の電極部に接続する。上記半導体発光素子7bは、従来のGaAs系やGaP系の半導体発光装置と同様に、半導体発光素子7bの上下両面に電極を有するので、従来のリードフレームをそのまま利用できるという利点がある。

【0134】(第5の実施形態) 図12(a), (b)は、本発明の第5の実施形態の半導体発光装置を示す断面図である。図12(a)の半導体発光装置は、基体としてのプリント配線基板18上に、樹脂からなる枠19を備える。このプリント配線基板18上であって上記樹脂枠19の内側に、導電性基板を有する半導体発光素子7bが配置されている。そして、上記樹脂枠19の内側に、蛍光体を含む封止樹脂としてのモールド樹脂134

を充填して半導体発光素子7bを封止している。

【0135】この半導体発光装置は、耐熱性を有するガラスエポキシ等からなる直方体形状のプリント基板18上に、樹脂からなる枠19を設けている。この樹脂枠19は、内側にモールド樹脂134を充填した際に半導体発光素子7bを樹脂134が十分に覆う程度の高さを有する。この枠19の内側において、プリント配線基板18上の一方の電極部18aと半導体発光素子7b下面のN側電極5bとを、導電性を有する接着剤によって接着して接続している。一方、半導体発光素子7bの上面に設けられたP側電極6bは、金属ワイヤー6pによってプリント配線基板18上の他方の電極部18bに接続している。これら電極部18a, 18bは、プリント配線基板18を貫通する図示しない断面円弧状のスルーホールを介して、プリント配線基板18の上面から実装面である下面まで立体的に引き回されて、プリント配線基板18下面の両端にまで夫々延びている。上記プリント配線基板18上かつ樹脂枠19の内側に、半導体発光素子7b全体を覆うように、蛍光体を分散させた透光性のエポキシ樹脂からなるモールド樹脂134が充填されている。上記半導体発光素子7bは、従来のGaAs系やGaP系の半導体発光素子と同様に上下両面に電極6b, 5bを有するので、従来のリードフレームを共通で利用できるという利点がある。なお、基体としては上記プリント配線基板の他に絶縁性フィルムを用いてもよい。

【0136】図12(b)の半導体発光装置は、基体としてのプリント基板18上に樹脂枠19aを備え、この樹脂枠19aの内側に、絶縁性基板を有する半導体発光素子7cを備えると共に蛍光体を分散させた封止樹脂としてのモールド樹脂134を充填している。上記樹脂枠19aは、半導体発光素子7cに面する側面が、半導体発光素子7cの側面から横方向に出射された光をプリント基板18の直角方向に反射するように傾斜している。

【0137】この半導体発光装置は、ガラスエポキシからなる直方体形状のプリント基板18上に、半導体発光素子7cに面する側面が傾斜した樹脂枠19aを備える。上記半導体発光素子7cは半導体積層側面を下に向けてプリント配線基板18に搭載されている。半導体発光素子7cが備えるP側電極6cとN側電極5cは、プリント配線基板18上の電極部18aと18bに、Auバンプを介して各々接続されている。上記電極部18a, 18bは、図12(a)に示した半導体発光装置と同様に、プリント配線基板18の上面から図示しないスルーホールを介して下面まで立体的に引き回されて、プリント配線基板18の下面両端にまで延長されている。なお、基体としては上記プリント配線基板18の他に絶縁性フィルムを用いてもよい。また、上記半導体発光素子7cはプリント配線基板18に直接接続したが、半導体発光素子7cを予め金属配線を施してSiからなるサブマウント等に搭載し、このサブマウントをプリント配

線基板 18 にダイボンドやワイヤーボンド等によって電氣的に接続してもよい。

【0138】この半導体発光装置は、半導体発光素子 7c の半導体積層側面を直接プリント配線基板 18 に実装しているので、半導体発光素子 7c の発光領域からの熱をサブマウントおよびリードフレームを通して外部へ素早く逃がすことができるという利点がある。

【0139】図 12 (a), (b) の半導体発光装置におけるモールド樹脂 134 は、図 8 (a), (b),

(c) のモールド樹脂 13 と同様の材料であり、上記モールド樹脂中の蛍光体の分布は、モールド樹脂の種類、蛍光体の種類、使用環境、条件、用途等に応じて様々な形態を取り得る。

【0140】図 12 (a), (b) において、上記樹脂枠 19, 19a はプリント配線基板 18 と別に形成した後、プリント配線基板 18 に張付けたが、厚めのプリント配線基板の一部を除去して凹部を形成して、この凹部の周りを枠にしてもよい。さらに、プリント配線基板に貫通穴を形成して、このプリント配線基板の底面に金属箔による電極兼配線を配置して、この電極兼配線の上に半導体発光素子を配置すると共に上記貫通穴部分を封止樹脂で封止してもよい。

【0141】また、図 12 (a), (b) の半導体発光装置において、半導体発光素子 7b, 7c は、図 1

(a) に示した半導体発光素子 7a でもよく、この半導体発光素子 7a を用いた場合には、金属ワイヤーによって半導体発光素子 7a の電極とプリント配線基板の電極部とを接続する。

【0142】(第 6 の実施形態) 図 13 は、本発明の第 6 の実施形態における半導体発光装置を示す断面図である。

【0143】この半導体発光装置は、図 12 (b) に示した半導体発光装置が備える枠と同様の枠 19a を有する。この枠 19a は、ガラスエポキシからなる直方体状の基体としてのプリント基板 18 上に設置されて、この枠 19a の半導体発光素子 7c に面した側面が、半導体発光素子 7c の側面からの光をプリント基板 18 の直角方向に反射するように傾斜している。上記半導体発光素子 7c は半導体積層側を図 13 において下側に向けて、図 13 において上側の基板側から光を射出するようにプリント配線基板 18 上に搭載されている。この半導体発光素子 7c の電極 6c, 5c は、図 12 (b) に示した半導体発光装置と同様に、バンプによってプリント配線基板 18 の電極部 18a, 18b に接続されている。上記プリント配線基板 18 上に配置された枠 19a の内側には、エポキシ樹脂からなる透光性の封止樹脂としてのモールド樹脂 135 を充填して上記半導体発光素子 7c を封止している。そして、上記枠 19a およびモールド樹脂 13 の上に、蛍光体 12 が所定の層厚を有して層状に形成されている。

【0144】この実施形態における半導体発光装置は、蛍光体 12 は半導体発光素子 7c の発光領域から略等距離の位置に均一の厚さで形成されているので、全ての蛍光体 12 の位置において、蛍光体 12 を通過する光量が略一定になって、ムラの無い均一な発光が可能である。また、上記蛍光体 12 は、半導体発光素子 7c から所定の距離をおいて形成されているので、蛍光体 12 に対する半導体発光素子の電氣的および熱的影響を緩和することができる。

【0145】上記実施形態では、蛍光体 12 は樹脂枠 19a の上面にも形成したが、樹脂枠 19a が遮光性の材料で形成されていれば、蛍光体 12 はモールド樹脂 135 の上のみ形成してもよい。また、樹脂枠 19a の高さを高くして、モールド樹脂 13 を半導体発光素子 7c の上端を僅かに越える程度に充填した後、上記樹脂枠 19a 内であって上記モールド樹脂 135 の上に、ポッティング等で蛍光体を配置してもよい。

【0146】上記樹脂枠 19a は、図 12 (b) の半導体発光装置に関して述べた際と同様に、厚めのプリント配線基板 18 の一部を除去して残った凸部を枠として使用してもよい。さらに、貫通穴を有するプリント配線基板の底部に、金属箔による電極兼配線を設けて凹部を形成しても良い。

【0147】また、外部への光取出し効率は落ちるが、半導体発光素子 7c に面した側面が垂直に形成された樹脂枠を利用してもよい。

【0148】なお、上記半導体発光素子 7c は、図 1 に示した半導体発光素子 7a, 7b を用いてもよい。特に、導電性基板を有する半導体発光素子 7b は、上側および下側に電極を備え、従来の GaAs 系や GaP 系の半導体発光素子と同様の電極構造であるので、従来のリードフレームをそのまま利用できるという利点がある。

【0149】(第 7 の実施形態) 図 14 (a), (b) は、本発明の第 7 の実施形態における半導体発光装置を示す断面図である。

【0150】図 14 (a) は、この半導体発光装置を発光方向から見た断面図であり、図 14 (b) は発光方向に対して直角方向から見た断面図である。

【0151】この半導体発光装置は、ガラスエポキシからなる直方体状の基体としてのプリント配線基板 18 上に、エポキシ樹脂等の接着剤 11 によって半導体発光素子 7a が接着されて、この半導体発光素子 7a の上面に設けられた P 側電極 6a と N 側電極 5a が、金属ワイヤー 6p, 5n によってプリント配線基板 18 の電極部 18a, 18b に各々接続されている。これらの電極部 18a, 18b は、プリント配線基板 18 を貫通して形成された断面円弧状のスルーホール 19, 19 を介してプリント配線基板 18 の下面に立体的に引き回されて、このプリント配線基板 18 の下面である実装面の両端まで延びている。なお、上記プリント配線基板 18 に換えて

絶縁性フィルムを用いてもよい。

【0152】さらに、上記半導体発光素子7a全体を、蛍光体を分散させた透光性のエポキシ樹脂からなる封止樹脂としてのモールド樹脂136によって封止している。このモールド樹脂136は、図14(b)において左側縁と下側縁が直線をなす略4分の1楕円形状の断面を有する一方、図14(a)において幅方向が高さ方向よりも長い矩形断面を有する。そして、上記モールド樹脂136の上に、上記半導体発光素子7aからの光を反射するための反射体20を形成している。

【0153】上記モールド樹脂136は、透光性を有し、かつ実装工程での半田リフローの際の高温にも耐え得る熱硬化性樹脂を用いるのが好ましく、プリント配線基板18上に、樹脂ポッティング法やトランスファモールド法、インジェクションモールド法等によって形成する。上記モールド樹脂136の上面は、図14(b)に示すように放物線をなして湾曲するとともに、この放物線の中心線I-Iよりも上方に半導体発光素子7aを配置している。また、上記モールド樹脂136の光の出射側面Aは平坦に形成して、プリント配線基板18の側面と略同一面にしている。なお、上記モールド樹脂136の曲面は、上記半導体発光素子7aが曲面の放物線の中心線I-Iよりも下方に位置するように形成してもよい。

【0154】上記反射体20は、半導体発光素子7aの光及び蛍光体12により波長変換された光を反射する材料を少なくとも含み、上記モールド樹脂136と同様に、半田リフローの際の高温にも耐え得る熱硬化性樹脂または熱可塑性樹脂を用いて、上記モールド樹脂136の上側面を覆うように樹脂ポッティング法やトランスファモールド法、インジェクションモールド法等によって形成する。この反射体20は、図14(b)の断面に示すように、下側縁端がモールド樹脂136の上側縁端と接して湾曲する一方、左側縁端がモールド樹脂136の光出射面Aと同一の平面をなすように、また、反射体20の右側縁端が直線をなして上記プリント配線基板18の右側端面に連続するように形成されている。そして、上記反射体の上端縁は上記プリント配線基板18に平行に形成されている。この半導体発光装置は、モールド樹脂136の上面と反射体20の下面との境界面が反射面となっている。この反射面で反射されて出射する光は、図14(a)において水平方向左側に拡散される一方、上下方向には反射体20およびプリント配線基板18によって遮られる。したがって、半導体発光素子7aからの直接光及び反射光は、水平方向に絞られた指向特性となる。具体的には、照射光における水平方向の半値角が $\pm 6.5^\circ$ 、垂直方向の半値角が $\pm 3.0^\circ$ の指向特性を有する。したがって、半導体発光素子7aからの光は、モールド樹脂136中の蛍光体12により波長変換されて、直接出射すると共に反射体20で反射されて、モ

ールド樹脂136の側面部から外部へ出射するので、水平方向に有効照射領域が広く、かつ高輝度なサイド発光型半導体発光装置を提供できる。

【0155】なお、反射体20は、モールド樹脂136と接する部分にのみ反射作用を有していればよいので、モールド樹脂136の湾曲した上側面、あるいは反射体20の湾曲部した下側面のいずれかに、例えば金属や白色塗料等からなる反射層を設けるだけでもよい。

【0156】上記半導体発光素子7aをプリント配線基板18に接着する樹脂は、半導体発光素子7aからの光が吸収されないものであれば特に限定無く利用可能である。例えば、半導体発光素子7aの熱特性改善のために熱伝導性のよい金属を混合した樹脂や、リードフレームマウント部方向に放出された光を効率よく反射・散乱させる材料を含有した樹脂等を用いてもよい。しかし、金属を含む樹脂を使用する場合は、P側電極とN側電極とが短絡しないように注意する必要がある。

【0157】なお、この実施形態における半導体発光装置において、上記半導体発光素子7aに換えて、図1(b)に示した上面および下面に夫々電極を備える半導体発光素子7bや、図1(c)に示した基板側から光を出射するタイプの半導体発光素子7cを用いてもよい。上記半導体発光素子7bは、従来のGaAs系やGaP系の半導体発光装置と同一の電極構造を有するので、従来のリードフレームをそのまま利用できるという利点がある。上記半導体発光素子7cは、半導体積層側面を直接電気配線に実装するので、発光領域からの熱をサブマウント・リードフレームを通して外部へ速やかに逃がしてやる事ができるという利点がある。

【0158】(第8の実施形態)図15(a), (b)は、本発明の第8の実施形態としてのサイド発光型半導体発光装置を示す断面図である。

【0159】図15(a)は、この半導体発光装置を発光方向から見た断面図を示し、図15(b)は発光方向に対して直角方向から見た断面図である。図15

(a), (b)の半導体発光装置は、上面と下面に電極を有する半導体発光素子7bを使用したことと、蛍光体を封止樹脂中に分散させずに、封止樹脂としてのモールド樹脂137の光の出射面A側に蛍光体12を層状に設けたこと以外は、図14(a), (b)の半導体発光装置と同一であり、同一の機能を有する部分には同一の参照番号を付して詳細な説明を省略する。

【0160】このサイド発光型半導体発光装置は、蛍光体12を半導体発光素子7bの発光領域から略等距離の位置に均一の層厚に形成したので、蛍光体12の略全域において通過する光の量が常に一定となり、ムラの無い均一な発光が可能になる。また、半導体発光素子7bから離間した位置に蛍光体12を配置したので、蛍光体12に対する半導体発光素子7bの電流や熱による影響を緩和できる。また、上記半導体発光素子7bにおいて上

面と下面に電極6b, 5bを配置したタイプは、従来のGaAs系やGaP系の半導体発光素子と電極構造が同一であるので、従来のリードフレームをそのまま利用できるという利点がある。

【0161】本発明の実施形態において、上記半導体発光素子7bは、図1(a)の半導体発光素子7aおよび図1(c)の半導体発光素子7cを使用してもよい。

【0162】(第9の実施形態)図16(a), (b)は、本発明の第9の実施形態であるサイド発光型半導体発光装置を示す図である。

【0163】図16(a)はこの半導体発光装置を発光方向から見た断面図であり、(b)は発光方向に対して直角方向から見た断面図である。この半導体発光装置は、基体としてのプリント配線基板18上に、半導体発光素子7cを封止する封止樹脂としてのモールド樹脂139を備える。このモールド樹脂139は、図16

(a)において楕円の下半分が除去されたような形状である略半楕円形状の断面を有すると共に、図16(b)において楕円の左側と下方が除去されたような形状である略4分の1楕円形状の断面を有する。すなわち、上記モールド樹脂139は、プリント配線基板18上において、光出射面Aを除く面が所定の曲率半径を有するドーム形状をなす。そして、このモールド樹脂139の外側面の曲面部分を覆って蛍光体としての蛍光体層12aが形成されていて、さらにその外側面に半導体発光素子7cからの光を反射するための反射体20が形成されている。

【0164】さらに、プリント配線基板18上の半導体発光素子7cの光出射面A側に、半導体発光素子7cからの光を直接外部へ出さないように遮断する遮蔽体としての障壁体21が設けられている。この障壁体21は、半導体発光装置94の発光面A側から見て(図16

(a)参照)、半導体発光素子7cの発光領域を遮る高さおよび幅を有し、半導体発光素子7cの光に対して不透明な樹脂や金属等が用いられる。また、障壁体21の材料として光を吸収する材料を利用してもよいが、その場合、光の利用効率が悪くなる。また、図16(b)に破線で示すように、半導体発光素子7cの周りを囲む樹脂枠からなる障壁体21aを用いてもよい。また、上記半導体発光素子7cから直接出射される光を遮るために、厚めのプリント配線基板の一部に凹部を形成して、この凹部に発光領域が隠れるように半導体発光素子を配置してもよい。半導体発光素子7cは、半導体積層側を直接プリント配線基板18に接続して搭載するので、発光領域からの熱をサブマウント・リードフレームを通して外部へ素早く逃がしてやる事ができると共に、半導体発光素子の発光領域が下方に位置するので障壁体の高さを低くすることができて、光の利用効率が大きい。なお、上述の遮蔽体21, 21aおよび凹部を、図14

(a), (b)に示した第7の実施形態の半導体発光装 50

置に用いることも可能である。

【0165】上記半導体発光素子7cからの出射光は上記蛍光体層12aで波長変換された後、この蛍光体層12aに接する反射体20で反射されて、再び蛍光体層12aで波長変換された後に、半導体発光装置外部に出射される。したがって、単に半導体発光素子からの光が透過するように光の出射方向に配置された蛍光体を備える半導体発光装置に較べて、この半導体発光装置は略二倍の波長変換効率を有する。したがって、蛍光体層12aを薄くしても十分な波長変換効果が期待できるので、蛍光体の使用量を削減できて、半導体発光装置のコストを低減できる。

【0166】上記実施形態における蛍光体層12aは光を透過させて波長変換を行ったが、非透過であって、光を波長変換すると共に反射させる蛍光体を反射体として形成してもよい。例えば、光を反射・散乱させる性質をもった微細粒子の表面に蛍光材料を塗布した蛍光体等が考えられる。

【0167】なお、本実施形態において、半導体発光素子7cに換えて図1(a), (b)に示す半導体発光素子7a, 7bを用いてもよい。特に、導電性基板を有する半導体発光素子7(b)は、上下両側面に電極を有する従来のGaAs系やGaP系の半導体発光素子と同様の電極構造を有するので、従来のリードフレームをそのまま利用できる。

【0168】(第10の実施形態)図17(a), (b)は、本発明の第10の実施形態としてのサイド発光型半導体発光装置を示す断面図である。

【0169】図17(a)は上記半導体発光装置を発光方向から見た断面図を示し、図17(b)は発光方向に対して直角方向から見た断面図である。本実施形態が、図16(a), (b)に示した第9の実施形態と異なる点は、半導体発光素子7cに換えて導電性基板を有する半導体発光素子7bを用いた点と、プリント配線基板18に換えて、貫通穴Bを有するガラスエポキシ基板の底面に、金属箔からなり電極兼配線を備えた極薄型プリント配線基板23を装着してなる基体としてのプリント配線基板18aを用いた点である。

【0170】図17(a), (b)に示すように、このサイド発光型半導体発光装置は、半導体発光素子7bを、プリント配線基板18aの貫通孔B内に没するように、上記極薄プリント配線基板23の上に設置している。したがって、半導体発光素子7bの高さをプリント配線基板18aの厚さで吸収できるので、半導体発光装置の薄型化が可能になると共に、半導体発光素子7bの発光領域が外部から完全に隠れるので、半導体発光素子7bから出射される光が直接外部に出ない。すなわち、蛍光体としての蛍光体層12aによって波長が変換された光のみが半導体発光装置の外部に出射されるので、半導体発光装置の色調が、さらに良くなる。なお、上記貫

通孔Bの深さは、少なくとも半導体発光素子7bの発光領域が、光の出射面A(図17(b)参照)側から見て隠れる程度であればよい。

【0171】なお、上記実施形態において、半導体発光素子7bは、図1(a)、(c)に示した半導体発光素子7a、7cを用いてもよい。特に、上記半導体発光素子7cは、貫通孔B内に配置した場合、貫通穴Bの底部近くに発光領域が位置するので、半導体発光装置を更に薄型にできる。

【0172】(第11の実施形態)図18(a)、(b)、(c)および図19(a)、(b)、(c)

は、本発明の第11の実施形態の半導体発光装置が出射する光の波長分布を示した図である。この半導体発光装置は、基体上に半導体発光素子を備え、この半導体発光素子の出射光は、390nm乃至420nmの波長領域のうちの410nmに発光波長のピークを有する。さらに、この半導体発光装置は、上記半導体発光素子の出射光を変換する第1、第2、第3の蛍光体を備える。上記半導体発光素子は、この半導体発光素子によって損傷しない樹脂からなる封止樹脂で封止されていて、この封止樹脂に、上記第1、第2、第3の蛍光体が、略均一に混合された状態で含まれている。上記第1の蛍光体は、 $0.5\text{MgF}_2 \cdot 3.5\text{MgO} \cdot \text{GeO}_2 : \text{Mn}$ の蛍光体からなり、上記半導体発光素子の出射光によって励起されて、発光波長が658nmに主ピークを有する赤色の光を出射する。上記第2の蛍光体は、 $\text{SrAl}_2\text{O}_4 : \text{Eu}$ の蛍光体からなり、発光波長が522nmに主ピークを有する緑色の光を出射する。上記第3の蛍光体は、 $\text{BaMgAl}_{10}\text{O}_{17} : \text{Eu}$ の蛍光体からなり、発光波長が452nmに主ピークを有する青色の光を出射する。この半導体発光装置は、上記第1、第2、第3の蛍光体からの出射光を混色することによって白色の光を出射し、携帯電話や携帯情報端末、パーソナルコンピュータ等の表示装置のバックライト用光源として用いられる。なお、上記半導体発光素子の発光波長のピークは、390nm乃至420nmの波長領域にあるが、400nm乃至420nmの波長領域にあれば、より好ましい。

【0173】図18(a)、(b)、(c)は、上記半導体発光装置において、上記第1、第2、第3の蛍光体の混合比率を変えた場合、出射光の波長分布に生じる変化を示した図である。いずれも、横軸は波長(nm)であり、縦軸は相対強度(%)である。また、いずれにおいても、上記封止樹脂の重量に対する上記第1、第2、第3の蛍光体の総重量の比率は、0.5である。

【0174】図18(a)は、第1、第2、第3の蛍光体の総量が100重量%であるとして、第1の蛍光体が47重量%、第2の蛍光体が13重量%、第3の蛍光体が40重量%である場合の半導体発光装置による出射光の波長分布を示した図である。この場合の半導体発光装置の出射光は、やや緑色がかかった色調の白色になる。

【0175】図18(b)は、第1、第2、第3の蛍光体の総量が100重量%であるとして、第1の蛍光体が56重量%、第2の蛍光体が11重量%、第3の蛍光体が33重量%である場合の半導体発光装置による出射光の波長分布を示した図である。この場合の半導体発光装置の出射光は、良好な色調の白色になる。

【0176】図18(c)は、第1、第2、第3の蛍光体の総量が100重量%であるとして、第1の蛍光体が65重量%、第2の蛍光体が26重量%、第3の蛍光体が9重量%である場合の半導体発光装置による出射光の波長分布を示した図である。この場合の半導体発光装置の出射光は、やや赤色がかかった色調の白色、いわゆる、昼白色になる。

【0177】また、第1の蛍光体としての $\text{La}_2\text{O}_3\text{S} : \text{Eu}$ と、第2の蛍光体としての $\text{BaMg}_2\text{Al}_{16}\text{O}_{27} : \text{Eu}, \text{Mn}$ と、第3の蛍光体としての $(\text{Sr}, \text{Ca}, \text{Mg}, \text{Ce})_{10}(\text{PO}_4)_6\text{Cl}_2 : \text{Eu}$ とを、順に72重量%、7重量%、21重量%の割合で備える半導体発光装置を形成した。この半導体発光装置の出射光は、良好な白色光であった。さらに、上記第1、第2、第3の蛍光体を、順に、58重量%、22重量%、20重量%の割合で備える半導体発光装置もまた、良好な白色の出射光が得られた。以上の実験結果を考慮すると、上記半導体発光装置の発光色は、第1の蛍光体、すなわち、赤色発光の蛍光体の混合比率が50重量%より少ないと、緑色がかかった色調の白色になる一方、上記第1の蛍光体の混合比率が70重量%より多いと、赤色がかかった色調の白色になることが分かった。また、上記半導体発光装置の発光色は、第2の蛍光体、すなわち、緑色発光の蛍光体の混合比率が7重量%より少ないと、赤色がかかった色調の白色になり、上記第2の蛍光体の混合比率が20重量%より多いと、緑色がかかった色調の白色になることが分かった。また、上記半導体発光装置の発光色は、第3の蛍光体、すなわち、青色発光の蛍光体の混合比率が20重量%より少ないと、赤色がかかった色調の白色になり、上記第3の蛍光体の混合比率が30重量%より多いと、緑色がかかった色調の白色になることが分かった。したがって、第11の実施形態の半導体発光装置は、封止樹脂の重量に対する第1乃至第3の蛍光体の総重量の比率が0.5である場合、第1、第2、第3の蛍光体が、各々56重量%、11重量%、33重量%の混合比率であると良好な白色の出射光が得られる。

【0178】図19(a)、(b)、(c)は、上記半導体発光装置において、封止樹脂の重量に対する第1、第2、第3の蛍光体の総重量の比率を変えた場合、出射光の波長分布に生じる変化を示した図である。いずれも、横軸は波長(nm)であり、縦軸は相対強度(%)である。また、いずれにおいても、第1、第2、第3の蛍光体の総量が100重量%であるとして、第1の蛍光

体が65重量%、第2の蛍光体が26重量%、第3の蛍光体が9重量%の混合比率である。

【0179】図19(a)は、封止樹脂の重量に対する第1、第2、第3の蛍光体の総重量の比率が、0.5である場合の半導体発光装置による出射光の波長分布を示した図である。この半導体発光装置の出射光は、やや赤色がかった色調の白色、いわゆる、昼白色になる。

【0180】図19(b)は、封止樹脂の重量に対する第1、第2、第3の蛍光体の総重量の比率が、0.66である場合の半導体発光装置による出射光の波長分布を示した図である。この半導体発光装置の出射光は、良好な色調の白色になる。

【0181】図19(c)は、封止樹脂の重量に対する第1、第2、第3の蛍光体の総重量の比率が、1.0である場合の半導体発光装置による出射光の波長分布を示した図である。この半導体発光装置の出射光は、やや緑色がかった色調の白色になる。

【0182】図19(a), (b), (c)より、上記半導体発光装置は、上記第1、第2、第3の蛍光体が、各々65重量%、26重量%、9重量%であって、封止樹脂の重量に対する第1、第2、第3の蛍光体の総重量の比率が0.5以上1.0以下の場合に、良好な色調の白色の出射光が得られることが分かる。

【0183】図20は、図19(a)に示した半導体発光装置の発光スペクトル150と、人間の比視感度151を考慮した半導体発光装置の実効発光スペクトル152とを示す図である。横軸は波長(nm)であり、縦軸は相対強度(%)である。

【0184】図20から分かるように、上記半導体発光装置の発光スペクトル150は、人間の比視感度151が有する波長領域より大きい発光波長領域を有するので、上記比視感度151の波長領域を網羅する波長領域の実効発光スペクトル152が得られるから、人間の視覚において、色調が良好な白色の発光色にできる。

【0185】さらに、上記半導体発光装置は、上記封止樹脂が半導体発光素子からの出射光によって損傷しない樹脂であるから、この封止樹脂は、例えば黒化などの不都合が生じない。したがって、半導体発光装置の輝度の低下などの不都合を防止でき、半導体発光装置の性能を長期に亘って安定にできる。

【0186】上記半導体発光装置において、上記第1、第2、第3の蛍光体に、各々複数種類の蛍光体を用いることによって、上記実効発光スペクトル152の波長領域を人間の比視感度151の波長領域範囲と略等しくしてもよい。これによって、半導体発光装置の発光色の色調を良好にできるとともに、半導体発光装置の発光波長領域を人間の可視領域のみにできるので、半導体発光装置の発光効率を向上できる。

【0187】本実施形態の半導体発光装置は、半導体発光素子を封止する封止樹脂に、上記第1、第2、第3の

蛍光体を略均一に混合したが、上記第1、第2、第3の蛍光体のみを混合し、この混合した蛍光体を、封止樹脂の表面に層状に配置してもよく、また、上記第1、第2、第3の蛍光体を、上記封止樹脂の表面に各々別個に層状に設けてもよい。この場合、光の発光・吸収波長などを考慮して、半導体発光素子に近い側から遠い側に向って、各々の層を、その層が含む蛍光体の発光波長が短い順に配置するのが好ましい。また、本実施形態の半導体装置は、上記第1乃至10の実施形態の半導体発光装置と同様の構造に形成してもよい。これによって、ランプ型、チップ部品型、サイド発光型の半導体発光装置において、良好な色調の白色発光を得ることができる。

【0188】(第12の実施形態)図21は、本発明の第12の実施形態の発光表示装置を示す模式図である。この発光表示装置200は、上記第11の実施形態の半導体発光装置からなる光源201と、光源201からの光205を導く導光板202と、この導光板202からの光を分光するカラーフィルタを備えた液晶パネル203とを有する液晶表示装置である。

【0189】上記光源201は、上記第1乃至11の実施形態の半導体発光装置のいずれを用いて形成してもよい。特に、上記発光表示装置200が、携帯電話や携帯情報端末、パーソナルコンピュータなどの表示装置として用いられる場合は、光源201として、上記第11の実施形態の白色発光の半導体発光装置が好適である。また、上記第11の実施形態の半導体発光装置が備える第1、第2、第3の蛍光体を、上記第4乃至6の実施形態の半導体発光装置の蛍光体として用いると、チップ部品形状を有して白色発光可能な半導体発光装置が得られる。この半導体発光装置は、チップ部品形状を有するので、発光表示装置200に実装する際の取り扱いが容易になる。また、上記チップ部品形状を有する半導体発光装置は、上記導光板202の側面202aに直接取り付けることができるので、発光光を効率良く導光板202に導くことができる。また、上記第7乃至10の実施形態の半導体発光装置に、第11の実施形態の蛍光体を搭載した半導体発光装置を用いて光源201を構成すると、この半導体発光装置はサイド発光型であるから、基体としてのプリント配線基板18が導光板202に略平行になるように、導光板の側面202aに半導体発光装置を取り付けることによって、この導光板202の光出射方向の発光表示装置200の厚みを効果的に小さくできる。なお、上記光源201は、複数の半導体発光装置を用いたが、光の強度が十分であれば1個の半導体発光装置によって構成してもよい。

【0190】上記導光板202は、例えばポリカーボネートやアクリル系樹脂などから形成する。また、光源201からの光が導入される側面202aと、導入した光を放出する光放出面202b以外の面に光反射部を設けると、光源201からの光を効率良く光放出面202b

から放出できる。また、導光板202への光は、1つの側面202aのみからではなく、例えば対向する2つの側面から導入してもよく、あるいは、3つおよび4つの側面から導入してもよい。さらに、光放出面202bにおける放出光の強度を均一にするために、導光板202中に光散乱剤を混入したり、上記光放出面202bと対向する図21における底側の面を傾斜させて、導光板の側面202aから導入された光を上記傾斜させた底側面で反射させて光放出面202bから放出してもよい。上記底側面に光散乱パターンを設けると、光放出面202bからの光206の強度が、さらに均一にできる。

【0191】上記液晶パネル203は、透明電極を設けた2つの透明な基板と、この2つの基板間に封入された液晶と、偏光板と、上記基板に貼り付けられたカラーフィルタを備える。上記カラーフィルタには、上記透明電極に印加する信号によって上記液晶を透過する光量が調節される複数の画素に対応して、赤色、緑色、青色のカラーフィルタが形成されている。このカラーフィルタは、シート状に形成したポリカーボネートやポリエチレンテレフタレートなどに、微小なハニカム形状あるいはデルタ配列形状の画素をなすように、光透過性の染料または顔料などで、赤色、緑色、青色に着色して、赤色、緑色、青色のカラーフィルタが形成されている。

【0192】図22は、上記カラーフィルタの分光特性を示した図であり、210が赤色のカラーフィルタの分光特性であり、211が緑色のカラーフィルタの分光特性であり、212は青色のカラーフィルタの分光特性である。このカラーフィルタの分光特性210、211、212に適合するように、上記光源201からの光の波長分布が調節されている。より詳しくは、光源201を構成する半導体発光装置において、半導体発光素子の発光波長や、第1、第2、第3の蛍光体の発光波長および混合比率や、第1乃至3の蛍光体の総重量と封止用樹脂の重量との配合比率などを調節して、光源201からの光205の波長分布を、上記カラーフィルタの分光特性210、211、212に適合させている。例えば、良好な色調を有して図19(b)の波長分布をなす半導体発光装置は、図22の分光特性に適合している。この半導体発光装置は、上記分光特性に適合するように、上記第1乃至3の蛍光体の総重量と封止用樹脂の重量との配合比率が調節されているからである。このように、上記光源201は上記カラーフィルタの分光特性に適合する波長分布を有するから、この光源201からの光205は、上記導光板202を介して液晶パネル203に導かれると、この液晶パネル203のカラーフィルタによって、輝度が高く、略単一の赤色、緑色、青色の光207に分光される。その結果、この発光表示装置200は、色調が良好な、しかも、高輝度かつ高コントラストの画像や映像が表示できる。

【0193】

【発明の効果】以上より明らかなように、本発明の半導体発光装置は、上記半導体発光素子は発光波長が390nm乃至420nmで人間の視感度が非常に低い短波長領域の出射光を有すると共に、この半導体発光素子からの出射光を600nm乃至670nmの赤色の発光波長に変換する蛍光体を備えるので、この蛍光体からの光は、人間の視感度を考慮すると、見かけ上、上記半導体発光素子からの直接光によって色調が殆ど変わらないから、この半導体発光装置は色調が良好で単色赤色の光を発光できる。また、上記半導体発光素子の発光波長は390nm乃至420nmであるので、上記半導体発光装置を構成する部品の損傷や、人体への悪影響を効果的に防止できる。

【0194】1実施形態の半導体発光装置は、上記蛍光体は、 $M_2O_2S:Eu$ (但し、MはLa, Gd, Yから選ばれるいずれか一つまたは2以上の元素)、 $0.5MgF_2 \cdot 3.5MgO \cdot GeO_2:Mn, Y_2O_3:Eu, Y(P, V)O_4:Eu, YVO_4:Eu$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなるので、上記半導体発光素子の発光波長に応じて最適な蛍光体を選択できて、良好な色調の単色赤色発光の半導体発光装置を得ることができ、複数の蛍光体を組合わせて、半導体発光素子の光の利用効率が高い半導体発光装置にできる。

【0195】本発明の半導体発光装置は、上記半導体発光素子は発光波長が390nm乃至420nmの出射光を有すると共に、この半導体発光素子からの出射光を500nm乃至540nmの緑色の発光波長に変換する蛍光体を備えるので、この蛍光体からの光は、人間の視感度を考慮すると、見かけ上、上記半導体発光素子からの直接光によって色調が殆ど変わらないから、この半導体発光装置は色調が良好で単色緑色の光を発光できる。また、上記半導体発光素子の発光波長は390nm乃至420nmであるので、上記半導体発光装置を構成する部品の損傷や、人体への悪影響を効果的に防止できる。

【0196】1実施形態の半導体発光装置は、上記蛍光体は、 $RMg_2Al_{16}O_{27}:Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、 $RMgAl_{10}O_{17}:Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、 $ZnS:Cu, SrAl_2O_4:Eu, SrAl_2O_4:Eu, Dy, ZnO:Zn, Zn_2Ge_2O_4:Mn, Zn_2SiO_4:Mn, Q_3MgSi_2O_8:Eu, Mn$ (但し、QはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、で表される蛍光体の群のうち、いずれか一つまたは2以上からなるので、上記半導体発光素子の発光波長に応じて最適な蛍光体を選択できて、緑色の単色発光の半導体発光装置を得ることができ、複数の蛍光体を組合わせて、半導体発光素子の光の利用効率が高い半導体発光装置にできる。

【0197】本発明の半導体発光装置は、上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有すると共に、この半導体発光素子からの出射光を410nm乃至480nmの青色の発光波長に変換する蛍光体を備えるので、この蛍光体からの光は、人間の視感度を考慮すると、見かけ上、上記半導体発光素子からの直接光によって色調が殆ど変わらないから、この半導体発光装置は色調が良好で単色青色の光を発光できる。また、上記半導体発光素子の発光波長は390nm乃至420nmであるので、上記半導体発光装置を構成する部品の損傷や、人体への悪影響を効果的に防止できる。

【0198】1実施形態の半導体発光装置は、上記蛍光体は、 $A_{10}(PO_4)_6Cl_2:Eu$ （但し、AはSr, Ca, Ba, Mg, Ceから選ばれるいずれか一つまたは2以上の元素）、 $XMg_2Al_16O_{27}:Eu$ （但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素）、 $XMgAl_{10}O_{17}:Eu$ （但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素）、 $ZnS:Ag, Sr_{10}(PO_4)_6Cl_2:Eu, Ca_{10}(PO_4)_6F_2:Sb, Z_3MgSi_2O_8:Eu$ （但し、ZはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素）、 $SrMgSi_2O_8:Eu, Sr_2P_2O_7:Eu, CaAl_2O_4:Eu, Nd$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなるので、上記半導体発光素子の発光波長に応じて最適な蛍光体を選択できて、青色の単色発光の半導体発光装置を得ることができ、複数の蛍光体を組合わせて、半導体発光素子の光の利用効率が高い半導体発光装置にできる。

【0199】本発明の半導体発光装置は、上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有すると共に、この半導体発光素子からの出射光を480nm乃至500nmの青緑色の発光波長に変換する蛍光体を備えるので、この蛍光体からの光は、人間の視感度を考慮すると、見かけ上、上記半導体発光素子からの直接光によって色調が殆ど変わらないから、この半導体発光装置は色調が良好で単色青緑色の光を発光できる。また、上記半導体発光素子の発光波長は390nm乃至420nmであるので、上記半導体発光装置を構成する部品の損傷や、人体への悪影響を効果的に防止できる。

【0200】1実施形態の半導体発光装置は、上記蛍光体は、 $Sr_4Al_{14}O_{25}:Eu, Sr_4Al_{14}O_{25}:Eu, Dy, Li_0(PO_4)_6Cl_2:Eu$ （但し、LはBa, Ca, Mgから選ばれるいずれか一つまたは2以上の元素）、 $Sr_2Si_3O_8 \cdot 2SrCl_2:Eu$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなるので、上記半導体発光素子の発光波長に応じて最適な蛍光体を選択できて、良好な色調の青緑色単色発光の半導体発光装置を得ることができ、複数の蛍光体を組合せて、半導体発光素子の光の利用効率が高い半導体発

光装置を得ることができる。

【0201】本発明の半導体発光装置は、上記半導体発光素子は、発光波長が390nm乃至420nmの出射光を有すると共に、この半導体発光素子からの出射光を570nm乃至600nmの橙色の発光波長に変換する蛍光体を備えるので、この蛍光体からの光は、人間の視感度を考慮すると、見かけ上、上記半導体発光素子からの直接光によって色調が殆ど変わらないから、この半導体発光装置は色調が良好で単色橙色の光を発光できる。また、上記半導体発光素子の発光波長は390nm乃至420nmであるので、上記半導体発光装置を構成する部品の損傷や、人体への悪影響を効果的に防止できる。

【0202】1実施形態の半導体発光装置は、上記蛍光体は、 $ZnS:Mn, ZnS:Cu, Mn, Co$ 、で表される蛍光体の群のうち、いずれか一つまたは2以上からなるので、上記半導体発光素子の発光波長に応じて最適な蛍光体を選択することができて、橙色の単色発光の半導体発光装置を得ることができる。

【0203】1実施形態の半導体発光装置は、半導体発光素子を搭載する基体の少なくとも一部と、上記半導体発光素子とを封止する封止樹脂が蛍光体を含んでいるので、半導体発光素子からの出射光を確実に波長変換できて、高効率の半導体発光装置にできる。また、封止樹脂を形成すれば蛍光体を配置できるから、蛍光体を別個に配置する必要がなくて、半導体発光装置の製造を容易にできる。

【0204】また、上記半導体発光装置は、発光波長が一定の波長領域を有する半導体発光素子と、所定の発光波長を有する蛍光体とを組み合わせることによって所望の発光波長を得るので、同一の製造工程で蛍光体を変えることのみによって、所望の発光波長の半導体発光装置を得ることができるから、半導体発光装置の製造コストを大幅に削減できる。

【0205】1実施形態の半導体発光装置は、半導体発光素子を、リードフレームの先端に形成されたカップ形状のマウント部の底に配置すると共に、もう一つのリードフレームに電気的に接続して、上記2つのリードフレームの少なくとも一部と上記半導体発光素子とを上記封止樹脂で封止しているので、上記カップ形状のマウント部で集められた半導体発光素子からの出射光が、上記封止樹脂を含む蛍光体によって確実に波長変換されるから、指向性が良く、かつ、発光効率が良くて色調の良い半導体発光装置を得ることができる。

【0206】1実施形態の半導体発光装置は、上記半導体発光素子を、一對のリードフレームの先端に連結された絶縁体の金属配線に直接接続して、上記一對のリードフレームの少なくとも一部と、上記絶縁体と、上記半導体発光素子とを上記封止樹脂で封止しているので、半導体発光素子をワイヤーボンディング等で金属配線に接続するよりも容易に半導体発光装置を製造できる。

【0207】1実施形態の半導体発光装置は、半導体発光素子を、リードフレームの先端に形成されたカップ形状のマウント部の底に配置すると共に、もう一つのリードフレームに電気的に接続して、上記カップ形状のマウント部に蛍光体を充填して、上記リードフレームの少なくとも一部と、上記半導体発光素子と、上記蛍光体とを封止樹脂で封止するので、半導体発光素子からの光を確実に波長変換できて高効率の半導体発光装置にすることができると共に、上記蛍光体の使用量を、上記実施形態におけるように封止樹脂に蛍光体を含有させるよりも少なくできる。

【0208】1実施形態の半導体発光装置は、半導体発光素子を、リードフレームの先端に形成されたカップ形状のマウント部の底に配置すると共に、もう一つのリードフレームに電気的に接続して、上記カップ形状のマウント部にコーティング部材を充填し、さらに上記コーティング部材の上に蛍光体を配置して、上記2つのリードフレームの少なくとも一部と、上記半導体発光素子と、上記コーティング部材と、上記蛍光体とを封止樹脂で封止するので、上記マウント部内の全てに蛍光体を充填する場合よりも蛍光体の使用量を少なくできる。また、上記コーティング部材によって上記半導体発光素子の発光部と蛍光体との間の距離を略均一にできるので、半導体発光装置の光を色むらが無く均一にできる。さらに、上記コーティング部材は上記半導体発光素子と蛍光体とを離間するので、半導体発光素子による蛍光体の電気的および熱的劣化を防止できる。

【0209】1実施形態の半導体発光装置は、半導体発光素子を基板の金属配線に接続して搭載し、上記半導体発光素子を、蛍光体を含んだ封止樹脂によって封止するので、上記半導体発光素子の種類を変えないで、上記封止樹脂に含まれる蛍光体の種類を変えるのみで所望の発光波長の半導体発光装置が得られるから、複数の所望の半導体発光装置が従来よりも容易に製造できて、その結果、半導体発光装置が低コストに製造できる。

【0210】1実施形態の半導体発光装置は、半導体発光素子が基板の金属配線に電気的に接続されていると共に基板の凹部内に配置されており、蛍光体が上記凹部に充填されているので、上記蛍光体の使用量を少量にできて製造コストを安価にでき、しかも、半導体発光素子からの光は確実に上記蛍光体で波長変換されるから、発光効率が良い半導体発光装置が得られる。

【0211】1実施形態の半導体発光装置は、上記凹部は、上記基板に配置された枠によって形成されているので、基板を例えば切削して凹部を形成する加工の手間が削減できる。また、上記枠の半導体発光素子側の面を、上記半導体発光素子からの出射光を集光する形状に加工すると、上記出射光の波長の変換効率をさらに向上できる。

【0212】1実施形態の半導体発光装置は、半導体発

光素子が基板の金属配線に電気的に接続されていると共に基板の凹部内に配置されており、この凹部に封止樹脂を充填していると共に、上記封止樹脂の上に蛍光体を配置しているので、上記実施形態のように基板の凹部の内側に蛍光体を充填するよりも、上記蛍光体の使用量を削減できる。また、上記封止樹脂は、半導体発光素子の発光部と蛍光体との間の距離を略均一にするので、色むらが殆ど無い均一の発光を得ることができる。また、上記封止樹脂は、上位半導体発光素子と蛍光体とを離間させるので、上記蛍光体に対する半導体発光素子の電気的および熱的影響を低減して、半導体発光装置の性能を安定にできる。

【0213】1実施形態の半導体発光装置は、半導体発光素子が基板の金属配線に接続されて、上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、蛍光体が上記封止樹脂に含まれているので、上記半導体発光素子の種類を変えないで、上記蛍光体の種類を変えることのみによって所望の発光波長の半導体発光装置が得られるから、従来よりも容易に、しかも安価に半導体発光装置が製造できる。また、上記半導体発光素子からの出射光と、上記反射体によって反射された反射光とが確実に波長変換されるから、光の利用効率が良い半導体発光装置を得ることができる。

【0214】1実施形態の半導体発光装置は、半導体発光素子は基板の金属配線と電気的に接続されており、上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備えると共に、上記半導体発光素子から半導体発光装置の外部に直接出射する光を遮る遮蔽体を備え、上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、蛍光体の層が、上記反射体において光が反射する面に設けられているので、半導体発光素子からの光は必ず上記反射体で反射されると共に波長変換されて、半導体発光装置の外部に出射するから、蛍光体を反射面のみに設ければよいので蛍光体の使用量が削減できて、安価に効率が良い半導体発光装置が得られる。さらに、上記蛍光体の層は、半導体発光素子から所定の距離をなす反射体の反射面に形成されて、半導体発光素子から略均一の距離をおいて配置されるので、色むらの無い均一発光の半導体発光装置にできる。さらに、半導体発光素子と蛍光体とが離間されるので、この蛍光体に対する半導体発光素子の電気的および熱的影響が緩和されて、安定した性能を有する半導体発光装置にできる。

【0215】1実施形態の半導体発光装置は、半導体発光素子は基板の金属配線と電気的に接続されており、上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備えると共に、上記半導体発光素子の発光部分が上記基板の凹部内に配置されていて、上記半導体

発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、蛍光体の層が、上記反射体において光が反射する面に設けられているので、上記半導体発光素子からの光は半導体発光装置の外部へ直接出射されずに、必ず上記反射体で反射されると共に波長変換されてから半導体発光装置の外部に出射されるから、色調が良好な出射光を有する半導体発光装置にできる。

【0216】1実施形態の半導体発光装置は、半導体発光素子は基板の金属配線と電気的に接続されており、上記半導体発光素子からの出射光の少なくとも一部を反射する反射体を備え、上記半導体発光素子を封止すると共に上記反射体からの反射光が透過する封止樹脂を備え、蛍光体の層が、上記封止樹脂の光が出射する面に設けられているので、半導体発光装置から出射される光は必ず波長変換されて、光の利用効率の良い半導体発光装置にできる。また、上記蛍光体の層は、半導体発光素子から略均一の距離をおいて配置されるので、色むらの無い均一発光の半導体発光装置にできると共に、上記蛍光体に対する半導体発光素子の電気的および熱的影響を緩和できて、安定した性能を有する半導体発光装置にできる。

【0217】本発明の半導体発光装置は、基体上に、発光波長が390nm乃至420nmの出射光を有する半導体発光素子を搭載し、発光波長が600nm乃至670nmの波長領域に主発光ピークを有する赤色の発光光を有する第1の蛍光体と、発光波長が500nm乃至540nmの波長領域に主発光ピークを有する緑色の発光光を有する第2の蛍光体と、発光波長が410nm乃至480nmの波長領域に主発光ピークを有する青色の出射光を有する第3の蛍光体とを備え、上記第1、第2、第3の蛍光体からの出射光の色の和が白色系であるので、上記半導体発光素子は人間の視感度が非常に低い短波長領域の発光波長を有する上に、上記各々の蛍光体が出射する光は、各々、赤色、緑色、青色の単色の光であるから、上記各々の蛍光体からの出射光が上記半導体発光素子からの直接の出射光によって色調が変化することなく、良好な色調の白色系の発光色を得ることができる。また、上記半導体発光素子から半導体発光装置外部に直接出射される光は、人間の可視領域において、蛍光体からの光と混色されていないから、経年変化によって半導体発光素子の発光性能が低下しても、半導体発光装置の輝度が低下するのみで、色調が変化することが防止できる。また、上記半導体発光素子の発光波長は390nm乃至420nmであるので、上記半導体発光装置を構成する部品の損傷や、人体への悪影響を効果的に防止できる。

【0218】1実施形態の半導体発光装置は、上記第1の蛍光体は、 $M_2O_2S : Eu$ (但し、MはLa, Gd, Yから選ばれるいずれか一つまたは2以上の元素)、 $0.5MgF_2 \cdot 3.5MgO \cdot GeO_2 : Mn, Y_2O_3 : Eu, Y(P, V)O_4 : Eu, YVO_4 : Eu,$

で表される蛍光体の群のうち、いずれか一つまたは2以上からなり、上記第2の蛍光体は、 $RMg_2Al_{16}O_{27} : Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、 $RMgAl_{10}O_{17} : Eu, Mn$ (但し、RはSr, Baから選ばれるいずれか一つまたは両方の元素)、 $ZnS : Cu, SrAl_2O_4 : Eu, SrAl_2O_4 : Eu, Dy, ZnO : Zn, Zn_2Ge_2O_4 : Mn, Zn_2SiO_4 : Mn, Q_3MgSi_2O_8 : Eu, Mn$ (但し、QはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、で表される蛍光体の群のうち、いずれか一つまたは2以上からなり、上記第3の蛍光体は、 $Al_3O_4 : Cl_2 : Eu$ (但し、AはSr, Ca, Ba, Mg, Ceから選ばれるいずれか一つまたは2以上の元素)、 $XMg_2Al_{16}O_{27} : Eu$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、 $XMgAl_{10}O_{17} : Eu$ (但し、XはSr, Baから選ばれるいずれか一つまたは両方の元素)、 $ZnS : Ag, Sr_{10}(PO_4)_6Cl_2 : Eu, Ca_{10}(PO_4)_6F_2 : Sb, Z_3MgSi_2O_8 : Eu$ (但し、ZはSr, Ba, Caから選ばれるいずれか一つまたは2以上の元素)、 $SrMgSi_2O_8 : Eu, Sr_2P_2O_7 : Eu, CaAl_2O_4 : Eu, Nd,$ で表される蛍光体の群のうち、いずれか一つまたは2以上からなるので、発光波長が390nm乃至420nmのうちのいずれの発光波長を有する半導体発光素子を用いても、この半導体発光素子の発光波長に対応して上記複数の蛍光体から適切な蛍光体を選択することによって、単色の赤色、および、緑色、および、青色の発光光が各々得ることができるから、これらの単色の赤色、緑色、青色の光の混色によって、良好な色調の白色系の光を得ることができる。また、上記蛍光体を複数の蛍光体を組合わせて形成することによって、半導体発光素子の発光波長の略全ての波長の光を、赤色、緑色、青色の波長に各々変換することができるので、半導体発光素子の出射光の利用効率を向上できて、高効率な白色系の発光色を有する半導体発光装置にできる。

【0219】1実施形態の半導体発光装置は、上記第1、第2、第3の蛍光体は、総量が100重量%であるとして、上記第1の蛍光体が50重量%以上70重量%以下、上記第2の蛍光体が7重量%以上20重量%以下、上記第3の蛍光体が20重量%以上30重量%以下であるので、上記第2の蛍光体が出射する緑色の光に比べて人間の視感度が低い第1および第3の蛍光体の出射光、すなわち、青色および赤色の光の強度を強めるから、人間の視感度を考慮して、良好な色調の白色系の発光色を有する半導体発光装置にできる。

【0220】1実施形態の半導体発光装置は、上記封止樹脂は、上記第1、第2、第3の蛍光体を含んでおり、上記封止樹脂の重量に対する上記第1、第2、第3の蛍

光体の総重量の比率が、0.5以上1以下であるので、自然光に近い白色系の発光色を有する半導体発光装置にできる。

【0221】1実施形態の発光表示装置は、上記半導体発光装置を用いた光源と、上記光源からの光を導く導光板と、上記導光板からの光を透過させて分光する赤、緑、青のカラーフィルタとを備え、上記半導体発光装置の出射光は、上記カラーフィルタの分光特性に適合した波長分布を有するので、上記半導体発光装置の出射光は、赤、緑、青の単色で、かつ、比較的大きい強度の光に分光できるから、光の利用効率が良好で高輝度の発光表示装置にできる。

【0222】1実施形態の発光表示装置は、半導体発光装置の出射光の波長分布が上記カラーフィルタの分光特性に適合するように、上記半導体発光素子の発光波長と、上記第1の蛍光体の発光波長と、上記第2の蛍光体の発光波長と、上記第3の蛍光体の発光波長と、上記第1、第2、第3の蛍光体の混合比率と、上記封止樹脂の重量に対する上記第1、第2、第3の蛍光体の総重量の比率とのうちの少なくとも一つを調節したので、上記半導体発光装置からの光を、上記カラーフィルタによって、確実に赤、緑、青の単色かつ比較的高い強度の光に分光できるから、上記発光表示装置は、色抜けなどが無く高輝度かつ高コントラストのフルカラー表示ができる。

【0223】1実施形態の発光表示装置は、上記発光表示装置は、液晶表示装置であるので、色抜けが殆ど無く、高輝度かつ高コントラストの液晶表示装置が得られる。

【図面の簡単な説明】

【図1】 図1(a), (b), (c)は、本発明において用いられる半導体発光素子の断面図である。

【図2】 図2(a)は、赤色の発光色について、蛍光体の発光スペクトルを示す図であり、図2(b)は蛍光体の励起スペクトルを示す図である。

【図3】 図3(a)は、赤色の発光色について、図2と異なる蛍光体の発光スペクトルを示す図であり、図3(b)は蛍光体の励起スペクトルを示す図である。

【図4】 図4(a)は、緑色の発光色について、蛍光体の発光スペクトルを示す図であり、図4(b)は蛍光体の励起スペクトルを示す図である。

【図5】 図5(a)は、緑色の発光色について、図4と異なる蛍光体の発光スペクトルを示す図であり、図5(b)は蛍光体の励起スペクトルを示す図である。

【図6】 図6(a)は、青色の発光色について、蛍光体の発光スペクトルを示す図であり、図6(b)は蛍光体の励起スペクトルを示す図である。

【図7】 図7(a)は、青色の発光色について、図6と異なる蛍光体の発光スペクトルを示す図であり、図7(b)は蛍光体の励起スペクトルを示す図である。

【図8】 図8(a), (b), (c)は、本発明の第1の実施形態における半導体発光装置を示す断面図である。

【図9】 図9(a), (b)は、本発明の第2の実施形態における半導体発光装置を示す断面図である。

【図10】 図10(a), (b)は、本発明の第3の実施形態における半導体発光装置を示す断面図である。

【図11】 図11(a), (b)は、本発明の第4の実施形態における半導体発光装置を示す断面図である。

【図12】 図12(a), (b)は、本発明の第5の実施形態における半導体発光装置を示す断面図である。

【図13】 本発明の第6の実施形態における半導体発光装置を示す断面図である。

【図14】 図14(a)は、本発明の第7の実施形態における半導体発光装置の正面から見た断面図であり、図14(b)は側面から見た断面図である。

【図15】 図15(a)は、本発明の第8の実施形態における半導体発光装置の正面から見た断面図であり、図15(b)は側面から見た断面図である。

【図16】 図16(a)は、本発明の第9の実施形態における半導体発光装置の正面から見た断面図であり、図16(b)は側面から見た断面図である。

【図17】 図17(a)は、本発明の第10の実施形態における半導体発光装置の正面から見た断面図であり、図17(b)は側面から見た断面図である。

【図18】 図18(a)は第1の蛍光体が47重量%、第2の蛍光体が13重量%、第3の蛍光体が40重量%である場合、図18(b)は、第1の蛍光体が56重量%、第2の蛍光体が11重量%、第3の蛍光体が33重量%である場合、図18(c)は、第1の蛍光体が65重量%、第2の蛍光体が26重量%、第3の蛍光体が9重量%である場合の半導体発光装置の出射光の波長分布を示した図である。

【図19】 図19(a)は、封止樹脂の重量に対する第1、第2、第3の蛍光体の総重量の比率が0.5である場合、図19(b)は0.66である場合、図19(c)は1.0である場合の半導体発光装置の出射光の波長分布を示した図である。

【図20】 図19(a)に示した半導体発光装置の発光スペクトル150と、人間の比視感度151を考慮した半導体発光装置の実効発光スペクトル152とを示す図である。

【図21】 本発明の第12の実施形態の発光表示装置を示す模式図である。

【図22】 本発明の発光表示装置が備えるカラーフィルタの分光特性を示した図である。

【符号の説明】

7a 半導体発光素子

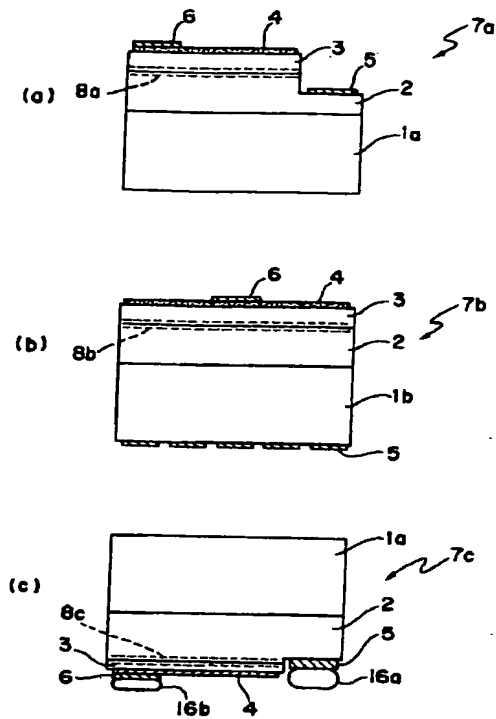
7b 半導体発光素子

7c 半導体発光素子

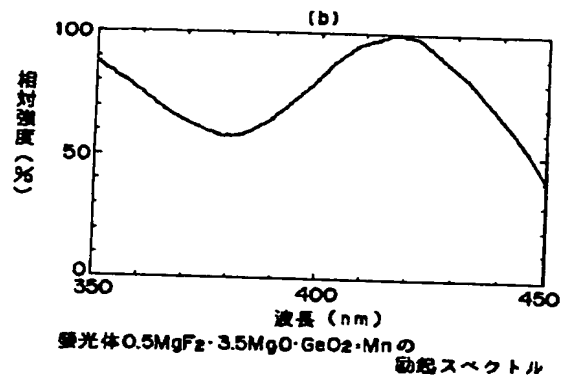
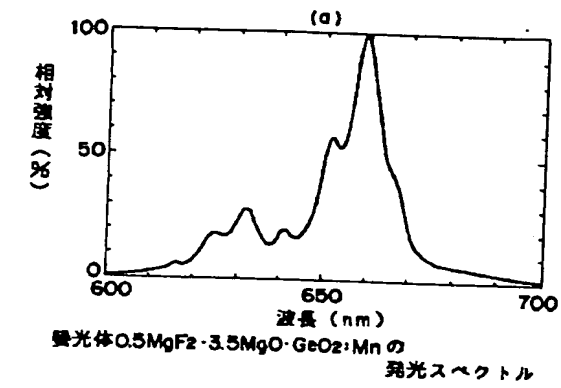
1.0 リードフレーム

1.2 蛍光体

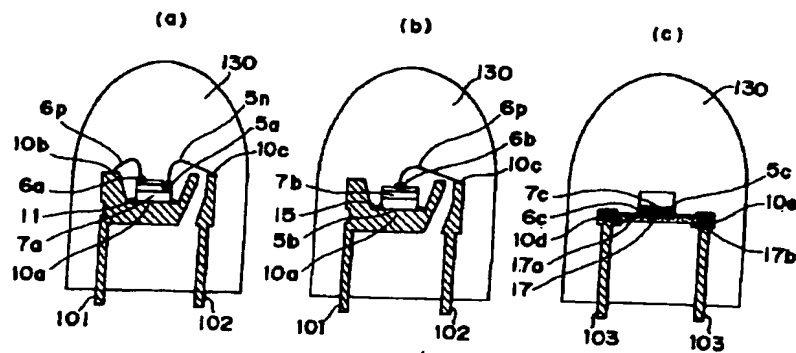
【図1】



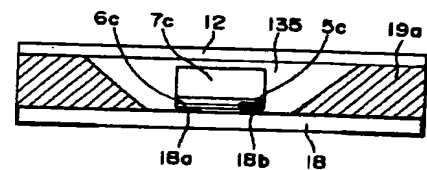
【図2】



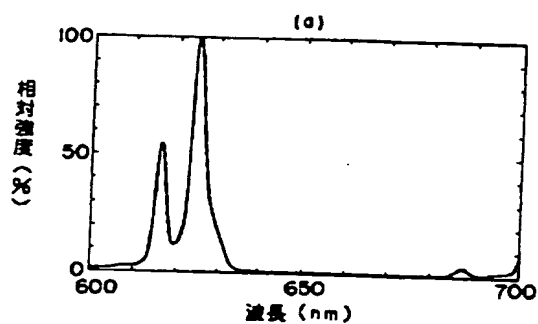
【図8】



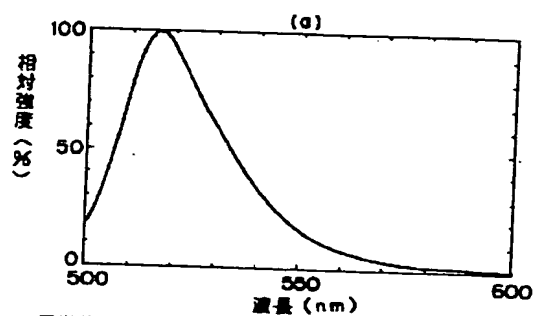
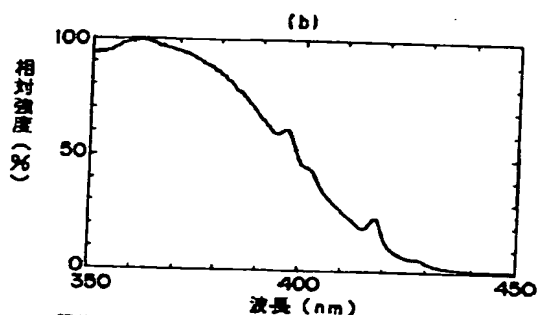
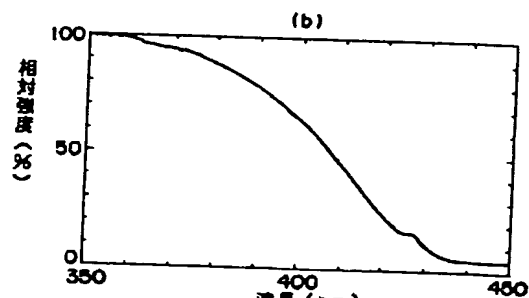
【図13】



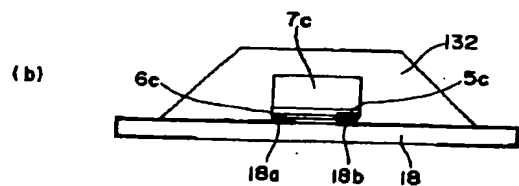
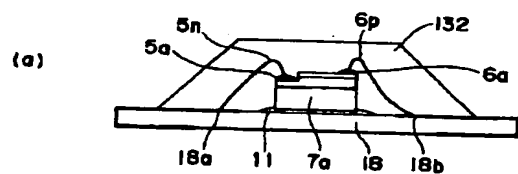
【図3】

蛍光体 $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ の発光スペクトル

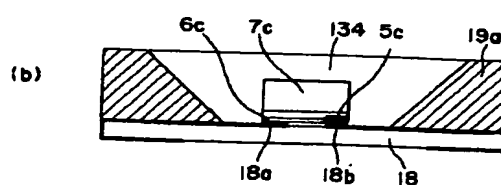
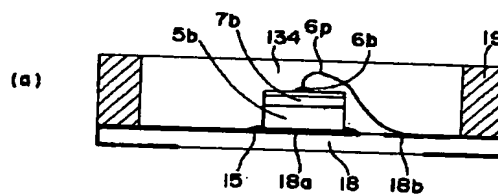
【図4】

蛍光体 $\text{BaMg}_2\text{Al}_{16}\text{O}_{27}:\text{Eu}, \text{Mn}$ の発光スペクトル蛍光体 $\text{La}_2\text{O}_2\text{S}:\text{Eu}$ の励起スペクトル蛍光体 $\text{BaMg}_2\text{Al}_{16}\text{O}_{27}:\text{Eu}, \text{Mn}$ の励起スペクトル

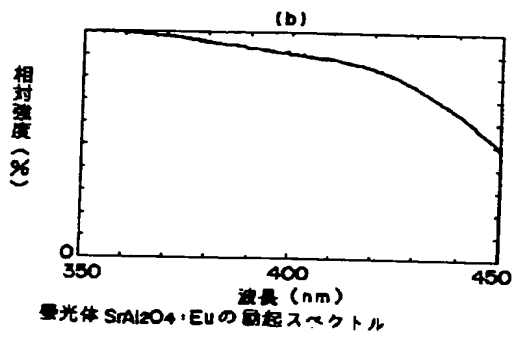
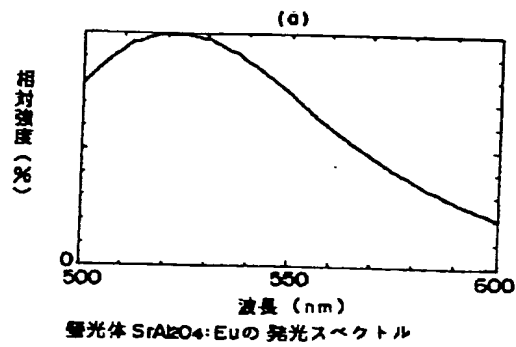
【図11】



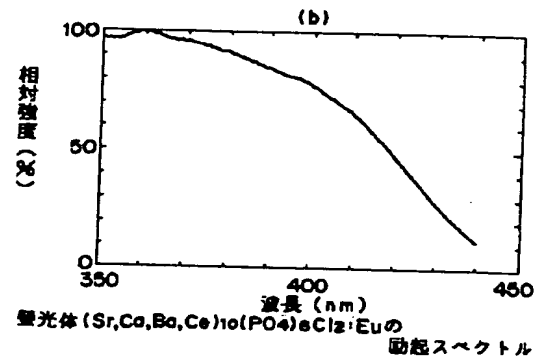
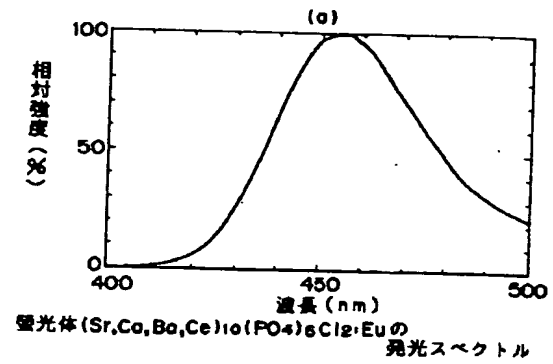
【図12】



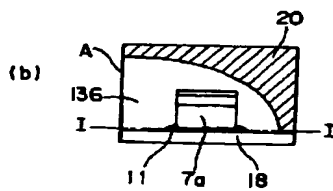
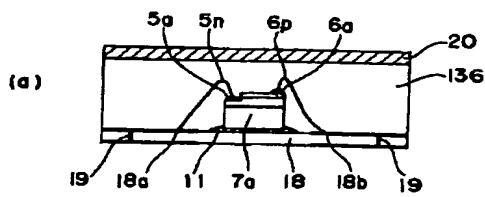
【図5】



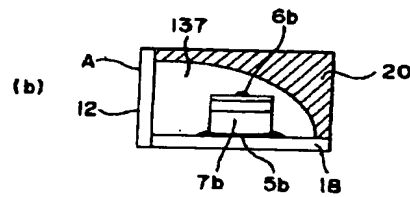
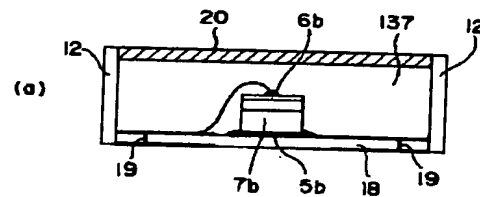
【図6】



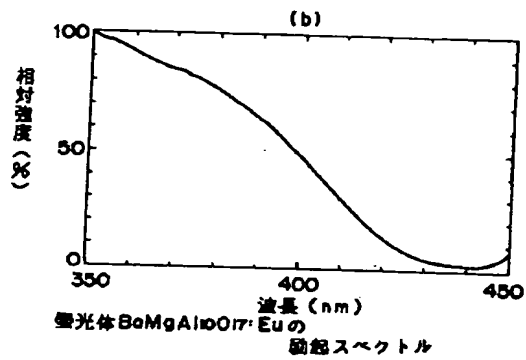
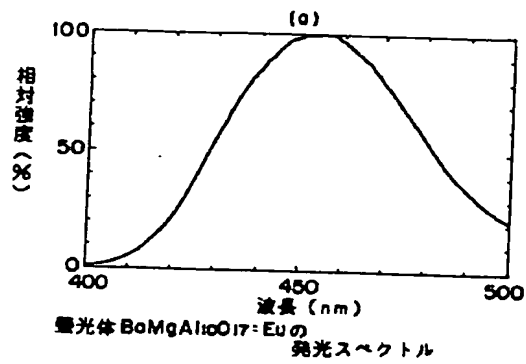
【図14】



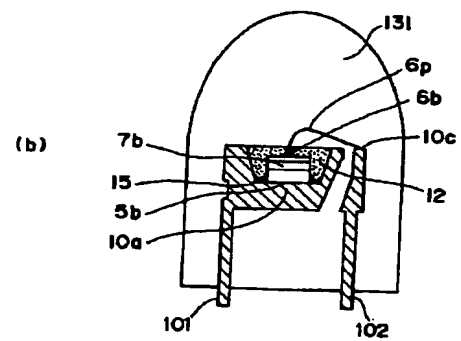
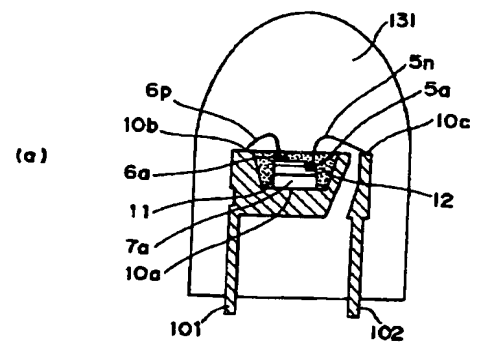
【図15】



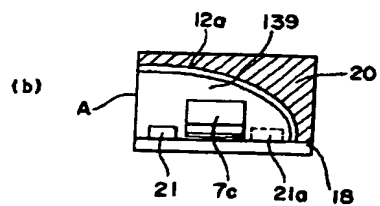
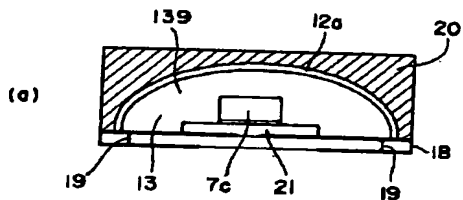
【図7】



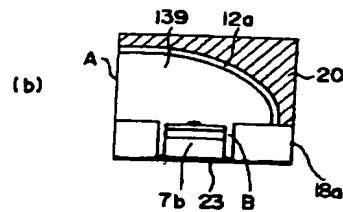
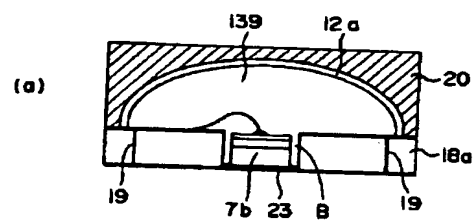
【図9】



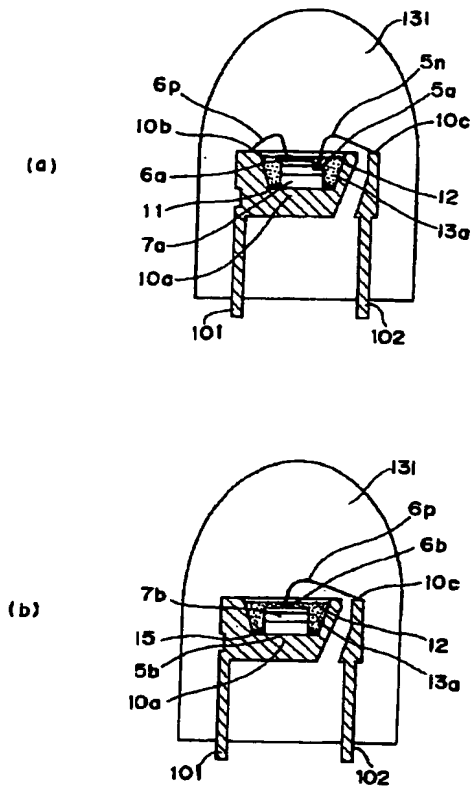
【図16】



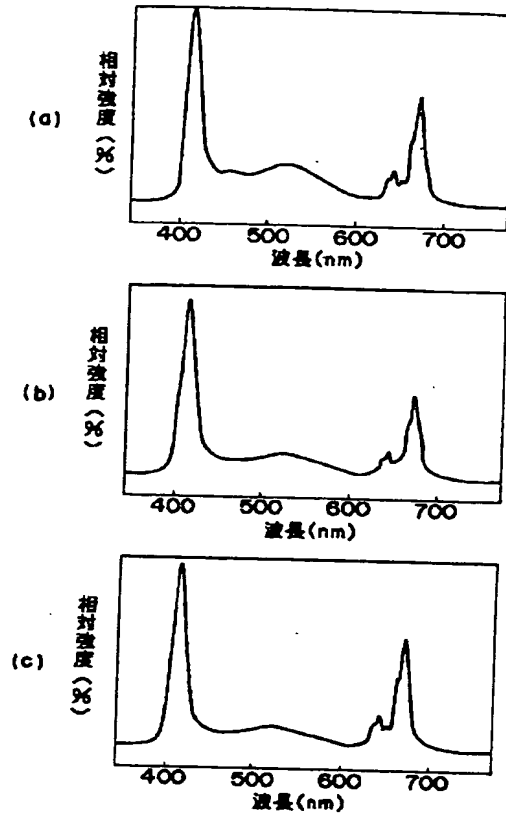
【図17】



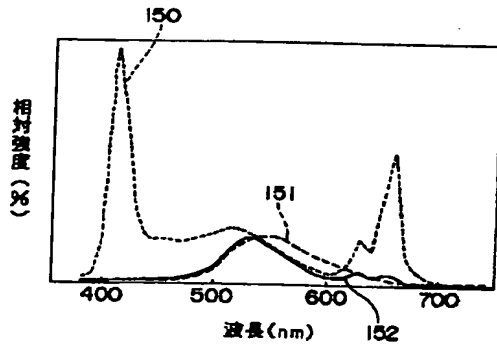
【図10】



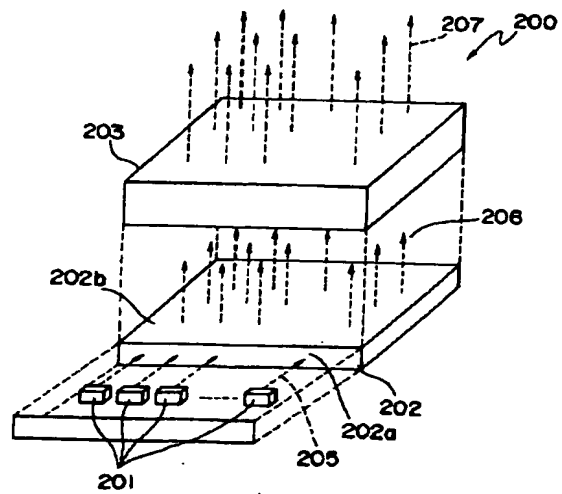
【図18】



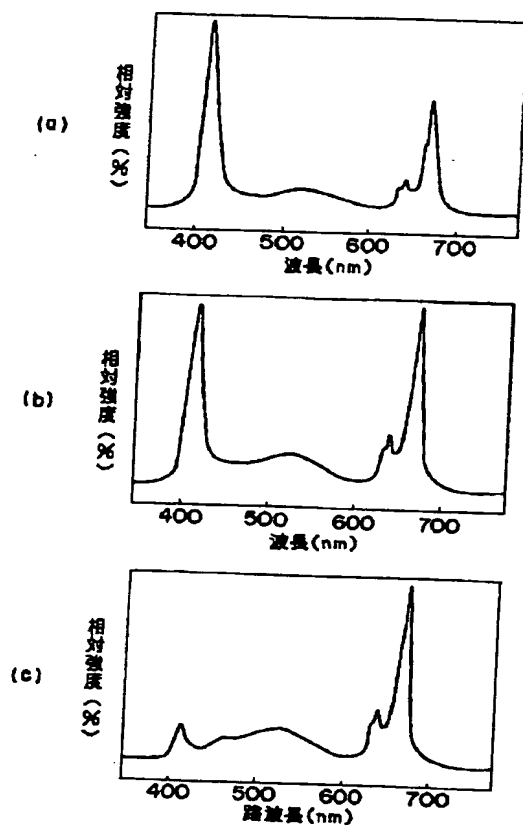
【図20】



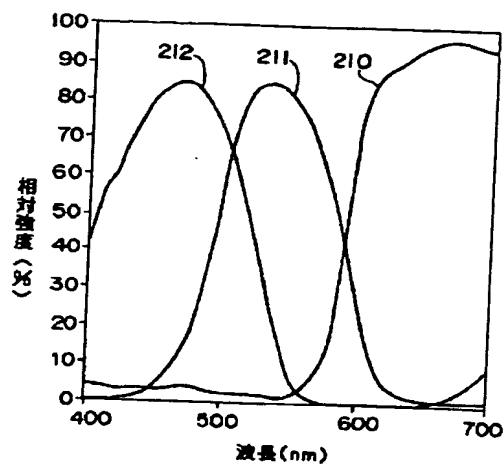
【図21】



【図19】



【図22】



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11/71
11/72
11/78
11/82
11/83
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CPC
CPD
CPM
CPR
CPS
CPT
CPV
CPW

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C P X
C Q A

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